

Deep-level transient spectroscopy: A new method to

Journal of Applied Physics

45, 3023-3032

DOI: 10.1063/1.1663719

Citation Report

#	ARTICLE	IF	CITATIONS
3	New method to determine the photoionization threshold energy of a deep level from photocapacitance. Applied Physics Letters, 1974, 25, 572-574.	1.5	20
4	Non-radiative recombination centers in GaAs λ -6P λ -4 red light-emitting diodes. Solid-State Electronics, 1975, 18, 635-640.	0.8	17
5	On the role of defect charge state in the stability of point defects in silicon. Solid State Communications, 1975, 16, 171-174.	0.9	105
6	Growth and characterization of GaP and GaAs λ -xPx. Journal of Crystal Growth, 1975, 31, 165-171.	0.7	22
7	Problems in optoelectronic semiconductors. Journal of Materials Science, 1975, 10, 714-726.	1.7	3
8	A study of electron traps in vapour-phase epitaxial GaAs. Applied Physics Berlin, 1975, 8, 15-21.	1.4	89
9	Fast transient capacitance measurements for implanted deep levels in silicon. Applied Physics Berlin, 1975, 8, 35-42.	1.4	21
10	A correlation method for semiconductor transient signal measurements. Journal of Applied Physics, 1975, 46, 2638-2644.	1.1	151
11	Relationships between residual defects and excess noise in ion-implanted MOSFETs. , 1976, , .		0
12	Electron λ irradiation λ induced divacancy in lightly doped silicon. Journal of Applied Physics, 1976, 47, 3776-3780.	1.1	232
13	Electrical properties of platinum in silicon as determined by deep λ level transient spectroscopy. Journal of Applied Physics, 1976, 47, 3172-3176.	1.1	54
14	Deep λ level distributions near p λ n junctions in LPE GaAs. Journal of Applied Physics, 1976, 47, 1533-1537.	1.1	48
15	Deep traps in GaAs revealed at high resolution by simple fast photocapacitance methods. Journal of Electronic Materials, 1976, 5, 91-107.	1.0	18
16	Non-extrinsic conduction in semi-insulating gallium arsenide. Solid State Communications, 1976, 20, 61-63.	0.9	16
17	Incorporation of deep centres in VPE GaAs. Applied Physics Berlin, 1976, 9, 117-119.	1.4	4
18	Electron and hole traps in N-GaAs crystals. Applied Physics Berlin, 1976, 11, 187-189.	1.4	13
19	Measurement of deep-level spatial distributions. Solid-State Electronics, 1976, 19, 341-342.	0.8	21
20	A study of the gold acceptor in a silicon p+n junction and an n-type MOS capacitor by thermally stimulated current and capacitance measurements. Solid-State Electronics, 1976, 19, 777-784.	0.8	40

#	ARTICLE	IF	CITATIONS
21	Electroluminescence in semiconductors. Journal of Luminescence, 1976, 12-13, 83-95.	1.5	14
22	Electrical traps in GaAs microwave f.e.t.s. Electronics Letters, 1976, 12, 297.	0.5	39
23	Influence of the growth conditions on the incorporation of deep levels in VPE GaAs. Journal of Applied Physics, 1976, 47, 4137-4144.	1.1	31
24	Degradation of bulk luminescence in GaP:Zn,O induced by laser excitation. Journal of Applied Physics, 1976, 47, 4061-4066.	1.1	24
25	Recombination-enhanced annealing of the E1 and E2 defect levels in 1-MeV electron-irradiated GaAs. Journal of Applied Physics, 1976, 47, 3587-3591.	1.1	131
26	Observation of athermal defect annealing in GaP. Applied Physics Letters, 1976, 28, 248-250.	1.5	124
27	Study of electron traps in GaAs grown by molecular beam epitaxy. Journal of Applied Physics, 1976, 47, 2558-2564.	1.1	199
28	Defect spatial distributions in annealed ion-implanted silicon measured by a transient capacitance technique. Applied Physics Letters, 1976, 29, 700-702.	1.5	33
29	The role of oxygen in irradiated arsenic-doped silicon. Applied Physics Letters, 1976, 29, 476-478.	1.5	18
30	Determination of interface and bulk trap states of IGFETs using deep level transient spectroscopy. Journal of Applied Physics, 1976, 47, 4574-4577.	1.1	75
31	Capacitance spectroscopy studies of degraded Al _x Ga _{1-x} As DH stripe geometry lasers. Journal of Applied Physics, 1976, 47, 4986-4992.	1.1	39
32	Solid-State Electronics: Scientific Basis for Future Advances. Science, 1977, 195, 1235-1240.	6.0	0
33	Electron beam induced annealing of defects in GaAs. Journal of Applied Physics, 1977, 48, 2795-2803.	1.1	28
34	The effect of gas phase stoichiometry on deep levels in vapor-grown GaAs. Applied Physics Letters, 1977, 31, 538-540.	1.5	64
35	Selenium implantation into silicon studied by DLTS technique. Applied Physics Letters, 1977, 31, 525-527.	1.5	30
36	Annealing of irradiation-induced defects in arsenic-doped silicon. Journal of Applied Physics, 1977, 48, 1840-1843.	1.1	40
37	Defect energy levels in boron-doped silicon irradiated with 1-MeV electrons. Physical Review B, 1977, 15, 3836-3843.	1.1	273
38	Transient capacitance deep level spectrometry instrumentation. Review of Scientific Instruments, 1977, 48, 237-239.	0.6	15

#	ARTICLE	IF	CITATIONS
39	Study of the main electron trap in Ga _{1-x} In _x As alloys. Physical Review B, 1977, 16, 3665-3675.	1.1	69
40	Background deep-level defects in VPE GaP. Journal of Applied Physics, 1977, 48, 1656-1658.	1.1	24
41	Electron irradiation damage in antimony-doped silicon. Journal of Applied Physics, 1977, 48, 734-738.	1.1	57
42	A search for interface states in an LPE GaAs/Al _x Ga _{1-x} As heterojunction. Applied Physics Letters, 1977, 31, 683-684.	1.5	31
43	III-V compound semiconductors. Topics in Applied Physics, 1977, , 63-132.	0.4	8
44	Nonradiative capture and recombination by multiphonon emission in GaAs and GaP. Physical Review B, 1977, 15, 989-1016.	1.1	1,102
45	The defect levels in p-type silicon doped with manganese. Journal of Applied Physics, 1977, 48, 3813-3818.	1.1	15
46	Large-Lattice-Relaxation Model for Persistent Photoconductivity in Compound Semiconductors. Physical Review Letters, 1977, 39, 635-639.	2.9	654
47	Electron traps in bulk and epitaxial GaAs crystals. Electronics Letters, 1977, 13, 191.	0.5	710
48	Electron trap annealing in neutron transmutation doped silicon. Applied Physics Letters, 1977, 31, 578-579.	1.5	30
49	Identification of the defect state associated with a gallium vacancy in GaAs and Al _x Ga _{1-x} As. Physical Review B, 1977, 15, 4874-4882.	1.1	178
50	A new spectroscopic technique for imaging the spatial distribution of nonradiative defects in a scanning transmission electron microscope. Applied Physics Letters, 1977, 31, 60-62.	1.5	102
51	A simple signal analyser for deep-level trap spectroscopy. Journal of Physics E: Scientific Instruments, 1977, 10, 1016-1018.	0.7	13
52	Detection of deep-level (0.63 eV) radiative defects during degradation in GaAs _{0.6} P _{0.4} light-emitting diodes. Solid-State Electronics, 1977, 20, 603-606.	0.8	10
53	Carbon interstitial in electron-irradiated silicon. Solid State Communications, 1977, 21, 109-111.	0.9	62
54	Trap-level spectroscopy by thermally stimulated release of trapped carriers. Journal of Electrostatics, 1977, 3, 25-36.	1.0	3
55	Determination of the emission rates and density profile of defect centres from voltage transients using a constant capacitance technique. Journal of Electrostatics, 1977, 3, 241-249.	1.0	1
56	Lifetime control in silicon power devices by electron or gamma irradiation. IEEE Transactions on Electron Devices, 1977, 24, 1103-1108.	1.6	68

#	ARTICLE	IF	CITATIONS
57	Geometrical factors in avalanche punchthrough erase. IEEE Transactions on Electron Devices, 1977, 24, 1108-1116.	1.6	9
58	Optimization of recombination levels and their capture cross section in power rectifiers and thyristors. Solid-State Electronics, 1977, 20, 225-232.	0.8	31
59	Determination of deep electron traps in GaAs by time-resolved capacitance measurement. Applied Physics Berlin, 1977, 13, 5-13.	1.4	14
60	Defects in laser damaged silicon observed by DLTS. Physica Status Solidi A, 1978, 48, K31-K34.	1.7	46
61	Electrical characteristics of sputtering-induced defects in n-type silicon. Vacuum, 1978, 28, 5-7.	1.6	25
62	Recombination enhanced defect reactions. Solid-State Electronics, 1978, 21, 1391-1401.	0.8	387
63	Photocapacitance of deep levels in GaAs:Cr and GaAs:O. Solid-State Electronics, 1978, 21, 1095-1098.	0.8	21
64	Transient current trap spectroscopy (TCTS) in GaAs/GaAlAs heterojunctions. Solid State Communications, 1978, 26, 679-683.	0.9	7
65	A case for large Auger recombination cross sections associated with deep centers in semiconductors. Solid State Communications, 1978, 25, 1071-1074.	0.9	27
66	Remarks on space-charge spectroscopy; An analysis on the temperature dependence of the junction capacitance. Acta Physica Academiae Scientiarum Hungaricae, 1978, 44, 103-109.	0.1	0
67	A comparison of gamma-induced degradation and forward bias-induced degradation in GaP:Zn,0 LEDs. Journal of Electronic Materials, 1978, 7, 589-617.	1.0	7
68	Impurity states in cobalt-doped silicon. Journal of Electronic Materials, 1978, 7, 383-401.	1.0	8
69	GaAs LPE growth and its application to FET. Journal of Crystal Growth, 1978, 45, 272-276.	0.7	5
70	Evidence for multiphonon emission from interface states in MOS structures. Solid State Communications, 1978, 25, 481-484.	0.9	83
71	Scanning photocurrent microscopy: A new technique to study inhomogeneously distributed recombination centers in semiconductors. Solid-State Electronics, 1978, 21, 1519-1524.	0.8	25
72	Measurements of residual defects and 1/f noise in ion-implanted p-channel MOSFET's. IEEE Transactions on Electron Devices, 1978, 25, 478-484.	1.6	12
73	Electrical Properties of 1.7-MeV-Electron-Irradiated Sulfur-Doped GaP. IEEE Transactions on Nuclear Science, 1978, 25, 1055-1060.	1.2	1
74	The electronic structure of impurities and other point defects in semiconductors. Reviews of Modern Physics, 1978, 50, 797-858.	16.4	645

#	ARTICLE	IF	CITATIONS
75	Trap depth and electron capture cross section determination by trap refilling experiments in Schottky diodes. Applied Physics Letters, 1978, 33, 200-202.	1.5	103
76	Pressure dependence of the deep level associated with oxygen in GaAs. Applied Physics Letters, 1978, 32, 764-766.	1.5	32
77	The electrical characterisation of semiconductors. Reports on Progress in Physics, 1978, 41, 157-257.	8.1	92
78	Deep level spectroscopy in high resistivity materials. Applied Physics Letters, 1978, 32, 821-823.	1.5	235
79	Electron traps in silicon doped by neutron transmutation. Journal Physics D: Applied Physics, 1978, 11, 2043-2057.	1.3	17
80	Laser Scanning Technique for the Detection of Resistivity and Lifetime Inhomogeneities in Semiconductor Devices. Physica Scripta, 1978, 18, 357-363.	1.2	20
81	New Charge-Storage Effect in Silicon ⁿ Diodes at Cryogenic Temperatures. Physical Review Letters, 1978, 41, 576-579.	2.9	31
82	Deep level capacitance spectroscopy of nitrogen doped VPE GaP. Journal of Applied Physics, 1978, 49, 5938-5943.	1.1	38
83	Current-voltage characteristics and deep levels in chromium doped semi-insulating GaAs. Applied Physics Letters, 1978, 32, 259-260.	1.5	17
84	Deep level traps and the conduction band structure of InP. Applied Physics Letters, 1978, 33, 957-959.	1.5	20
85	Mechanism of performance limitations in heavily doped silicon devices. Applied Physics Letters, 1978, 33, 531-533.	1.5	40
86	Capacitance spectroscopy of degraded GaAsP light-emitting diodes. Journal of Applied Physics, 1978, 49, 2973-2977.	1.1	15
87	Tin doping effects in GaAs films grown by molecular beam epitaxy. Journal of Applied Physics, 1978, 49, 4854-4861.	1.1	182
88	Defect distribution near the surface of electron irradiated silicon. Applied Physics Letters, 1978, 33, 547-548.	1.5	53
89	Optical transitions via the deep O donor in GaP. I. Phonon interaction in low-temperature spectra. Physical Review B, 1978, 18, 809-829.	1.1	102
90	Niveaux profonds dans les matériaux à haute résistivité : Si et Cds. Revue De Physique Appliquée, 1978, 13, 565-569.	0.4	6
91	Electron and hole capture cross-sections at deep centers in gallium arsenide. Revue De Physique Appliquée, 1979, 14, 853-861.	0.4	153
92	Phonon assisted tunnel emission of electrons from deep levels in GaAs. Journal De Physique, 1979, 40, 1161-1172.	1.8	83

#	ARTICLE	IF	CITATIONS
93	Characterisation of electron traps in Cu ₂ S-CdS polycrystalline cells by capacitance transient measurements. Journal of Physics C: Solid State Physics, 1979, 12, 2313-2321.	1.5	18
94	Active C realisation for the general biquadratic voltage transfer functions. Electronics Letters, 1979, 15, 725.	0.5	2
95	Studies of Neutron-Produced Defects in Silicon by Deep-Level Transient Spectroscopy. Japanese Journal of Applied Physics, 1979, 18, 309-315.	0.8	130
96	Discrete frequency synthesis using an analogue r.o.m.. Electronics Letters, 1979, 15, 350.	0.5	4
97	High-resolution analysis of exponentially decaying transients for physics d.l.t.s. experiments. Electronics Letters, 1979, 15, 724.	0.5	9
98	The effect of non-exponential transients on the determination of deep-trap activation energies by deep-level transient spectroscopy. Journal of Physics C: Solid State Physics, 1979, 12, 4833-4838.	1.5	20
99	Deep level transient spectroscopy for diodes with large leakage currents. Review of Scientific Instruments, 1979, 50, 1571-1573.	0.6	14
100	Room temperature instability of electron induced defects in n-type silicon containing germanium. Applied Physics Letters, 1979, 35, 769-770.	1.5	4
101	Novel variable-temperature chuck for use in the detection of deep levels in processed semiconductor wafers. Review of Scientific Instruments, 1979, 50, 983-987.	0.6	5
102	Ion-electron (configurational) interface states in MOS structures. Applied Physics Letters, 1979, 35, 807-809.	1.5	14
103	Determination of the interface states in GaAs MOS diodes by deep-level transient spectroscopy. Applied Physics Letters, 1979, 35, 932-934.	1.5	40
104	Energy-resolved DLTS measurement of interface states in MIS structures. Applied Physics Letters, 1979, 34, 802-804.	1.5	97
105	Electrical properties of platinum in silicon. Journal of Applied Physics, 1979, 50, 3396-3403.	1.1	99
106	Defect studies in multilayer epitaxial GaAs by transient capacitance. Journal of Applied Physics, 1979, 50, 5526.	1.1	1
107	Minority-carrier generation in InP/SiO ₂ capacitors. Applied Physics Letters, 1979, 35, 86-88.	1.5	9
108	Direct evidence for the nonassignment to oxygen of the main electron trap in GaAs. Journal of Applied Physics, 1979, 50, 4022-4026.	1.1	114
109	Effects of the growth conditions on the incorporation of deep levels in vapor-grown GaAs. Journal of Applied Physics, 1979, 50, 4808-4813.	1.1	24
110	Laser-irradiation effects on unencapsulated GaAs studied by capacitance spectroscopy. Applied Physics Letters, 1979, 35, 156-158.	1.5	14

#	ARTICLE	IF	CITATIONS
111	A study of the deep electron traps in semiconducting CdS. Journal of Applied Physics, 1979, 50, 1375-1380.	1.1	26
112	Characterization of grain boundaries using deep level transient spectroscopy. Journal of Applied Physics, 1979, 50, 8006-8009.	1.1	25
113	The sulfur-related trap in GaAs _{1-x} P _x . Journal of Applied Physics, 1979, 50, 6334-6343.	1.1	75
114	Saturable optical absorption of the deep Te-complex center in Al _{0.4} Ga _{0.6} As. Physical Review B, 1979, 20, 654-663.	1.1	24
115	Deep Level Transient Spectroscopy of Bulk Traps and Interface States in Si MOS Diodes. Japanese Journal of Applied Physics, 1979, 18, 113-122.	0.8	281
116	Investigation of Semiconductor Materials and Devices by High Voltage STEM Techniques. Crystal Research and Technology: Journal of Experimental and Industrial Crystallography, 1979, 14, 1177-1184.	0.3	4
117	Application of the MOSFET device structure in characterizing imperfection centers in indium-doped silicon. Solid-State Electronics, 1979, 22, 391-397.	0.8	3
118	Defect annealing in phosphorus implanted silicon: A D.L.T.S. study. Applied Physics Berlin, 1979, 18, 275-278.	1.4	17
119	Electron traps in CdS single crystals obtained by admittance spectroscopy on the hetero- and Schottky junctions. Applied Physics Berlin, 1979, 18, 345-352.	1.4	13
120	DLTS capacitance studies on deep level centres in VPE GaP: N. Physica Status Solidi A, 1979, 51, 79-86.	1.7	15
121	Long-Term Radiation Transients in GaAs FETs. IEEE Transactions on Nuclear Science, 1979, 26, 5080-5086.	1.2	28
122	Gamma-induced trapping levels in si with and without gold doping. Journal of Electronic Materials, 1979, 8, 437-457.	1.0	10
123	Carrier lifetime in silicon and its impact on solar cell characteristics. Topics in Applied Physics, 1979, , 173-211.	0.4	14
124	Titanium in silicon as a deep level impurity. Solid-State Electronics, 1979, 22, 801-808.	0.8	66
125	Electric field effect on the thermal emission of traps in semiconductor junctions. Journal of Applied Physics, 1979, 50, 5484.	1.1	488
126	Constant capacitance DLTS measurement of defect density profiles in semiconductors. Journal of Applied Physics, 1979, 50, 4828-4833.	1.1	92
127	Thermally stimulated luminescence and conductivity. Topics in Applied Physics, 1979, , 35-92.	0.4	22
128	Deep level transient spectroscopy studies of Ni and Zn diffused vapor phase epitaxial GaAs. Journal of Applied Physics, 1979, 50, 6845-6859.	1.1	55

#	ARTICLE	IF	CITATIONS
129	Trapping characteristics and a donor-complex (DX) model for the persistent-photoconductivity trapping center in Te-doped Al _x Ga _{1-x} As. Physical Review B, 1979, 19, 1015-1030.	1.1	848
130	Dynamic quenching of photocapacitance in CdS-Cu evaporated thin films. Journal of Applied Physics, 1979, 50, 483-488.	1.1	7
131	Direct measurement of pyroelectric figures of merit of proper and improper ferroelectrics. Journal of Applied Physics, 1979, 50, 4942-4950.	1.1	30
132	Infrared quenching of photocapacitance in evaporated ZnS-Ag thin films. Journal of Applied Physics, 1979, 50, 3638-3643.	1.1	10
133	Detection of minority-carrier traps using transient spectroscopy. Electronics Letters, 1979, 15, 349.	0.5	90
134	Recombination enhanced annealing effect in AlGaAs/GaAs remote junction heterostructure lasers. IEEE Journal of Quantum Electronics, 1979, 15, 674-684.	1.0	16
135	Surface states in an n-GaAs/plasma grown native oxide - A modified deep level transient spectroscopy measurement. Surface Science, 1979, 86, 826-834.	0.8	5
136	Deep-level-transient spectroscopy: System effects and data analysis. Journal of Applied Physics, 1979, 50, 5093.	1.1	84
137	Electron traps in n-InP grown by the synthesis solute-diffusion method. Electronics Letters, 1979, 15, 513.	0.5	3
138	Electronic Defects in Metalorganic GaAlAs. Materials Research Society Symposia Proceedings, 1980, 2, 481.	0.1	3
139	Transient Capacitance Studies of a Low-Lying Electron Trap in n-type Silicon. Materials Research Society Symposia Proceedings, 1980, 2, 241.	0.1	0
140	Processing Effects on the Electrical and Optical Properties of Sulfur-Related Defect Centers in Silicon and Similarities to the Oxygen Donor. Materials Research Society Symposia Proceedings, 1980, 2, 79.	0.1	0
141	Growth-parameter dependence of deep levels in molecular-beam-epitaxial GaAs. Electronics Letters, 1980, 16, 171.	0.5	73
142	The impact of molybdenum on silicon and silicon solar cell performance. Solid-State Electronics, 1980, 23, 1185-1190.	0.8	46
143	Effect of titanium, copper and iron on silicon solar cells. Solid-State Electronics, 1980, 23, 415-422.	0.8	112
144	Contribution of the Radiative Mechanism to Electron Capture at the B Centre in Gallium Arsenide. Physica Status Solidi (B): Basic Research, 1980, 101, K69.	0.7	10
146	Degradation of light-emitting diodes (Review). Journal of Applied Spectroscopy, 1980, 33, 1157-1174.	0.3	1
147	A study of deformation-produced deep levels in n-GaAs using deep level transient capacitance spectroscopy. Applied Physics Berlin, 1980, 21, 257-261.	1.4	47

#	ARTICLE	IF	CITATIONS
148	Observation of electron and hole traps in hydrogenated amorphous silicon by voltage- and laser-excited deep level transient spectroscopy. Solar Cells, 1980, 2, 331-347.	0.6	17
149	The electron trap associated with an anion vacancy in ZnSe and ZnSxSe1-x. Solid State Communications, 1980, 34, 359-361.	0.9	40
150	Evaluation of activation energy by means of different trap spectroscopy techniques. Solid State Communications, 1980, 34, 419-422.	0.9	3
151	Optical absorption and photoluminescence of vanadium in n-type GaAs. Solid State Communications, 1980, 36, 171-173.	0.9	28
152	Electron capture cross-section in copper doped CdS. Solid State Communications, 1980, 35, 727-728.	0.9	5
153	Isothermal and non-isothermal C-V trap measurements—A critical comparison. Solid-State Electronics, 1980, 23, 703-713.	0.8	2
154	Radiation induced traps of zinc phosphate and phosphide. Solid-State Electronics, 1980, 23, 93-98.	0.8	6
155	Deep level defects in CdS/GaAs heterojunctions. Thin Solid Films, 1980, 71, 33-39.	0.8	1
156	Impurities in silicon solar cells. IEEE Transactions on Electron Devices, 1980, 27, 677-687.	1.6	420
157	Liquid phase epitaxial growth of high resistivity GaAs layers by impurity doping. Electronics and Communications in Japan, 1980, 63, 109-117.	0.1	0
158	Study of gallium arsenide deep centers by capacitance spectroscopy. Soviet Physics Journal (English) Tj ETQq0 0 0 rBT /Overlock 10 Tf 0.0 1	0.0	1
159	Trap spectroscopy of a-Si:H diodes using transient current techniques. Journal of Electronic Materials, 1980, 9, 713-726.	1.0	34
160	Defect characterization at the growth interface in GaAs epitaxy by metallorganic and chloride depositions. Journal of Electronic Materials, 1980, 9, 213-229.	1.0	7
161	Capacitance transient spectra of processing- and radiation-induced defects in silicon solar cells. Journal of Electronic Materials, 1980, 9, 419-434.	1.0	8
162	Determination of capture cross section and surface-states concentration profile using the surface-acoustic-wave convolver. IEEE Transactions on Electron Devices, 1980, 27, 461-466.	1.6	6
163	Stability of performance and interfacial problems in GaAs MESFET's. IEEE Transactions on Electron Devices, 1980, 27, 1037-1045.	1.6	93
164	Hot hole effect on surface-state density and minority-carrier generation rates in Si-MOS diodes measured by DLTS. IEEE Transactions on Electron Devices, 1980, 27, 1238-1243.	1.6	16
165	Current transient spectroscopy: A high-sensitivity DLTS system. IEEE Transactions on Electron Devices, 1980, 27, 2217-2225.	1.6	80

#	ARTICLE	IF	CITATIONS
166	A computer-controlled deep-level transient spectroscopy system for semiconductor process control. IEEE Transactions on Electron Devices, 1980, 27, 2226-2231.	1.6	23
167	Depleted layer spectroscopy. Lecture Notes in Physics, 1980, , 69-96.	0.3	8
168	Threshold energy for atomic displacement in electron irradiated germanium. Revue De Physique Appliquée, 1980, 15, 15-19.	0.4	34
169	Isothermal Capacitance Transient Spectroscopy for Determination of Deep Level Parameters. Japanese Journal of Applied Physics, 1980, 19, L335-L338.	0.8	153
170	Defect Characterization by Junction Spectroscopy. Materials Research Society Symposia Proceedings, 1980, 2, 85.	0.1	1
171	Detailed electrical characterisation of the deep Cr acceptor in GaAs. Journal of Physics C: Solid State Physics, 1980, 13, 3855-3882.	1.5	143
172	DLTS Study of Cr Trap Density in Thermally Converted Semi-Insulating GaAs. Japanese Journal of Applied Physics, 1980, 19, L409-L412.	0.8	0
173	Photo-Excited DLTS: Measurement of Minority Carrier Traps. Japanese Journal of Applied Physics, 1980, 19, L436-L438.	0.8	21
174	Heat Treatment of Zn-Doped p-Type InP. Japanese Journal of Applied Physics, 1980, 19, 1789-1790.	0.8	9
175	Determination of the free energy level of deep centers, with application to GaAs. Applied Physics Letters, 1980, 37, 413-415.	1.5	63
176	Automatic calibration circuit for a deep level transient spectrometer. Review of Scientific Instruments, 1980, 51, 143-144.	0.6	3
177	Interstitial boron in silicon: A negative-U system. Physical Review B, 1980, 22, 921-931.	1.1	137
178	Fast digital apparatus for capacitance transient analysis. Review of Scientific Instruments, 1980, 51, 1205-1211.	0.6	41
179	Energy dependence of deep level introduction in electron irradiated GaAs. Journal of Applied Physics, 1980, 51, 2038.	1.1	172
180	An annealing study of electron irradiation-induced defects in GaAs. Journal of Applied Physics, 1980, 51, 4150-4157.	1.1	126
181	Thermal generation of carriers in gold-doped silicon. Journal of Applied Physics, 1980, 51, 6252-6257.	1.1	14
182	A correlation between electron traps and growth processes in GaAs prepared by molecular beam epitaxy. Applied Physics Letters, 1980, 36, 311-312.	1.5	129
183	Deep electron traps in organometallic vapor phase grown Al _x Ga _{1-x} As. Journal of Applied Physics, 1980, 51, 5434.	1.1	51

#	ARTICLE	IF	CITATIONS
184	Deep levels in scanned electron-beam annealed silicon. Applied Physics Letters, 1980, 36, 425-428.	1.5	25
185	Admittance spectroscopy of deep levels in Hg _{1-x} Cd _x Te. Journal of Applied Physics, 1980, 51, 6233-6237.	1.1	30
186	Evidence for a shallow level structure in the bulk of semi-insulating GaAs. Journal of Applied Physics, 1980, 51, 4894-4897.	1.1	19
187	Chemical identification of deep energy levels in Si:Se. Journal of Applied Physics, 1980, 51, 6238-6242.	1.1	34
188	Interaction of deep-level traps with the lowest and upper conduction minima in InP. Journal of Applied Physics, 1980, 51, 423-432.	1.1	72
189	Deep levels in ZnSe/GaAs heterojunctions. Journal of Applied Physics, 1980, 51, 5859-5863.	1.1	33
190	Deep sulfur-related centers in silicon. Journal of Applied Physics, 1980, 51, 4212-4217.	1.1	98
191	Hydrogen passivation of point defects in silicon. Applied Physics Letters, 1980, 36, 670-671.	1.5	164
192	Wavelength-modulated photocapacitance spectroscopy. Journal of Applied Physics, 1980, 51, 1863-1865.	1.1	8
193	Direct Measurement of the Bulk Density of Gap States in n-Type Hydrogenated Amorphous Silicon. Physical Review Letters, 1980, 45, 197-200.	2.9	122
194	A deep level transient spectroscopy system using single-gated signal averager. Review of Scientific Instruments, 1980, 51, 1277-1279.	0.6	3
195	Large Lattice Relaxation Processes in Semiconductors. Springer Series in Solid-state Sciences, 1980, , 19-33.	0.3	10
196	Improved characterization of impurities in semiconductors from thermal carrier measurements. Journal of Applied Physics, 1980, 51, 1054-1059.	1.1	4
197	Complex nature of gold-related deep levels in silicon. Physical Review B, 1980, 22, 3917-3934.	1.1	227
198	Deep level defects in polycrystalline cadmium sulfide. Journal of Applied Physics, 1980, 51, 4305-4309.	1.1	23
199	A DLTS study of the gap states of amorphous Si _{1-x} H _x alloys. Journal of Non-Crystalline Solids, 1980, 35-36, 581-586.	1.5	23
200	Primary defects in low-fluence ion-implanted silicon. Applied Physics Letters, 1980, 36, 48-50.	1.5	24
201	Determination of shallow defect levels using thermally stimulated current in implant-layer/substrate junctions of GaAs MESFETs. IEEE Electron Device Letters, 1980, 1, 253-255.	2.2	3

#	ARTICLE	IF	CITATIONS
202	A high sensitivity bridge for the measurement of deep states in semiconductors. Journal of Physics E: Scientific Instruments, 1980, 13, 1055-1061.	0.7	15
203	Chapter 6 Photovoltaic Infrared Detectors. Semiconductors and Semimetals, 1981, , 201-311.	0.4	53
204	Transient radiation study of GaAs metal semiconductor field effect transistors implanted in Cr-doped and undoped substrates. Journal of Applied Physics, 1981, 52, 6630-6636.	1.1	29
205	LPE and VPE In _{1-x} Ga _x As _y P _{1-y} /InP: Transport properties, defects, and device considerations. IEEE Journal of Quantum Electronics, 1981, 17, 150-161.	1.0	35
206	Activation of arsenic-implanted silicon using an incoherent light source. Applied Physics Letters, 1981, 39, 150-152.	1.5	60
207	Deep level transient spectroscopy studies of trapping parameters for centers in indium-doped silicon. Journal of Applied Physics, 1981, 52, 5159-5163.	1.1	23
208	Optical and capacitance spectroscopy of InP:Fe. Journal of Physics C: Solid State Physics, 1981, 14, 5069-5079.	1.5	65
209	Deep-level optical spectroscopy in GaAs. Physical Review B, 1981, 23, 5335-5359.	1.1	427
210	Molecular Beam Epitaxy of III-V Compounds: Technology and Growth Process. Annual Review of Materials Research, 1981, 11, 171-210.	5.5	58
211	Molecular-beam epitaxial growth of InP homoepitaxial layers and their electrical and optical properties. Journal of Applied Physics, 1981, 52, 2852-2859.	1.1	42
212	Chemical trends of deep impurity levels in covalent semiconductors. , 1981, , 191-219.		42
213	DLTS response due to localized states in hydrogenated amorphous silicon. Journal of Non-Crystalline Solids, 1981, 46, 221-234.	1.5	2
214	Fundamentals of junction measurements in the study of deep energy levels in semiconductors. Journal of Physics E: Scientific Instruments, 1981, 14, 1032-1042.	0.7	91
215	Methods for Evaluating Parameters from Thermally Stimulated Curves. , 1981, , 144-182.		6
216	Electronic States Associated with Grain Boundaries in Silicon. Materials Research Society Symposia Proceedings, 1981, 5, 131.	0.1	0
217	Quenched-In Defects in CW Laser-Annealed Si. Materials Research Society Symposia Proceedings, 1981, 4, 313.	0.1	2
218	CW Laser Induced Deep Level Defects in Virgin Silicon.. Materials Research Society Symposia Proceedings, 1981, 4, 325.	0.1	2
219	Deep hole traps in VPE p-type InP. Electronics Letters, 1981, 17, 685.	0.5	6

#	ARTICLE	IF	CITATIONS
220	Temperature dependence of peak heights in deep-level transient spectroscopy. Electronics Letters, 1981, 17, 838.	0.5	11
221	Low leakage current GaAs diodes. IEEE Transactions on Electron Devices, 1981, 28, 796-800.	1.6	15
222	Determination of the channel temperature in a GaAs MESFET from the emission transients of deep traps. Solid-State Electronics, 1981, 24, 551-555.	0.8	2
223	Deep states in transition metal diffused gallium phosphide. Solid-State Electronics, 1981, 24, 249-256.	0.8	39
224	Electrical and optical properties of deep levels in MOVPE grown GaAs. Journal of Crystal Growth, 1981, 55, 164-172.	0.7	93
225	Space-charge analysis for the admittance of semiconductor junctions with deep impurity levels. Applied Physics A: Solids and Surfaces, 1981, 26, 191-202.	1.4	9
226	A simple charge-based DLTS technique. Physica Status Solidi A, 1981, 63, 711-716.	1.7	39
227	DLTS method using a single temperature scanning. Physica Status Solidi A, 1981, 64, 85-93.	1.7	16
228	Dotierungseigenschaften von Eisen in Silizium. Physica Status Solidi A, 1981, 64, 215-224.	1.7	105
229	Eigenschaften der Energieniveaus von Versetzungen in Silizium. Physica Status Solidi A, 1981, 65, 389-401.	1.7	9
230	Eigenschaften repulsiver Zentren in Silizium. Physica Status Solidi A, 1981, 66, 541-549.	1.7	9
231	Photocapacitance study of deep levels in n-CdTe single crystals. Physica Status Solidi A, 1981, 66, 725-736.	1.7	2
232	Magnetic Field Dependence of Defect State in GaAs. Physica Status Solidi (B): Basic Research, 1981, 105, K19.	0.7	1
233	An investigation of the origin of the main electron trap in GaAs. Solid-State Electronics, 1981, 24, 287-291.	0.8	2
234	Measurement of space charge generation-recombination current in Hg _{1-x} CdxTe photodiodes by deep level transient spectroscopy. Solid-State Electronics, 1981, 24, 719-723.	0.8	7
235	Spectroscopic line fitting to DLTS data. Solid-State Electronics, 1981, 24, 1009-1013.	0.8	9
236	Transient distortion and nth order filtering in deep level transient spectroscopy (DnLTS). Solid-State Electronics, 1981, 24, 25-36.	0.8	96
237	Deep levels in MOCVD GaAs grown under different Ga/As mol fractions. Journal of Crystal Growth, 1981, 55, 154-163.	0.7	35

#	ARTICLE	IF	CITATIONS
238	Non-radiative multiphonon transitions. Journal of Luminescence, 1981, 24-25, 689-696.	1.5	11
239	Excited states at deep centers in silicon and II-VI compounds. Journal of Luminescence, 1981, 23, 55-72.	1.5	1
240	Detection of deep centers in semiconductors by strain modulated electron spin resonance: Pt+ in si. Solid State Communications, 1981, 38, 1037-1039.	0.9	8
241	D.L.T.S. measurements of a germanium M-I-S interface. Journal of Electronic Materials, 1981, 10, 571-589.	1.0	15
242	Minority carrier traps in epitaxial gallium arsenide phosphide. Journal of Electronic Materials, 1981, 10, 361-377.	1.0	2
243	Growth of High-Quality $\text{Al}_x\text{Ga}_{1-x}\text{As}$ By OMVPE for laser devices. Journal of Electronic Materials, 1981, 10, 239-253.	1.0	48
244	Bulk traps in silicon-on-sapphire by conductance DLTS. IEEE Transactions on Electron Devices, 1981, 28, 299-304.	1.6	30
245	Photo-excited DLTS: Measurement of minority carrier traps. Electronics and Communications in Japan, 1981, 64, 120-127.	0.1	0
246	Generation of defects at Si-SiO_2 interface in electron beam lithography. Electronics and Communications in Japan, 1981, 64, 98-104.	0.1	0
247	Principles of the optimum lock-in averaging in DLTS measurement. Acta Physica Academiae Scientiarum Hungaricae, 1981, 50, 285-290.	0.1	47
248	Electric field enhanced emission from non-Coulombic traps in semiconductors. Journal of Applied Physics, 1981, 52, 7409-7415.	1.1	210
249	Metastable Electron-Hole-Pair Self-Trapping at a Deep Center in InP. Physical Review Letters, 1981, 47, 142-144.	2.9	15
250	Carbon-acceptor pair centers (Xcenters) in silicon. Journal of Applied Physics, 1981, 52, 5148-5158.	1.1	77
251	Temperature and energy dependences of capture cross sections at surface states in Si metal-oxide-semiconductor diodes measured by deep level transient spectroscopy. Journal of Applied Physics, 1981, 52, 3504-3508.	1.1	78
252	Tellurium donors in silicon. Physical Review B, 1981, 24, 4571-4586.	1.1	136
253	Deep level transient spectroscopy of electron traps and sensitizing centers in undoped CdS single crystals. Journal of Applied Physics, 1981, 52, 261-268.	1.1	20
254	In-depth profiles of deep-trap concentration in Fe-implanted n-type silicon. Journal of Applied Physics, 1981, 52, 5143-5147.	1.1	3
255	Deep-level transient spectroscopy system using a spectrum analyzer. Journal of Applied Physics, 1981, 52, 546-549.	1.1	9

#	ARTICLE	IF	CITATIONS
256	The effect of substrate growth temperature on deep levels in $\text{Al}_x\text{Ga}_{1-x}\text{As}$ grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 1981, 52, 6165-6167.	1.1	41
257	Deep center characterization by optically controlled paramagnetic resonance in AgGaS_2 . <i>Journal of Applied Physics</i> , 1981, 52, 5037-5042.	1.1	12
258	Determination of the drift mobility in high conductivity amorphous silicon. <i>Journal of Applied Physics</i> , 1981, 52, 1387-1391.	1.1	9
259	A study of deep level in bulk InP by transient spectroscopy. <i>Journal of Applied Physics</i> , 1981, 52, 6158-6164.	1.1	29
260	Capture cross section determination by transient current trap filling experiments. <i>Journal of Applied Physics</i> , 1981, 52, 6704-6712.	1.1	36
261	Deep electron traps in hydrogenated amorphous silicon. <i>Physical Review B</i> , 1981, 24, 7457-7459.	1.1	86
262	Radiation Defects in n-Type Germanium Studied by Deep Level Transient Spectroscopy. <i>Japanese Journal of Applied Physics</i> , 1981, 20, L519-L522.	0.8	12
263	Single Thermal Scan DLTS Method. <i>Japanese Journal of Applied Physics</i> , 1981, 20, 1589-1590.	0.8	4
264	Effects of the Growth Conditions on Deep Level Concentration in MOCVD GaAs. <i>Japanese Journal of Applied Physics</i> , 1981, 20, L429-L432.	0.8	39
265	Comparison of Neutron and 2 MeV Electron Damage in N-Type Silicon by Deep-Level Transient Spectroscopy. <i>IEEE Transactions on Nuclear Science</i> , 1981, 28, 3564-3568.	1.2	38
266	Long-length fibre containing high-strength splices. <i>Electronics Letters</i> , 1981, 17, 670.	0.5	13
267	Evaluation of interface states in MOS structures by DLTS with a bipolar rectangular weighting function. <i>Journal Physics D: Applied Physics</i> , 1981, 14, 895-898.	1.3	25
268	X-Y plotter capacitance meter interface for deep level spectroscopy. <i>Journal of Physics E: Scientific Instruments</i> , 1981, 14, 367-372.	0.7	6
269	Phase Shift Spectroscopy of Modulated Photocurrent: Its Application to Gold Levels in Crystalline Si. <i>Japanese Journal of Applied Physics</i> , 1981, 20, L689-L692.	0.8	10
270	A sensitive and inexpensive signal analyser for deep level studies. <i>Journal of Physics E: Scientific Instruments</i> , 1981, 14, 464-467.	0.7	26
271	Formation of Thick, Thermally-Stable High-Resistivity-Layers in GaAs by Oxygen Ion Implantation. <i>Japanese Journal of Applied Physics</i> , 1981, 20, 901-907.	0.8	24
272	Determination of the Density of State Distribution of a-Si:H by Isothermal Capacitance Transient Spectroscopy. <i>Japanese Journal of Applied Physics</i> , 1981, 20, L549-L552.	0.8	46
273	A Modulated DLTS Method for Large Signal Analysis (C2-DLTS). <i>Japanese Journal of Applied Physics</i> , 1981, 20, L45-L47.	0.8	22

#	ARTICLE	IF	CITATIONS
274	Electron irradiation effects in p-type GaAs. Journal of Applied Physics, 1982, 53, 8691-8696.	1.1	34
275	Sn and Te doping of molecular beam epitaxial GaAs using a SnTe source. Journal of Applied Physics, 1982, 53, 3010-3018.	1.1	35
276	A study of the chemical oxide/InP interface states. Journal of Applied Physics, 1982, 53, 7450-7453.	1.1	14
277	Motion of deep gold-related centers in reverse-biased silicon junction diodes at room temperature. Applied Physics Letters, 1982, 41, 1148-1150.	1.5	7
278	Change of interface state spectrum in Al/SiO ₂ /Si structures with biasing during electron irradiation. Applied Physics Letters, 1982, 40, 601-603.	1.5	14
279	Characterization and annealing behavior of deep levels in CdTe epitaxial layers. Journal of Applied Physics, 1982, 53, 4948-4954.	1.1	23
280	A novel method to detect nonexponential transients in deep level transient spectroscopy. Journal of Applied Physics, 1982, 53, 7397-7400.	1.1	36
281	Evidence of intrinsic double acceptor in GaAs. Applied Physics Letters, 1982, 41, 532-534.	1.5	107
282	Deep level defects in heteroepitaxial zinc selenide. Journal of Applied Physics, 1982, 53, 3076-3084.	1.1	31
283	Electron irradiation induced deep levels in InP. Applied Physics Letters, 1982, 41, 956-958.	1.5	68
284	Compensation mechanisms related to boron implantation in GaAs. Journal of Applied Physics, 1982, 53, 8706-8715.	1.1	56
285	Hydrogen passivation of a bulk donor defect (E _c +0.36 eV) in GaAs. Journal of Applied Physics, 1982, 53, 4509-4511.	1.1	52
286	Energy dependence of electron-capture cross section of gap states in n-type a-Si:H. Physical Review B, 1982, 25, 4313-4316.	1.1	62
287	Intrinsic density n _i (T) in GaAs: Deduced from band gap and effective mass parameters and derived independently from Cr acceptor capture and emission coefficients. Journal of Applied Physics, 1982, 53, 520-531.	1.1	158
288	External generation of gate delays in a boxcar integrator—Application to deep level transient spectroscopy. Review of Scientific Instruments, 1982, 53, 210-213.	0.6	5
289	Profiling of deep impurities by persistent photocurrent measurements. Applied Physics Letters, 1982, 41, 628-629.	1.5	40
290	Determination of the density of localized states in fluorinated a-Si using deep level transient spectroscopy. Applied Physics Letters, 1982, 41, 178-180.	1.5	18
291	Quenched-in defects in laser annealed silicon. Applied Physics Letters, 1982, 40, 418-420.	1.5	16

#	ARTICLE	IF	CITATIONS
292	Measurement of the density of gap states in hydrogenated amorphous silicon by space charge spectroscopy. Physical Review B, 1982, 25, 5285-5320.	1.1	463
293	Charge transient spectroscopy. Applied Physics Letters, 1982, 41, 1063-1065.	1.5	80
294	Hydrogen passivation of gold-related deep levels in silicon. Physical Review B, 1982, 26, 7105-7108.	1.1	113
295	Hydrogen passivation of copper-related defects in germanium. Applied Physics Letters, 1982, 40, 253-255.	1.5	46
296	Photoluminescence studies of the 1.911-eV Cu-related complex in GaP. Physical Review B, 1982, 26, 827-845.	1.1	81
297	Transient capacitance spectroscopy in polycrystalline silicon. Journal of Applied Physics, 1982, 53, 8633-8638.	1.1	20
298	Characterization of electron traps in indium tin oxide on p-type InP solar cells. Journal of Applied Physics, 1982, 53, 3085-3087.	1.1	4
299	Observation of deep levels associated with the GaAs/Al _x Ga _{1-x} As interface grown by molecular beam epitaxy. Applied Physics Letters, 1982, 40, 520-522.	1.5	58
300	Spectroscopic study of vanadium in GaP and GaAs. Physical Review B, 1982, 25, 5598-5606.	1.1	77
301	Transient-Capacitance Measurement of the Grain Boundary Levels in Semiconductors. Physical Review Letters, 1982, 48, 424-427.	2.9	29
302	Nonadiabatic formulation for radiationless transitions induced by classical lattice vibrations. Physical Review B, 1982, 26, 3547-3558.	1.1	10
303	Thermal and electrical stability of gamma-ray induced defects in germanium. Radiation Effects, 1982, 61, 135-141.	0.4	2
304	The mobility of $\hat{\Gamma}^3$ -ray induced defects in reverse biased germanium n ⁺ p diodes. Radiation Effects, 1982, 68, 11-13.	0.4	4
305	Relation between Cr-Level and Main Electron Trap (EL2) in Boat-Grown Bulk GaAs. Japanese Journal of Applied Physics, 1982, 21, 1479-1484.	0.8	8
306	New gamma-radiation damage centres observed in germanium by deep level transient spectroscopy. Radiation Effects, 1982, 60, 129-134.	0.4	5
307	Defect States in n-Type Germanium Irradiated with 1.5 MeV Electrons. Japanese Journal of Applied Physics, 1982, 21, 930-935.	0.8	23
308	Isothermal Capacitance Transient Spectroscopy in MIS Structures. Japanese Journal of Applied Physics, 1982, 21, 1628-1632.	0.8	28
309	Reduction in $\hat{\Gamma}^3$ -ray damage in hydrogenated silicon. Radiation Effects, 1982, 68, 25-27.	0.4	10

#	ARTICLE	IF	CITATIONS
310	Deep Level Fourier Spectroscopy for Determination of Deep Level Parameters. Japanese Journal of Applied Physics, 1982, 21, 462-466.	0.8	29
311	Hole traps in n-type Ga _{1-x} Al _x As grown by organometallic vapour phase epitaxy. Electronics Letters, 1982, 18, 75.	0.5	19
312	Note on the Analysis of DLTS and C2-DLTS. Japanese Journal of Applied Physics, 1982, 21, 67-70.	0.8	14
313	Improved thermometry for deep-level measurements. Journal of Physics E: Scientific Instruments, 1982, 15, 499-501.	0.7	0
314	Deep levels introduced by electron irradiation of InP. Journal of Physics C: Solid State Physics, 1982, 15, L1007-L1012.	1.5	17
315	Evaluation of Minority-Carrier Traps at the Interface in MOS Structures by Optical DLTS. Japanese Journal of Applied Physics, 1982, 21, L165-L166.	0.8	7
316	Hydrogen passivation of deep donor centres in high-purity epitaxial GaAs. Electronics Letters, 1982, 18, 715.	0.5	21
317	Hydrogen-induced DLTS signal in pd/n-Si Schottky diodes. Electronics Letters, 1982, 18, 314.	0.5	21
318	Use of thermal annealing for radiation hardening of germanium to γ -rays. Radiation Effects, 1982, 67, 63-67.	0.4	4
319	Pulsed Electron Beam Annealing Induced Deep Level Defects in Virgin Silicon. Materials Research Society Symposia Proceedings, 1982, 13, 449.	0.1	1
320	Process-Induced Defects in High-Purity GaAs. Materials Research Society Symposia Proceedings, 1982, 14, 283.	0.1	1
321	Electronic Properties of Grain Boundaries in GaAs: A Study of Oriented Bicrystals Prepared by Epitaxial Lateral Overgrowth. Materials Research Society Symposia Proceedings, 1982, 14, 375.	0.1	6
322	Degradation Behavior of Optoelectronic Devices. Materials Research Society Symposia Proceedings, 1982, 14, 477.	0.1	4
323	Metastable Defect Configurations in Semiconductors. Materials Research Society Symposia Proceedings, 1982, 14, 95.	0.1	3
324	Deep level defects in gamma-ray irradiated ge doped with pb or sn. Radiation Effects, 1982, 68, 35-38.	0.4	0
325	New method for determining distribution of interface states in an MIS system. Electronics Letters, 1982, 18, 290.	0.5	2
326	DLTS studies of deep traps in CdTe. Journal of Physics C: Solid State Physics, 1982, 15, L573-L583.	1.5	18
327	Transient capacitance studies of an electron trap at $E_c + E_T = 0.105$ eV in phosphorus-doped silicon. Journal of Applied Physics, 1982, 53, 5715-5719.	1.1	62

#	ARTICLE	IF	CITATIONS
328	Charge collection scanning electron microscopy. Journal of Applied Physics, 1982, 53, R51-R80.	1.1	737
329	Point Defects in GaP, GaAs, and InP. Advances in Electronics and Electron Physics, 1982, 58, 81-141.	0.6	69
330	Deep levels and associated carrier recombination processes in Zn-annealed ZnSe single crystals. Journal of Physics C: Solid State Physics, 1982, 15, 5497-5505.	1.5	15
331	Defect production and lifetime control in electron and γ -irradiated silicon. Journal of Applied Physics, 1982, 53, 5720-5732.	1.1	298
332	Simple microcomputer-based apparatus for combined DLTS-CV measurement. Review of Scientific Instruments, 1982, 53, 1001-1006.	0.6	13
333	Electron traps in ZnSe grown by liquid-phase epitaxy. Journal of Applied Physics, 1982, 53, 1018-1022.	1.1	19
334	Impurity and defect levels in beryllium-doped GaAs grown by molecular beam epitaxy. Journal of Applied Physics, 1982, 53, 6391-6398.	1.1	43
335	Deep levels in ion-implanted Si after beam annealing. Applied Physics Letters, 1982, 40, 68-71.	1.5	14
336	Mobility of copper centers in reverse-biased germanium junction diodes. Applied Physics Letters, 1982, 41, 176-178.	1.5	12
337	Deep level studies of oxygen doped GaAs-Au Schottky barrier diodes. Journal of Electronic Materials, 1982, 11, 321-333.	1.0	1
338	Accelerated degradation in GaP and GaAs _{1-x} Al _x (x=0.15-0.32) visible LEDs by contaminant Cu during forward bias operation. Journal of Electronic Materials, 1982, 11, 631-645.	1.0	5
339	Capture cross sections of the gold donor and acceptor states in n-type Czochralski silicon. Solid-State Electronics, 1982, 25, 643-649.	0.8	59
340	Electron and hole traps in the Cu _x S-CdS heterojunction. Journal of Crystal Growth, 1982, 59, 240-245.	0.7	6
341	Deep level transient spectroscopy of neutron irradiated semiconductors. Journal of Nuclear Materials, 1982, 108-109, 700-708.	1.3	10
342	The influence of post-emitter processing on the current gain of bipolar transistors. IEEE Transactions on Electron Devices, 1982, 29, 430-435.	1.6	3
343	DLTS Studies of Neutron Damage in P-Type Silicon. IEEE Transactions on Nuclear Science, 1982, 29, 1387-1392.	1.2	4
344	Interpretation of profiles obtained by C(V) technique in presence of deep traps: Application to proton irradiated GaAs samples. Solid-State Electronics, 1982, 25, 577-582.	0.8	11
345	Physical characterization of deep bulk levels by the MOS conductance technique. Solid-State Electronics, 1982, 25, 5-14.	0.8	4

#	ARTICLE	IF	CITATIONS
346	Deep metal-related centres in germanium. Solid-State Electronics, 1982, 25, 305-311.	0.8	23
347	Electron trap behaviour in Te-doped GaAs _{0.6} P _{0.4} . Solid-State Electronics, 1982, 25, 325-333.	0.8	25
348	A study of deep metal-related centres in germanium by capacitance spectroscopy. Solid-State Electronics, 1982, 25, 499-503.	0.8	14
349	Junction structure effects on constant capacitance DLTS and ODLTS spectra. Solid-State Electronics, 1982, 25, 893-901.	0.8	9
350	Optical characterization of deep energy levels in semiconductors. Progress in Crystal Growth and Characterization, 1982, 5, 47-88.	0.8	18
351	Study of E3 trap annealing in GaAs by DDLTS technique. Solid State Communications, 1982, 44, 41-45.	0.9	8
352	Investigation of deep levels in epitaxially grown CdS and CdTe layers. Journal of Crystal Growth, 1982, 59, 229-233.	0.7	10
353	DLTS investigation of some II-VI Compounds. Journal of Crystal Growth, 1982, 59, 234-239.	0.7	18
354	DLTS studies of deep levels in semiconducting N-CdTe single crystals. Journal of Physics and Chemistry of Solids, 1982, 43, 5-12.	1.9	28
355	The structure and properties of metal-semiconductor interfaces. Surface Science Reports, 1982, 2, 123-326.	3.8	890
356	Bound defect states in IV-VI semiconductors. Applied Physics A: Solids and Surfaces, 1982, 29, 177-189.	1.4	29
357	A study of electronic states near the interface in ferroelectric-semiconductor heterojunction prepared by rf sputtering of PbTiO ₃ . Applied Physics A: Solids and Surfaces, 1982, 28, 161-166.	1.4	61
358	A capacitance meter of high absolute sensitivity suitable for scanning DLTS application. Physica Status Solidi A, 1982, 71, 159-167.	1.7	27
363	Energy Levels of Some Rare-Earth Related Impurities in Germanium. Physica Status Solidi (B): Basic Research, 1982, 109, K135.	0.7	2
364	Degradation Characteristics of Au-Si Nuclear Detectors by a Few MeV Charged Particle Irradiation. IEEE Transactions on Nuclear Science, 1983, 30, 371-375.	1.2	5
365	Characterization of electron traps in ion-implanted GaAs MESFET's on undoped and Cr-doped LEC semi-insulating substrates. IEEE Transactions on Electron Devices, 1983, 30, 586-592.	1.6	24
366	Planar Be-implanted GaAs junction formation using swept-line electron beam annealing. IEEE Transactions on Electron Devices, 1983, 30, 1755-1760.	1.6	5
367	Electrical and optical properties of MOVPE grown GaAs _{1-x} P _x . Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics, 1983, 2, 1742-1747.	0.4	7

#	ARTICLE	IF	CITATIONS
368	Deep level effects in silicon and germanium after plasma hydrogenation. Journal of Electronic Materials, 1983, 12, 1003-1014.	1.0	12
369	Nonequilibrium deep-center trapping in liquid epitaxy on gallium arsenide. Soviet Physics Journal (English Translation of Izvestiia Vysshikh Uchebnykh Zavedenii, Fizika), 1983, 26, 889-898.	0.0	0
370	Deep centers in gallium arsenide associated with intrinsic structural defects. Soviet Physics Journal (English Translation of Izvestiia Vysshikh Uchebnykh Zavedenii, Fizika), 1983, 26, 919-927.	0.0	0
371	Resonance charge relaxation in physical barrier layers. Soviet Physics Journal (English Translation of) Tj ETQq1 1 0.784314 rgBT /Overl	0.0	4
372	Deep level investigation of Cr/n-GaAs schottky barrier diodes. Materials Chemistry and Physics, 1983, 9, 315-320.	2.0	1
373	A DLTS study of electron irradiated InP. Journal of Crystal Growth, 1983, 64, 200-205.	0.7	9
374	A study of grown-in impurities in silicon by deep-level transient spectroscopy. Solid-State Electronics, 1983, 26, 1039-1051.	0.8	74
375	Fourier-transformation analysis of deep level transient signals in semiconductors. Solid-State Electronics, 1983, 26, 689-694.	0.8	30
376	The mobility of a nickel-related centre in reverse biased germanium n+p diodes. Solid-State Electronics, 1983, 26, 1019-1021.	0.8	5
379	GaAs Anodic Oxide Interface Examination by Deep Level Transient Current Spectroscopy. Physica Status Solidi A, 1983, 77, 323-330.	1.7	5
380	Electron Traps and Deep Levels in Cadmium Selenide. Physica Status Solidi A, 1983, 77, 535-544.	1.7	16
381	Electrical and Optical Characteristics of GaAs _{0.6} P _{0.4} LEDs Fabricated by Zn Semi-Closed Diffusion Method. Physica Status Solidi A, 1983, 77, 741-747.	1.7	2
382	DLTS investigation of electron traps in As-grown and Cd-fired CdS. Physica Status Solidi A, 1983, 78, 267-275.	1.7	5
384	Caractérisation de structures MIS (Al _x Si ₃ N ₄ i _x GaAs) par différentes méthodes capacitives. Physica Status Solidi A, 1983, 80, 185-193.	1.7	4
385	DLTS Investigations of SiO ₂ Interface States of Electron Beam Irradiated MOS Structures. Physica Status Solidi (B): Basic Research, 1983, 118, K133.	0.7	4
386	Investigation of impurity levels in n-type indium selenide by means of Hall effect and deep level transient spectroscopy. Applied Physics A: Solids and Surfaces, 1983, 31, 139-145.	1.4	69
387	Passivation of gallium arsenide by reactively sputtered gallium nitride thin films. Microelectronics Journal, 1983, 14, 43-48.	1.1	1
388	The electronic properties of dangling bonds in silicon. Physica B: Physics of Condensed Matter & C: Atomic, Molecular and Plasma Physics, Optics, 1983, 116, 79-84.	0.9	2

#	ARTICLE	IF	CITATIONS
389	The hole trapping defects in irradiated germanium as studied by DLTS. <i>Physica B: Physics of Condensed Matter & C: Atomic, Molecular and Plasma Physics, Optics</i> , 1983, 116, 343-348.	0.9	3
390	Manifestations of deep levels point defects in GaAs. <i>Physica B: Physics of Condensed Matter & C: Atomic, Molecular and Plasma Physics, Optics</i> , 1983, 116, 371-383.	0.9	20
391	The effects of deep levels in GaAs MESFETs. <i>Physica B: Physics of Condensed Matter & C: Atomic, Molecular and Plasma Physics, Optics</i> , 1983, 117-118, 44-49.	0.9	10
392	Transition metal impurities in InP : Defect complexes and native defects. <i>Physica B: Physics of Condensed Matter & C: Atomic, Molecular and Plasma Physics, Optics</i> , 1983, 117-118, 176-178.	0.9	6
393	Silicon molecular beam epitaxy. <i>Thin Solid Films</i> , 1983, 106, 1-136.	0.8	138
394	Deep level transient spectroscopy of interface and bulk trap states in InP metal/oxide/semiconductor structures. <i>Thin Solid Films</i> , 1983, 103, 141-153.	0.8	21
395	Thermal emission rates and capture cross-section of majority carriers at titanium levels in silicon. <i>Solid-State Electronics</i> , 1983, 26, 1-6.	0.8	29
396	Characterization of epitaxial films of CdTe and CdS grown by hot-wall epitaxy. <i>Solar Energy Materials and Solar Cells</i> , 1983, 9, 199-206.	0.4	8
397	Point defects in II-VI compounds. <i>Progress in Crystal Growth and Characterization</i> , 1983, 6, 103-162.	0.8	32
398	Deep level transient spectroscopy of hole traps in Zn-annealed ZnTe. <i>Solid State Communications</i> , 1983, 46, 795-798.	0.9	7
399	Influence from free-carrier tails in deep level transient spectroscopy (DLTS). <i>Solid State Communications</i> , 1983, 46, 255-258.	0.9	25
400	Electric field effects on radiation defects annealing in p-InP. <i>Solid State Communications</i> , 1983, 46, 673-675.	0.9	7
401	Optical and thermal properties of Fe in GaP. <i>Solid State Communications</i> , 1983, 48, 427-430.	0.9	19
402	Photovoltaic and electrical properties of n-CdS/p-Si heterojunction solar cells. <i>Journal of Crystal Growth</i> , 1983, 61, 494-498.	0.7	7
403	Electron irradiation defects in InP. <i>Journal of Crystal Growth</i> , 1983, 64, 194-199.	0.7	14
404	Impurity and Defect Levels (Experimental) in Gallium Arsenide. <i>Advances in Electronics and Electron Physics</i> , 1983, , 63-160.	0.6	63
405	Deep defect states in quenched, gamma-irradiated germanium. <i>Radiation Effects</i> , 1983, 69, 39-46.	0.4	8
406	A specific trap level at 78 meV in undoped liquid encapsulated Czochralski grown GaAs-Si materials. <i>Journal of Applied Physics</i> , 1983, 54, 6767-6770.	1.1	20

#	ARTICLE	IF	CITATIONS
407	Electrical characterization of grain boundaries in GaAs. Journal of Applied Physics, 1983, 54, 1429-1440.	1.1	26
408	Deep level, quenched-in defects in silicon doped with gold, silver, iron, copper or nickel. Journal of Physics C: Solid State Physics, 1983, 16, 1665-1673.	1.5	80
409	Positron annihilation in electron-irradiated n-type gap crystals. Radiation Effects, 1983, 79, 123-130.	0.4	13
410	Energy concepts of insulator-semiconductor interface traps. Journal of Applied Physics, 1983, 54, 5240-5244.	1.1	54
411	Photoionization cross section of electron irradiation induced levels in silicon. Journal of Applied Physics, 1983, 54, 5112-5116.	1.1	11
412	Interface states at the SiO ₂ -Si interface. Surface Science, 1983, 132, 422-455.	0.8	143
413	Chapter 2 The Electrical and Photoelectronic Properties of Semi-Insulating GaAs. Semiconductors and Semimetals, 1983, , 75-170.	0.4	107
414	Annealing of electron-induced defects in n-type germanium. Physical Review B, 1983, 28, 3372-3377.	1.1	40
415	Deep level transient spectroscopy evaluation of nonexponential transients in semiconductor alloys. Journal of Applied Physics, 1983, 54, 5117-5122.	1.1	194
416	Copper-related deep level defects in III-V semiconductors. Journal of Applied Physics, 1983, 54, 3203-3212.	1.1	82
417	Characterization of deep levels in modulation-doped AlGaAs/GaAs FET's. IEEE Electron Device Letters, 1983, 4, 360-362.	2.2	33
418	Frequency-domain study of trapping dynamics in SiGaAs. Journal of Physics C: Solid State Physics, 1983, 16, L1159-L1164.	1.5	7
419	Photo-Induced Current Transient Spectroscopy in High-Resistivity Bulk Material. I. Computer Controlled Multi-Channel PICTS System with High-Resolution. Japanese Journal of Applied Physics, 1983, 22, 621-628.	0.8	85
420	Emission and capture measurements on deep levels in InP. Journal of Physics C: Solid State Physics, 1983, 16, 4173-4180.	1.5	7
421	Confirmation of Tunneling Current via Traps by DLTS Measurements in InGaAs Photodiodes. Japanese Journal of Applied Physics, 1983, 22, L364-L366.	0.8	20
422	Photo-Induced Current Transient Spectroscopy in High-Resistivity Bulk Material. II. Influence of Non-Exponential Transient on Determination of Deep Trap Parameters. Japanese Journal of Applied Physics, 1983, 22, 629-635.	0.8	33
423	DLTS Study of RIE-Induced Deep Levels in Si Using p+n Diode Arrays. Japanese Journal of Applied Physics, 1983, 22, 281-286.	0.8	32
424	Oxygen-Related Defects in Irradiated Germanium. Japanese Journal of Applied Physics, 1983, 22, L353-L355.	0.8	23

#	ARTICLE	IF	CITATIONS
425	Current DLTS with a Bipolar Rectangular Weighting Function for a Neutron-Irradiated P-Type Si. Japanese Journal of Applied Physics, 1983, 22, 371-371.	0.8	10
426	Palladium and platinum related levels in silicon: Effect of a hydrogen plasma. Journal of Applied Physics, 1983, 54, 3613-3615.	1.1	63
427	Degradation mechanism of Mo/GaAs _{0.6} P _{0.4} Schottky barriers. Journal of Applied Physics, 1983, 54, 4482-4489.	1.1	1
428	Spectrum analyzer of exponentially decaying signals. Review of Scientific Instruments, 1983, 54, 1362-1363.	0.6	4
429	Defect Symmetry from Stress Transient Spectroscopy. Physical Review Letters, 1983, 51, 1286-1289.	2.9	47
430	Deep levels in InGaAsP/InP pn diodes grown by vapor phase epitaxy. Journal of Applied Physics, 1983, 54, 806-813.	1.1	7
431	Transient capacitance measurements on resistive samples. Journal of Applied Physics, 1983, 54, 2907-2910.	1.1	99
432	Platinum diffusion into silicon from PtSi. Applied Physics Letters, 1983, 43, 1118-1120.	1.5	33
433	Hydrogen passivation of a nickel related defect in germanium. Journal of Applied Physics, 1983, 54, 1156-1158.	1.1	7
434	Transient capacitance spectroscopy on large quantum well heterostructures. Journal of Applied Physics, 1983, 54, 4689-4691.	1.1	57
435	Analysis of nonexponential transient capacitance in silicon diodes heavily doped with platinum. Journal of Applied Physics, 1983, 54, 2786-2791.	1.1	31
436	Hydrogen passivation of deep metal related donor centers in germanium. Journal of Applied Physics, 1983, 54, 820-823.	1.1	30
437	Techniques for improving the Si-SiO ₂ interface characterization. Journal of Applied Physics, 1983, 54, 5183-5198.	1.1	9
438	Studies of deep levels in Si epitaxy grown by SiCl ₄ -H ₂ system. Journal of Applied Physics, 1983, 54, 6773-6775.	1.1	2
439	Hydrogen passivation of laser induced defects in germanium. Journal of Applied Physics, 1983, 54, 440-441.	1.1	13
440	Variation of the midgap electron traps (EL2) in liquid encapsulated Czochralski GaAs. Journal of Applied Physics, 1983, 54, 6448-6451.	1.1	113
441	Time dependent response of interface states in indium phosphide metal-insulator-semiconductor capacitors investigated with constant capacitance deep level transient spectroscopy. Journal of Applied Physics, 1983, 54, 4014-4021.	1.1	70
442	The electrical properties of deep copper and nickel related centers in silicon. Journal of Applied Physics, 1983, 54, 1375-1379.	1.1	78

#	ARTICLE	IF	CITATIONS
443	Electrical properties of Fe in GaAs. Journal of Applied Physics, 1983, 54, 814-819.	1.1	76
444	Hydrogen passivation of argon sputter-etch induced electrically active defects on Ge, Si, and GaAs. Radiation Effects, 1983, 79, 21-27.	0.4	8
445	AsH ₃ to Ga(CH ₃) ₃ Mole Ratio Dependence of Dominant Deep Levels in MOCVD GaAs. Japanese Journal of Applied Physics, 1983, 22, 923-929.	0.8	47
446	DLTS Determination of the Mo Acceptor Level in Mo-GaAs _{0.6} P _{0.4} Schottky Diodes. Japanese Journal of Applied Physics, 1983, 22, L336-L337.	0.8	0
447	Electrical Resistivity of Undoped GaAs Single Crystals Grown by Magnetic Field Applied LEC Technique. Japanese Journal of Applied Physics, 1983, 22, L325-L327.	0.8	24
448	Deep Levels in InP Grown by MOCVD. Japanese Journal of Applied Physics, 1983, 22, 658-662.	0.8	32
449	A Capacitance Investigation of InGaAs/InP Isotype Heterojunction. Japanese Journal of Applied Physics, 1983, 22, 1502-1509.	0.8	59
450	Distribution of the Main Electron Trap EL2 in Undoped LEC GaAs. Japanese Journal of Applied Physics, 1983, 22, L502-L504.	0.8	9
451	Deformation-induced point defects in germanium. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1983, 48, 55-61.	0.6	15
452	Chapter 1 Deep Levels in Wide Band-Gap III-V Semiconductors. Semiconductors and Semimetals, 1983, , 1-74.	0.4	20
453	Characterization of Silicon Epitaxial Films. Edpacs, 1983, , 73-145.	0.5	2
454	Chapter 4 Models for Mid-Gap Centers in Gallium Arsenide. Semiconductors and Semimetals, 1984, , 233-361.	0.4	0
455	Metal-Semiconductor Schottky Barrier Junctions and Their Applications. , 1984, ,		285
456	Effect of Metals Used for Schottky Barrier Contacts on DLTS Signals for LEC n-GaAs Crystals. Japanese Journal of Applied Physics, 1984, 23, L313-L315.	0.8	29
457	Defect Photoluminescence in Quenched High-Purity Silicon. Japanese Journal of Applied Physics, 1984, 23, 622-627.	0.8	0
458	A deep centre with excited states in MOVPE GaP grown under high phosphorus pressure. Journal of Physics C: Solid State Physics, 1984, 17, 6521-6533.	1.5	18
459	A simple circuit to aid direct measurement of capture cross sections of deep level impurities. Journal of Physics E: Scientific Instruments, 1984, 17, 949-951.	0.7	2
460	Effects of Growth Conditions on Electron Trap Concentrations in Si-Doped Al _{0.2} Ga _{0.8} As Grown by MBE. Japanese Journal of Applied Physics, 1984, 23, L112-L114.	0.8	12

#	ARTICLE	IF	CITATIONS
461	Electronic properties of native deep-level defects in liquid-phase epitaxial GaAs. Journal of Physics C: Solid State Physics, 1984, 17, 259-272.	1.5	47
462	On the exploitation of thermally stimulated capacitance measurements. Journal Physics D: Applied Physics, 1984, 17, 2047-2051.	1.3	6
463	Quenched-in deep acceptors in germanium. Journal of Physics C: Solid State Physics, 1984, 17, 2375-2379.	1.5	7
464	Deep-centre characterisation by thermally controlled paramagnetic resonance: TCPR. Journal of Physics C: Solid State Physics, 1984, 17, 2391-2399.	1.5	5
465	Chemical trends in the activation energies of DXcenters. Applied Physics Letters, 1984, 45, 1322-1323.	1.5	77
466	Dynamics of capture from free-carrier tails in depletion regions and its consequences in junction experiments. Journal of Applied Physics, 1984, 55, 4266-4274.	1.1	43
467	Uniaxial stress apparatus for deep level transient spectroscopy studies. Review of Scientific Instruments, 1984, 55, 210-212.	0.6	10
468	Deep and shallow levels in indium phosphide irradiated with 200 keV deuterons. Journal of Applied Physics, 1984, 55, 3595-3602.	1.1	12
469	Modifications to the Boonton 72BD capacitance meter for deep-level transient spectroscopy applications. Review of Scientific Instruments, 1984, 55, 200-203.	0.6	24
470	Deep levels in CdTe. Journal of Applied Physics, 1984, 55, 3605-3612.	1.1	44
471	Improved Schottky capacitance spectroscopy method for the study of interface states in metal-semiconductor junctions. Applied Physics Letters, 1984, 45, 1212-1214.	1.5	19
472	Dynamic defect reactions induced by multiphonon nonradiative recombination of injected carriers at deep levels in semiconductors. Physical Review B, 1984, 29, 4616-4630.	1.1	77
473	Deuterium in germanium: Interaction with point defects. Journal of Applied Physics, 1984, 55, 1464-1471.	1.1	27
474	Transient capacitance spectroscopy of Na-induced surface states at the Si/SiO ₂ interface. Journal of Applied Physics, 1984, 55, 971-979.	1.1	22
475	Determination of trapped charge emission rates from nonexponential capacitance transients due to high trap densities in semiconductors. Journal of Applied Physics, 1984, 55, 565-570.	1.1	59
476	Interpretation of deep-level optical spectroscopy and deep-level transient spectroscopy data: Application to irradiation defects in GaAs. Physical Review B, 1984, 30, 5822-5834.	1.1	55
477	Characterization of CdS/CdTe thin-film solar cells by admittance spectroscopy and deep-level transient spectroscopy. Journal of Applied Physics, 1984, 56, 3508-3517.	1.1	31
478	Energy and orientation dependence of electron-irradiation-induced defects in InP. Physical Review B, 1984, 30, 1119-1121.	1.1	41

#	ARTICLE	IF	CITATIONS
479	Study of electric field enhanced emission of deep levels using a new emission spectroscopic technique. Applied Physics Letters, 1984, 44, 211-213.	1.5	9
480	Hole traps in p-type electrochemically deposited CdTe thin films. Journal of Applied Physics, 1984, 55, 1020-1022.	1.1	25
481	Photocurrent deep level transient spectroscopy in silicon. Journal of Applied Physics, 1984, 55, 3636-3643.	1.1	19
482	Deep energy levels in ZnSxSe1-x alloys. Journal of Applied Physics, 1984, 56, 2768-2777.	1.1	12
483	The nature of the dominant β^3 -induced defects in high-purity germanium. Radiation Effects, 1984, 81, 293-308.	0.4	7
484	Electronically active defects in cw beam-annealed Si. II. Deep level transient spectroscopy. Journal of Applied Physics, 1984, 55, 3083-3091.	1.1	16
485	Phonon-kick mechanism for defect reactions enhanced by electronic excitation. Journal of Physics C: Solid State Physics, 1984, 17, 6071-6086.	1.5	31
486	Hydrogen-related deep levels in proton-bombarded silicon. Journal of Physics C: Solid State Physics, 1984, 17, 6317-6329.	1.5	128
487	Predictions of Deep-Impurity-Level Energies in Semiconductors. Advances in Electronics and Electron Physics, 1984, , 101-159.	0.6	34
488	A Study of Deep Levels in MOCVD-Grown InP/Semi-Insulating InP Structure. Japanese Journal of Applied Physics, 1984, 23, 79-83.	0.8	7
489	Deep Electron Traps in Undoped GaAs Grown by MOCVD. Japanese Journal of Applied Physics, 1984, 23, L296-L298.	0.8	16
490	Electron induced degradation and recovery under space conditions of lithium-doped silicon solar cells. Radiation Effects, 1984, 81, 263-275.	0.4	3
491	Electrical and optical properties of the neutral nickel acceptor in gallium phosphide. Journal of Physics C: Solid State Physics, 1984, 17, 6161-6167.	1.5	10
492	Physics of Schottky Barrier Junctions. , 1984, , 1-60.		30
493	A modeling technique for characterizing ion-implanted material using C-V and DLTS data. Solid-State Electronics, 1984, 27, 367-373.	0.8	14
494	The effects of plasma and ion beam processing on the properties of n-GaAs Schottky diodes. Vacuum, 1984, 34, 209-213.	1.6	10
495	Theoretical discussion of deep level optical and thermal spectroscopy in semiconductors: Application to E1 and E2 in GaAs. Solid State Communications, 1984, 51, 509-513.	0.9	9
496	Identification of deep radiative levels in VPE ZnSe. Journal of Luminescence, 1984, 31-32, 433-435.	1.5	0

#	ARTICLE	IF	CITATIONS
497	A Simple and Low-Cost Personal Computer-Based Automatic Deep-Level Transient Spectroscopy System for Semiconductor Devices Analysis. IEEE Transactions on Instrumentation and Measurement, 1984, 33, 259-263.	2.4	10
498	Electrical and optical properties of GaP grown on Si by MOVPE. Journal of Crystal Growth, 1984, 68, 340-344.	0.7	28
499	Analysis of DLTS Curves Corresponding to Non-Exponential Transients. Physica Status Solidi A, 1984, 81, 353-360.	1.7	8
500	Dispersion of Laser-Induced Nonlinear Optical Susceptibility in CdS. Physica Status Solidi A, 1984, 84, 555-560.	1.7	5
501	Non-Exponential Capacitance Transient Due to Field-Enhanced Emission of Electrons from Deep Traps. Physica Status Solidi A, 1984, 84, 621-630.	1.7	4
502	Analysis of DLTS Curves of Aggregated Deep Level Impurities. Physica Status Solidi A, 1984, 85, 219-226.	1.7	6
503	Some peculiar features of small-signal charge DLTS response of GaAs MOS capacitors. Physica Status Solidi A, 1984, 86, 795-804.	1.7	23
504	Time-resolved defect production and annealing during electron-beam processing of silicon. Applied Physics A: Solids and Surfaces, 1984, 33, 251-254.	1.4	3
505	Trap spectrum of the "new oxygen donor" in silicon. Applied Physics A: Solids and Surfaces, 1984, 34, 155-161.	1.4	45
506	The significance of trapping centre concentration in photorefractive crystals used for degenerate four-wave mixing. Optical and Quantum Electronics, 1984, 16, 355-358.	1.5	6
507	Personal computer-based automatic measurement system applicable to deep-level transient spectroscopy. Review of Scientific Instruments, 1984, 55, 637-639.	0.6	5
508	Pulsed admittance spectroscopy. Journal of Applied Physics, 1984, 56, 352-356.	1.1	6
509	Effects of leakage current on deep level transient spectroscopy. Applied Physics Letters, 1984, 44, 790-792.	1.5	47
510	Electrical properties of deep silver- and iron-related centres in silicon. Journal of Physics C: Solid State Physics, 1984, 17, 6701-6710.	1.5	33
511	Complete electrical characterization of recombination properties of titanium in silicon. Journal of Applied Physics, 1984, 56, 1021-1031.	1.1	66
512	Determination of the capture cross section and degeneracy factor of Si-SiO ₂ interface states. Applied Physics Letters, 1984, 44, 988-990.	1.5	20
513	Improvements in the determination of interface state density using deep level transient spectroscopy. Journal of Applied Physics, 1984, 56, 1744-1751.	1.1	54
514	Chapter 1 Beam Processing of Silicon. Semiconductors and Semimetals, 1984, 17, 1-70.	0.4	1

#	ARTICLE	IF	CITATIONS
515	Chapter 3 Optical and Electrical Properties of Pulsed Laser-Annealed Silicon. Semiconductors and Semimetals, 1984, , 95-164.	0.4	13
516	Chapter 6 Light-Emitting-Diode Reliability. Semiconductors and Semimetals, 1985, , 239-279.	0.4	1
517	Interface Study of Mo/GaAs. Materials Research Society Symposia Proceedings, 1985, 48, 137.	0.1	3
518	DIRECT OBSERVATION OF INTERFACE TRAPS IN OMVPE-GROWN SELECTIVELY AlGaAs/GaAs HETEROSTRUCTURE USING MODIFIED DLTS. Materials Research Society Symposia Proceedings, 1985, 56, 295.	0.1	2
519	Dlts Study of Oxide Traps Near the Si-SiO ₂ Interface. Materials Research Society Symposia Proceedings, 1985, 54, 586.	0.1	0
520	Gap states in phosphorus-doped amorphous silicon studied by isothermal capacitance transient spectroscopy. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1985, 52, 33-57.	0.6	90
521	Anodic oxidation of compound semiconductors and the electrical properties of interfaces.. Bulletin of the Japan Institute of Metals, 1985, 24, 746-753.	0.1	0
523	Analysis of Non-Exponential Filling in DLTS on p-n Junctions. Application to Dominant Traps in AlGaAs Lasers. Physica Status Solidi A, 1985, 89, 629-637.	1.7	0
524	On the Role of the Back Contact in DLTS Experiments with Schottky Diodes. Physica Status Solidi A, 1985, 89, 693-698.	1.7	12
525	On the application of the photo-EPR technique to the studies of photoionization, DAP recombination, and non-radiative recombination processes. Physica Status Solidi A, 1985, 90, 11-52.	1.7	72
526	Third-order optical polarizability of ZnS at low temperature. Physica Status Solidi A, 1985, 92, 603-607.	1.7	0
527	Room-temperature irradiation of p-type Silicon. Physica Status Solidi A, 1985, 92, 609-614.	1.7	21
528	Express methods of determining the parameters of deep centers in semiconductors from the data of nonsteady capacitive spectroscopy. Journal of Applied Spectroscopy, 1985, 43, 1247-1250.	0.3	0
529	Deep-level transient spectroscopy of rare-earth-Zinc oxide varistors. Journal of Materials Science Letters, 1985, 4, 1442-1444.	0.5	5
530	Chemical and structural characterisation of In _{0.53} Ga _{0.47} As epitaxial layers. Physica B: Physics of Condensed Matter & C: Atomic, Molecular and Plasma Physics, Optics, 1985, 129, 81-91.	0.9	1
531	Transient capacitance spectroscopy in heavily compensated materials. Physica B: Physics of Condensed Matter & C: Atomic, Molecular and Plasma Physics, Optics, 1985, 129, 422-425.	0.9	3
532	High resolution capacitance spectroscopy of LPE In _{0.53} Ga _{0.47} As grown on Fe doped InP-substrate and VPE GaAs grown on Cr-doped GaAs-substrate. Physica B: Physics of Condensed Matter & C: Atomic, Molecular and Plasma Physics, Optics, 1985, 129, 426-429.	0.9	5
533	The convergent effect of the annealing temperatures of electron irradiated defects in FZ silicon grown in hydrogen. Solid State Communications, 1985, 53, 975-978.	0.9	19

#	ARTICLE	IF	CITATIONS
534	The preferential alignment of negatively and neutrally charged A-centers in silicon under $\sim 100\%$ uniaxial stress. Solid State Communications, 1985, 56, 201-204.	0.9	4
535	Laser annealing of defects in CdTe epitaxial layers. Journal of Crystal Growth, 1985, 72, 246-251.	0.7	14
536	Study of non-exponential electron capture by the main electron trap in GaAs _{0.62} P _{0.38} . Solid State Communications, 1985, 53, 485-488.	0.9	22
537	Deep-level transient spectroscopy measurements using high Schottky barriers. Solid-State Electronics, 1985, 28, 1215-1221.	0.8	31
538	Scanning deep level transient spectroscopy (SDLTS). Scanning, 1985, 7, 273-289.	0.7	21
539	Neutron-induced trapping levels in aluminum gallium arsenide. Journal of Electronic Materials, 1985, 14, 95-118.	1.0	24
540	Transient capacitance spectroscopy in heavily compensated semiconductors. Solid-State Electronics, 1985, 28, 485-492.	0.8	51
541	Constant capacitance DLTS circuit for measuring high purity semiconductors. Solid-State Electronics, 1985, 28, 639-641.	0.8	17
542	Measurement of recombination lifetime profiles in epilayers using a conductivity modulation technique. IEEE Transactions on Electron Devices, 1985, 32, 1708-1713.	1.6	15
543	Gamma-Ray Irradiation Effects in Light-Emitting Diodes and Photodiodes for Fiber Optics. IEEE Transactions on Nuclear Science, 1985, 32, 4453-4460.	1.2	5
544	Transient Behavior of Transverse Acoustoelectric Voltage and Nondestructive Characterization of Semiconductor Surfaces. IEEE Transactions on Sonics and Ultrasonics, 1985, 32, 778-790.	1.0	9
545	Deep Levels of High Resistivity Sb Doped CdTe. Japanese Journal of Applied Physics, 1985, 24, 361-362.	0.8	21
546	An electron-trapping defect level associated with the 235K annealing stage in electron-irradiation n-GaAs. Journal of Physics C: Solid State Physics, 1985, 18, 43-54.	1.5	19
547	Defect Levels in Thermally-Quenched Silicon Crystals. Japanese Journal of Applied Physics, 1985, 24, 1018-1021.	0.8	10
548	Defect levels in monocrystalline and polycrystalline silicon MOS devices: a comparison. Journal Physics D: Applied Physics, 1985, 18, 661-670.	1.3	3
549	The determination of deep level concentrations in high resistivity semiconductors by DLTS, with special reference to germanium. Journal Physics D: Applied Physics, 1985, 18, 2041-2058.	1.3	20
550	DLTS Study on the Gradation of the Trap Concentration Profiles in n-CdTe Crystals. Japanese Journal of Applied Physics, 1985, 24, 1488-1492.	0.8	9
551	Photo-Deep-Level Fourier Spectroscopy in Semi-Insulating Bulk Materials. Japanese Journal of Applied Physics, 1985, 24, 1454-1458.	0.8	7

#	ARTICLE	IF	CITATIONS
552	A New Method (the Three-Point Method) of Determining Transient Time Constants and its Application to DLTS. Japanese Journal of Applied Physics, 1985, 24, 1356-1358.	0.8	9
553	A microcomputer-based deep level transient spectroscopy (DLTS) system. Journal of Physics E: Scientific Instruments, 1985, 18, 926-929.	0.7	14
554	Capture processes at double donors in silicon. Physical Review B, 1985, 31, 3659-3666.	1.1	38
555	Energy Level of the 0 to + Charge Transition of Substitutional Manganese in Silicon. Physical Review Letters, 1985, 55, 758-760.	2.9	14
556	Defect reactions on the phosphorus sublattice in low-temperature electron-irradiated InP. Physical Review B, 1985, 31, 5551-5553.	1.1	13
557	Frequency-scanned deep-level transient spectroscopy. Journal of Applied Physics, 1985, 57, 628-630.	1.1	29
558	Characterization of Si-SiO ₂ interface states: Comparison between transient capacitance and conductance techniques. Journal of Applied Physics, 1985, 58, 2077-2079.	1.1	21
559	Transient capacitance analysis of III-V semiconductors with organic-inorganic semiconductor contact barrier diodes. Applied Physics Letters, 1985, 46, 506-508.	1.5	5
560	Grown-in defects in multi-layer GaAs grown by metalorganic chemical vapor deposition under different growth conditions. Applied Physics Letters, 1985, 47, 1180-1182.	1.5	6
561	Deep-level transient spectroscopy studies of minority carrier traps in neutron-irradiated silicon. Journal of Applied Physics, 1985, 57, 2325-2327.	1.1	7
562	Steady-state and transient capacitance of a p-n junction in the presence of high density of deep levels. Journal of Applied Physics, 1985, 58, 1064-1066.	1.1	3
563	Effect of recombination on the open-circuit voltage of a silicon solar cell. Journal of Applied Physics, 1985, 57, 4746-4751.	1.1	13
564	Detection sensitivity and spatial resolution of reverse-bias pulsed deep-level transient spectroscopy for studying electric field-enhanced carrier emission. Journal of Applied Physics, 1985, 57, 1016-1021.	1.1	11
565	Probing of impurity potential well at the Si/SiO ₂ interface by electric-field-enhanced emission. Journal of Applied Physics, 1985, 57, 2823-2829.	1.1	8
566	Deep level in some perovskite oxides as gas sensor materials. Applied Physics Letters, 1985, 47, 1183-1184.	1.5	4
567	Slow-relaxation phenomena in photoconductivity for semi-insulating GaAs. Journal of Applied Physics, 1985, 58, 3485-3493.	1.1	34
568	Thermally generated electron traps in boron-implanted, phosphorus-doped silicon. Journal of Applied Physics, 1985, 58, 2225-2229.	1.1	12
569	Interface circuit between a capacitance meter (PAR 410) and a microcomputer (Apple II). Review of Scientific Instruments, 1985, 56, 2147-2150.	0.6	0

#	ARTICLE	IF	CITATIONS
570	Defect analysis in polycrystalline silicon solar cells. Journal of Applied Physics, 1985, 57, 5506-5511.	1.1	14
571	Origin of deep levels in the depletion region of $\text{p}^+\text{-ZnTe/n}^+\text{-CdTe}$ heterojunction determined by DLTS. Journal of Applied Physics, 1985, 57, 4668-4671.	1.1	7
572	Electrical properties of dislocations and point defects in plastically deformed silicon. Physical Review B, 1985, 32, 6571-6581.	1.1	287
573	Direct Trap-Density Analysis with Junction Capacitance Transient: Trap Density Spectroscopy (TDS). Japanese Journal of Applied Physics, 1985, 24, L437-L438.	0.8	17
574	Alloy Fluctuation Effect on Electronic Transition Properties of DX Center Observed with Modified Deep Level Transient Spectroscopy. Japanese Journal of Applied Physics, 1985, 24, 303-310.	0.8	33
575	Far-Infrared Magneto-optical Study of Semi-Insulating Gallium Arsenide: A New Model for the Metastable State of EL2. Japanese Journal of Applied Physics, 1985, 24, L641-L643.	0.8	6
576	Effects of Carrier Gas and Substrate on the Electrical Properties of Epitaxial GaAs Grown by the Single Flat Temperature Zone Chloride VPE Method. Japanese Journal of Applied Physics, 1985, 24, 1036-1042.	0.8	4
577	Electronic properties of semiconductor alloy systems. Reports on Progress in Physics, 1985, 48, 1091-1154.	8.1	168
578	Grain boundaries in semiconductors. Journal of Physics C: Solid State Physics, 1985, 18, 4079-4119.	1.5	248
579	Optimization and preservation of deep level transient spectroscopy signal response. Journal of Applied Physics, 1985, 57, 4619-4622.	1.1	10
580	Capacitance transient analysis of configurationally bistable defects in semiconductors. Journal of Applied Physics, 1985, 58, 2628-2633.	1.1	24
581	Iron and the iron-boron complex in silicon. Journal of Applied Physics, 1985, 57, 1941-1943.	1.1	78
582	Electron irradiation effect on minority carrier lifetime and other electrical characteristics in silicon power devices. Radiation Physics and Chemistry (1977), 1985, 25, 827-841.	0.4	5
583	Transition-metal impurities in III-V compounds. Journal of Physics C: Solid State Physics, 1985, 18, 3615-3661.	1.5	239
584	Transient spectroscopy of $\text{Si}^{\bullet-}/\text{SiO}_2$ interface states. Surface Science, 1985, 162, 680-686.	0.8	7
585	Calculation of surface generation and recombination velocities at the $\text{Si}^{\bullet-}/\text{SiO}_2$ interface. Journal of Applied Physics, 1985, 58, 4267-4276.	1.1	174
586	Effects of CF_4 plasma etching of SiO_2 on the properties of MOS structures formed on the remaining SiO_2 films. Journal Physics D: Applied Physics, 1985, 18, L1-L4.	1.3	0
587	Irradiation-induced defects in GaAs. Journal of Physics C: Solid State Physics, 1985, 18, 3839-3871.	1.5	412

#	ARTICLE	IF	CITATIONS
588	Defect states in p-type silicon crystals induced by plastic deformation. Journal of Applied Physics, 1985, 57, 287-292.	1.1	30
589	Carrier transport through grain boundaries in semiconductors. Physical Review B, 1986, 33, 3952-3966.	1.1	345
590	Investigation of deep levels in high-resistivity bulk materials by photo-induced current transient spectroscopy. I. Review and analysis of some basic problems. Journal Physics D: Applied Physics, 1986, 19, 57-70.	1.3	94
591	Deep level transient spectroscopy of interfacial traps at ion-implanted ultrahigh-p Si Schottky barriers. Applied Physics Letters, 1986, 49, 1784-1786.	1.5	9
592	Study of electron traps in GaAs resulting from infrared rapid thermal annealing. Journal of Applied Physics, 1986, 59, 3131-3136.	1.1	42
593	Evaluation of a defect capture cross section for minority carriers: Application to GaAs. Journal of Applied Physics, 1986, 59, 808-812.	1.1	6
594	Cathodoluminescence scanning electron microscopy of semiconductors. Journal of Applied Physics, 1986, 59, R1-R24.	1.1	231
595	Growth condition dependence of EL2 concentrations in magnetic field applied liquid-encapsulated Czochralski GaAs crystals. Journal of Applied Physics, 1986, 59, 982-984.	1.1	5
596	Electronic Structure of 3d Transition-Atom Impurities in Semiconductors. Solid State Physics, 1986, 39, 275-464.	1.3	230
597	Characterization of defects in semiconductors by combined application of SEM(EBIC) and SDLTS*. Journal of Microscopy, 1986, 141, 129-142.	0.8	10
598	Modulating Functions Waveform Analysis of Multi-Exponential Transients for Deep-Level Transient Spectroscopy. Materials Research Society Symposia Proceedings, 1986, 69, 337.	0.1	16
599	Multi-Exponential Analysis of DLTS by Contin. Materials Research Society Symposia Proceedings, 1986, 69, 343.	0.1	10
600	Optical Current DLTS with a Bipolar Rectangular Weighting Function for High-Resistivity Neutron Transmutation Doped Silicon. Materials Research Society Symposia Proceedings, 1986, 69, 349.	0.1	0
601	Deep Level Transient Spectroscopy: Defect Characterization in Semiconductor Devices. Materials Research Society Symposia Proceedings, 1986, 69, 75.	0.1	20
602	Evidence for Polycrystalline Si Surface Layer Formation by Argon Implantation and its Passivation by Atomic Hydrogen. Materials Research Society Symposia Proceedings, 1986, 76, 203.	0.1	0
603	Dolts of Polysilicon for Solar Cell Applications. Materials Research Society Symposia Proceedings, 1986, 71, 81.	0.1	0
604	A Model for the Application of Dlts on Normally-on Hemt Structures. Materials Research Society Symposia Proceedings, 1986, 82, 145.	0.1	1
605	Selective detection of deep recombinative centers. Solid-State Electronics, 1986, 29, 861-863.	0.8	2

#	ARTICLE	IF	CITATIONS
606	Comparative study of admittance spectroscopy and DLTS in determining trap levels of CdTe-ZnTe heterojunctions. <i>Solid-State Electronics</i> , 1986, 29, 253-256.	0.8	3
607	The role of impurities in III/V semiconductors grown by organometallic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , 1986, 75, 91-100.	0.7	85
608	Electron irradiation-induced defects in p-type silicon at 80 K. <i>Journal of Physics and Chemistry of Solids</i> , 1986, 47, 1147-1151.	1.9	6
609	Deep level defects in narrow gap semiconductors. <i>Physica Status Solidi (B): Basic Research</i> , 1986, 133, 17-46.	0.7	47
611	Isothermal DLTS method using sampling time scanning. <i>Physica Status Solidi A</i> , 1986, 95, 283-289.	1.7	14
612	Charge-Dependent Defect Traces in the DLTS and MCTS Spectra of Silicon. <i>Physica Status Solidi A</i> , 1986, 96, 637-642.	1.7	0
613	Validity of quasi-static capacitance-voltage measurements applied to hydrogenated amorphous silicon diodes. <i>Applied Physics A: Solids and Surfaces</i> , 1986, 40, 171-176.	1.4	3
614	Multi-exponential analysis of DLTS. <i>Applied Physics A: Solids and Surfaces</i> , 1986, 39, 197-202.	1.4	41
615	Interface effects of SIPOS passivation. <i>IEEE Transactions on Electron Devices</i> , 1986, 33, 779-787.	1.6	17
616	Suppression of drain conductance transients, drain current oscillations, and low-frequency generation-recombination noise in GaAs FET's using buried channels. <i>IEEE Transactions on Electron Devices</i> , 1986, 33, 925-928.	1.6	30
617	MeV ion damage in III-V semiconductors: Saturation and thermal annealing of strain in GaAs and GaP crystals. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1986, 16, 44-49.	0.6	4
618	Dielectric spectroscopy of semi-insulating gallium arsenide. <i>Semiconductor Science and Technology</i> , 1986, 1, 71-92.	1.0	48
619	Deep states in GaAs LEC crystals. <i>Solid-State Electronics</i> , 1986, 29, 483-488.	0.8	17
620	On the carrier emission from donor-related centres in GaAs _{1-x} P _x and Al _x Ga _{1-x} As. <i>Solid-State Electronics</i> , 1986, 29, 83-88.	0.8	17
621	A new method of analysis of photoluminescence decay curves. <i>Journal of Luminescence</i> , 1986, 35, 17-23.	1.5	2
622	A New Switching Effect in Semi-Insulating GaAs and Its Use for Deep Level Spectroscopy. <i>Japanese Journal of Applied Physics</i> , 1986, 25, 1684-1690.	0.8	4
623	Nondestructive Characterization of Deep Levels in Semi-Insulating GaAs Wafers Using Microwave Impedance Measurement. <i>Japanese Journal of Applied Physics</i> , 1986, 25, L874-L877.	0.8	9
624	Deep Levels in GaAs Grown Using Superlattice Intermediate Layers on Si Substrates by MOCVD. <i>Japanese Journal of Applied Physics</i> , 1986, 25, 1510-1513.	0.8	28

#	ARTICLE	IF	CITATIONS
625	A Simple Method to Determine $\hat{\nu}$ from Isothermal Capacitance Measurements. Japanese Journal of Applied Physics, 1986, 25, 916-917.	0.8	1
626	Room-Temperature Annealing Effects on Radiation-Induced Defects in InP Crystals and Solar Cells. Japanese Journal of Applied Physics, 1986, 25, 1650-1656.	0.8	13
627	Method of Analysis of a Single-Peak DLTS spectrum with Two Overlapping Deep-Trap Responses. Japanese Journal of Applied Physics, 1986, 25, 205-208.	0.8	17
628	Admittance spectroscopy of silicon Zener diodes. Semiconductor Science and Technology, 1986, 1, 150-160.	1.0	18
629	Hasegawa's Three Point Method for Determining Transient Time Constants. Japanese Journal of Applied Physics, 1986, 25, 1136-1137.	0.8	2
630	Optical and Thermal Ionization of Iron-Related Defects in Silicon. Japanese Journal of Applied Physics, 1986, 25, 234-237.	0.8	26
631	Revised model of the native deep-level defects in liquid-phase epitaxial GaAs. Semiconductor Science and Technology, 1986, 1, 275-279.	1.0	5
632	Paired temperature spectroscopy: a novel method to characterise traps in semiconductors. Journal of Physics C: Solid State Physics, 1986, 19, 2177-2187.	1.5	6
633	Considerations for capacitance DLTS measurements using a lock-in amplifier. Review of Scientific Instruments, 1986, 57, 1597-1603.	0.6	21
634	Nonradiative-recombination-enhanced defect-structure transformation in low-temperature γ -ray-irradiated InP. Physical Review B, 1986, 34, 3041-3044.	1.1	49
635	A deep level transient spectroscopy analysis of electron and hole traps in bulk-grown GaAs. Journal of Applied Physics, 1986, 59, 158-163.	1.1	67
636	Capacitance transient studies of a metastable defect in silicon. Physical Review B, 1986, 34, 1310-1313.	1.1	11
637	Direct observation of effective mass filtering in InGaAs/InP superlattices. Applied Physics Letters, 1986, 49, 812-814.	1.5	26
638	Bulk electron traps in zinc oxide varistors. Journal of Applied Physics, 1986, 60, 4186-4190.	1.1	232
639	A study of deep levels by transient spectroscopy on p-type liquid-phase epitaxial $GaxIn_{1-x}AsyP_{1-y}$ grown on semi-insulating InP. Journal of Applied Physics, 1986, 59, 1536-1543.	1.1	15
640	Passivation of deep level defects in molecular beam epitaxial GaAs by hydrogen plasma exposure. Applied Physics Letters, 1986, 49, 1098-1100.	1.5	106
641	Reliability Investigation of 1 Micron Depletion Mode IC MESFETs. Reliability Physics Symposium, 1986, , .	0.0	10
642	Deep-level transient spectroscopy studies of defects in GaAs-AlGaAs superlattices. Journal of Applied Physics, 1986, 60, 2882-2885.	1.1	18

#	ARTICLE	IF	CITATIONS
643	Determination of high-density interface state parameters in metal-insulator-semiconductor structures by deep-level transient spectroscopy. Journal of Applied Physics, 1986, 60, 3592-3598.	1.1	51
644	Deep electron trapping center in Si-doped InGaAlP grown by molecular-beam epitaxy. Journal of Applied Physics, 1986, 59, 3489-3494.	1.1	72
645	Investigation of trapping states in a Nb-doped rutile by admittance spectroscopy. Journal of Applied Physics, 1986, 60, 4191-4196.	1.1	24
646	Photoluminescence killer center in AlGaAs grown by molecular-beam epitaxy. Journal of Applied Physics, 1986, 59, 2833-2836.	1.1	79
647	Deep level transient spectroscopy of hole defects in bulk-grown p-GaAs using Schottky barrier diodes. Applied Physics Letters, 1986, 48, 130-132.	1.5	19
648	Copper centers in CdSe. Journal of Applied Physics, 1986, 60, 1670-1675.	1.1	22
649	Fast computer-controlled deep level transient spectroscopy system for versatile applications in semiconductors. Review of Scientific Instruments, 1986, 57, 1373-1377.	0.6	33
650	Lattice Relaxation Accompanying Carrier Capture and Emission by Deep Electronic Levels in Semiconductors. Physical Review Letters, 1986, 57, 2069-2072.	2.9	18
651	Anomalous majority-carrier peaks in deep level transient spectroscopy. Journal of Applied Physics, 1986, 59, 168-172.	1.1	4
652	Deep level defect study of molecular beam epitaxially grown silicon films. Applied Physics Letters, 1986, 48, 287-289.	1.5	12
653	Electron traps in dislocation-free In-alloyed liquid encapsulated Czochralski GaAs and their annealing properties. Applied Physics Letters, 1986, 48, 1664-1665.	1.5	24
654	Photoelectron paramagnetic resonance studies of the dynamical parameters of shallow donor states in ZnS lattice (ZnS:Sc, ZnS:Al). Journal of Applied Physics, 1986, 59, 466-475.	1.1	8
655	New vacancy-related defects in n-type silicon. Physical Review B, 1986, 33, 1452-1455.	1.1	67
656	Influence of hydrostatic pressure on the platinum levels in silicon. Physical Review B, 1986, 33, 8892-8895.	1.1	36
657	Measurement of deep states in undoped amorphous silicon by current transient spectroscopy. Journal of Applied Physics, 1986, 59, 4079-4086.	1.1	26
658	Oxide traps in Si-SiO ₂ structures characterized by tunnel emission with deep-level transient spectroscopy. Physical Review B, 1986, 34, 1171-1183.	1.1	62
659	Profiling of defects using deep level transient spectroscopy. Journal of Applied Physics, 1986, 60, 973-979.	1.1	59
660	Theory of pressure effects on nonradiative capture. Physical Review B, 1986, 34, 4155-4161.	1.1	0

#	ARTICLE	IF	CITATIONS
661	Quenched-in defects in flashlamp-annealed silicon. Applied Physics Letters, 1986, 49, 199-200.	1.5	25
662	Signature and capture cross section of copper-related hole traps in p-type high-purity germanium. Semiconductor Science and Technology, 1986, 1, 53-57.	1.0	31
663	Thermal annealing behaviour of proton-irradiated Au-Ti-GaAs and Al-GaAs Schottky barrier diodes. International Journal of Electronics, 1987, 62, 461-471.	0.9	0
664	Nonradiative e-h Recombination Characteristics of Mid-Gap Electron Trap in Al _x Ga _{1-x} As (x=0.4) Grown by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1987, 26, L266-L269.	0.8	24
665	A Simple Method to Determine the Capture Cross Section of Deep Levels in GaAs by Thermally Stimulated Current. Japanese Journal of Applied Physics, 1987, 26, L283-L284.	0.8	11
666	Electrical Properties of Interface-Traps in Selectively Doped AlGaAs/GaAs Heterostructures. Japanese Journal of Applied Physics, 1987, 26, 2026-2032.	0.8	16
667	Spectral Analysis of Deep Level Transient Spectroscopy (SADLTS). Japanese Journal of Applied Physics, 1987, 26, 1634-1640.	0.8	40
668	Propriétés des défauts de surface produits par recuit laser continu sur GaAs. Revue De Physique Appliquée, 1987, 22, 1451-1458.	0.4	2
669	Broadening in the deep-level transient spectra of defects in GaAs _{1-x} Sb _x alloys. Journal of Physics C: Solid State Physics, 1987, 20, 3603-3611.	1.5	4
670	Observation of Fermi level pinning at the GaAs-plasma-oxide interface. Semiconductor Science and Technology, 1987, 2, 636-642.	1.0	5
671	Photo-induced current transient spectroscopy for high-resistivity neutron-transmutation-doped silicon. Semiconductor Science and Technology, 1987, 2, 251-254.	1.0	6
672	Electron Relaxation Properties and Transient Spectroscopy of Hydrogenated Amorphous Silicon. Japanese Journal of Applied Physics, 1987, 26, 524-530.	0.8	4
673	Paired temperature spectroscopy (PATS) for gap states in ordered and disordered semiconductors: II. Experimental applications. Semiconductor Science and Technology, 1987, 2, 726-731.	1.0	2
674	Paired temperature spectroscopy (PATS) for gap states in ordered and disordered semiconductors: I. Theoretical analysis. Semiconductor Science and Technology, 1987, 2, 716-725.	1.0	5
675	DLTS Study of Heat Treatments on CdTe Crystals. Japanese Journal of Applied Physics, 1987, 26, 588-591.	0.8	11
676	Electrodeless Method for Measuring Photoconductivity Spectrum of Heat Treated Silicon. Japanese Journal of Applied Physics, 1987, 26, 312-313.	0.8	1
677	Theoretical and experimental determination of deep trap profiles in semiconductors. Journal of Applied Physics, 1987, 61, 1063-1067.	1.1	26
678	Measurement of the grain-boundary states in semiconductors by deep-level transient spectroscopy. Physical Review B, 1987, 36, 5895-5905.	1.1	54

#	ARTICLE	IF	CITATIONS
679	Improved surface nitridation of SiO ₂ thin films in low ammonia pressures. Applied Physics Letters, 1987, 50, 171-173.	1.5	16
680	Detection of minority-carrier defects by deep level transient spectroscopy using Schottky barrier diodes. Journal of Applied Physics, 1987, 61, 2546-2549.	1.1	35
681	New characterization method of deep levels in semi-insulating GaAs wafers using microwave impedance measurement. Journal of Applied Physics, 1987, 61, 2910-2915.	1.1	2
682	Accurate measurement of the temperature of a junction. Review of Scientific Instruments, 1987, 58, 122-124.	0.6	2
683	Experimental identification of the energy level of substitutional manganese in silicon. Journal of Applied Physics, 1987, 62, 3785-3790.	1.1	12
684	Refinements in the method of moments for analysis of multiexponential capacitance transients in deep-level transient spectroscopy. Journal of Applied Physics, 1987, 61, 182-190.	1.1	35
685	Electron traps in GaAs _{0.6} P _{0.4} p+n diodes fabricated by Zn implantation and rapid thermal annealing. Journal of Applied Physics, 1987, 62, 1298-1304.	1.1	4
686	Transient spectroscopy using the Hall effect. Applied Physics Letters, 1987, 50, 1438-1440.	1.5	10
687	The effects of the nonabrupt depletion edge on deep-trap profiles determined by deep-level transient spectroscopy. Journal of Applied Physics, 1987, 61, 5303-5307.	1.1	14
688	Recombination in solar-grade polycrystalline silicon. Journal of Applied Physics, 1987, 61, 2672-2674.	1.1	5
689	Defect-state generation in Czochralski-grown (100) silicon rapidly annealed with incoherent light. Journal of Applied Physics, 1987, 61, 156-160.	1.1	29
690	Distortions in optical deep level transient spectroscopy on semi-insulating GaAs with a conducting layer of finite thickness. Journal of Applied Physics, 1987, 61, 567-573.	1.1	6
691	Electrical properties of nickel-related deep levels in silicon. Journal of Applied Physics, 1987, 61, 1449-1455.	1.1	24
692	Characterization of silver-related deep levels in silicon. Journal of Applied Physics, 1987, 62, 2853-2857.	1.1	28
693	Effect of the capture coefficient in deep-level transient spectroscopy measurements. Journal of Applied Physics, 1987, 61, 5055-5061.	1.1	19
694	Study of interface states in the metal-semiconductor junction using deep level transient spectroscopy. Applied Physics Letters, 1987, 50, 341-343.	1.5	29
695	Radiation defect distribution in proton-irradiated silicon. Journal of Applied Physics, 1987, 62, 3464-3466.	1.1	28
696	Divacancy production in low-temperature electron-irradiated silicon. Physical Review B, 1987, 35, 7511-7514.	1.1	12

#	ARTICLE	IF	CITATIONS
697	High acceptor production rate in electron-irradiated n-type GaAs: Impact on defect models. Applied Physics Letters, 1987, 51, 843-845.	1.5	13
698	Carrier dynamics in quantum wells behaving as giant traps. Journal of Applied Physics, 1987, 62, 3845-3847.	1.1	29
699	Negative-Udefect: Interstitial boron in silicon. Physical Review B, 1987, 36, 1094-1104.	1.1	74
700	Defect production in electron-irradiated, n-type GaAs. Journal of Applied Physics, 1987, 62, 3660-3664.	1.1	31
701	Deep level transient spectroscopy studies of epitaxial silicon layers on silicon-on-insulator substrates formed by oxygen implantation. Applied Physics Letters, 1987, 51, 1078-1079.	1.5	19
702	Process-induced and gold acceptor defects in silicon. Physical Review B, 1987, 36, 8049-8062.	1.1	37
703	Electrical activity of defects in molecular beam epitaxially grown GaAs on Si and its reduction by rapid thermal annealing. Applied Physics Letters, 1987, 51, 1013-1015.	1.5	46
704	Variations of electron traps in bulk GaAs by rapid thermal processing. Journal of Applied Physics, 1987, 62, 528-533.	1.1	28
705	A new sequential four-rate-window DLTS system. IEEE Transactions on Instrumentation and Measurement, 1987, IM-36, 115-119.	2.4	8
706	The Effects of High and Low Dose Hydrogen Ion Implantations on Al/n-Si Schottky Diodes. Materials Research Society Symposia Proceedings, 1987, 104, 297.	0.1	0
707	Effects of Growth Conditions on EL-2 Concentration in OMVPE- GaAs. Materials Research Society Symposia Proceedings, 1987, 104, 397.	0.1	0
708	Electrical and Electronic Properties of Grain Boundaries in Silicon. Materials Research Society Symposia Proceedings, 1987, 106, 53.	0.1	12
709	Electrical Characterization of Defects in GaAs Grown on Si by MBE. Materials Research Society Symposia Proceedings, 1987, 91, 233.	0.1	3
710	Application of a Low Frequency Technique to the Study of Amorphous Materials.. Materials Research Society Symposia Proceedings, 1987, 95, 77.	0.1	0
711	Deep levels and disorder in semiconductor alloys experimental aspects. , 1987, , 190-200.		0
712	DLTS characterization of proton implantation defects in P-type GaAs by using schottky barrier diodes. Radiation Effects, 1987, 103, 197-202.	0.4	3
713	Ion implantation of boron in germanium. Journal of Applied Physics, 1987, 61, 2469-2477.	1.1	45
714	Photoinduced transient spectroscopy and photoluminescence studies of copper contaminated liquid-encapsulated Czochralski-grown semi-insulating GaAs. Journal of Applied Physics, 1987, 62, 2329-2336.	1.1	29

#	ARTICLE	IF	CITATIONS
715	Determination of carrier capture cross sections of traps by deep level transient spectroscopy of semiconductors. Journal of Applied Physics, 1987, 62, 2865-2870.	1.1	26
716	Transient photoconductivity measurements in semi-insulating GaAs. I. An analog approach. Journal of Applied Physics, 1987, 62, 2424-2431.	1.1	87
717	Application of deep level transient spectroscopy to metal-oxide-semiconductor relaxation transients. Journal of Applied Physics, 1987, 62, 576-581.	1.1	28
718	The capture barrier of the DX center in Si-doped Al _x Ga _{1-x} As. Journal of Applied Physics, 1987, 62, 4786-4797.	1.1	136
719	Determination of trapping dynamics of semi-insulating GaAs by frequency-dependent photoconductivity. Semiconductor Science and Technology, 1987, 2, 233-239.	1.0	7
720	Field effect on thermal emission from the 0.85 eV hole level in GaP. Journal of Applied Physics, 1987, 62, 4471-4474.	1.1	8
721	Thermal emission and capture rates of holes at the gold donor level in silicon. Journal of Applied Physics, 1987, 62, 4773-4780.	1.1	7
722	Deep levels as local probes for the study of superlattices. Journal of Applied Physics, 1987, 62, 3772-3777.	1.1	15
723	Pressure dependence of impurity levels in semiconductors: The deep gold acceptor level and shallow donor and acceptor levels in silicon. Physical Review B, 1987, 35, 7575-7584.	1.1	26
724	Pressure dependence of deep electronic levels in semiconductors: The oxygen-vacancy pair (or A center) in silicon. Physical Review B, 1987, 36, 4841-4848.	1.1	23
725	Les propriétés électriques de la macule $\xi = 25$ du silicium et leur évolution en fonction de traitements de recuit. Revue De Physique Appliquée, 1987, 22, 585-590.	0.4	6
726	An anomalous feature on the DLTS spectrum of silicon. Solid State Communications, 1987, 62, 719-722.	0.9	4
727	Alloy disorder broadening of defect energy levels. Solid State Communications, 1987, 61, 105-107.	0.9	3
728	Observation of bias-dependent capture-emission processes in MBE-grown GaAs layers. Solid-State Electronics, 1987, 30, 221-226.	0.8	1
729	Gas source molecular beam epitaxy of GaInAs(P): Gas sources, single quantum wells, superlattice p-i-n's and bipolar transistors. Journal of Crystal Growth, 1987, 81, 249-260.	0.7	64
732	High-temperature thermal nitridation and low-temperature electron-beam-enhanced nitridation of SiO ₂ thin films. Physica Status Solidi A, 1987, 100, 187-198.	1.7	12
733	On the quenched-in defects in n-type silicon. Physica Status Solidi A, 1987, 100, 239-244.	1.7	0
734	About the origin of the 0.15 to 0.20 eV defect level in cadmium telluride. Physica Status Solidi A, 1987, 100, 251-258.	1.7	45

#	ARTICLE	IF	CITATIONS
735	Annealing Studies of Defects Pertinent to Radiation Damage in Si:B. <i>Physica Status Solidi A</i> , 1987, 102, 639-644.	1.7	27
738	Hydrogen in crystalline semiconductors. <i>Applied Physics A: Solids and Surfaces</i> , 1987, 43, 153-195.	1.4	913
739	Acceptor levels in indium selenide. An investigation by means of the Hall effect, deep-level-transient spectroscopy and photoluminescence. <i>Applied Physics A: Solids and Surfaces</i> , 1987, 44, 249-260.	1.4	45
740	Rapid thermal annealing of electrically-active defects in virgin and implanted silicon. <i>Applied Physics A: Solids and Surfaces</i> , 1987, 42, 227-232.	1.4	6
741	A new method of analysis of DLTS-spectra. <i>Applied Physics A: Solids and Surfaces</i> , 1987, 44, 107-110.	1.4	31
742	InP-SiO ₂ metal-insulator-semiconductor structure parameters investigated with DLTS and other capacitance techniques. <i>Solid State Communications</i> , 1987, 64, 411-416.	0.9	6
743	Suppression of copper-related level in LEC pGaAs by platinum diffusion. <i>Solid-State Electronics</i> , 1987, 30, 415-417.	0.8	1
744	A method to improve the speed and sensitivity of constant-capacitance voltage transient measurements. <i>Solid-State Electronics</i> , 1987, 30, 513-518.	0.8	12
745	Electrically active defects in liquid phase epitaxial interfaces in the In _{0.53} Ga _{0.47} As/InP system. <i>Journal of Crystal Growth</i> , 1987, 83, 219-232.	0.7	11
746	Space charge capacity on semiconductor electrodes at electronic non-equilibrium. <i>Journal of Electroanalytical Chemistry and Interfacial Electrochemistry</i> , 1987, 221, 23-31.	0.3	4
747	Characterization and analysis of detector materials and processes. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 1987, 253, 313-318.	0.7	11
748	JFET/SOS devices. II. Gamma-radiation-induced effects. <i>IEEE Transactions on Electron Devices</i> , 1988, 35, 359-364.	1.6	8
749	A computer controlled system for transient capacitance measurements of deep levels in semiconductor. <i>IEEE Transactions on Instrumentation and Measurement</i> , 1988, 37, 86-89.	2.4	5
750	Deep levels in n-type HgCdTe. <i>Journal of Crystal Growth</i> , 1988, 86, 484-489.	0.7	7
751	Investigation of deep impurities in schottky diodes on high-resistivity silicon. <i>Physica Status Solidi A</i> , 1988, 105, 511-520.	1.7	3
752	Some properties of MIS structures prepared by plasma oxidation of Al layers on GaAs. <i>Physica Status Solidi A</i> , 1988, 106, 659-667.	1.7	2
753	Effect of lattice defects in the collector region of npn Si transistors on the degradation of hFE. <i>Physica Status Solidi A</i> , 1988, 107, 429-439.	1.7	20
754	Silver related deep levels in silicon. <i>Physica Status Solidi A</i> , 1988, 109, 273-278.	1.7	8

#	ARTICLE	IF	CITATIONS
755	Notes on the carbon-associated deep level complex in irradiated silicon. Physica Status Solidi A, 1988, 109, 421-426.	1.7	2
756	Deep electronic levels in carbon-implanted silicon. Physica Status Solidi A, 1988, 109, 531-536.	1.7	0
758	Process of defect formation in the collector region of an electron-irradiated npn Si transistor. Physica Status Solidi A, 1988, 110, 301-308.	1.7	2
759	Recovery mechanism of lattice defects formed in the collector region for electron-irradiated npn Si transistors. Physica Status Solidi A, 1988, 110, 677-686.	1.7	2
760	Platinum contamination of oxide grown by plasma anodization of gallium arsenide. Surface and Interface Analysis, 1988, 11, 553-558.	0.8	3
761	A study of annealing effects on deep level profile distributions in GaAs by capacitive methods. Thin Solid Films, 1988, 162, 13-19.	0.8	1
762	Deep Level Transient Fourier Spectroscopy (DLTFS)â€”A technique for the analysis of deep level properties. Solid-State Electronics, 1988, 31, 1733-1742.	0.8	333
763	Dielectric spectroscopy of silicon barrier devices. Solid-State Electronics, 1988, 31, 1277-1288.	0.8	37
764	Characterizing traps in MESFETs using internal transconductance (gm) frequency dispersion. Solid-State Electronics, 1988, 31, 1315-1320.	0.8	16
765	Recombination centers and electrical characteristics in silicon power P-I-N diodes irradiated with high energy electrons. International Journal of Radiation Applications and Instrumentation Nuclear Tracks and Radiation Measurements, 1988, 31, 809-819.	0.0	3
766	Purification techniques and analytical methods for gaseous and metallic impurities in high-purity silane. Journal of Crystal Growth, 1988, 89, 28-38.	0.7	29
767	Deep levels and minority carrier lifetime in MOVPE p-type GaAs. Journal of Crystal Growth, 1988, 93, 569-575.	0.7	1
768	The type-conversion phenomenon in electron-irradiated GaAs. Journal of Physics and Chemistry of Solids, 1988, 49, 97-102.	1.9	7
769	Test of a distribution for electron trap lifetimes in zns which is related to the maximum entropy principle. Journal of Physics and Chemistry of Solids, 1988, 49, 633-637.	1.9	0
770	Dominant donor trap in n-type epitaxial GaAs grown by CSVT. Journal of Physics and Chemistry of Solids, 1988, 49, 1349-1353.	1.9	5
771	Deep level transient spectroscopy studies of n-CdTe and p-CdTe. Solar Cells, 1988, 24, 279-286.	0.6	4
772	Digital deep level transient spectroscopy considered for discrimination of traps closely spaced in emission coefficients in semiconductors. Journal of Electronic Materials, 1988, 17, 187-191.	1.0	13
773	A DLTS study of defects formed in silicon during ion beam mixing. Nuclear Instruments & Methods in Physics Research B, 1988, 35, 234-237.	0.6	5

#	ARTICLE	IF	CITATIONS
774	Complex plane analysis of trapping phenomena in zinc oxide based varistor grain boundaries. Journal of Applied Physics, 1988, 63, 2337-2345.	1.1	120
775	Deep levels in α -GaAs grown by metalorganic vapor phase epitaxy. Journal of Applied Physics, 1988, 64, 4975-4986.	1.1	23
776	Native defects in gallium arsenide. Journal of Applied Physics, 1988, 64, R65-R92.	1.1	378
777	A study of iron-related centers in heavily boron-doped silicon by deep-level transient spectroscopy. Journal of Applied Physics, 1988, 64, 6306-6310.	1.1	16
778	An improved deep level transient spectroscopy method. Journal of Applied Physics, 1988, 63, 1801-1804.	1.1	13
779	Dependence of the photorefectance of semi-insulating GaAs on temperature and pump chopping frequency. Applied Physics Letters, 1988, 52, 2058-2060.	1.5	47
780	Effect of Schottky barrier height on EL2 measurement by deep-level transient spectroscopy. Journal of Applied Physics, 1988, 64, 2469-2472.	1.1	25
781	Kink effect in submicrometer-gate MBE-grown InAlAs/InGaAs/InAlAs heterojunction MESFETs. IEEE Electron Device Letters, 1988, 9, 630-632.	2.2	65
782	Effects of controlled As pressure annealing on deep levels of liquid-encapsulated Czochralski GaAs single crystals. Journal of Applied Physics, 1988, 64, 3987-3993.	1.1	23
783	Deep-level transient spectroscopy detection of defects created in epitaxial GaAs after electron-beam metallization. Journal of Applied Physics, 1988, 64, 2422-2425.	1.1	23
784	Entropy-Driven Metastabilities in Defects in Semiconductors. Physical Review Letters, 1988, 61, 1627-1630.	2.9	23
785	Radiation-induced defect states in low to moderately boron-doped silicon. Journal of Applied Physics, 1988, 64, 6301-6305.	1.1	6
786	Novel method to determine capture cross-section activation energies by deep-level transient spectroscopy techniques. Applied Physics Letters, 1988, 52, 660-661.	1.5	46
787	Effect of arsenic source on the growth of high-purity GaAs by molecular beam epitaxy. Applied Physics Letters, 1988, 52, 1721-1723.	1.5	32
788	Characteristics of electron traps in Si-implanted and rapidly thermal-annealed GaAs. Journal of Applied Physics, 1988, 63, 414-420.	1.1	19
789	Characterization of tungsten-related deep levels in bulk silicon crystal. Journal of Applied Physics, 1988, 63, 2304-2306.	1.1	32
790	Deep states in silicon-on-insulator substrates prepared by oxygen implantation using current deep level transient spectroscopy. Applied Physics Letters, 1988, 53, 871-873.	1.5	31
791	Electronic spectroscopy of zero-dimensional systems. Physical Review B, 1988, 38, 2172-2175.	1.1	98

#	ARTICLE	IF	CITATIONS
792	Characterization of the Mn acceptor level in GaAs. Journal of Applied Physics, 1988, 64, 1564-1567.	1.1	20
793	System effects in double-channel gated-integrator-based deep-level transient spectroscopy. Journal of Applied Physics, 1988, 64, 6311-6314.	1.1	5
794	Deep-level transient spectroscopy studies of near-surface hole and electron traps in Zn-doped InP using high barrier Yb/InP Schottky diodes. Journal of Applied Physics, 1988, 64, 3999-4005.	1.1	11
795	DX-centerlike traps and persistent photoconductivity in Te-doped Al _x Ga _{1-x} Sb on GaSb. Journal of Applied Physics, 1988, 64, 1897-1901.	1.1	29
796	Chalcogens in germanium. Physical Review B, 1988, 37, 6916-6928.	1.1	51
797	Effect of oxygen on the migration of the carbon interstitial defect in silicon. Physical Review B, 1988, 37, 4175-4179.	1.1	3
798	Defect centers and changes in the electrical characteristics of Al/n-type Si Schottky diodes induced by hydrogen-ion implantations. Physical Review B, 1988, 37, 8982-8987.	1.1	14
799	Alternating donorlike-acceptorlike configurationally bistable defect in irradiated phosphorus-doped silicon. Physical Review B, 1988, 38, 10116-10119.	1.1	11
800	Thermal emission of holes from defects in uniaxially stressed p-type silicon. Physical Review B, 1988, 38, 9857-9869.	1.1	5
801	Effect of neutron irradiation on responsivity of p-n photodetectors. Journal of Applied Physics, 1988, 64, 4245-4247.	1.1	1
802	Physical parameters of GaInAs/Si ₃ N ₄ interface states obtained by the conductance method. Applied Physics Letters, 1988, 53, 1192-1194.	1.5	6
803	Barrier modulation deep-level transient spectroscopy on semiconductor-insulator-semiconductor structures: Basic principles and numerical simulations. Journal of Applied Physics, 1988, 63, 1554-1562.	1.1	3
804	Minority-carrier emission effect in deep level transient spectroscopy measurements on Schottky diodes. Journal of Applied Physics, 1988, 63, 5357-5362.	1.1	15
805	Transient space charge limited current spectroscopy method of measuring the position and concentration of trap levels in semi-insulating materials. Review of Scientific Instruments, 1988, 59, 2468-2470.	0.6	1
806	Deep level transient spectroscopy on single, isolated interface traps in field-effect transistors. Applied Physics Letters, 1988, 52, 634-636.	1.5	34
807	Spatial and energetic distribution of Si-SiO ₂ near-interface states. Physical Review B, 1988, 38, 13124-13132.	1.1	61
808	Development of a scanning minority-carrier transient spectroscopy technique with optical injection and full transient analysis. Journal of Applied Physics, 1988, 64, 4031-4040.	1.1	10
809	Evidence for a substitutional Mg acceptor level in silicon. Physical Review B, 1988, 38, 10483-10489.	1.1	16

#	ARTICLE	IF	CITATIONS
810	Analysis of Thermally Stimulated Current Spectroscopy in Semiinsulating GaAs. I. Initialization. Japanese Journal of Applied Physics, 1988, 27, 260-268.	0.8	16
811	Deep Levels in Non-Doped and Donor-Doped GaP. Japanese Journal of Applied Physics, 1988, 27, 153-154.	0.8	6
812	The electron capture cross section of Se+in silicon. Semiconductor Science and Technology, 1988, 3, 847-852.	1.0	6
813	The relationship of the D-X centre in Al _x Ga _{1-x} As and other III-V alloys with the conduction band structure. Semiconductor Science and Technology, 1988, 3, 1145-1156.	1.0	31
814	The influence of the RC product on capture cross section measurements in semiconductors. Semiconductor Science and Technology, 1988, 3, 839-846.	1.0	1
815	Frequency-resolved capacitance spectroscopy-a new approach to measuring deep levels in semiconductors. Journal of Physics E: Scientific Instruments, 1988, 21, 1022-1024.	0.7	5
816	DLTS Study for Energy-Broadening of the Defect Level on Introducing Radiation Damage in GaP. Japanese Journal of Applied Physics, 1988, 27, 2107-2112.	0.8	6
817	Deep Level Induced by Thermal Oxidation in CZ n-Type Silicon. Japanese Journal of Applied Physics, 1988, 27, 1906-1909.	0.8	4
818	A conductance DLTS system to analyse multiple exponential decays. Semiconductor Science and Technology, 1988, 3, 1083-1093.	1.0	7
819	NECM: free carrier profilometry in semiconductors in the presence of high trap density by non-equilibrium capacitance measurements. Journal of Physics E: Scientific Instruments, 1988, 21, 559-564.	0.7	5
820	Changes of DLTS Spectrum with Gold Concentration and Gold-Diffusion Temperature in N-Type Silicon. Japanese Journal of Applied Physics, 1988, 27, 1778-1779.	0.8	7
821	Distribution of Deep Level Parameters in Spectral Analysis of DLTS (SADLTS). Japanese Journal of Applied Physics, 1988, 27, 556-562.	0.8	32
822	Distribution Profiles and Annealing Characteristics of Defects in GaAs Induced by Low-Energy FIB Irradiation. Japanese Journal of Applied Physics, 1988, 27, L2037-L2039.	0.8	14
823	Depletion-Discharge Transient Spectroscopy: Direct Determination of the Density of Deep Emission States in Amorphous Semiconductors. Japanese Journal of Applied Physics, 1988, 27, L320-L322.	0.8	6
824	Deep-level transient spectroscopy and Hall effect studies of NTD silicon with different initial resistivities. Semiconductor Science and Technology, 1988, 3, 645-653.	1.0	6
825	Variations of Electron Traps in MBE Al _x Ga _{1-x} As by Rapid Thermal Processing. Materials Research Society Symposia Proceedings, 1988, 126, 221.	0.1	0
826	Effects of Rapid Thermal Processing on SiO ₂ /GaAs Interfaces. Materials Research Society Symposia Proceedings, 1988, 126, 215.	0.1	1
827	Impurity - Dislocation Interactions in MBE Silicon. Materials Research Society Symposia Proceedings, 1988, 138, 239.	0.1	0

#	ARTICLE	IF	CITATIONS
828	Chapter 3: Deep Levels in 111-V Compound Semiconductors Grown by Molecular Beam Epitaxy. Semiconductors and Semimetals, 1988, 26, 143-228.	0.4	1
829	MOS interface states: overview and physicochemical perspective. Semiconductor Science and Technology, 1989, 4, 961-969.	1.0	208
830	Vibronic states of silicon-silicon dioxide interface traps. Semiconductor Science and Technology, 1989, 4, 1106-1115.	1.0	28
831	Copper-Related Deep Levels and Their Annealing Kinetics in Germanium. Japanese Journal of Applied Physics, 1989, 28, 763-769.	0.8	16
832	Temperature formation of the inversion layer in metal-oxide-semiconductor structures: Theoretical model and application to the determination of minority-carrier capture cross sections of the gold acceptor level in silicon. Journal of Applied Physics, 1989, 66, 5920-5929.	1.1	4
833	Electrical studies on plasma and reactive-ion-etched silicon. Journal of Applied Physics, 1989, 66, 5388-5393.	1.1	25
834	Photoionization of deep traps in AlGaAs/GaAs quantum wells. Journal of Applied Physics, 1989, 65, 3937-3942.	1.1	38
835	Transfer loss in acoustic charge transport devices due to electron traps induced by proton bombardment. Journal of Applied Physics, 1989, 66, 6150-6157.	1.1	1
836	An electron trap related to phosphorus deficiency in high-purity InP grown by metalorganic chemical vapor deposition. Journal of Applied Physics, 1989, 65, 3072-3075.	1.1	20
837	Temperature dependence of reactive ion etching of GaAs with CCl ₂ F ₂ :O ₂ . Journal of Applied Physics, 1989, 66, 3839-3849.	1.1	25
838	Observation and characterization of deep donor centers (DXcenters) in Si-doped AlAs. Journal of Applied Physics, 1989, 66, 3042-3046.	1.1	15
839	Multicarrier trapping by copper microprecipitates in silicon. Physical Review Letters, 1989, 62, 3074-3077.	2.9	111
840	Charged point defects in GaAs crystals evaluated by nuclear-magnetic-resonance spin echo. Journal of Applied Physics, 1989, 66, 3178-3186.	1.1	16
841	Zn-induced impurity levels in layer semiconductor InSe. Journal of Applied Physics, 1989, 66, 3647-3650.	1.1	25
842	Characterization of Ga out-diffusion from GaAs into SiO ₂ films during thermal annealing. Journal of Applied Physics, 1989, 66, 5833-5836.	1.1	57
843	Experimental and theoretical characterization of trap-related transfer loss in acoustic charge transport devices. Journal of Applied Physics, 1989, 66, 3883-3891.	1.1	4
844	Generation of several kinds of oxygen-related thermal donors around 520 °C in Czochralski silicon. Journal of Applied Physics, 1989, 66, 3926-3929.	1.1	12
845	Defect states in 2.0-MeV electron-irradiated phosphorus-doped silicon. Journal of Applied Physics, 1989, 65, 4779-4788.	1.1	10

#	ARTICLE	IF	CITATIONS
846	Limitation to Shockleyâ€“Readâ€“Hall model due to direct photoionization of the defect states. Journal of Applied Physics, 1989, 65, 2409-2415.	1.1	26
847	Influence of entropy properties on measured trap energy distributions at insulatorâ€“semiconductor interfaces. Applied Physics Letters, 1989, 55, 47-49.	1.5	8
848	A simple measure of defect concentration in heavily compensated semiconductor. Journal of Applied Physics, 1989, 65, 5228-5230.	1.1	1
849	Lightâ€“induced changes of gapâ€“state profile in phosphorusâ€“doped hydrogenated amorphous silicon. Applied Physics Letters, 1989, 54, 439-441.	1.5	4
850	Transient spectroscopy and disorder. Radiation Effects and Defects in Solids, 1989, 111-112, 385-392.	0.4	0
851	Investigation of the negative peak in photoinduced transient spectra of semiâ€“insulating gallium arsenide. Journal of Applied Physics, 1989, 65, 215-226.	1.1	32
852	Deepâ€“level transient spectroscopy study of nâ€“type GaAs epitaxial layers grown by closeâ€“spaced vapor transport. Journal of Applied Physics, 1989, 65, 1126-1129.	1.1	6
853	Deepâ€“level transient spectroscopy in MOS structures with a dualâ€“channel boxcar integrator and arbitrarily chosen gateâ€“widthâ€“data analysis. Review of Scientific Instruments, 1989, 60, 3485-3491.	0.6	5
854	Electrical characterization of inadvertent midgap levels in GaP. Journal of Applied Physics, 1989, 65, 3919-3922.	1.1	6
855	An analysis of complex spectra from deep level transient capacitance measurements. Journal of Applied Physics, 1989, 66, 1199-1205.	1.1	8
856	Temperature dependence of acceptorâ€“hole recombination in germanium. Applied Physics Letters, 1989, 55, 1424-1426.	1.5	10
857	Ironâ€“related deep levels in nâ€“type silicon. Journal of Applied Physics, 1989, 65, 3923-3927.	1.1	17
858	Dopantâ€“dependent formation and annealing of the dominant native deepâ€“level defect in liquidâ€“phase epitaxial AlGaAs. Journal of Applied Physics, 1989, 65, 3470-3476.	1.1	14
859	Deep levels in nâ€“InP grown by molecular beam epitaxy. Applied Physics Letters, 1989, 54, 1436-1438.	1.5	16
860	Sensitivity analysis of bulk traps detection in analog deepâ€“level transient spectroscopy measurement systems with exponentially weighted average. Review of Scientific Instruments, 1989, 60, 106-112.	0.6	10
861	A new family of thermal donors generated around 450â€“%Â°C in phosphorusâ€“doped Czochralski silicon. Journal of Applied Physics, 1989, 65, 600-605.	1.1	28
862	Electrical and optical characterization of metastable deep-level defects in GaAs. Physical Review B, 1989, 40, 2940-2945.	1.1	28
863	A deep level in Znâ€“doped InGaAlP. Journal of Applied Physics, 1989, 66, 5394-5397.	1.1	16

#	ARTICLE	IF	CITATIONS
864	On the 0.34 eV hole trap in irradiated boron-doped silicon. <i>Radiation Effects and Defects in Solids</i> , 1989, 111-112, 273-280.	0.4	1
865	Role of Electron Traps on the Thermal Conversion and Its Suppression for Liquid-Encapsulated Czochralski GaAs Single Crystals. <i>Japanese Journal of Applied Physics</i> , 1989, 28, 1750-1755.	0.8	3
866	Deep-level transient spectroscopy studies of thermal donor annihilation in silicon by rapid thermal annealing. <i>Journal of Materials Research</i> , 1989, 4, 241-243.	1.2	4
867	Multixponential Analysis of Deep Level Transient Spectroscopy (C2-MEDLTS). <i>Japanese Journal of Applied Physics</i> , 1989, 28, 649-652.	0.8	4
868	Defect Formation in GaAs by Subthreshold Energy (0.2-3 keV) Electron Irradiation. <i>Japanese Journal of Applied Physics</i> , 1989, 28, 2430-2435.	0.8	7
869	Anomalous DLTS signals due to small fluctuations in the reverse bias voltage on a Si diode. <i>Journal of Physics E: Scientific Instruments</i> , 1989, 22, 1051-1052.	0.7	1
870	Analysis of Weighting Function in Transient Spectroscopy for Precise Measurement of Deep States. <i>Japanese Journal of Applied Physics</i> , 1989, 28, 39-45.	0.8	9
871	Method for Estimating Accurate Deep-Trap Densities from DLTS of Junctions Containing Several Kinds of Deep-Traps. <i>Japanese Journal of Applied Physics</i> , 1989, 28, 1402-1406.	0.8	11
872	Poole-Frenkel-assisted emission from deep levels in electron-irradiated germanium. <i>Semiconductor Science and Technology</i> , 1989, 4, 739-742.	1.0	15
873	The influence of dose and protecting mask on electrically active defects induced by ion implantation in silicon. <i>Journal of Electronic Materials</i> , 1989, 18, 85-90.	1.0	3
874	Effects of melt composition on deep electronic states and compensation ratios inn-type LEC gallium arsenide. <i>Journal of Electronic Materials</i> , 1989, 18, 151-155.	1.0	15
875	Application of the divisor method to multiple peak DLTS spectra. <i>Journal of Electronic Materials</i> , 1989, 18, 763-766.	1.0	4
876	An efficient technique for analyzing deep level transient spectroscopy data. <i>Journal of Electronic Materials</i> , 1989, 18, 543-547.	1.0	10
877	An MeV-ion implanter for large area applications. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1989, 36, 345-349.	0.6	49
878	Deep-level spectroscopy of Cr-doped GaAs using nondestructive acousto-electric voltage measurements. <i>Solid-State Electronics</i> , 1989, 32, 749-754.	0.8	3
879	Deep-level transient spectroscopy of Al _x Ga _{1-x} As/GaAs using nondestructive acousto-electric voltage measurement. <i>IEEE Transactions on Electron Devices</i> , 1989, 36, 1189-1195.	1.6	21
880	Ionization radiation induced degradation of MOSFET channel frequency response. <i>IEEE Transactions on Nuclear Science</i> , 1989, 36, 1359-1366.	1.2	4
881	Proton-irradiated silicon: Complete electrical characterization of the induced dominant deep defects after long-term annealing. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1989, 2, 87-90.	1.7	6

#	ARTICLE	IF	CITATIONS
882	Electronic properties of defects created by 1.6 GeV argon ions in silicon. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1989, 2, 105-110.	1.7	12
883	Transition metals in silicon and their gettering behaviour. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1989, 4, 63-69.	1.7	30
884	Effects of deuterium plasma treatments on the electrical properties of boron-doped silicon. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1989, 4, 147-151.	1.7	4
885	Effect of sputter-etching conditions on the barrier characteristics and the process-induced defects in (Ti-W)/Si Schottky diodes. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1989, 4, 387-391.	1.7	4
886	Correlation between fill factors of amorphous silicon solar cells, and their i layer densities of states as determined by DLTS. <i>Solar Cells</i> , 1989, 27, 341-346.	0.6	5
887	Deep-level transient spectroscopy of AlGaAs and CuInSe ₂ . <i>Solar Cells</i> , 1989, 27, 347-356.	0.6	18
888	Study of deep traps using the frequency-dependence of the temperature derivative of PN junction capacitance. <i>Solid-State Electronics</i> , 1989, 32, 25-32.	0.8	9
889	Fast ion induced defects in silicon and semiconductor applications. <i>Vacuum</i> , 1989, 39, 199-202.	1.6	1
891	Ionization Assisted Transformations of Defects in Carbon Implanted Silicon. <i>Physica Status Solidi A</i> , 1989, 112, 405-410.	1.7	0
894	Deep Level Transient Spectroscopy Measurements in InSe Single Crystals. <i>Physica Status Solidi A</i> , 1989, 114, 253-257.	1.7	5
896	Application of isothermal current deep level transient spectroscopy to solar cells. <i>Journal of Applied Physics</i> , 1989, 65, 2173-2176.	1.1	2
897	Pressure dependence of deep electronic levels in semiconductors: Phosphorus-vacancy pair (or) Tj ETQq1 1 0.784314 rgBT / Overlock 10	1.1	18
898	Thermal donor annihilation and defect production in n-type silicon by rapid thermal annealing. <i>Journal of Applied Physics</i> , 1989, 66, 3651-3655.	1.1	38
899	Conduction-band offsets in pseudomorphic In _x Ga _{1-x} As/Al _{0.2} Ga _{0.8} As quantum wells (0.07% x 0.18) measured by deep-level transient spectroscopy. <i>Physical Review B</i> , 1989, 40, 1058-1063.	1.1	91
900	Individual defects at the Si:SiO ₂ interface. <i>Semiconductor Science and Technology</i> , 1989, 4, 1116-1126.	1.0	156
901	Characterisation of deep electron states in LEC grown GaAs material. <i>Semiconductor Science and Technology</i> , 1989, 4, 427-434.	1.0	21
902	Fast-Ion-Induced Defects in Silicon Studied by Deep Level Transient Spectroscopy. , 1989, , 231-236.		0
903	Optimization studies of materials for optically controlled semiconductor switches. , 0, , .		4

#	ARTICLE	IF	CITATIONS
904	Low frequency and microwave characterization of submicron-gate In _{0.52} Al _{0.48} As/In _{0.53} Ga _{0.47} As/In _{0.52} Al _{0.48} As heterojunction metal-semiconductor field-effect transistors grown by molecular-beam epitaxy. Journal of Applied Physics, 1989, 66, 6168-6174.	1.1	7
905	A deep-level transient spectroscopy study of high electron mobility transistors subjected to lifetime stress tests. Journal of Applied Physics, 1989, 66, 5613-5617.	1.1	10
906	A cheap capacitance meter for the measurement of fast transients and suitable for deep-level transient spectroscopy. Journal of Physics E: Scientific Instruments, 1989, 22, 664-666.	0.7	4
907	Trends in diffusion-length measurements in the original and dielectrically isolated-tub pi-silicon as a function of processing. IEEE Transactions on Electron Devices, 1989, 36, 750-760.	1.6	0
908	Deep-Level Transient Spectroscopy Studies of Rapid Thermal Processed GaAs with SiO ₂ Encapsulant. Materials Research Society Symposia Proceedings, 1989, 146, 431.	0.1	1
909	Transient Current and Transient Capacitance Measurements of Defects in AlGaAs Hemts. Materials Research Society Symposia Proceedings, 1989, 163, 789.	0.1	0
910	Distribution of Gap States in Highly Photosensitive a-SiC:H. Materials Research Society Symposia Proceedings, 1989, 149, 167.	0.1	2
911	Deep Level Transient Spectroscopy Study of Thin Film Diamond. Materials Research Society Symposia Proceedings, 1989, 162, 309.	0.1	5
912	Defect-Formation Dependence on Group V-Dopant Atoms in Electron-Irradiated Silicon. Materials Research Society Symposia Proceedings, 1989, 163, 283.	0.1	0
913	High-Resolution Spectroscopy of Point Defects in Silicon. Materials Research Society Symposia Proceedings, 1989, 163, 3.	0.1	5
914	Defect Levels in the Near-Surface Region of 2.0 MeV 16O+ Ion Implanted n-GaAs.. Materials Research Society Symposia Proceedings, 1989, 163, 979.	0.1	1
915	Deep Level Transient Spectroscopy System. IFAC Postprint Volumes IPPV / International Federation of Automatic Control, 1989, 22, 285-290.	0.4	0
916	Characterization of the Interface States in ZnO Varistors by DLTS Method. Journal of the Ceramic Society of Japan, 1989, 97, 1211-1218.	1.3	33
917	Temperature Dependent Recombination Lifetime in Silicon: Influence of Trap Level. Materials Research Society Symposia Proceedings, 1990, 209, 567.	0.1	0
918	Contactless Deep Level Transient Spectroscopy Using Microwave Reflection. Materials Research Society Symposia Proceedings, 1990, 209, 523.	0.1	2
919	Deep Level Defect Characterization of MBE Grown InGaAs/GaAs Heterostructures.. Materials Research Society Symposia Proceedings, 1990, 209, 697.	0.1	1
920	DLTS analysis of carrier generation transients in thin SOI MOSFETs. IEEE Transactions on Electron Devices, 1990, 37, 262-266.	1.6	7
921	Effects of carrier confinement by InGaAs/GaAs heterointerface barrier on deep trap concentration profiling. IEEE Transactions on Electron Devices, 1990, 37, 2158-2164.	1.6	4

#	ARTICLE	IF	CITATIONS
922	A compact microcomputer-based deep level transient spectroscopy measurement system. IEEE Transactions on Instrumentation and Measurement, 1990, 39, 467-472.	2.4	1
923	Opto-electronic modulation spectroscopy (OEMS). Journal of Electronic Materials, 1990, 19, 13-18.	1.0	13
924	The effect of post-implantation annealing temperature on the deep states present in SIMOX MOSFETs as observed using enhancement mode current DLTS. Journal of Electronic Materials, 1990, 19, 449-452.	1.0	7
925	Restructuring of defects in silicon by action of subthreshold-energy electrons. Soviet Physics Journal (English Translation of Izvestiia Vysshikh Uchebnykh Zavedenii, Fizika), 1990, 33, 487-491.	0.0	0
926	Doping mechanisms of gallium arsenide with tin in gas phase epitaxy processes. Soviet Physics Journal (English Translation of Izvestiia Vysshikh Uchebnykh Zavedenii, Fizika), 1990, 33, 491-494.	0.0	1
927	Charge-state controlled behaviour of the interstitial carbon defect in Czochralski-grown Si. Journal of Physics and Chemistry of Solids, 1990, 51, 1301-1304.	1.9	0
928	Impurity ionization in MOSFETs at very low temperatures. Cryogenics, 1990, 30, 1056-1063.	0.9	72
929	Estimation of Trap Concentration in Linearly Graded Junctions Using DLTS. Physica Status Solidi A, 1990, 117, 251-257.	1.7	3
930	A DLTS Study of InAs MIS Structures. Physica Status Solidi A, 1990, 117, 509-514.	1.7	2
931	Deep Trap Levels in Zn-Annealed ZnSe Single Crystals. Physica Status Solidi A, 1990, 117, 515-525.	1.7	14
932	Attempts to Probe the Semi-Insulating GaAs/Plasma Oxide Interface by Small-Signal Charge DLTS. Physica Status Solidi A, 1990, 119, 701-710.	1.7	2
934	The Role of Group-V Impurities in Defect Formation in Irradiated Silicon. Physica Status Solidi A, 1990, 120, 539-546.	1.7	6
936	Characterization of Electron Traps in Au _{1-x} Cd _{1-x} ZnS Polycrystalline Schottky Diodes by Capacitance Transient Measurements. Physica Status Solidi A, 1990, 121, 587-594.	1.7	0
938	Zero-Phonon versus Classical Absorption Thresholds Due to Photoexcitation Cross-Section Bands of the A Centre in GaAs. Physica Status Solidi (B): Basic Research, 1990, 162, K47.	0.7	7
939	Boron-related deep centers in 6H-SiC. Applied Physics A: Solids and Surfaces, 1990, 51, 231-237.	1.4	124
940	The electrical properties of zinc in silicon. Applied Physics A: Solids and Surfaces, 1990, 50, 151-156.	1.4	33
941	Scanning-DLTS investigation of point defect inhomogeneities in semiconducting materials. Microelectronic Engineering, 1990, 12, 171-178.	1.1	1
942	Deep level transient spectroscopic studies of the perovskite oxides as gas sensor material. Applied Surface Science, 1990, 41-42, 212-215.	3.1	0

#	ARTICLE	IF	CITATIONS
943	Surface state characterization at the oxide-silicon and nitroxide-silicon interfaces. <i>Microelectronics Journal</i> , 1990, 21, 23-28.	1.1	1
944	Studies of metal-induced surface defects in czochralski Si following rapid thermal processing with thermal wave method. <i>Journal of Crystal Growth</i> , 1990, 103, 206-216.	0.7	3
945	Investigation of neutron radiation defects in silicon by high discriminability deep level transient spectroscopy (HDDLTS). <i>Journal of Crystal Growth</i> , 1990, 103, 282-286.	0.7	3
946	Spatial distributions of induced traps in silicon by rapid thermal processing. <i>Journal of Crystal Growth</i> , 1990, 103, 297-302.	0.7	1
947	Characterization of defects in semiconductors by deep level transient spectroscopy. <i>Journal of Crystal Growth</i> , 1990, 106, 116-126.	0.7	18
948	Deep centers in S+ implanted ZnSe. <i>Journal of Crystal Growth</i> , 1990, 101, 454-457.	0.7	1
949	On the interface traps in GaAs Au-refractory barriers. <i>Solid State Communications</i> , 1990, 73, 29-30.	0.9	0
950	Characterization of electron irradiation induced defects in Γ -doped GaAs superlattice structures. <i>Solid State Communications</i> , 1990, 76, 1041-1043.	0.9	0
951	Oxygen-related deep centres in LEC grown GaAs crystals. <i>Solid State Communications</i> , 1990, 73, 495-498.	0.9	2
952	Direct analysis of the photocurrent transient in semi-insulating GaAs. <i>Solid State Communications</i> , 1990, 74, 935-939.	0.9	18
953	Optical-MCTS of proton-irradiated n-type gallium arsenide. <i>Solid State Communications</i> , 1990, 74, 209-213.	0.9	4
954	Dynamics of deep level trapping in space charge regions. <i>Solid-State Electronics</i> , 1990, 33, 139-142.	0.8	30
955	Electrical properties of GaAs homojunctions grown by MOCVD on GaAs and Si substrates. <i>Solid-State Electronics</i> , 1990, 33, 1131-1137.	0.8	3
956	Dielectric characterisation of semiconductors. <i>Solid-State Electronics</i> , 1990, 33, 737-742.	0.8	27
957	On the determination of the defect parameters of repulsive centers by deep level transient spectroscopy. <i>Solid-State Electronics</i> , 1990, 33, 579-583.	0.8	5
958	Characterisation of the time-dependent properties of GaAs FETs. <i>Semiconductor Science and Technology</i> , 1990, 5, 395-403.	1.0	13
959	Multiexponential and Spectral Analysis of Carrier Emission Processes from Co-Related Deep Levels in p-Silicon. <i>Japanese Journal of Applied Physics</i> , 1990, 29, 2026-2030.	0.8	5
960	Stretched Exponential Capacitance Transient and Emission Rate Spectrum of DX-Centers. <i>Japanese Journal of Applied Physics</i> , 1990, 29, L101-L102.	0.8	1

#	ARTICLE	IF	CITATIONS
961	Evaluation of the Si-SiO ₂ Interface by the Measurement of the Surface Recombination Velocity by the Dual-Mercury Probe Method. Japanese Journal of Applied Physics, 1990, 29, L2300-L2303.	0.8	12
962	Deep level transient spectroscopy of n-AlGaAs/GaAs high electron mobility transistors. Electronics Letters, 1990, 26, 159.	0.5	3
963	Evidence for Phosphorus Passivation of Plasma-Induced Damage at GaAs Surface Probed by EL2 Traps. Japanese Journal of Applied Physics, 1990, 29, L1575-L1577.	0.8	11
964	Generation-recombination noise in Al _x Ga _{1-x} As: temperature dependence. Semiconductor Science and Technology, 1990, 5, 1030-1039.	1.0	5
965	Carbon-related radiation damage centres and processes in p-type Si. Semiconductor Science and Technology, 1990, 5, 645-648.	1.0	31
966	Problems of relaxation spectroscopy of localised electron states. Semiconductor Science and Technology, 1990, 5, 675-685.	1.0	8
967	The modulating-function waveform analysis method and deep levels in semiconductors. Journal of Physics Condensed Matter, 1990, 2, 10359-10370.	0.7	4
968	Hole trap annealing in neutron-transmutation-doped silicon with different initial resistivities. Semiconductor Science and Technology, 1990, 5, 663-668.	1.0	3
969	Defect states in carbon and oxygen implanted p-type silicon. Journal of Applied Physics, 1990, 67, 270-275.	1.1	3
970	Deep levels in undoped bulk InP after rapid thermal annealing. Journal of Applied Physics, 1990, 68, 1665-1668.	1.1	15
971	Device geometry and temperature dependence of deep level transient spectroscopy spectra of GaAs metal-semiconductor field-effect transistors. Journal of Applied Physics, 1990, 67, 3895-3897.	1.1	0
972	A new method to analyze multiexponential transients for deep level transient spectroscopy. Journal of Applied Physics, 1990, 67, 4126-4132.	1.1	17
973	Transient spectroscopy of deep levels in thin semiconductor films. Journal of Applied Physics, 1990, 68, 6526-6528.	1.1	3
974	Shallow levels, deep levels and electrical characteristics in Zn-doped GaInP/InP. Journal of Applied Physics, 1990, 67, 3711-3716.	1.1	10
975	Absorber versus trap model in solitary semiconductor lasers. Journal of Applied Physics, 1990, 67, 2168-2170.	1.1	5
976	Deep levels in Ga-doped ZnSe grown by molecular beam epitaxy. Journal of Applied Physics, 1990, 67, 1389-1392.	1.1	17
977	Defect annealing in electron-irradiated boron-doped silicon. Physical Review B, 1990, 41, 1019-1027.	1.1	3
978	Effects of copper precipitation in $\lambda=25$ silicon bicrystals by deep level transient spectroscopy. Journal of Applied Physics, 1990, 68, 638-645.	1.1	16

#	ARTICLE	IF	CITATIONS
979	Origin and characteristics of alpha-particle-induced permanent junction leakage. IEEE Transactions on Electron Devices, 1990, 37, 730-736.	1.6	9
980	Deep levels and impurities at growth-interrupted interfaces: Temperature- and gas-switched metalorganic chemical vapor deposition of GaAs with tertiarybutylarsenic. Journal of Applied Physics, 1990, 67, 2100-2108.	1.1	7
981	Single-gate deep level transient spectroscopy technique. Journal of Applied Physics, 1990, 67, 560-563.	1.1	2
982	Electrical and optical properties of defect states induced by air plasma process in n+ epitaxial silicon. Journal of Applied Physics, 1990, 68, 1520-1525.	1.1	0
983	Role of the mid-gap level as the dominant recombination center in platinum doped silicon. Journal of Applied Physics, 1990, 67, 1130-1132.	1.1	24
984	Growth temperature dependence of EL2 concentration in GaAs grown by metalorganic vapor-phase epitaxy using tertiarybutylarsine. Journal of Applied Physics, 1990, 68, 4064-4067.	1.1	4
985	Noncontact energy level analysis of metallic impurities in silicon crystals. Applied Physics Letters, 1990, 57, 2832-2834.	1.5	27
986	Effects of leakage current on isothermal capacitance transient spectroscopy signals for midgap levels in GaAs. Journal of Applied Physics, 1990, 67, 1380-1383.	1.1	15
987	Deep electron traps in GaAs layers grown on (100)Si substrates by metalorganic chemical vapor deposition. Journal of Applied Physics, 1990, 67, 2454-2456.	1.1	3
988	Deep level transient spectroscopy analysis of spatially dependent doping profiles. Journal of Applied Physics, 1990, 67, 200-216.	1.1	10
989	A deep-level transient spectroscopy technique for the characterization of charge-carrier emission centers in nonabrupt pn junctions. Journal of Applied Physics, 1990, 67, 3500-3510.	1.1	10
990	Defect clustering in silicon emitter junctions. Journal of Applied Physics, 1990, 68, 6434-6441.	1.1	6
991	Influence of copper doping on the performance of optically controlled GaAs switches. Journal of Applied Physics, 1990, 67, 1124-1126.	1.1	12
992	EL2 trends in As-rich GaAs grown by close-spaced vapor transport. Journal of Applied Physics, 1990, 67, 1879-1883.	1.1	9
993	Identification of band-gap states by deep level transient spectroscopy on radioactive probes: The case of Au and Pt in silicon. Applied Physics Letters, 1990, 56, 1122-1124.	1.5	69
994	Pulsed laser annealing of GaAs implanted with Se and Si. Optical Engineering, 1990, 29, 329.	0.5	18
995	Oxygen adsorption and VDR effect in (Sr, Ca)TiO _{3-x} based ceramics. Journal of Materials Research, 1990, 5, 2910-2922.	1.2	54
996	Hole and electron traps in AlGaAs single and double heterojunction red light-emitting diodes. International Journal of Electronics, 1990, 68, 729-741.	0.9	1

#	ARTICLE	IF	CITATIONS
998	DETERMINATION OF THE DEEP-STATE CONCENTRATION IN SEMI-INSULATING GaAs BASED ON NEW CAPACITANCE AND CONDUCTANCE DLTS. , 1990, , 1599-1604.		2
999	Deep level transient spectroscopy analysis of fast ion tracks in silicon. Journal of Applied Physics, 1990, 67, 1266-1271.	1.1	62
1000	DLTS study of EFG solar cells. , 0, , .		1
1001	A plasma etching-induced defect state in electron-irradiated n-type bulk section. Journal of Applied Physics, 1990, 68, 897-899.	1.1	7
1002	Formation of several kinds of oxygen-related donors around 500°C and effects of carbon in Czochralski silicon. Journal of Applied Physics, 1990, 68, 1921-1923.	1.1	7
1003	Defect clusters in zinc oxide. Journal of Applied Physics, 1990, 67, 6760-6763.	1.1	39
1004	Grain-boundary interface electron traps in commercial zinc oxide varistors. Journal of Applied Physics, 1990, 68, 6495-6500.	1.1	39
1005	Deep center characterization by photo-induced transient spectroscopy. Journal of Applied Physics, 1990, 68, 3370-3376.	1.1	47
1006	Bistable interstitial-carbon-substitutional-carbon pair in silicon. Physical Review B, 1990, 42, 5765-5783.	1.1	176
1007	A new correlation method for improvement in selectivity of bulk trap measurements from capacitance and voltage transients. Review of Scientific Instruments, 1990, 61, 1319-1325.	0.6	37
1008	Ion implantation for isolation of III-V semiconductors. Materials Science and Engineering Reports, 1990, 4, 313-363.	5.8	306
1009	Studies of defects in n-type CdTe by charge transient spectroscopy. Journal of Applied Physics, 1990, 67, 2475-2481.	1.1	26
1010	Proton irradiation of silicon: Complete electrical characterization of the induced recombination centers. Journal of Applied Physics, 1990, 68, 2702-2707.	1.1	63
1011	On the capacitance control in deep level spectroscopy. Measurement Science and Technology, 1991, 2, 899-906.	1.4	1
1012	New application for isothermal capacitance transient spectroscopy: Identification of tunneling in semiconductor-insulator interfaces. Applied Physics Letters, 1991, 58, 137-139.	1.5	3
1013	Investigation of the electrical properties of Cd-doped indium selenide. Journal of Applied Physics, 1991, 70, 6847-6853.	1.1	17
1014	Capacitance switching method of eliminating false transients on the Boonton 72B capacitance meter in deep-level transient spectroscopy applications. Measurement Science and Technology, 1991, 2, 127-130.	1.4	1
1015	Optical reflectance of aluminum-doped zinc oxide powders. Journal of Applied Physics, 1991, 69, 959-964.	1.1	18

#	ARTICLE	IF	CITATIONS
1016	Local electrical dissipation imaged by scanning force microscopy. Applied Physics Letters, 1991, 59, 2171-2173.	1.5	123
1017	Sidewall damage in a silicon substrate caused by trench etching. Applied Physics Letters, 1991, 58, 2942-2944.	1.5	17
1018	Inhomogeneities in plastically deformed silicon single crystals. II. Deep-level transient spectroscopy investigations of p- and n-doped silicon. Physical Review B, 1991, 44, 1600-1612.	1.1	56
1019	Direct determination of the electron-tunneling escape time from a GaAs/Al _x Ga _{1-x} As quantum well by transient-capacitance spectroscopy. Physical Review B, 1991, 44, 3157-3161.	1.1	24
1021	Deep state of hydrogen in crystalline silicon: Evidence for metastability. Physical Review Letters, 1991, 66, 2360-2363.	2.9	126
1022	Chapter 5 Neutralization of Deep Levels in Silicon. Semiconductors and Semimetals, 1991, , 65-89.	0.4	12
1023	New model for the characterization of bulk traps by current deep level transient spectroscopy in metal-oxide-semiconductor transistors. Journal of Applied Physics, 1991, 70, 3333-3337.	1.1	9
1024	DLTS: Deep Level Transient Spectroscopy.. Hybrids, 1991, 7, 29-36.	0.0	0
1025	Constant Depth DLTS Measurements on Compound Semiconductors. Materials Research Society Symposia Proceedings, 1991, 240, 239.	0.1	0
1026	Investigation of Metal Induced Surface Defects in Czochralski Si Following Rapid Thermal Processing by Thermal Wave Modulated Reflectance Method. Materials Research Society Symposia Proceedings, 1991, 224, 81.	0.1	0
1027	Non-Contact, Wafer-Scale Deep Level Transient Spectroscopy (DLTS) Based on Surface Photovoltage (SPV). Materials Research Society Symposia Proceedings, 1991, 240, 129.	0.1	1
1028	Production of Midgap Electron Traps by Ga Out-Diffusion in Rapid-Thermal-Processed GaAs with SiO ₂ Encapsulants. Materials Research Society Symposia Proceedings, 1991, 240, 853.	0.1	0
1029	Decay of photovoltage of junction diodes. Solid-State Electronics, 1991, 34, 1201-1206.	0.8	7
1030	Control of barrier height of MIS tunnel diodes using deep level impurities. Solid-State Electronics, 1991, 34, 367-371.	0.8	8
1031	Generation-recombination noise in Al _x Ga _{1-x} As. Solid-State Electronics, 1991, 34, 23-32.	0.8	10
1032	Investigation of the CaF ₂ /p-type Si(100) interface by conductance and deep level transient spectroscopy. Solid-State Electronics, 1991, 34, 867-873.	0.8	5
1033	Deep level transient spectroscopy study of CaF ₂ GaAs(111) and SrF ₂ GaAs(111) structures grown by molecular beam epitaxy. Thin Solid Films, 1991, 204, 133-138.	0.8	1
1034	Effects of low energy Ar ⁺ ion bombardment on GaAs. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1991, 9, 489-500.	1.7	3

#	ARTICLE	IF	CITATIONS
1035	The use of rapid thermal annealing for studying contamination in silicon. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1991, 10, L11-L14.	1.7	4
1036	Radiation damage in InP solar cells. <i>Solar Cells</i> , 1991, 31, 331-348.	0.6	23
1037	Deep-level defects and numerical simulation of radiation damage in GaAs solar cells. <i>Solar Cells</i> , 1991, 31, 349-377.	0.6	21
1038	A review of selected techniques for characterizing radiation-induced defects in solar cells. <i>Solar Cells</i> , 1991, 31, 379-394.	0.6	3
1039	Leakage current, annealing, and deep defect production studies in neutron irradiated n-type Si-detectors. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 1991, 301, 215-218.	0.7	15
1040	Microscopic defect level characterization of semi-insulating compound semiconductors by TSC and PICTS. <i>Applied Surface Science</i> , 1991, 50, 377-382.	3.1	9
1041	An investigation of metal/GaAs(100) interfaces by deep level transient spectroscopy. <i>Applied Surface Science</i> , 1991, 50, 424-427.	3.1	1
1042	Effect of substrate temperature on the concentration of point defects in vapour phase epitaxial GaP: N,S. <i>Journal of Crystal Growth</i> , 1991, 108, 699-709.	0.7	10
1043	The space charge capacitance of non-degenerate semiconductors with shallow and deep impurity levels. <i>Journal of Electroanalytical Chemistry and Interfacial Electrochemistry</i> , 1991, 317, 27-42.	0.3	5
1044	Germanium as a deep level in AlGaAs grown by organometallic vapor phase epitaxy. <i>Journal of Electronic Materials</i> , 1991, 20, 583-587.	1.0	12
1045	Observation of some new traps introduced by low-energy Ar ⁺ ion bombardment on n-GaAs. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1991, 59-60, 1023-1027.	0.6	2
1046	The influence of implantation temperature and subsequent annealing on residual implantation defects in silicon. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1991, 55, 637-641.	0.6	14
1047	Radiation damage of silicon detectors by monoenergetic neutrons and electrons. <i>Nuclear Physics, Section B, Proceedings Supplements</i> , 1991, 23, 324-332.	0.5	16
1048	Defect energy levels from current transient recording. <i>Nuclear Physics, Section B, Proceedings Supplements</i> , 1991, 23, 333-339.	0.5	0
1049	Degradation of ion implanted GaAs MESFETs. <i>Quality and Reliability Engineering International</i> , 1991, 7, 339-342.	1.4	0
1050	Isothermal Capacitance Transient Spectroscopy of Grain-Boundary Interfacial States in Beryllium Oxide-Doped Silicon Carbide Ceramics. <i>Journal of the American Ceramic Society</i> , 1991, 74, 2675-2678.	1.9	3
1051	Electrical characterization of Si-donor-related shallow and deep states in InGaAlP alloys grown by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , 1991, 115, 498-503.	0.7	27
1052	The Origin of Electrically Active Centers in a Near-Coincidence $\Sigma 9$ Grain Boundary in Germanium. <i>Physica Status Solidi (B): Basic Research</i> , 1991, 166, 347-358.	0.7	5

#	ARTICLE	IF	CITATIONS
1053	The Utility of Preparing $Ci \times U$ Plots Prior to DLTS Scans. <i>Physica Status Solidi A</i> , 1991, 123, 341-348.	1.7	0
1054	Formation of New Donors and Structural Defects During Low-Temperature Oxygen Precipitation in CZ-Grown Silicon. <i>Physica Status Solidi A</i> , 1991, 123, 357-368.	1.7	6
1055	Evaluation of Deep Level Transient Spectra Originating from Continuous Distributions of Deep Energy Levels. <i>Physica Status Solidi A</i> , 1991, 124, 295-309.	1.7	1
1056	Investigation of FZ-Silicon Doped with Pt. <i>Physica Status Solidi A</i> , 1991, 125, 263-272.	1.7	0
1057	Resolution of Major Deep Levels in Au- and Pt-Doped Si. <i>Physica Status Solidi A</i> , 1991, 125, 741-748.	1.7	2
1058	A model of the small-signal charge DLTS response of traps distributed in both energy and space. <i>Physica Status Solidi A</i> , 1991, 127, 167-177.	1.7	9
1059	A TEM and DLTS Study of a near $\hat{\Gamma}25$ CdTe Bicrystal. <i>Physica Status Solidi A</i> , 1991, 128, 37-43.	1.7	8
1061	Deep level transient spectroscopy on radioactive impurities: Demonstration for Si:111In*. <i>Applied Physics A: Solids and Surfaces</i> , 1991, 53, 95-101.	1.4	21
1062	Single, individual traps in MOSFETs. <i>Physica Scripta</i> , 1991, T35, 273-280.	1.2	29
1063	Optical Transitions via the Structure-Defect Levels Due to Lattice Vacancies in InSb. <i>Japanese Journal of Applied Physics</i> , 1991, 30, 1169-1175.	0.8	3
1064	ICTS of MOS Interface States Enhanced by Gold Diffusion. <i>Japanese Journal of Applied Physics</i> , 1991, 30, L1293-L1295.	0.8	12
1065	Characterization of SIMOX-MOS transistors by photo-induced current transient spectroscopy. <i>Semiconductor Science and Technology</i> , 1991, 6, 937-939.	1.0	2
1066	Intrinsic Gettering of Iron Impurities in Silicon Wafers. <i>Japanese Journal of Applied Physics</i> , 1991, 30, 3580-3583.	0.8	21
1067	Electron Traps in Si p+nn+Diodes Created by 10 MeV Electron Irradiation. <i>Japanese Journal of Applied Physics</i> , 1991, 30, 1194-1195.	0.8	1
1068	Detection of near-surface defects in semiconductors by deep-level transient spectroscopy. <i>Measurement Science and Technology</i> , 1991, 2, 623-627.	1.4	4
1069	The surface photovoltage response time in the large gap semiconductors under subbandgap illumination. <i>Semiconductor Science and Technology</i> , 1991, 6, 875-880.	1.0	1
1070	Deep level transient spectroscopy based on conductance transients. <i>Applied Physics Letters</i> , 1991, 58, 364-366.	1.5	7
1071	Simulated lock-in amplifier deep level transient spectroscopy. <i>Review of Scientific Instruments</i> , 1991, 62, 2831-2832.	0.6	7

#	ARTICLE	IF	CITATIONS
1072	A study of the effects of thermal oxidation and hydrogen passivation on CVD polysilicon pin solar cells using DLTS. , 0, , .		1
1073	Interactions between superconducting $\text{YBa}_2\text{Cu}_3\text{O}_{7-x}$ and silicon using different buffer layers. Journal of Applied Physics, 1991, 70, 3364-3366.	1.1	8
1074	Temperature dependence of minority-carrier lifetime in iron-diffused p-type silicon wafers. Journal of Applied Physics, 1991, 69, 3077-3081.	1.1	41
1075	Accurate determination of the conduction-band offset of a single quantum well using deep level transient spectroscopy. Applied Physics Letters, 1991, 58, 1047-1049.	1.5	33
1076	Relationship of the gold related donor and acceptor levels in silicon. Journal of Applied Physics, 1991, 69, 2714-2716.	1.1	13
1077	Morphology of platinum silicide films prepared by conventional and rapid thermal annealing and deep levels induced in silicon. Journal of Applied Physics, 1991, 70, 3109-3114.	1.1	14
1078	Changes in the silicon thermal donor energy level as a function of anneal time. Applied Physics Letters, 1991, 58, 2114-2116.	1.5	9
1079	Chemical etching-induced defects in phosphorus-doped silicon. Journal of Applied Physics, 1991, 70, 1295-1308.	1.1	70
1080	Comparison of defects produced by 14-MeV neutrons and 1-MeV electrons in n-type silicon. Journal of Applied Physics, 1991, 70, 1261-1264.	1.1	7
1081	Fermi-level dependence of defect profiles in H+ bombarded silicon. Applied Physics Letters, 1991, 59, 3583-3585.	1.5	9
1082	Thermally activated capture of charge carriers into irradiation induced Si/SiO ₂ interface states. Journal of Applied Physics, 1991, 70, 6927-6933.	1.1	13
1083	Interaction of gold-related and irradiation-induced defects in silicon. Journal of Applied Physics, 1991, 69, 8205-8209.	1.1	11
1084	Brewster angle spectroscopy: A new method for characterization of defect levels in semiconductors. Applied Physics Letters, 1991, 59, 1470-1472.	1.5	14
1085	Annealing and profile of interstitial iron in boron-doped silicon. Applied Physics Letters, 1991, 59, 2133-2135.	1.5	17
1086	Deep-level transient spectroscopy on p-type silicon crystals containing tungsten impurities. Journal of Applied Physics, 1991, 70, 5401-5403.	1.1	11
1087	Effects of secondary laser illumination during the transient measurement in optical and electrical deep level transient spectroscopy. Applied Physics Letters, 1991, 59, 1861-1863.	1.5	2
1088	Deep-level transient spectroscopy characterization of silicon-silicon interfaces. Journal of Applied Physics, 1991, 69, 7640-7644.	1.1	2
1089	The influence of ion flux on defect production in MeV proton-irradiated silicon. Journal of Applied Physics, 1991, 70, 3025-3030.	1.1	59

#	ARTICLE	IF	CITATIONS
1090	A multipoint correlation method for bulk trap and interface state measurements in MOS structures from capacitance, voltage, and current transients. Review of Scientific Instruments, 1991, 62, 1955-1963.	0.6	6
1091	Simulation of current-voltage characteristics of Ti ϵ /nSi Schottky diodes using defects parameters extracted from deep level transient spectroscopy. Journal of Applied Physics, 1991, 69, 3357-3359.	1.1	6
1092	Current deep-level transient spectroscopy in MOS structures with a boxcar integrator and an arbitrary gate-width data analysis. Review of Scientific Instruments, 1991, 62, 1037-1046.	0.6	8
1093	Carrier removal and changes in electrical properties of neutron irradiated GaAs. Journal of Applied Physics, 1991, 70, 4931-4937.	1.1	29
1094	Deep-level transient spectroscopy: Increased accuracy of interpretation of silicon/silicon dioxide interface state data by the assistance of computer simulations. Journal of Applied Physics, 1991, 70, 6915-6926.	1.1	24
1095	A quantitative treatment for deep level transient spectroscopy under minority-carrier injection. Journal of Applied Physics, 1991, 70, 209-214.	1.1	6
1096	Capture barrier and the ionization entropy of the DX center in Se-doped Al ϵ Ga ϵ As. Journal of Applied Physics, 1991, 69, 1425-1428.	1.1	4
1097	Deep level transient spectroscopy of irradiated p-type InP grown by metalorganic chemical vapor deposition. Journal of Applied Physics, 1991, 69, 1435-1439.	1.1	31
1098	Effects of electron deep traps on generation lifetime in denuded zone of n-type Si wafer. Journal of Applied Physics, 1991, 69, 6979-6981.	1.1	7
1099	Experimental analysis of temperature dependence of deep-level capture cross-section properties at the Au oxidized InP interface. Journal of Applied Physics, 1991, 69, 7159-7165.	1.1	15
1100	Proton and electron irradiation of MOCVD InP solar cells: Experimental results and radiation modeling. , 0, , .		9
1101	Defect states in ZnSe single crystals irradiated with gamma rays. Journal of Applied Physics, 1991, 69, 291-297.	1.1	20
1102	Neutron-induced defects in high-purity germanium. Journal of Applied Physics, 1991, 69, 2033-2043.	1.1	25
1103	In ϵ .53Ga ϵ .47As/InP heterojunctions with low interface defect densities. Journal of Applied Physics, 1991, 69, 342-351.	1.1	13
1104	Investigation of interface states in (Sr,Ca)TiO ϵ 3-based ceramics. Journal of Applied Physics, 1991, 70, 1539-1547.	1.1	11
1105	Characteristics of deep levels in n-type CdTe. Journal of Physics Condensed Matter, 1991, 3, 8619-8634.	0.7	43
1106	Low-cost digital system for photoinduced transient spectroscopy. Measurement Science and Technology, 1991, 2, 430-434.	1.4	0
1107	Dielectric Anomalies and Photoconductivity in Host Insulator Cu ϵ 2O Correlatively with High-Tc Superconductivity. Journal of the Physical Society of Japan, 1991, 60, 3625-3628.	0.7	9

#	ARTICLE	IF	CITATIONS
1108	Frequency-Dependent Conductivity in Polycrystalline Chemical Vapor Deposited Diamond Films. Japanese Journal of Applied Physics, 1992, 31, L4-L6.	0.8	23
1109	Generation of the EL2 defect in n-GaAs irradiated by high energy protons. Semiconductor Science and Technology, 1992, 7, 1237-1240.	1.0	22
1110	High-resolution DLTS and its application to lattice-mismatch-induced deep levels in InGaP. Semiconductor Science and Technology, 1992, 7, 1441-1445.	1.0	3
1111	Deep-Level Transient Spectroscopy of Interface States in ZnO/PrCoOx/ZnO Thin-Film Junctions. Japanese Journal of Applied Physics, 1992, 31, L1429-L1431.	0.8	10
1112	Characterization of EL2 in GaAs wafers by scanning isothermal transient spectroscopy. Semiconductor Science and Technology, 1992, 7, A196-A201.	1.0	9
1113	Non-Contact, No Wafer Preparation Deep Level Transient Spectroscopy Based on Surface Photovoltage. Japanese Journal of Applied Physics, 1992, 31, L1185-L1187.	0.8	11
1114	On the spatial resolution of small-signal DLTS: the need for a quantum model. Semiconductor Science and Technology, 1992, 7, 516-523.	1.0	5
1115	Comparison of isothermal and boxcar methods of analysis of photocurrent transients. Semiconductor Science and Technology, 1992, 7, 953-960.	1.0	2
1116	Mapping of non-radiative point defect distributions in semiconductors using scanning DLTS. Semiconductor Science and Technology, 1992, 7, A207-A210.	1.0	1
1117	Polycrystalline Diamond/Hydrogenated Amorphous Silicon P-N Heterojunction. Japanese Journal of Applied Physics, 1992, 31, L388-L391.	0.8	11
1118	Simultaneous detection of optical constants $\hat{\mu}_1$ and $\hat{\mu}_2$ by Brewster angle reflectivity measurements. Applied Physics Letters, 1992, 60, 2403-2405.	1.5	11
1119	Use of low-frequency capacitance in deep level transient spectroscopy measurements to reduce series resistance effects. Journal of Applied Physics, 1992, 72, 3535-3538.	1.1	9
1120	Space radiation effects on optoelectronic materials and components for a 1300 nm fiber optic data bus. IEEE Transactions on Nuclear Science, 1992, 39, 1982-1989.	1.2	41
1121	Passivation induced deep levels in GaInAsPIN planar photodiodes. Journal of Applied Physics, 1992, 71, 4436-4439.	1.1	4
1122	Electron-irradiation-induced defects in Si-Ge alloys. Physical Review B, 1992, 46, 10113-10118.	1.1	24
1123	A study of metal-oxide-semiconductor capacitors fabricated on SF ₆ and SF ₆ +Cl ₂ reactive-ion-etched Si. Journal of Applied Physics, 1992, 71, 2710-2716.	1.1	7
1124	Determination of insulator/semiconductor interface trap density by correlation deep level transient spectroscopy method. Journal of Applied Physics, 1992, 72, 4125-4129.	1.1	4
1125	Evolution of electrical magnitudes in gradual p-n junctions with deep levels during the emission of majority carriers. Journal of Applied Physics, 1992, 72, 4946-4953.	1.1	9

#	ARTICLE	IF	CITATIONS
1126	Effect of carrier concentration on the properties of irradiation-induced defects in p-type indium phosphide grown by metalorganic chemical vapor deposition. Journal of Applied Physics, 1992, 71, 4201-4207.	1.1	13
1127	Using thermally stimulated currents to visualize defect clusters in neutron-irradiated silicon. Journal of Applied Physics, 1992, 72, 4007-4013.	1.1	15
1128	Effect of radiation induced defects on the capacitance of silicon detectors. Journal of Applied Physics, 1992, 71, 1517-1521.	1.1	6
1129	Effect of hydrogenation on deep-level traps in InP on GaAs. Journal of Applied Physics, 1992, 71, 509-511.	1.1	5
1130	A multipoint correlation method with binomial weighting coefficients for deep-level measurements in metal-oxide-semiconductor devices. Journal of Applied Physics, 1992, 71, 2259-2269.	1.1	16
1131	Thermal-diffusivity measurements of ultrahigh thermal conductors with use of scanning photothermal rate-window spectrometry: Chemical-vapor-deposition diamonds. Physical Review B, 1992, 46, 13526-13538.	1.1	13
1132	Point defect injection into silicon due to low-temperature surface modifications. Applied Physics Letters, 1992, 61, 1426-1428.	1.5	31
1133	Characterization of deep level traps in ultrasubmicron modulation-doped field-effect transistors on InP substrate using improved photo-induced current spectroscopy (PICS). , 0, , .		0
1134	Deep levels analysis of Si doped MBE grown AlInAs layers. , 0, , .		6
1135	Analysis of photoinduced current transient spectroscopy (PICTS) data by a regularization method. Journal of Physics Condensed Matter, 1992, 4, 6131-6140.	0.7	30
1136	Characterization of Interface States in ZnO Varistors using Isothermal Capacitance Transient Spectroscopy. Journal of the Ceramic Society of Japan, 1992, 100, 1239-1244.	1.3	20
1137	Non-Contact, No Wafer Preparation Deep Level Transient Spectroscopy (DLTS) Based on Surface Photovoltage (SPV). Materials Research Society Symposia Proceedings, 1992, 261, 217.	0.1	1
1138	Deep Level Energy Analysis of Surface and Bulk Defects Using a Noncontact Laser/Microwave Photoconductance Technique. Materials Research Society Symposia Proceedings, 1992, 261, 235.	0.1	0
1139	Study of Electrical Properties of Defects in Soi Films by Wafer Bonding. Materials Research Society Symposia Proceedings, 1992, 262, 349.	0.1	3
1140	Intrinsic Gettering of Iron in Czochralski Silicon Crystals. Materials Research Society Symposia Proceedings, 1992, 262, 963.	0.1	1
1141	Influence of Electric Field on the Formation of Neutron, Electron and β -Ray Radiation Defects in Silicon. Materials Research Society Symposia Proceedings, 1992, 279, 117.	0.1	1
1142	Capacitance Transients on Diodes: A Practical Approach to Characterize Levels with Long Time Constants. IETE Journal of Research, 1992, 38, 356-360.	1.8	0
1143	Isothermal capacitance transient spectroscopy measurements on polycrystalline diamond/hydrogenated amorphous silicon heterojunctions. Applied Physics Letters, 1992, 61, 1808-1810.	1.5	15

#	ARTICLE	IF	CITATIONS
1144	Deep level spectroscopy in semiconductors using transient surface photovoltage. , 0, , .		0
1145	Lock-in rate-window thermomodulation (thermal wave) and photomodulation spectrometry. Review of Scientific Instruments, 1992, 63, 2977-2988.	0.6	16
1146	A novel computer based pseudo-logarithmic capacitance/conductance DLTS system specifically designed for transient analysis. Review of Scientific Instruments, 1992, 63, 5733-5741.	0.6	17
1147	Impact of illumination level and oxide parameters on Shockley-Read-Hall recombination at the Si-SiO ₂ interface. Journal of Applied Physics, 1992, 71, 4422-4431.	1.1	412
1148	On the relationship between the feedback charge method, charge transient spectroscopy and C-V measurements of semiconductors and insulators. Measurement Science and Technology, 1992, 3, 726-731.	1.4	14
1149	First observation of the EL2 lattice defect in indium gallium arsenide grown by molecular-beam epitaxy. Physical Review Letters, 1992, 68, 2168-2171.	2.9	35
1150	Fundamental properties of intrinsic gettering of iron in a silicon wafer. Journal of Applied Physics, 1992, 72, 895-898.	1.1	76
1151	Defect levels in H ⁺ , D ⁺ , and He ⁺ bombarded silicon. Journal of Applied Physics, 1992, 72, 2167-2173.	1.1	72
1152	TEM and DLTS Investigations of the Electrical Activity of $\Sigma 17$ and $\Sigma 41$ Grain Boundaries in Germanium. Physica Status Solidi (B): Basic Research, 1992, 170, 403-411.	0.7	3
1153	DLTS studies of low-temperature annealing in lithium-doped silicon. Physica Status Solidi A, 1992, 130, 53-60.	1.7	1
1154	Improvement of Energy Resolution of the Box-Car System in Isothermal DLTS Methods. Physica Status Solidi A, 1992, 132, 127-132.	1.7	2
1155	Spatial Sensitivity Reversal in a Modified DLTS. Physica Status Solidi A, 1992, 132, 133-144.	1.7	1
1156	Impurity Levels in As-Doped Indium Selenide Single Crystals. Physica Status Solidi A, 1992, 133, 421-428.	1.7	3
1157	Investigation of a New Metastable Defect in Boron-Doped Cz-Si. Physica Status Solidi A, 1992, 133, 429-437.	1.7	3
1158	Characterization of unstable point defects in crystals. Solid State Communications, 1992, 82, 267-270.	0.9	7
1159	Photo-induced current measurement for the characterization of deep-level traps in lattice-matched MODFETs on InP substrate. Solid-State Electronics, 1992, 35, 1129-1137.	0.8	3
1160	A new method to measure fast defect transients in semiconductor and/or insulator samples. Solid-State Electronics, 1992, 35, 228-230.	0.8	6
1161	An improved feedback circuit for constant-capacitance voltage transient measurements. Solid-State Electronics, 1992, 35, 387-389.	0.8	6

#	ARTICLE	IF	CITATIONS
1162	A novel algorithm for higher order filtering in DLTS. <i>Solid-State Electronics</i> , 1992, 35, 1737-1743.	0.8	25
1163	Diffusion effects at Pt δ -GaAs interfaces. <i>Thin Solid Films</i> , 1992, 215, 50-51.	0.8	2
1164	Hall effect and deep level transient spectroscopy measurements in indium selenide doped with chlorine. <i>Solar Energy Materials and Solar Cells</i> , 1992, 28, 223-232.	3.0	6
1165	Variations in the structural and electrical properties as a function of depth in CdTe layers grown on InSb substrates. <i>Journal of Crystal Growth</i> , 1992, 117, 233-237.	0.7	2
1166	Schottky junctions on phosphidized GaAs surfaces. <i>Applied Surface Science</i> , 1992, 56-58, 311-316.	3.1	16
1167	Metal on GaAs: from Schottky barriers to ohmic contacts. <i>Applied Surface Science</i> , 1992, 56-58, 335-340.	3.1	2
1168	Electrical and spectroscopic analysis of neutron-irradiated silicon detectors. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 1992, 315, 182-187.	0.7	8
1169	Deep-level transient spectroscopy of detector-grade high-resistivity float-zone silicon. <i>Journal of Electronic Materials</i> , 1992, 21, 533-541.	1.0	5
1170	Importance of the choice of the profile model for ap-n junction in the location of deep levels. <i>Journal of Electronic Materials</i> , 1992, 21, 883-886.	1.0	2
1171	Effects of electrode geometry and polarity on the occurrence of negative peaks in optical transient current spectroscopy applied to semi-insulating gallium arsenide. <i>Journal of Electronic Materials</i> , 1992, 21, 901-909.	1.0	0
1172	Application of defect spectroscopy to silicon processing technology. <i>Journal of Electronic Materials</i> , 1992, 21, 1093-1097.	1.0	0
1173	DLTS detection of hole traps in MBE grown δ -GaAs using schottky barrier diodes. <i>Journal of Electronic Materials</i> , 1992, 21, 1127-1131.	1.0	3
1174	Charge transient spectroscopy studies on metal/Langmuir-Blodgett/GaAs structures. <i>Thin Solid Films</i> , 1992, 210-211, 324-326.	0.8	0
1175	Identification of band gap states by deep level transient spectroscopy on radioactive probes. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1992, 63, 186-188.	0.6	7
1176	Energy spectroscopy studies of radiation-induced damaged surfaces and interfaces in SiO ₂ /Si by light charged particles. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1992, 71, 278-290.	0.6	8
1177	On the correlation of implantation defects and implanted species. <i>Mikrochimica Acta</i> , 1992, 107, 179-187.	2.5	3
1178	Defect complexes in neutron irradiated silicon detectors: evaluation and effects. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 1993, 326, 344-349.	0.7	8
1179	Deep levels in δ -FeSi ₂ /n-Si heterojunctions. <i>Solid State Communications</i> , 1993, 86, 309-312.	0.9	8

#	ARTICLE	IF	CITATIONS
1180	The Meyer-Neldel rule in emission rates from defects in copper indium diselenide. <i>Solid State Communications</i> , 1993, 87, 199-202.	0.9	6
1181	Low-frequency gain dispersion in ion-implanted InP JFETs. <i>Solid-State Electronics</i> , 1993, 36, 1445-1453.	0.8	3
1182	Use of finite gate widths in multipoint correlation methods for DLTS characterization of semiconductors. <i>Solid-State Electronics</i> , 1993, 36, 119-124.	0.8	3
1183	Modeling the transient response of channel-substrate interface traps to gate voltage steps in GaAs FETs. <i>Solid-State Electronics</i> , 1993, 36, 229-236.	0.8	11
1184	Acousto-electric deep-level transient spectroscopy in semiconductors. <i>Solid-State Electronics</i> , 1993, 36, 697-703.	0.8	8
1185	Measurement and modeling of drain current DLTS in enhancement SOI MOSFETs. <i>Microelectronics Journal</i> , 1993, 24, 647-657.	1.1	5
1186	Reliability issues of silicon-dioxide structures—Application to FLOTOX EEPROM cells. <i>Microelectronics Reliability</i> , 1993, 33, 1867-1908.	0.9	5
1187	New method of deep level transient spectroscopy analysis: a five emission rate method. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1993, 20, 214-220.	1.7	2
1188	Application of deep-level transient spectroscopy for monitoring point defects in III-V semiconductors. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1993, 20, 221-224.	1.7	3
1189	Electron traps in wide-gap n-Hg _{0.3} Cd _{0.7} Te characterized by time-resolved photoconductivity. <i>Applied Physics A: Solids and Surfaces</i> , 1993, 57, 427-430.	1.4	0
1190	DLTS measurements on metal/langmuir-blodgett films/Si structures. <i>Physica Status Solidi A</i> , 1993, 138, 191-198.	1.7	3
1191	Determination of deep-level parameters by isothermal deep-level transient spectroscopy with optical excitation. <i>Physica Status Solidi A</i> , 1993, 138, 241-248.	1.7	4
1192	Parameter evaluation in automated digital deep-level transient spectroscopy (DLTS). <i>IEEE Transactions on Instrumentation and Measurement</i> , 1993, 42, 913-919.	2.4	7
1193	Current-voltage characteristics and charge DLTS spectra of proton-bombarded Schottky diodes on semi-insulating GaAs. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1993, 83, 145-152.	0.6	19
1194	Defect levels in silicon bombarded with light ions. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1993, 80-81, 573-577.	0.6	1
1195	Evidence of interaction between two DX centers in N-Type AlGaAs from RDLTS and temperature dependent pulse-width DLTS measurements. <i>Journal of Electronic Materials</i> , 1993, 22, 165-170.	1.0	4
1196	Charge-extraction technique for studying the surface states in MOS devices. <i>IEEE Transactions on Electron Devices</i> , 1993, 40, 923-931.	1.6	8
1197	Investigation of compensation defects in CdTe:Cl samples grown by different techniques. <i>Journal of Applied Physics</i> , 1993, 74, 6667-6670.	1.1	29

#	ARTICLE	IF	CITATIONS
1198	Electrical characteristic frequency dispersion of diamond polycrystalline films. <i>Diamond and Related Materials</i> , 1993, 2, 1336-1340.	1.8	9
1199	Trap states elucidated by a.c. conductance measurement in polycrystalline chemically vapour-deposited diamond films. <i>Diamond and Related Materials</i> , 1993, 2, 803-807.	1.8	24
1200	Photoinduced current transient spectroscopy of boron doped diamond. <i>Applied Physics Letters</i> , 1993, 63, 767-769.	1.5	17
1201	Isothermal capacitance transient spectroscopy study of defect states in polycrystalline diamond films. <i>Diamond and Related Materials</i> , 1993, 2, 1179-1184.	1.8	6
1202	Energy splitting of the EL2 level in Si-implanted GaAs/GaAs by field-effect deep-level transient spectroscopy. <i>Journal of Applied Physics</i> , 1993, 73, 1309-1314.	1.1	5
1203	Deep level transient spectroscopy of high-energy heavy ion irradiation-induced defects in n-type germanium. <i>Journal of Applied Physics</i> , 1993, 74, 868-871.	1.1	86
1204	Electron and neutron radiation-induced order effect in gallium arsenide. <i>IEEE Transactions on Nuclear Science</i> , 1993, 40, 1350-1359.	1.2	36
1205	Determination of electron recombination parameters in GaAs/AlGaAs quantum wells by impedance spectroscopy. <i>Applied Physics Letters</i> , 1993, 62, 1143-1145.	1.5	21
1206	Coulomb energy of traps in semiconductor space-charge regions. <i>Journal of Applied Physics</i> , 1993, 74, 2649-2657.	1.1	76
1207	Transient current measurements for the determination of the Fermi level in semiconductors. <i>Measurement Science and Technology</i> , 1993, 4, 1489-1492.	1.4	1
1208	Investigation of Deep Levels In X-Ray Detector Material With Photo Induced Current Transient Spectroscopy (Picts). <i>Materials Research Society Symposia Proceedings</i> , 1993, 302, 231.	0.1	1
1209	Direct Evidence for a Charge-Controlled Optical Quenching of EL2 Centers in Semi-Insulating GaAs. <i>Japanese Journal of Applied Physics</i> , 1993, 32, 1889-1897.	0.8	8
1210	Grown-in point defects in vapour phase epitaxial GaAs _{0.6} P _{0.4} Te. <i>Semiconductor Science and Technology</i> , 1993, 8, 538-543.	1.0	3
1212	Adaptation of deep level transient spectroscopy for narrow bandgap semiconductor materials. <i>Semiconductor Science and Technology</i> , 1993, 8, S90-S94.	1.0	2
1213	Stretched Exponential Relaxation of Persistent Photoconductivity Due to the Si-Related DX Centre in Al _x Ga _{1-x} As. <i>Europhysics Letters</i> , 1993, 24, 779-784.	0.7	14
1214	Observation of Deep Level in p-n Junction Diode of 6H:SiC. <i>Japanese Journal of Applied Physics</i> , 1993, 32, L1670-L1672.	0.8	4
1215	An easy and accurate method to determine simultaneously the free energy level and the capture cross section of a trap centre. <i>Semiconductor Science and Technology</i> , 1993, 8, 530-537.	1.0	1
1216	Investigation on Defects in Czochralski Silicon with High-Sensitive Laser/Microwave Photoconductance Technique. <i>Japanese Journal of Applied Physics</i> , 1993, 32, 298-302.	0.8	11

#	ARTICLE	IF	CITATIONS
1217	Gamma Induced Centres in Liquid Phase Epitaxial Gallium Arsenide. Japanese Journal of Applied Physics, 1993, 32, 166-167.	0.8	0
1218	An efficient and low cost optical excitation system: application to deep-level spectroscopy. Measurement Science and Technology, 1993, 4, 538-540.	1.4	0
1219	Point defects in n-type silicon implanted with low doses of MeV boron and silicon ions. Semiconductor Science and Technology, 1993, 8, 481-487.	1.0	26
1220	FTDLTS: a novel isothermal DLTS method using Fourier transforms. Measurement Science and Technology, 1993, 4, 325-336.	1.4	6
1221	A new method for the study of excitons in semiconductors. Semiconductor Science and Technology, 1993, 8, 518-524.	1.0	2
1222	A critical analysis of capacitance transient signals due to DX centres in n-type AlGaAs. Semiconductor Science and Technology, 1993, 8, 1258-1266.	1.0	5
1223	Gallium-related defect centers in molecular-beam-epitaxy-grown ZnSe films: Influence of electric field on thermal emission of electrons. Physical Review B, 1993, 47, 9641-9649.	1.1	20
1224	Characterization of deep-level defects in GaAs irradiated by 1 MeV electrons. Journal of Applied Physics, 1993, 73, 640-647.	1.1	24
1225	Defect studies in oxygen-ion irradiated silicon-based metal-insulator-semiconductor structures. Journal of Applied Physics, 1993, 74, 4343-4346.	1.1	9
1226	Junction Properties of Polycrystalline Diamond/Hydrogenated Amorphous Silicon-p-n Heterojunctions. Japanese Journal of Applied Physics, 1993, 32, 3739-3747.	0.8	2
1227	Characterization of Si-SiO ₂ interface states: Comparison between different charge pumping and capacitance techniques. Journal of Applied Physics, 1993, 74, 3932-3935.	1.1	27
1228	Electrical characteristics of layer semiconductor GaSe doped with Cd. Journal of Applied Physics, 1993, 73, 4686-4688.	1.1	16
1229	High-temperature uniaxial stress apparatus for semiconductor defect symmetry determination. Review of Scientific Instruments, 1993, 64, 221-224.	0.6	2
1230	Thermally stimulated current spectroscopy: Experimental techniques for the investigation of silicon detectors. Review of Scientific Instruments, 1993, 64, 932-936.	0.6	29
1231	Defects in electron irradiated GaInP. Journal of Applied Physics, 1993, 73, 7229-7231.	1.1	35
1232	Isothermal capacitance transient spectroscopy of electron and hole emissions from interface states in metal-oxide-semiconductor transistors. Journal of Applied Physics, 1993, 73, 4457-4461.	1.1	10
1233	Deep level transient spectroscopy on focused ion beam written in-plane capacitances. Journal of Applied Physics, 1993, 74, 6088-6093.	1.1	0
1234	Re-emission of iron originally gettered by oxygen precipitates in a silicon wafer. Journal of Applied Physics, 1993, 74, 1440-1441.	1.1	22

#	ARTICLE	IF	CITATIONS
1235	Defect identification in semiconductors by Brewster angle spectroscopy. Journal of Applied Physics, 1993, 73, 4975-4987.	1.1	27
1236	Characterization of deep levels introduced by alpha radiation in n-type silicon. Journal of Applied Physics, 1993, 73, 3698-3708.	1.1	30
1237	Electronic states created in p-Si subjected to plasma etching: The role of inherent impurities, point defects, and hydrogen. Applied Physics Letters, 1993, 62, 958-960.	1.5	20
1238	A theory of ion beam induced charge collection. Journal of Applied Physics, 1993, 74, 3789-3799.	1.1	84
1239	Analysis of defect energy levels in the limit of low emission rates. Journal of Applied Physics, 1993, 73, 2854-2858.	1.1	2
1240	Lithium-ion mobility improvement in floating-zone silicon by external gettering. Applied Physics Letters, 1993, 63, 343-345.	1.5	10
1241	Hydrogen enhancement of silicon thermal donor formation. Applied Physics Letters, 1993, 62, 2081-2083.	1.5	8
1242	A deep-level transient spectroscopy variation for the determination of displacement threshold energies in GaAs. Journal of Applied Physics, 1993, 73, 2781-2785.	1.1	9
1243	A numerical procedure to determine near midgap level defect parameters in Schottky diodes with significant leakage current densities. Review of Scientific Instruments, 1993, 64, 2655-2660.	0.6	0
1244	A method to correct for leakage current effects in deep level transient spectroscopy measurements on Schottky diodes. Journal of Applied Physics, 1993, 74, 3936-3943.	1.1	21
1245	Study of alpha-radiation-induced deep levels in n-type silicon. Journal of Applied Physics, 1993, 73, 4240-4247.	1.1	27
1246	Electron paramagnetic resonance of multistable interstitial-carbon substitutional-group-V-atom pairs in silicon. Physical Review B, 1993, 47, 6363-6380.	1.1	35
1247	The analysis of the temperature dependence of photoconductive frequency-resolved spectroscopy in the presence of carrier trapping: Application to polycrystalline silicon. Journal of Applied Physics, 1993, 73, 2958-2964.	1.1	7
1248	Quantitative study of the contribution of deep and shallow levels to the compensation mechanisms in annealed InP. Journal of Applied Physics, 1993, 74, 5538-5545.	1.1	38
1249	Numerical fitting of transient decays in the high defect density limit. Journal of Applied Physics, 1993, 74, 6636-6641.	1.1	0
1250	Influence of sintering temperature on electrical properties of ZnO varistors. Journal of Applied Physics, 1993, 74, 695-703.	1.1	84
1251	A new technique to decompose closely spaced interface and bulk trap states using temperature dependent pulse-width deep level transient spectroscopy method: An application to PT/CdS photodetector. Journal of Applied Physics, 1993, 73, 760-766.	1.1	6
1252	Local oxidation of GaP wafers heated by a Nd:YAG laser beam. Journal of Applied Physics, 1993, 73, 4009-4015.	1.1	6

#	ARTICLE	IF	CITATIONS
1253	Deep-level transient charge spectroscopy of Sn donors in $\text{Al}_x\text{Ga}_{1-x}\text{As}$. Journal of Applied Physics, 1993, 73, 1802-1806.	1.1	29
1254	Deep hole traps in ϵ -type nitrogen-doped ZnSe grown by molecular beam epitaxy. Applied Physics Letters, 1993, 63, 358-360.	1.5	34
1255	Field effect on thermal emission from the 0.40 eV electron level in InGaP. Journal of Applied Physics, 1993, 73, 771-774.	1.1	23
1256	Trap behavior in nonintentionally doped AlGaAs/GaAs single quantum well structures. Journal of Applied Physics, 1993, 73, 271-276.	1.1	20
1257	Photoconductive frequency-resolved spectroscopy of semiconductors: an analysis of lifetime distributions. Semiconductor Science and Technology, 1993, 8, 1277-1282.	1.0	7
1258	Effects of Interface States on Applied Voltage Dependence of Double Schottky Barrier (Part 1). Journal of the Ceramic Society of Japan, 1993, 101, 1125-1130.	1.3	7
1259	Chapter 6 DX and Related Defects in Semiconductors. Semiconductors and Semimetals, 1993, 38, 235-291.	0.4	23
1260	Deep-Level Transient Spectroscopy Studies of Czochralski-Grown N -Type Silicon. Materials Research Society Symposia Proceedings, 1993, 324, 373.	0.1	0
1261	Defect Reduction by Thermal Cyclic Growth in GaAs Grown on Si by MOVPE. Materials Research Society Symposia Proceedings, 1993, 325, 437.	0.1	2
1262	Deep Levels Induced by SiCl_4 Reactive Ion Etching in GaAs. Materials Research Society Symposia Proceedings, 1993, 325, 443.	0.1	3
1263	Divacancy distributions in fast ion irradiated silicon. Radiation Effects and Defects in Solids, 1994, 128, 179-186.	0.4	10
1264	Radiation effects in bulk silicon. Radiation Effects and Defects in Solids, 1994, 127, 267-293.	0.4	5
1265	Copper in ultra-pure germanium: determination of the electrically active fraction. Semiconductor Science and Technology, 1994, 9, 1050-1053.	1.0	3
1266	Deep-level transient spectroscopy study of bonded wafers. Semiconductor Science and Technology, 1994, 9, 1366-1369.	1.0	3
1267	Observation of hydrogen in commercial Czochralski-grown silicon wafers. Semiconductor Science and Technology, 1994, 9, 1733-1735.	1.0	11
1268	Influence of donor density in ZnO on $\text{ZnO}/\text{PrCoO}_{2-x}$ thin-film junctions: Role of O_{2-x} and Al dopant in varistors. Journal of Materials Research, 1994, 9, 669-673.	1.2	6
1269	Detection of slow traps in the oxide of MOS transistors by a new current DLTS technique. Electronics Letters, 1994, 30, 484-485.	0.5	6
1270	Dominant Deep Level in Annealed Low-Temperature GaAs Layers Grown by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1994, 33, L1651-L1654.	0.8	13

#	ARTICLE	IF	CITATIONS
1271	Characterization of the damage induced in boron-implanted and RTA annealed silicon by the capacitance-voltage transient technique. <i>Semiconductor Science and Technology</i> , 1994, 9, 1637-1648.	1.0	17
1272	Passivation of Shallow and Deep Levels by Hydrogen Plasma Exposure in AlGaAs Grown by Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 1994, 33, 3348-3353.	0.8	3
1273	Photocapacitance Measurement on Intentionally Undoped n-Type Ga _{0.9} Al _{0.1} As Grown by Stoichiometry Control Method. <i>Japanese Journal of Applied Physics</i> , 1994, 33, 1753-1758.	0.8	2
1274	Deep Impurity Centers in CdS Single Crystals Studied by Spectral Analysis of Deep Level Transient Spectroscopy. <i>Japanese Journal of Applied Physics</i> , 1994, 33, 3480-3481.	0.8	4
1275	A new figure of merit and methodology for quantitatively determining defect resolution capabilities in deep level transient spectroscopy analysis. <i>Journal of Applied Physics</i> , 1994, 75, 4570-4575.	1.1	10
1276	Deep levels in 6H-SiC wafers and step-controlled epitaxial layers. <i>Applied Physics Letters</i> , 1994, 65, 581-583.	1.5	17
1277	Calibration of deep level measurement systems in semiconductors. , 0, , .		0
1278	Electrical studies on H-implanted silicon. <i>Physical Review B</i> , 1994, 49, 5291-5299.	1.1	22
1279	Hole traps produced by swift heavy ion irradiation in p-type germanium. <i>Journal of Applied Physics</i> , 1994, 75, 1852-1854.	1.1	9
1280	Anomalous Electronic Properties of a Hydrogen-Related Deep Donor in ²⁸ Si. <i>Physical Review Letters</i> , 1994, 73, 312-315.	2.9	12
1281	Symmetry determination of the EL2 defect by numerical fitting of capacitance transients under uniaxial stress. <i>Physical Review B</i> , 1994, 49, 1690-1695.	1.1	4
1282	Comparison of covariance linear predictive modeling to the modulation function method for use in deep level transient spectroscopy. <i>Journal of Applied Physics</i> , 1994, 75, 4560-4569.	1.1	12
1283	Switching between deep level transient spectroscopy and feedback charge capacitance modes in a versatile time-domain spectrometer. <i>Review of Scientific Instruments</i> , 1994, 65, 2244-2248.	0.6	38
1284	Analysis of transients in semiconductor/semi-insulator junctions. <i>Journal of Applied Physics</i> , 1994, 75, 2035-2041.	1.1	2
1285	Deep level defects in proton irradiated Zn and Cd doped InP. <i>Journal of Applied Physics</i> , 1994, 75, 1384-1389.	1.1	6
1286	Precise evaluation of deep level concentrations in capacitance transient analyses. <i>Journal of Applied Physics</i> , 1994, 76, 791-795.	1.1	6
1287	Hall effect and impurity levels in lead doped indium selenide. <i>Journal of Applied Physics</i> , 1994, 75, 3982-3986.	1.1	1
1288	Deep levels in alpha-irradiated platinum doped n-type silicon. <i>Journal of Applied Physics</i> , 1994, 76, 2553-2555.	1.1	3

#	ARTICLE	IF	CITATIONS
1289	Deep electron states in chlorine-doped ZnSe films grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 1994, 75, 7382-7388.	1.1	29
1290	Deep level transient spectroscopy investigation of a deep trap in float-zone Si. <i>Journal of Applied Physics</i> , 1994, 75, 645-647.	1.1	3
1291	Transient phenomena on the temperature elevation of semi-insulating GaP wafers heated locally by a Nd:YAG laser beam. <i>Journal of Applied Physics</i> , 1994, 76, 216-222.	1.1	1
1292	Demonstration of gallium-defect annealing at 280 K in irradiated GaAs and Al _x Ga _{1-x} As. <i>Physical Review B</i> , 1994, 49, 5695-5698.	1.1	7
1293	Deep traps in molecular-beam-epitaxial GaAs grown at low temperatures. <i>Journal of Applied Physics</i> , 1994, 76, 1029-1032.	1.1	39
1294	Hydrogen passivation of gold in p-type silicon involving hydrogen-gold-related deep levels. <i>Physical Review B</i> , 1994, 49, 7801-7804.	1.1	29
1295	Electrical properties of contact etched Si: A comparison between magnetically enhanced and conventional reactive ion etching. <i>Journal of Applied Physics</i> , 1994, 76, 2270-2278.	1.1	28
1296	Observation of the center in 6H-SiC diodes grown by chemical vapor deposition. <i>Applied Physics Letters</i> , 1994, 64, 2730-2732.	1.5	39
1297	Electrical and structural studies of copper and nickel precipitates in a $\lambda=25$ silicon bicrystal. <i>Journal of Applied Physics</i> , 1994, 76, 952-958.	1.1	36
1298	U-shaped distribution of interface states in metal-(Langmuir-Blodgett) Si structures with phthalocyanine Langmuir-Blodgett films. <i>Thin Solid Films</i> , 1994, 243, 463-467.	0.8	4
1299	Determination of capture rates from non-equilibrium quasistatic C_{t} characteristics of MIS capacitors. <i>Physica Status Solidi A</i> , 1994, 141, 163-173.	1.7	0
1300	Effect of deep level impurities on the grain boundary potential of a polycrystalline semiconductor. <i>Physica Status Solidi A</i> , 1994, 142, 117-125.	1.7	7
1303	Studies of deep-level defects at III-V heterointerfaces. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1994, 28, 387-392.	1.7	2
1304	Scanning deep-level transient spectroscopy investigations on gallium arsenide. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1994, 24, 28-34.	1.7	2
1305	Stoichiometry of III-V compounds. <i>Materials Science and Engineering Reports</i> , 1994, 12, 273-426.	14.8	54
1306	Formation of anodic plasma oxides on InP, GaAs and Si through Al and Sm overlayers. <i>Applied Surface Science</i> , 1994, 78, 239-248.	3.1	0
1307	Excess capacitance of Al/n-GaAs Schottky diodes prepared on Ar-(Ar + H)-ion-beam-etched surfaces. <i>Applied Surface Science</i> , 1994, 74, 135-145.	3.1	1
1308	Influence of tunnel effects on the kinetics of the photocapacitance in nonideal heterojunctions. <i>Solid-State Electronics</i> , 1994, 37, 1680-1682.	0.8	1

#	ARTICLE	IF	CITATIONS
1309	A spectral analysis method to directly determine minority carrier generation lifetime using the pulsed MOS structure. <i>Solid-State Electronics</i> , 1994, 37, 31-36.	0.8	26
1310	Resistivity profile measurements of proton-irradiated n-type silicon. <i>Solid-State Electronics</i> , 1994, 37, 55-60.	0.8	30
1311	Observation of discrete energy levels of interface traps in sub- μm MOSFETs. <i>Solid-State Electronics</i> , 1994, 37, 1799-1808.	0.8	2
1312	On the influence of an ultrathin Al overlayer on GaAs plasma oxide growth kinetics. <i>Thin Solid Films</i> , 1994, 249, 44-49.	0.8	1
1313	MOSFET parameter extraction from static, dynamic and transient current measurements. <i>Microelectronics Journal</i> , 1994, 25, 41-61.	1.1	10
1314	Emission and capture of electrons in multiquantum-well structures. <i>IEEE Journal of Quantum Electronics</i> , 1994, 30, 2875-2888.	1.0	77
1315	Analysis of photoinduced current transient spectroscopy (PICTS) data by a regularisation method: Application of compensation defects in CdTe. <i>Advanced Materials for Optics and Electronics</i> , 1994, 3, 269-274.	0.6	3
1316	Apparatus for magnetic moment measurement using channeling in bent crystals. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1994, 90, 150-155.	0.6	6
1317	Deep Level Transient Spectroscopy techniques and systems. <i>Acta Physica Hungarica</i> , 1994, 74, 129-138.	0.1	1
1318	Radiation damage in silicon detectors. <i>Rivista Del Nuovo Cimento</i> , 1994, 17, 1-63.	2.0	37
1319	Improvement in the determination of accuracy of enthalpy of ionization from the isothermal deep level transient spectroscopy. <i>European Physical Journal D</i> , 1994, 44, 745-752.	0.4	1
1320	Computerized digitizing technique for DLTS measurements. <i>IEEE Transactions on Instrumentation and Measurement</i> , 1994, 43, 936-939.	2.4	0
1321	Measurement of electrophysical properties of silicon carbide epitaxial films. <i>Diamond and Related Materials</i> , 1994, 3, 1393-1397.	1.8	21
1322	Deep level transient spectroscopy characterization of ferroelectric $\text{Pb}(\text{Zr},\text{Ti})\text{O}_3$ thin films. <i>Applied Physics Letters</i> , 1994, 64, 2670-2672.	1.5	38
1323	A deep level spectroscopic technique for determining capture cross section activation energy of Si-related DX centers in $\text{Al}_x\text{Ga}_{1-x}\text{As}$. <i>Journal of Applied Physics</i> , 1994, 75, 8243-8245.	1.1	5
1324	Semiconductor surface spectroscopies: the early years. <i>Surface Science</i> , 1994, 299-300, 92-101.	0.8	42
1325	Studies of deep levels in high resistivity silicon detectors irradiated by high fluence fast neutrons using a thermally stimulated current spectrometer. <i>IEEE Transactions on Nuclear Science</i> , 1994, 41, 964-970.	1.2	24
1326	Identification of tunneling emission in Si/SiO_2 interfaces by multipoint correlation method with binomial weighting coefficients. <i>Journal of Applied Physics</i> , 1994, 76, 352-358.	1.1	2

#	ARTICLE	IF	CITATIONS
1327	Laplace transform deep-level transient spectroscopic studies of defects in semiconductors. Journal of Applied Physics, 1994, 76, 194-198.	1.1	176
1328	Measurement of capacitance transients with attoFarad resolution in a microwave varactor diode after Co/sup 60/ irradiation. IEEE Transactions on Nuclear Science, 1994, 41, 2502-2510.	1.2	2
1329	Analysis of amorphous-silicon devices. , 0, , .		5
1330	Radiation-induced defect introduction rates in semiconductors. IEEE Transactions on Nuclear Science, 1994, 41, 1913-1923.	1.2	20
1331	A simple technique for determining deep-level concentrations in high-resistivity semiconductors using capacitance transients. IEEE Transactions on Nuclear Science, 1994, 41, 343-348.	1.2	3
1332	lithium-gold-related defect complexes in n-type silicon. Physica Scripta, 1994, T54, 12-15.	1.2	1
1333	Chapter 3 Characterization Techniques for Oxygen in Silicon. Semiconductors and Semimetals, 1994, 42, 53-93.	0.4	3
1334	Special Issue. Surface Control Technology for LSI Processes. Analysis of Metallic Contamination on a Wafer.. Hyomen Gijutsu/Journal of the Surface Finishing Society of Japan, 1994, 45, 6-11.	0.1	1
1335	Laplace transform deep level transient spectroscopy: new insight into defect microscopy. Materials Science and Technology, 1995, 11, 1071-1073.	0.8	2
1336	<title>Novel evaluation method of silicon epitaxial layer lifetimes by photoluminescence technique</title>. , 1995, 2638, 113.		7
1337	Chapter 7 Characterization of CdTe Nuclear Detector Materials. Semiconductors and Semimetals, 1995, , 259-289.	0.4	2
1338	Characterization of Interface States in Semiconducting (Ba, Sr)TiO₃ Ceramics by Isothermal Transient Capacitance Method. Journal of the Ceramic Society of Japan, 1995, 103, 1006-1010.	1.3	2
1339	Improvement of Pin Photodiodes on the Soi Layer by Rapid Thermal Annealing. Materials Research Society Symposia Proceedings, 1995, 378, 731.	0.1	0
1340	Phenomena Related to Concurrent Multiple Complex Plane Representations of the Immittance Data. Materials Research Society Symposia Proceedings, 1995, 411, 113.	0.1	5
1341	Evaluation of the bonded silicon on insulator (SOI) wafer and the characteristics of PIN photodiodes on the bonded SOI wafer. IEEE Transactions on Electron Devices, 1995, 42, 239-243.	1.6	8
1342	Self annealing effect on neutron irradiated silicon detectors investigated by TSC analysis. Nuclear Physics, Section B, Proceedings Supplements, 1995, 44, 488-495.	0.5	3
1343	Annealing effects on resistivity and hall coefficient of neutron irradiated silicon. Nuclear Physics, Section B, Proceedings Supplements, 1995, 44, 496-502.	0.5	1
1344	DLTS measurement of energetic levels, generated in silicon detectors. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1995, 361, 461-465.	0.7	12

#	ARTICLE	IF	CITATIONS
1345	Development of current-based microscopic defect analysis methods and associated optical filling techniques for the investigation on highly irradiated high resistivity silicon detectors. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1995, 364, 108-117.	0.7	20
1346	Silicon as an advanced window material for high power gyrotrons. Journal of Infrared, Millimeter and Terahertz Waves, 1995, 16, 863-877.	0.6	42
1350	The ohmic contact to the silicon Schottky barrier using vanadium silicide and gold or silver metallization. Applied Surface Science, 1995, 91, 352-354.	3.1	5
1351	Peak and side data analyses to measure deep levels by DLS-82E lock-in spectrometer. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1995, 32, 51-55.	1.7	1
1352	Deep centers and electroluminescence in 4H α -SiC diodes with a p-type base region. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1995, 29, 181-184.	1.7	36
1353	Temperature dependence of I-V and C-V characteristics of Schottky diodes. Renewable Energy, 1995, 6, 567-572.	4.3	7
1354	Properties of epitaxially grown CdTe layers doped with indium. Thin Solid Films, 1995, 267, 79-83.	0.8	15
1355	Electrical characterization of sputter-deposition-induced defects in epitaxially grown n-GaAs layers. Vacuum, 1995, 46, 1087-1090.	1.6	8
1356	Femtosecond modulated reflectance investigation of In _{0.5} Ga _{0.5} P and In _{0.5} Ga _{0.5} P _{0.99} As _{0.01} lattice-matched to GaAs (100) substrate. Solid State Communications, 1995, 93, 497-499.	0.9	0
1357	Effects of electron trapping on diffusion time-of-flight measurement in GaAs. Solid-State Electronics, 1995, 38, 1811-1816.	0.8	0
1358	Temperature effects on pin diode forward bias resistance. Solid-State Electronics, 1995, 38, 1879-1885.	0.8	10
1359	Side data analysis of deep level transient spectroscopy spectra for a multipoint correlation method with binomial weighting coefficients. Solid-State Electronics, 1995, 38, 1051-1057.	0.8	7
1360	Investigations on Au, Ag, and Al schottky diodes on liquid encapsulated czochralski grown n-GaAs. Journal of Electronic Materials, 1995, 24, 813-817.	1.0	4
1361	Accurate measurement of capture cross sections in deep level transient spectroscopy: Application to EL2 in GaAs. Journal of Electronic Materials, 1995, 24, 1461-1464.	1.0	7
1362	Quantitative surface photovoltage spectroscopy of semiconductor interfaces. Journal of Electronic Materials, 1995, 24, 379-385.	1.0	26
1363	Point defects in MeV ion-implanted silicon studied by deep level transient spectroscopy. Nuclear Instruments & Methods in Physics Research B, 1995, 106, 183-190.	0.6	55
1364	Effect of Ge-related mechanical strain on defect and impurity behaviour in ion-implanted silicon. Nuclear Instruments & Methods in Physics Research B, 1995, 106, 262-266.	0.6	6
1365	A comparative study of deep levels created by low dose implantation of hydrogen, oxygen and silicon into MOCVD grown n-GaAs. Nuclear Instruments & Methods in Physics Research B, 1995, 106, 313-317.	0.6	1

#	ARTICLE	IF	CITATIONS
1366	Defect levels of proton-irradiated silicon with doses ranging from $1 \text{ \AA}^{-1} \cdot 10^{12} \text{ cm}^{-2}$ to $1 \text{ \AA}^{-1} \cdot 10^{13} \text{ cm}^{-2}$. Nuclear Instruments & Methods in Physics Research B, 1995, 95, 213-218.	0.6	13
1367	Deep defect levels and mechanical strain in Ge+-implanted silicon. Nuclear Instruments & Methods in Physics Research B, 1995, 96, 245-248.	0.6	12
1368	A study of electronic transitions in semiconductors by dielectric spectroscopy. Physica B: Condensed Matter, 1995, 212, 17-24.	1.3	2
1369	Evolution of electrical activity and structure of nickel precipitates with the treatment temperature of a $\lambda=25$ silicon bicrystal. Journal of Applied Physics, 1995, 77, 1875-1880.	1.1	24
1370	Interface state measurements by the DLS-82E lock-in spectrometer. Review of Scientific Instruments, 1995, 66, 4283-4288.	0.6	5
1371	A sensitive technique for detecting low concentrations of deep level traps: Current-source deep level transient spectroscopy. Journal of Applied Physics, 1995, 78, 5431-5438.	1.1	1
1372	Convenient determination of concentration and energy in deep-level transient spectroscopy. Journal of Applied Physics, 1995, 77, 1407-1410.	1.1	15
1373	On the local structure of optically active Er centers in Si. Applied Physics Letters, 1995, 66, 490-492.	1.5	50
1374	Characterization of deep levels and carrier compensation created by proton irradiation in undoped GaAs. Journal of Applied Physics, 1995, 78, 1481-1487.	1.1	32
1375	A field-assisted emission model of interface states in heterostructure devices. Journal of Applied Physics, 1995, 78, 7382-7386.	1.1	0
1376	Carrier trapping in ultrafast metal-semiconductor-metal photodetectors on InGaAs/GaAs-on-GaAs superlattices. Journal of Applied Physics, 1995, 77, 1785-1794.	1.1	5
1377	Deep levels in indium selenide single crystals doped with iodine. Journal of Applied Physics, 1995, 78, 5427-5430.	1.1	3
1378	Lithium-gold-related defect complexes in type crystalline silicon. Journal of Applied Physics, 1995, 77, 3146-3154.	1.1	11
1379	Deep-level transient spectroscopy and electrical characterization of ion-implanted p-n junctions into undoped InP. Journal of Applied Physics, 1995, 78, 5325-5330.	1.1	10
1380	Effects of column III alkyl sources on deep levels in GaN grown by organometallic vapor phase epitaxy. Applied Physics Letters, 1995, 67, 1721-1723.	1.5	116
1381	Hole capture by center defects in 6H-silicon carbide. Journal of Applied Physics, 1995, 77, 318-322.	1.1	11
1382	Temperature-time duality and deep level spectroscopies. Journal of Applied Physics, 1995, 77, 3155-3161.	1.1	30
1383	Deep center related to hydrogen and carbon in type silicon. Journal of Applied Physics, 1995, 78, 4478-4486.	1.1	21

#	ARTICLE	IF	CITATIONS
1384	Electronic and transformation properties of a metastable defect introduced in n-type GaAs by $\hat{1}\pm$ -particle irradiation. <i>Physical Review B</i> , 1995, 51, 17521-17525.	1.1	17
1385	Capacitance-voltage measurement of charged defect concentration profile near semiconductor depletion zones. <i>Journal of Applied Physics</i> , 1995, 77, 1627-1634.	1.1	13
1386	Interaction between copper and point defects in silicon irradiated with 2-MeV electrons. <i>Physical Review B</i> , 1995, 52, 2522-2527.	1.1	28
1387	Degradation and annealing of electron-irradiated diffused junction InP solar cells. <i>Journal of Applied Physics</i> , 1995, 78, 7368-7375.	1.1	7
1388	Double integration of current transients in response to an abrupt change of applied bias: Application to dielectrics. <i>Review of Scientific Instruments</i> , 1995, 66, 5360-5366.	0.6	1
1389	Reduction of deep defect concentration in chlorine-doped ZnSe by after-growth thermal treatment. <i>Journal of Applied Physics</i> , 1995, 77, 2026-2028.	1.1	10
1390	Depletion width and capacitance transient formulas for deep traps of high concentration. <i>Journal of Applied Physics</i> , 1995, 78, 2848-2850.	1.1	23
1391	Intrinsic origin and composition dependence of deep-level defects at the inverted GaAs/Al _x Ga _{1-x} As interface grown by molecular-beam epitaxy. <i>Journal of Applied Physics</i> , 1995, 77, 5773-5781.	1.1	21
1392	Hydrogen passivation and its effects on carrier trapping by dislocations in InP/GaAs heterostructures. <i>Journal of Applied Physics</i> , 1995, 77, 3885-3898.	1.1	21
1393	Metal contamination characterization in CCD image sensors. , 0, , .		6
1394	Reaction kinetics of hydrogen-gold complexes in silicon. <i>Physical Review B</i> , 1995, 52, 4884-4895.	1.1	72
1395	Long-wavelength acoustic-mode-enhanced electron emission from Se and Te donors in silicon. <i>Physical Review B</i> , 1995, 52, 14598-14606.	1.1	15
1396	Molecular Beam Epitaxy of High-Quality GaAs and AlGaAs. , 1995, , 114-274.		10
1397	The gamma ray radiation effects in high-electron-mobility transistors. <i>Semiconductor Science and Technology</i> , 1995, 10, 1445-1451.	1.0	5
1398	Transient acoustoelectric spectroscopy measurements for the characterization of GaAs epilayer structures. <i>Semiconductor Science and Technology</i> , 1995, 10, 965-969.	1.0	3
1399	Discharging Current Transient Spectroscopy for Evaluating Traps in Insulators. <i>Japanese Journal of Applied Physics</i> , 1995, 34, L185-L187.	0.8	33
1400	Single Junctions in ZnO Varistors Studied by Current-Voltage Characteristics and Deep Level Transient Spectroscopy. <i>Japanese Journal of Applied Physics</i> , 1995, 34, 1765-1771.	0.8	44
1401	Characterization of Deep Levels in N-Type Si Epitaxial Layer. <i>Japanese Journal of Applied Physics</i> , 1995, 34, L1245-L1247.	0.8	1

#	ARTICLE	IF	CITATIONS
1402	Influence of Fe Contamination in Czochralski-Grown Silicon Single Crystals on LSI-Yield Related Crystal Quality Characteristics. Japanese Journal of Applied Physics, 1995, 34, 409-413.	0.8	12
1403	Electrical properties of RF sputtered In-ZnTe Schottky diodes. Semiconductor Science and Technology, 1995, 10, 348-352.	1.0	3
1404	Tunnel ionization of shallow acceptors and donors in GaAs. Journal of Physics Condensed Matter, 1995, 7, 2133-2146.	0.7	11
1405	Property of Radiation-Induced Defects in Germanium Single Crystals. Japanese Journal of Applied Physics, 1995, 34, 3204-3208.	0.8	6
1406	Temperature dependence of the capture cross section determined by DLTS on an MOS structure. Semiconductor Science and Technology, 1995, 10, 1510-1519.	1.0	20
1407	Deep levels in silicon after iron silicide formation. Semiconductor Science and Technology, 1995, 10, 1645-1651.	1.0	6
1408	High resolution method for the analysis of admittance spectroscopy data. Journal of Applied Physics, 1995, 77, 3851-3857.	1.1	12
1409	Deep Level Transient Spectroscopy (DLTS). Kluwer International Series in Engineering and Computer Science, 1995, , 109-126.	0.2	1
1410	Deep-level defects responsible for persistent photoconductivity in Ga-doped Cd _{1-x} Mn _x Te. Physical Review B, 1995, 51, 17499-17505.	1.1	20
1411	Deep level transient spectroscopy of InP quantum dots. Applied Physics Letters, 1995, 67, 3016-3018.	1.5	91
1412	Photoluminescence and photoconductivity in CdIn ₂ Te ₄ . Journal of Applied Physics, 1995, 78, 5654-5659.	1.1	6
1413	On the applicability of deep-level transient spectroscopy for the investigation of deep centers in silicon created by fast neutron irradiation. Applied Physics A: Materials Science and Processing, 1995, 61, 107-109.	1.1	3
1414	Acoustoelectric charge injection in semiconductors. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 1995, 42, 876-882.	1.7	2
1415	Deep level defects in alpha particle irradiated 6H silicon carbide. Journal of Applied Physics, 1995, 78, 2996-3000.	1.1	32
1416	Electron trapping kinetics at dislocations in relaxed Ge _{0.3} Si _{0.7} /Si heterostructures. Journal of Applied Physics, 1995, 77, 3248-3256.	1.1	76
1417	Deep levels in nitrogen-implanted GaAs. Journal of Applied Physics, 1995, 78, 4261-4263.	1.1	12
1418	Bandlike and localized states at extended defects in silicon. Physical Review B, 1995, 52, 13726-13729.	1.1	159
1419	Wave form analysis of constant capacitance voltage transient deep level transient spectroscopy using an iterative feedback system. Review of Scientific Instruments, 1996, 67, 809-812.	0.6	1

#	ARTICLE	IF	CITATIONS
1420	AC analysis of amorphous silicon devices. IEEE Transactions on Computer-Aided Design of Integrated Circuits and Systems, 1996, 15, 1324-1331.	1.9	5
1421	Determination of defect distributions from admittance measurements and application to Cu(In,Ga)Se ₂ based heterojunctions. Journal of Applied Physics, 1996, 80, 4411-4420.	1.1	681
1422	Lifetime in proton irradiated silicon. Journal of Applied Physics, 1996, 79, 3906.	1.1	159
1423	Effect of dry etching and subsequent annealing of Si/SiGe/Si heterostructure. Journal of Applied Physics, 1996, 79, 4402.	1.1	9
1424	The 'fractional thermally stimulated current' (FTSC) method: application to deep impurity levels in semi-insulating InP. Semiconductor Science and Technology, 1996, 11, 935-940.	1.0	9
1425	Silicon carbide alphavoltaic battery. , 1996, , .		9
1426	Passivation and reactivation of deep Fe and Cu levels in p-type GaAs. , 0, , .		1
1427	Source of Ge centers in AlGaAs grown by organometallic vapor phase epitaxy and the effect of impurity getters. Applied Physics Letters, 1996, 68, 1368-1370.	1.5	0
1428	Optical admittance studies of vanadium donor level in high-resistivity p-type 6H-SiC. Journal of Applied Physics, 1996, 79, 253-258.	1.1	24
1429	Electrical Characterization of Engineering Materials. Active and Passive Electronic Components, 1996, 19, 139-169.	0.3	34
1430	Electro-thermal stress and high electric field effects in CVD-Grown 4H-SiC P-N junction diodes. AIP Conference Proceedings, 1996, , .	0.3	0
1431	Comparison Of Gettering Ability between I/I Defects And Si Substrate. Materials Research Society Symposia Proceedings, 1996, 442, 181.	0.1	0
1432	Effects of H ⁺ -Implantation On Electron Traps In N-Type Si Induced by P ⁺ Pre-Implantation. Materials Research Society Symposia Proceedings, 1996, 442, 281.	0.1	0
1433	Charge Transient Spectroscopy Study Of Deep Centers In Cvd Diamond And Diamond-Like Films. Materials Research Society Symposia Proceedings, 1996, 442, 687.	0.1	15
1434	Characterization of the Thin Diamond-Like Carbon Films Deposited Using Rf Inductively Coupled CH ₄ -Plasma Source. Materials Research Society Symposia Proceedings, 1996, 446, 413.	0.1	2
1435	Electrical Properties of the Multilayer Structures Based on Ultrathin Diamond-Like Carbon Films. Materials Research Society Symposia Proceedings, 1996, 452, 845.	0.1	0
1436	Annihilation Process of New Donors in N-Type Carbon-Rich CZ Silicon. Materials Transactions, JIM, 1996, 37, 1438-1442.	0.9	0
1437	Swift-heavy-ion induced damage in germanium: An evaluation of defect introduction rates. Journal of Applied Physics, 1996, 79, 7555-7562.	1.1	23

#	ARTICLE	IF	CITATIONS
1438	Effect of composition on deep levels in heteroepitaxial $GexSi_{1-x}$ layers and evidence for dominant intrinsic recombination-Generation in relaxed ge layers on Si. Journal of Electronic Materials, 1996, 25, 1028-1036.	1.0	15
1439	Defect production in Si by ion bombardment under the influence of internal mechanical strain. Nuclear Instruments & Methods in Physics Research B, 1996, 115, 557-560.	0.6	2
1440	Preparing crystals for channeling experiments at high energies. Nuclear Instruments & Methods in Physics Research B, 1996, 119, 308-315.	0.6	3
1441	Modelling the effects of electrical traps in radiation detectors. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1996, 377, 197-205.	0.7	0
1442	Influence of radiation-induced clusters on transport properties of silicon. Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics, 1996, 18, 621-633.	0.4	0
1443	Defect evolution in MeV ion-implanted silicon. Nuclear Instruments & Methods in Physics Research B, 1996, 120, 27-32.	0.6	18
1444	Investigation of BF ₂ ⁺ implants in silicon through SiO ₂ films Redistribution of fluorine and boron under rapid thermal annealing. Nuclear Instruments & Methods in Physics Research B, 1996, 120, 68-73.	0.6	2
1445	Effects of surface potential fluctuations on DLTS of MOS structure. Solid-State Electronics, 1996, 39, 243-249.	0.8	7
1446	Non-exponential capacitance transient in deep level transient spectroscopy (DLTS) measurements. Solid-State Electronics, 1996, 39, 321-322.	0.8	2
1447	Deep levels in Au-POxNyHz-(n)InP MIS structures. Solid-State Electronics, 1996, 39, 929-934.	0.8	0
1448	Simulation of forward bias injection in proton irradiated silicon pn-junctions. Solid-State Electronics, 1996, 39, 1087-1092.	0.8	14
1449	Depletion approximation in semiconductor trap filling analysis: Application to EL2 in GaAs. Solid-State Electronics, 1996, 39, 1398-1400.	0.8	2
1450	New approach to bias scan DLTS for rapid evaluation of interface states in MOS structures. Solid-State Electronics, 1996, 39, 1507-1514.	0.8	3
1451	Anomaly in the growth rate of anodic oxide films due to the presence of a (Sm + Sm ₂ O ₃) overlayer at a GaAs surface. Thin Solid Films, 1996, 272, 21-28.	0.8	0
1452	Neutron induced defects in silicon detectors characterized by DLTS and TSC methods. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1996, 377, 258-264.	0.7	23
1453	Deep centers in AlGaAs/GaAs GRIN-SCHSQW laser structures grown by MBE and MOCVD. Journal of Crystal Growth, 1996, 169, 643-648.	0.7	1
1454	Irradiation effects on Au ⁻ -Si nuclear detectors by 10 MeV $\hat{\pm}$ -particles. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1996, 380, 76-78.	0.7	1
1455	A study of the dark currents of InSb charge injection devices. Optical and Quantum Electronics, 1996, 28, 1287-1294.	1.5	0

#	ARTICLE	IF	CITATIONS
1456	Electrical Characteristics of Chemical Vapor Deposited Diamond Films. <i>Physica Status Solidi A</i> , 1996, 154, 371-384.	1.7	7
1457	Positron annihilation studies of defect properties in semi-insulating GaAs. <i>Physica Status Solidi A</i> , 1996, 156, 277-284.	1.7	6
1458	Practical methods to improve DLTS data smoothing. <i>Physica Status Solidi A</i> , 1996, 156, 413-420.	1.7	3
1459	Additive double gate analysis in photoinduced current transient spectroscopy: Application to cuprous oxide. <i>Physica Status Solidi (B): Basic Research</i> , 1996, 196, 163-173.	0.7	10
1460	Effects of iron contamination on the electrical activity of a silicon bicrystal. <i>Journal Physics D: Applied Physics</i> , 1996, 29, 3096-3100.	1.3	10
1461	Deep Trap Measurement in $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ Isothermal Capacitance and Deep-Level Transient Spectroscopy. <i>Japanese Journal of Applied Physics</i> , 1996, 35, 3374-3375.	0.8	1
1462	Electron and hole capture kinetics at gold - hydrogen complexes in n-type silicon. <i>Semiconductor Science and Technology</i> , 1996, 11, 1704-1712.	1.0	20
1463	Annealing of irradiated epitaxial InP solar cells. <i>Journal of Applied Physics</i> , 1996, 80, 4315-4321.	1.1	11
1464	Plasma Etching Induced Damage to Strained Si/SiGe/Si heterostructure. , 0, , .		0
1465	Significance of blackbody radiation in deep level transient spectroscopy. <i>Journal of Applied Physics</i> , 1996, 79, 9385-9387.	1.1	7
1466	Deep level transient spectroscopy of hole emission from nitrided oxide/silicon interface traps. , 0, , .		0
1467	A simple and inexpensive circuit for emission and capture deep level transient spectroscopy. <i>Review of Scientific Instruments</i> , 1996, 67, 257-261.	0.6	13
1468	Characterization of traps in GaAs/W Schottky diodes by optical and electrical deep level transient spectroscopy methods. <i>Journal of Applied Physics</i> , 1996, 80, 4389-4394.	1.1	5
1469	Band bending within inhomogeneously doped semiconductors with multilevel impurities. II. Examples. <i>Physical Review B</i> , 1996, 53, 13419-13426.	1.1	1
1470	Direct Determination of the Interaction between Vacancies on InP(110) Surfaces. <i>Physical Review Letters</i> , 1996, 76, 2089-2092.	2.9	64
1471	A modified method of side data analysis of deep level transient spectroscopy spectra. <i>Journal of Applied Physics</i> , 1996, 79, 1468-1475.	1.1	0
1472	Improved linear prediction for deep level transient spectroscopy analysis. <i>Journal of Applied Physics</i> , 1996, 80, 2805-2814.	1.1	1
1473	Isothermal capacitance transient spectroscopy study of deep electron traps in low resistivity m^{t} -grown ZnSe single crystals. <i>Journal of Applied Physics</i> , 1996, 80, 6740-6748.	1.1	7

#	ARTICLE	IF	CITATIONS
1474	Electrical behavior of implanted carbon impurities in fluorine co-implanted GaAs. Journal of Applied Physics, 1996, 80, 3834-3839.	1.1	1
1475	Electrical properties of layer semiconductor GaSe doped with Cu. Journal of Applied Physics, 1996, 80, 4779-4781.	1.1	16
1476	Effect of Ge-related mechanical strain on defect and impurity behaviour in ion-implanted silicon. , 1996, , 262-266.		0
1477	Surface States Due to Fe Atoms Deposited on a TiO ₂ Surface Coated with a Porous SiO ₂ Film. The Journal of Physical Chemistry, 1996, 100, 7106-7113.	2.9	1
1478	Brief Measurement of Diffusion Profiles of Deep Impurities by Moving Schottky Contact. Japanese Journal of Applied Physics, 1996, 35, 3686-3687.	0.8	2
1479	Deep Level Transient Spectroscopy Depth Profile Measurements of Polycrystalline Zinc Oxide Ceramic. Japanese Journal of Applied Physics, 1996, 35, L1158-L1160.	0.8	11
1480	Structural and electrical investigation of implantation damage annealing in CdTe. Semiconductor Science and Technology, 1996, 11, 947-951.	1.0	6
1481	Shift in Threshold Voltage and Schottky Barrier Height of Molybdenum Gate Gallium Arsenide Field Effect Transistors after High Forward Gate Current Test. Japanese Journal of Applied Physics, 1996, 35, L883-L886.	0.8	3
1482	The Dynamics of Thermal Annealing in Arsenic-Ion-Implanted GaAs. Japanese Journal of Applied Physics, 1996, 35, L192-L194.	0.8	1
1483	Identification of deep defects in high-resistivity undoped LEC-GaAs irradiated with protons. Journal Physics D: Applied Physics, 1996, 29, 3101-3105.	1.3	4
1484	Dependence of effective carrier lifetime in iron-doped silicon crystals on the carrier injection level. Semiconductor Science and Technology, 1996, 11, 1713-1717.	1.0	13
1485	Models of deep centres in gallium phosphide. Semiconductor Science and Technology, 1996, 11, 495-501.	1.0	13
1486	Spatial Distributions of Individual Traps in a Si/SiO ₂ Interface. Japanese Journal of Applied Physics, 1997, 36, 1380-1382.	0.8	11
1487	A Simple Graphical Method for Evaluating the Polarization and Relaxation Times of Dipoles or Densities and Energy Levels of Traps in a Dielectric Film from Transient Discharge Current. Japanese Journal of Applied Physics, 1997, 36, 3569-3575.	0.8	5
1488	Electronically Induced Instability of a Hydrogen-Carbon Complex in Silicon and Its Dissociation Mechanism. Japanese Journal of Applied Physics, 1997, 36, 6579-6590.	0.8	21
1489	Electronic Defect Levels in Ultra-Shallow p+n Junctions Formed by Low-Energy B Ion Implantation into Ge-Preamorphized Silicon. Japanese Journal of Applied Physics, 1997, 36, 4346-4350.	0.8	7
1490	Defect Characterization of Sputter Deposited Au Contacts on N-Type Si _{1-x} Ge _x . Japanese Journal of Applied Physics, 1997, 36, 633-637.	0.8	0
1491	Schottky contacts on reactive-ion etched InGaP. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1997, 15, 2016.	1.6	1

#	ARTICLE	IF	CITATIONS
1492	Characterization of the radiation-enhanced diffusion of dry-etch damage in n-GaAs. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1997, 15, 2648.	1.6	1
1493	Photoinduced transient spectroscopy of deep levels in GaAs/Ga _{1-x} Al _x As multiple quantum wells. Journal of Applied Physics, 1997, 82, 4986-4989.	1.1	3
1494	New interpretation of the dominant recombination center in platinum doped silicon. Applied Physics Letters, 1997, 70, 1584-1586.	1.5	16
1495	The resolution limit of traditional correlation functions for deep level transient spectroscopy. Review of Scientific Instruments, 1997, 68, 3861-3865.	0.6	20
1496	Trivalent behavior of palladium in silicon. Applied Physics Letters, 1997, 71, 1379-1381.	1.5	24
1497	Structures and defects in arsenic-ion-implanted GaAs films annealed at high temperatures. Journal of Applied Physics, 1997, 81, 7295-7300.	1.1	5
1498	Single-level interface states in semiconductor structures investigated by admittance spectroscopy. Applied Physics Letters, 1997, 70, 1432-1434.	1.5	7
1499	Differential isothermal capacitance transient spectroscopy for the studies of deep levels in semiconductors. Review of Scientific Instruments, 1997, 68, 2116-2120.	0.6	2
1500	Electrical properties of platinum-hydrogen complexes in silicon. Physical Review B, 1997, 55, 16176-16185.	1.1	68
1501	Investigation of carrier removal in electron irradiated silicon diodes. Journal of Applied Physics, 1997, 82, 3239-3249.	1.1	24
1502	Deep level capture barrier in molecular beam epitaxial grown Al _{1-x} Sb _{1-y} measured by isothermal capacitance transient spectroscopy. Applied Physics Letters, 1997, 71, 506-508.	1.5	4
1503	Deep level transient spectroscopy of CdS/CdTe thin film solar cells. Journal of Applied Physics, 1997, 82, 1423-1426.	1.1	34
1504	Ultrafast excitonic room temperature nonlinearity in neutron irradiated quantum wells. Applied Physics Letters, 1997, 70, 158-160.	1.5	4
1505	Depth profiles of vacancy- and interstitial-type defects in MeV implanted Si. Journal of Applied Physics, 1997, 81, 1639-1644.	1.1	67
1506	Improved methods for investigating boron related defects in 6H-SiC using deep level transient spectroscopy., 1997, , .		0
1507	Conductance DLTS analysis of the correlation between power slump and gate lag. , 0, , .		6
1508	Chapter 6 Photothermal Deep-Level Transient Spectroscopy of Impurities and Defects in Semiconductors. Semiconductors and Semimetals, 1997, , 179-211.	0.4	1
1509	Interface states in In _{0.5} Ga _{0.5} P/Al _x Ga _{1-x} As heterostructures grown by liquid phase epitaxy. Journal of Applied Physics, 1997, 81, 7362-7366.	1.1	8

#	ARTICLE	IF	CITATIONS
1510	Electrically active defects in as-implanted, deep buried layers in p-type silicon. <i>Journal of Applied Physics</i> , 1997, 81, 260-263.	1.1	9
1511	Electronic properties of defects introduced in GaAs during sputter deposition of gold Schottky contacts. <i>Materials Science and Technology</i> , 1997, 13, 945-948.	0.8	7
1512	Study on Deep Level Traps in P-HgCdTe With DLTS. <i>Materials Research Society Symposia Proceedings</i> , 1997, 487, 625.	0.1	0
1513	Electrical Defects of Shallow (P+/N) Junctions Formed by Boron Implantation into Ge-Preamorphized Si-Substrates. <i>Materials Research Society Symposia Proceedings</i> , 1997, 469, 413.	0.1	1
1514	Study on Deep Level Traps in p-HgCdTe With DLTS. <i>Materials Research Society Symposia Proceedings</i> , 1997, 484, 347.	0.1	1
1515	Detection statistics of deep levels in minority carrier transient spectroscopy. <i>Journal of Applied Physics</i> , 1997, 81, 251-259.	1.1	17
1516	Ion-beam annealing of electron traps in n-type Si by post-H ⁺ implantation. <i>Journal of Applied Physics</i> , 1997, 82, 1053-1057.	1.1	3
1517	Electronic states in ZnSe/ZnTe type-II superlattice studied by capacitance transient spectroscopy. <i>Journal of Applied Physics</i> , 1997, 82, 3402-3407.	1.1	4
1518	Photoinduced admittance spectroscopy to detect the shallow electron traps in nitrogen-doped highly compensated ZnSe. <i>Journal of Applied Physics</i> , 1997, 81, 2425-2428.	1.1	6
1519	Generation of vacancy-type point defects in single collision cascades during swift-ion bombardment of silicon. <i>Physical Review B</i> , 1997, 55, 10498-10507.	1.1	92
1520	An improved analysis for the determination of trap levels in silicon from laser microwave photoconductive decay measurements. <i>Applied Physics Letters</i> , 1997, 71, 3218-3220.	1.5	6
1521	Pinning behavior of gold-related levels in Si using Si _{1-x} Ge _x alloy layers. <i>Physical Review B</i> , 1997, 56, 13202-13217.	1.1	22
1522	Electronic defect and trap-related current of (Ba _{0.4} Sr _{0.6})TiO ₃ thin films. <i>Journal of Applied Physics</i> , 1997, 81, 6762-6766.	1.1	97
1523	Metastable hole traps in high-resistivity silicon. <i>Semiconductor Science and Technology</i> , 1997, 12, 284-290.	1.0	0
1524	DLTS investigation of acceptor states in P3MeT Schottky barrier diodes. <i>Synthetic Metals</i> , 1997, 85, 1341-1342.	2.1	11
1525	Optical and electrical properties of metal-diamond-like atomic-scale composite (DLASC) films and DLASC/Si heterostructures. <i>Thin Solid Films</i> , 1997, 292, 91-95.	0.8	11
1526	Effect of deep levels on current excitation in 6H-SiC diodes. <i>Semiconductors</i> , 1997, 31, 1049-1052.	0.2	8
1527	Deep-level transient spectroscopy in InAs/GaAs laser structures with vertically coupled quantum dots. <i>Semiconductors</i> , 1997, 31, 1074-1079.	0.2	30

#	ARTICLE	IF	CITATIONS
1528	Investigation of the parameters of deep centers in n-6HSiC epitaxial layers obtained by gas-phase epitaxy. Semiconductors, 1997, 31, 896-898.	0.2	2
1529	Deep level transient spectroscopy under conditions of current-carrier exchange between two allowed bands. Semiconductors, 1997, 31, 371-374.	0.2	2
1530	Nature of E c $\hat{\sim}$ 0.37 eV centers and the formation of high-resistivity layers in n-type silicon. Semiconductors, 1997, 31, 847-851.	0.2	1
1531	The effect of pulsed magnetic fields on Cz-Si crystals. Journal of Experimental and Theoretical Physics, 1997, 84, 760-773.	0.2	19
1532	Deep-level characterization of p-n junction devices using trigonometric weight functions. IEEE Transactions on Instrumentation and Measurement, 1997, 46, 1156-1159.	2.4	1
1533	Improved lifetime characteristics in heavy ion irradiated silicon. Nuclear Instruments & Methods in Physics Research B, 1997, 127-128, 410-413.	0.6	9
1534	Radioactive isotopes in solid state physics. Nuclear Instruments & Methods in Physics Research B, 1997, 126, 396-405.	0.6	6
1535	Behaviour of radiation defects under the influence of mechanical strain in ion-implanted silicon. Nuclear Instruments & Methods in Physics Research B, 1997, 127-128, 38-42.	0.6	0
1536	Defect levels of proton-irradiated silicon with a dose of 3.6 Å^{-1} – 1013cm $\hat{\sim}$ 2. Nuclear Instruments & Methods in Physics Research B, 1997, 132, 439-446.	0.6	8
1537	Title is missing!. Journal of Materials Science: Materials in Electronics, 1997, 8, 239-245.	1.1	10
1538	Computer controlled microwave transient photoconductivity for the nondestructive characterization of GaAs substrates. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1997, 44, 223-227.	1.7	4
1539	Electrical characteristics of GaN/6H-SiC n-p heterojunctions. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1997, 46, 74-78.	1.7	22
1540	Deep level defects in n- and p-type Fe implanted InP. Physica A: Statistical Mechanics and Its Applications, 1997, 242, 161-165.	1.2	2
1541	Evaluation of silicon diodes made on a variety of high-resistivity phosphorus-doped substrates. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1997, 385, 137-144.	0.7	3
1542	Measurements on a hole trap in neutron-irradiated silicon. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1997, 388, 361-364.	0.7	2
1543	Attempts to correlate hydrogen plasma-induced and Si3N4/GaAs interface-related surface states: a charge deep-level transient spectroscopy study. Applied Surface Science, 1997, 108, 187-196.	3.1	8
1544	Electrical activity and structural configuration of transition metals (Cu, Ni, Fe) in silicon bicrystals. Journal of Materials Science, 1997, 4, 303.	1.2	10
1545	High resolution diffraction and DLTS investigation results of the epitaxial layers produced with the MOCVD method. Vacuum, 1997, 48, 269-271.	1.6	0

#	ARTICLE	IF	CITATIONS
1546	A study of carrier-trap generation by Fowler-Nordheim tunneling stress on polycrystalline-silicon/SiO ₂ /silicon structures. <i>Solid-State Electronics</i> , 1997, 41, 41-46.	0.8	1
1547	Space charge transients of deep level defects characterised by Auger capture. <i>Solid-State Electronics</i> , 1997, 41, 585-590.	0.8	2
1548	Electron irradiation during Schottky gate metal evaporation and its effect on the stability of InGaAs/AlGaAs HEMTs. <i>Solid-State Electronics</i> , 1997, 41, 1457-1461.	0.8	2
1549	Deep Defect Centers in Silicon Carbide Monitored with Deep Level Transient Spectroscopy. <i>Physica Status Solidi A</i> , 1997, 162, 199-225.	1.7	372
1550	Investigation of Radiation Damage in Silicon Produced by Fast Neutron Irradiation with Lifetime Measurements and Deep Level Transient Spectroscopy. <i>Physica Status Solidi A</i> , 1997, 163, 27-32.	1.7	4
1551	Defects in Cu(In, Ga) Se ₂ semiconductors and their role in the device performance of thin-film solar cells. , 1997, 5, 121-130.		69
1552	Deep level transient spectroscopy of synthetic type IIb diamond. <i>Journal of Applied Physics</i> , 1998, 84, 6105-6108.	1.1	23
1553	Current-voltage characteristics of GaN and AlGaIn p-i-n diodes. <i>Semiconductors</i> , 1998, 32, 335-338.	0.2	4
1554	Analysis of capacitance-relaxation signals consisting of several exponentials. <i>Semiconductors</i> , 1998, 32, 617-618.	0.2	1
1555	Kinetics of electric field screening in a space-charge region with a leakage channel and low-temperature conductance of surface channels in high-resistivity n-Si. <i>Semiconductors</i> , 1998, 32, 1277-1283.	0.2	1
1556	On the use of the matrix pencil method for deep level transient spectroscopy: MP-DLTS. <i>IEEE Transactions on Instrumentation and Measurement</i> , 1998, 47, 692-697.	2.4	6
1557	Migration and interaction of point defects at room temperature in crystalline silicon. <i>Rivista Del Nuovo Cimento</i> , 1998, 21, 1-52.	2.0	6
1558	Characterization of phosphorus in layer semiconductor GaSe. <i>Journal of Luminescence</i> , 1998, 79, 79-84.	1.5	11
1559	Ion irradiation induced defects in epitaxial GaAs layers. <i>Solid-State Electronics</i> , 1998, 42, 277-282.	0.8	7
1560	Metal/n-CdTe interfaces: A study of electrical contacts by deep level transient spectroscopy and ballistic electron emission microscopy. <i>Solid-State Electronics</i> , 1998, 42, 595-604.	0.8	23
1561	IMPATT oscillations in fast recovery diodes due to temporarily charged radiation-induced deep levels. <i>Solid-State Electronics</i> , 1998, 42, 931-938.	0.8	26
1562	Recent developments and progress on electrical contacts to CdTe, CdS and ZnSe with special reference to BARRIER contacts to CdTe. <i>Progress in Crystal Growth and Characterization of Materials</i> , 1998, 36, 249-290.	1.8	64
1563	Systematic modelling and comparisons of capacitance and current-based microscopic defect analysis techniques for measurements of high-resistivity silicon detectors after irradiation. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 1998, 403, 399-416.	0.7	31

#	ARTICLE	IF	CITATIONS
1564	Progress on avalanche photodiodes for the CMS electromagnetic calorimeter. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1998, 409, 564-569.	0.7	0
1565	Investigation of radiation defects in n+â€“pâ€“p+ planar silicon neutron detectors. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1998, 412, 387-391.	0.7	0
1566	A study of impurity-free vacancy disordering in GaAs-AlGaAs for improved modeling. IEEE Journal of Selected Topics in Quantum Electronics, 1998, 4, 661-668.	1.9	14
1567	Proximity gettering of platinum in proton irradiated silicon. Journal of Applied Physics, 1998, 84, 4214-4218.	1.1	21
1568	Deep energy levels in CdTe and CdZnTe. Journal of Applied Physics, 1998, 83, 2121-2126.	1.1	274
1569	Chapter 5.2 High-Pressure Study of DX Centers Using Capacitance Techniques. Semiconductors and Semimetals, 1998, 54, 457-484.	0.4	0
1570	Electrical characterization of InP/GaN quantum dots by space charge spectroscopy. Journal of Applied Physics, 1998, 84, 3747-3755.	1.1	58
1571	Explanation for carrier removal and type conversion in irradiated silicon solar cells. Applied Physics Letters, 1998, 72, 1226-1228.	1.5	19
1572	Deposition of SiNx:H thin films by the electron cyclotron resonance and its application to Al/SiNx:H/Si structures. Journal of Applied Physics, 1998, 83, 332-338.	1.1	48
1573	Band-gap states of Ti, V, and Cr in 4H-SiC: Identification and characterization by elemental transmutation of radioactive isotopes. Physical Review B, 1998, 57, 12181-12196.	1.1	55
1574	Diamond-like carbon films deposited using a broad, uniform ion beam from an RF inductively coupled CH4-plasma source. Diamond and Related Materials, 1998, 7, 965-972.	1.8	31
1575	Effects of post-growth treatment and coating with ultrathin metal layers on the band bending and field electron emission of diamond films. Journal of Applied Physics, 1998, 84, 2882-2889.	1.1	54
1576	The effects of annealing on the distributions of deep and shallow states in CdTe single crystals. Journal of Physics Condensed Matter, 1998, 10, 2807-2815.	0.7	2
1577	Characterization of an n-GaAs layer grown on a GaAs substrate cleaned by an electron cyclotron resonance hydrogen plasma. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 216.	1.6	0
1578	Deep-Level Transient Spectroscopy Study of Hydrogen-Related Traps Formed by Wet Chemical Etching in Electron-Irradiated n-Type Silicon. Japanese Journal of Applied Physics, 1998, 37, 1815-1816.	0.8	12
1579	Critical analysis of weighting functions for the deep level transient spectroscopy of semiconductors. Measurement Science and Technology, 1998, 9, 477-484.	1.4	22
1580	Annealing Behavior of Deep Trap Level in p-GaTe. Japanese Journal of Applied Physics, 1998, 37, 3282-3283.	0.8	13
1581	Electronic properties of Si/Si[sub 1â”xâ”y]Ge[sub x]C[sub y] heterojunctions. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 1639.	1.6	6

#	ARTICLE	IF	CITATIONS
1582	Study of shallow donor formation in hydrogen-implanted n-type silicon. <i>Semiconductor Science and Technology</i> , 1998, 13, 194-199.	1.0	21
1583	Application of the singular value decompositionâ€“Prony method for analyzing deep-level transient spectroscopy capacitance transients. <i>Review of Scientific Instruments</i> , 1998, 69, 2459-2463.	0.6	8
1584	Electrical characterization of defects introduced in p-Si $_{1-x}$ Gex during electron-beam deposition of Sc Schottky barrier diodes. <i>Applied Physics Letters</i> , 1998, 72, 1069-1071.	1.5	24
1585	Determination of parameters of deep level defects from numerical fit of deep level transient spectroscopy spectra: Analysis of accuracy and sensitivity to noise. <i>Review of Scientific Instruments</i> , 1998, 69, 244-250.	0.6	5
1586	Laplace-transform deep-level transient spectroscopy studies of the G4 goldâ€“hydrogen complex in silicon. <i>Applied Physics Letters</i> , 1998, 73, 3126-3128.	1.5	31
1587	Averaging and recording of digital deep-level transient spectroscopy transient signals. <i>Review of Scientific Instruments</i> , 1998, 69, 2464-2474.	0.6	9
1588	Kinetics of electron charging and discharging on embedded W disks in GaAs. <i>Physical Review B</i> , 1998, 58, R4207-R4210.	1.1	11
1589	A study of deep centers in Zn $_{1-x}$ MgxSe crystals using deep-level transient spectroscopy. <i>Journal of Applied Physics</i> , 1998, 84, 5345-5347.	1.1	2
1590	Growth mode-related generation of electron traps at the inverted AlAs/GaAs interface. <i>Journal of Applied Physics</i> , 1998, 83, 1496-1498.	1.1	11
1591	Temperature and injection dependence of the Shockleyâ€“Readâ€“Hall lifetime in electron-irradiated p-type silicon. <i>Journal of Applied Physics</i> , 1998, 83, 4206-4212.	1.1	17
1592	Electrical characterization of two deep electron traps introduced in epitaxially grown n-GaN during He-ion irradiation. <i>Applied Physics Letters</i> , 1998, 73, 3745-3747.	1.5	101
1593	Bistable behavior of a medium-deep center related to EL5 and EL6 in n-type bulk GaAs. <i>Journal of Applied Physics</i> , 1998, 84, 3167-3174.	1.1	21
1594	Electrical properties of extremely low doped GaSb Schottky diodes. <i>Journal of Applied Physics</i> , 1998, 84, 1426-1429.	1.1	8
1595	Two signals in electrically detected magnetic resonance of platinum-doped silicon pâ€“n junctions. <i>Journal of Applied Physics</i> , 1998, 84, 2193-2198.	1.1	4
1596	Observation of near-surface electrically active defects in n-type 6Hâ€“SiC. <i>Journal of Applied Physics</i> , 1998, 83, 3649-3651.	1.1	1
1597	Effect of ammonia flow rate on impurity incorporation and material properties of Si-doped GaN epitaxial films grown by reactive molecular beam epitaxy. <i>Journal of Applied Physics</i> , 1998, 84, 6680-6685.	1.1	21
1598	Constant-resistance deep-level transient spectroscopy in submicron metal-oxide-semiconductor field-effect transistors. <i>Journal of Applied Physics</i> , 1998, 83, 820-825.	1.1	15
1599	Deep and shallow electronic states at ultrathin InAs insertions in GaAs investigated by capacitance spectroscopy. <i>Journal of Applied Physics</i> , 1998, 84, 6135-6140.	1.1	28

#	ARTICLE	IF	CITATIONS
1600	Near interface oxide trap capture kinetics in metal-oxide-semiconductor transistors: Modeling and measurements. <i>Journal of Applied Physics</i> , 1998, 84, 6178-6186.	1.1	16
1601	Below-Gap Spectroscopy of Undoped GaAs/AlGaAs Quantum Wells by Two-Wavelength Excited Photoluminescence. <i>Japanese Journal of Applied Physics</i> , 1998, 37, 3210-3213.	0.8	10
1602	Investigation of epitaxial silicon layers as a material for radiation hardened silicon detectors. <i>IEEE Transactions on Nuclear Science</i> , 1998, 45, 585-590.	1.2	11
1603	Study of Deep Levels in Mesa-Type HgCdTe Device. <i>Japanese Journal of Applied Physics</i> , 1998, 37, 4027-4031.	0.8	4
1604	Studies of Deep Levels in HgCdTe Grown on CdZnTe and Si Substrates. <i>Japanese Journal of Applied Physics</i> , 1998, 37, 4032-4036.	0.8	6
1605	Photovoltaics characterization: A survey of diagnostic measurements. <i>Journal of Materials Research</i> , 1998, 13, 2684-2708.	1.2	15
1606	Development of Computer Controlled Deep Level Transient Spectroscopy System. <i>IETE Technical Review (Institution of Electronics and Telecommunication Engineers, India)</i> , 1998, 15, 105-110.	2.1	0
1607	Electronic Properties and Deep Levels in Germanium-Silicon. <i>Semiconductors and Semimetals</i> , 1998, 56, 293-346.	0.4	5
1608	The residual electrically active damage in low energy boron implanted silicon: rapid thermal annealing and implant mass effects. <i>EPJ Applied Physics</i> , 1998, 3, 49-52.	0.3	3
1609	Electrical Characterization of Sputter Deposition Induced Defects in n-GaN. <i>Materials Research Society Symposia Proceedings</i> , 1998, 537, 1.	0.1	0
1610	Electrical Properties of Transition Metal Hydrogen Complexes in Silicon. <i>Materials Research Society Symposia Proceedings</i> , 1998, 513, 345.	0.1	6
1611	Formation of Hydrogen-Related Traps in Electron-Irradiated N-type Silicon by Wet Chemical Etching. <i>Materials Research Society Symposia Proceedings</i> , 1998, 513, 363.	0.1	2
1612	Effects of CF ₄ Reactive ion Etching on Si-Doped Al _{0.2} Ga _{0.8} As. <i>Materials Research Society Symposia Proceedings</i> , 1998, 535, 243.	0.1	0
1613	Surface Phenomena of the Thin Diamond-Like Carbon Films. <i>Materials Research Society Symposia Proceedings</i> , 1998, 555, 345.	0.1	5
1614	Contactless transient spectroscopy for the measurement of localized states in semiconductors. , 1998, , .		2
1615	Electrical Characterization of Sputter Deposition Induced Defects in n-GaN. <i>MRS Internet Journal of Nitride Semiconductor Research</i> , 1999, 4, 612-617.	1.0	1
1616	Shallow level analysis in irradiated silicon. , 0, , .		0
1617	Chapter 2 Defect Identification Using Capacitance Spectroscopy. <i>Semiconductors and Semimetals</i> , 1999, , 93-152.	0.4	12

#	ARTICLE	IF	CITATIONS
1618	Characterization of InGaAs Phosphidized by a Plasma Process. Japanese Journal of Applied Physics, 1999, 38, 1139-1142.	0.8	1
1619	Effects of Impurity between Epitaxial Layer and Substrate on Current Transient for GaAs Metal-Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 1999, 38, 22-25.	0.8	2
1620	Annealing and Hydrogenation Behaviors of Electron-Beam Induced Defects in n-type Si. Japanese Journal of Applied Physics, 1999, 38, 4047-4048.	0.8	3
1621	Mechanical strain and electrically active defects in Si implanted with Ge ⁺ ions. Semiconductor Science and Technology, 1999, 14, 565-569.	1.0	3
1622	Deep levels in low temperature GaAs probed by field effect deep level transient spectroscopy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 60.	1.6	5
1623	Effect of rapid thermal annealing on radio-frequency magnetron-sputtered GaN thin films and Au/GaN Schottky diodes. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 1545.	1.6	8
1624	Evaluation of Interface States in ZnO Varistors by Spectral Analysis of Deep Level Transient Spectroscopy. Japanese Journal of Applied Physics, 1999, 38, 899-900.	0.8	22
1625	Stability of proximity gettering of platinum in silicon implanted with alpha particles at low doses. Applied Physics Letters, 1999, 75, 364-366.	1.5	6
1626	Field-enhanced emission rate and electronic properties of a defect introduced in n-GaN by 5.4 MeV He-ion irradiation. Applied Physics Letters, 1999, 74, 809-811.	1.5	25
1627	Theory of transient spectroscopy of multiple quantum well structures. Journal of Applied Physics, 1999, 86, 1510-1513.	1.1	2
1628	Analysis of deep levels in a phenylenevinylene polymer by transient capacitance methods. Applied Physics Letters, 1999, 74, 1144-1146.	1.5	44
1629	Light-illumination-induced transformation of electron traps in hydrogen-implanted n-type silicon. Journal of Applied Physics, 1999, 86, 5630-5635.	1.1	17
1630	Capacitance transient spectroscopy in metal-insulator-metal systems and its application to the determination of trap parameters in polyimide films. Journal of Applied Physics, 1999, 85, 1089-1094.	1.1	15
1631	Effect of temperature errors on accuracy of deep traps parameters obtained from transient measurements. Review of Scientific Instruments, 1999, 70, 3425-3428.	0.6	2
1632	The influence of diffusion temperature and ion dose on proximity gettering of platinum in silicon implanted with alpha particles at low doses. Applied Physics Letters, 1999, 74, 3329-3331.	1.5	19
1633	A system for radiation damage monitoring. IEEE Transactions on Nuclear Science, 1999, 46, 1766-1773.	1.2	10
1634	2 MeV electron irradiation of silicon at elevated temperatures: Influence on platinum diffusion and creation of electrically active defects. Journal of Applied Physics, 1999, 85, 3556-3560.	1.1	10
1635	Deep trap in InGaAs grown by gas source molecular beam epitaxy. Journal of Applied Physics, 1999, 85, 633-634.	1.1	8

#	ARTICLE	IF	CITATIONS
1636	A Dopant-Related Defect in Te-Doped AlInP. Japanese Journal of Applied Physics, 1999, 38, 4720-4721.	0.8	5
1637	Mg-related Deep Levels in AlInP. Japanese Journal of Applied Physics, 1999, 38, 4049-4050.	0.8	4
1638	Exploring solid state physics properties with radioactive isotopes. Reports on Progress in Physics, 1999, 62, 527-597.	8.1	26
1639	Thermoelectric voltage spectroscopy for studying compensation in semi-insulating wide energy band gap materials. Solid State Communications, 1999, 112, 31-34.	0.9	3
1640	Fast detrapping and extraction of holes in Al _{0.25} Ga _{0.75} As/GaAs structures. Solid-State Electronics, 1999, 43, 993-995.	0.8	0
1641	A new determination of minority carrier generation characteristics in a MOS channelâ€”CCD process by DLTS. Solid-State Electronics, 1999, 43, 1225-1230.	0.8	2
1642	Defect introduction in epitaxially grown n-GaN during electron beam deposition of Ru schottky contacts. Physica B: Condensed Matter, 1999, 273-274, 84-87.	1.3	25
1643	Metastable-like behaviour of a sputter deposition-induced electron trap in n-GaN. Physica B: Condensed Matter, 1999, 273-274, 92-95.	1.3	18
1644	Hydrogenation and passivation of electron-beam-induced defects in N-type Si. Physica B: Condensed Matter, 1999, 273-274, 228-230.	1.3	4
1645	Deep-level defects near the surface of Be-doped GaAs grown by molecular beam epitaxy. Physica B: Condensed Matter, 1999, 273-274, 693-696.	1.3	3
1646	Similarities in the electrical properties of transition metalâ€”hydrogen complexes in silicon. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 58, 134-140.	1.7	44
1647	Enhanced diffusion of platinum in electron-irradiated silicon. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 57, 161-164.	1.7	8
1648	Deep level defects in H ⁺ implanted 6Hâ€”SiC epilayers and in silicon carbide on insulator structures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 61-62, 382-388.	1.7	10
1649	Thermal behavior of the KSbMoO ₆ ionic conductive ceramic. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 63, 234-237.	1.7	2
1650	Characterisation of deep level trap centres in 6H-SiC p-n junction diodes. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 66, 106-110.	1.7	3
1651	The evolution of interstitial-type defects in silicon during platinum diffusion from 400 to 600Â°C following 2-MeV electron irradiation. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 68, 67-71.	1.7	0
1652	Nano-scale properties of defects in compound semiconductor surfaces. Surface Science Reports, 1999, 33, 121-303.	3.8	165
1653	A two-level model for heavily irradiated silicon detectors. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1999, 425, 343-346.	0.7	14

#	ARTICLE	IF	CITATIONS
1654	New experimental and analysis methods in I-DLTS. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1999, 426, 109-113.	0.7	11
1655	Capacitance spectroscopy of deep states in InAs/GaAs quantum dot heterostructures. Semiconductors, 1999, 33, 157-164.	0.2	16
1656	Deep-level transient spectroscopy of radiation-induced levels in 6H-SiC. Semiconductors, 1999, 33, 1188-1192.	0.2	15
1657	Substrate misorientation effects on Zn _{1-x} Mg _x Se layers grown on GaAs(111) by molecular beam epitaxy. Journal of Crystal Growth, 1999, 203, 355-361.	0.7	0
1658	Radiotracer spectroscopy of deep levels in the semiconductor band gap. , 1999, 120/121, 69-79.		6
1659	ICTS Measurements of Single Grain Boundaries in ZnO:rare-earth Varistor. , 1999, 4, 55-59.		15
1660	Metastable population of self-organized InAs/GaAs quantum dots. Journal of Electronic Materials, 1999, 28, 491-495.	1.0	21
1661	Constant-resistance deep-level transient spectroscopy in Si and Ge JFET's. IEEE Transactions on Electron Devices, 1999, 46, 204-213.	1.6	8
1662	Dynamics of incomplete ionized dopants and their impact on 4H/6H-SiC devices. IEEE Transactions on Electron Devices, 1999, 46, 598-604.	1.6	33
1663	Residual defects in Cz-silicon after low dose self-implantation and annealing from 400°C to 800°C. Nuclear Instruments & Methods in Physics Research B, 1999, 147, 106-110.	0.6	4
1664	Low temperature proximity gettering of platinum in proton irradiated silicon via interstitial cluster dissociation. Nuclear Instruments & Methods in Physics Research B, 1999, 147, 127-131.	0.6	8
1665	Measuring the generation lifetime profile modified by MeV H ⁺ ion implantation in silicon. Nuclear Instruments & Methods in Physics Research B, 1999, 147, 111-115.	0.6	5
1666	Anomalous field dependence of deep level emission in proton irradiated silicon. Nuclear Instruments & Methods in Physics Research B, 1999, 147, 427-431.	0.6	3
1667	Emission kinetics of electron traps introduced in n-GaN during He-ion irradiation. Nuclear Instruments & Methods in Physics Research B, 1999, 148, 474-477.	0.6	7
1668	Damage induced in semiconductors by swift heavy ion irradiation. Nuclear Instruments & Methods in Physics Research B, 1999, 156, 64-71.	0.6	58
1669	Study on the evolution and nature of interstitial-type defects following proton and alpha particle implantation during low-dose proximity gettering of platinum. Nuclear Instruments & Methods in Physics Research B, 1999, 155, 60-66.	0.6	6
1670	How to Distinguish between Discrete and Distributed Charge Relaxations in Charge Transient Spectroscopy. Physica Status Solidi A, 1999, 172, 519-528.	1.7	4
1671	CV and DLTS Experiments in Boron-Doped Diamond. Physica Status Solidi A, 1999, 174, 117-127.	1.7	13

#	ARTICLE	IF	CITATIONS
1672	Sputter deposition-induced electron traps in epitaxially grown n-GaN. Applied Physics Letters, 1999, 74, 2173-2175.	1.5	48
1673	Proton bombardment-induced electron traps in epitaxially grown n-GaN. Applied Physics Letters, 1999, 74, 407-409.	1.5	92
1674	Photocapacitance study of boron-doped chemical-vapor-deposited diamond. Physical Review B, 1999, 60, 2476-2479.	1.1	17
1675	Electron escape from InAs quantum dots. Physical Review B, 1999, 60, 14265-14268.	1.1	146
1676	Defect energy levels in electron-irradiated and deuterium-implanted 6H silicon carbide. Physical Review B, 1999, 59, 10823-10829.	1.1	73
1677	Majority- and minority-carrier traps in Te-doped AlInP. Applied Physics Letters, 1999, 74, 284-286.	1.5	8
1678	Photoinduced current transient spectroscopy of deep defects in n-type ultrapure germanium. Journal of Applied Physics, 1999, 86, 940-945.	1.1	13
1679	Photocurrents in P3MeT Schottky barrier diodes. Synthetic Metals, 1999, 101, 431-432.	2.1	3
1680	Development and Applications of a New Deep Level Transient Spectroscopy Method and New Averaging Techniques. Advances in Imaging and Electron Physics, 1999, 109, 1-161.	0.1	2
1683	Metastable behavior of current-voltage characteristics in Hg _{1-x} Cd _x Te p-n junctions. , 2000, , .		1
1684	Ion-implanted silicon detectors of nuclear radiation. , 0, , .		0
1685	Deep level transient spectroscopy characterization of porous GaP layers. , 0, , .		0
1686	Characterization of deep levels in Si-MOS structure using ICTS measurement. Electrical Engineering in Japan (English Translation of Denki Gakkai Ronbunshi), 2000, 130, 76-86.	0.2	2
1687	Photocurrent Transients in Presence of a Double Impurity in Semi-Insulating Semiconductors. Physica Status Solidi A, 2000, 178, 755-763.	1.7	0
1688	Characterization of Ga _{0.52} In _{0.48} P/GaAs single quantum well structures grown by solid source molecular beam epitaxy using deep level transient spectroscopy. Journal of Crystal Growth, 2000, 212, 49-55.	0.7	2
1689	Effect of deep levels on the characteristics of InGa _{1-x} P/In _{0.20} Ga _{0.80} As/GaAs high-electron mobility transistor grown by solid-source MBE. Journal of Crystal Growth, 2000, 217, 33-39.	0.7	2
1690	Deep levels in Sb-doped ZnSe fabricated by metalorganic vapor-phase epitaxy. Journal of Crystal Growth, 2000, 221, 398-403.	0.7	4
1691	Laplace defect spectroscopy for recognition of deep-level fine structures. Journal of Crystal Growth, 2000, 210, 247-250.	0.7	5

#	ARTICLE	IF	CITATIONS
1692	Characterization of metastable hydrogen-related defects in n-GaAs by isothermal constant-capacitance voltage transient spectroscopy. <i>Journal of Crystal Growth</i> , 2000, 210, 260-263.	0.7	3
1693	Effects of an inhomogeneous carrier concentration depth profile on deep-level transient spectroscopy measurements. <i>Journal of Crystal Growth</i> , 2000, 210, 384-387.	0.7	4
1694	Deep level effects on the characteristics of Al _{0.24} Ga _{0.76} As/In _{0.20} Ga _{0.80} As/GaAs and In _{0.48} Ga _{0.52} P/In _{0.20} Ga _{0.80} As/GaAs high electron mobility transistors grown by solid source molecular beam epitaxy. <i>Solid-State Electronics</i> , 2000, 44, 1909-1916.	0.8	1
1695	Effects of thin oxide in metal-semiconductor and metal-insulator-semiconductor epi-GaAs Schottky diodes. <i>Solid-State Electronics</i> , 2000, 44, 1089-1097.	0.8	139
1696	Deep traps in CdTe induced by ion implantation and annealing. <i>Journal of Physics and Chemistry of Solids</i> , 2000, 61, 1839-1846.	1.9	4
1697	Study of thin gate dielectric films using deep level transient spectroscopy. <i>Microelectronics Journal</i> , 2000, 31, 451-458.	1.1	4
1698	Annihilation and formation of electron traps in hydrogen-implanted n-type silicon by light illumination. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2000, 71, 1-5.	1.7	4
1699	Metallisation induced electron traps in epitaxially grown n-type GaN. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2000, 71, 77-81.	1.7	10
1700	Microscopic characterization of defects using scanning tunneling microscopy. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2000, 71, 120-127.	1.7	9
1701	Proximity gettering of platinum in silicon following implantation with alpha particles at low doses. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2000, 71, 182-185.	1.7	0
1702	Carrier emission processes in InAs quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000, 7, 388-392.	1.3	5
1703	Transient capacitance measurements of the transport and trap states distributions in a conjugated polymer. <i>Organic Electronics</i> , 2000, 1, 21-26.	1.4	34
1704	Experimental evidence of deep electron and hole trapping levels in high fluence proton irradiated p-n Si junctions using optical charging spectroscopy. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2000, 439, 221-227.	0.7	5
1705	Carrier profiles and electron traps at a growth-interrupted layer in GaAs fabricated by a focused ion beam and molecular beam epitaxy combined system. <i>Applied Surface Science</i> , 2000, 159-160, 277-281.	3.1	4
1706	Electronic characterization of single grain boundary in ZnO:Pr varistors. <i>Ceramics International</i> , 2000, 26, 645-650.	2.3	10
1707	Thermal annealing of defects in InGaAs/GaAs heterostructures with three-dimensional islands. <i>Semiconductors</i> , 2000, 34, 195-204.	0.2	20
1708	Deep-level centers in undoped p-GaAs layers grown by liquid phase epitaxy. <i>Semiconductors</i> , 2000, 34, 541-544.	0.2	7
1709	Band offsets in Zn _{1-x} Cd _x Te/ZnTe single-quantum-well structures grown by molecular-beam epitaxy on GaAs(001) substrates. <i>Semiconductors</i> , 2000, 34, 960-964.	0.2	6

#	ARTICLE	IF	CITATIONS
1710	Very slow charge trapping and release in ion implanted GaAs [MESFETs]. IEEE Transactions on Electron Devices, 2000, 47, 512-516.	1.6	1
1711	The effect of InAs quantum layer and quantum dots on the electrical characteristics of GaAs structures. Microelectronic Engineering, 2000, 51-52, 85-92.	1.1	14
1712	Band alignment in ZnCdTe/ZnTe and ZnCdSe/ZnSe SQW structures grown on GaAs(100) by MBE. Nanotechnology, 2000, 11, 241-245.	1.3	9
1713	High-temperature hysteretic electronic effects of $(\text{Al}_x\text{Ga}_{1-x})_{0.5}\text{In}_{0.5}\text{P}$ ($x>0.65$). Journal of Electronic Materials, 2000, 29, 231-236.	1.0	0
1714	Nature of the effect of an increase in the charge-carrier lifetime for irradiated n-Si<P, Rh>. Russian Physics Journal, 2000, 43, 527-530.	0.2	0
1715	Phosphorus Vacancy as a Deep Level in AlInP Layers. Japanese Journal of Applied Physics, 2000, 39, L567-L568.	0.8	3
1716	The radiation-induced defects production in P-type silicon doped by impurities of transitional elements. Radiation Effects and Defects in Solids, 2000, 152, 171-180.	0.4	1
1717	Interaction of hydrogen with the vacancy-oxygen pair produced in n-type silicon by electron irradiation. Semiconductor Science and Technology, 2000, 15, 126-129.	1.0	17
1718	Experimental evidence for complementary spatial sensitivities of capacitance and charge deep-level transient spectroscopies. Semiconductor Science and Technology, 2000, 15, 378-385.	1.0	5
1719	Unusual features in trap emission characteristics of heavily damaged silicon induced by MeV ion implantation. Semiconductor Science and Technology, 2000, 15, 985-991.	1.0	8
1720	Deep levels and irradiation effects in n-GaN. Journal of Physics Condensed Matter, 2000, 12, 10161-10167.	0.7	28
1721	Ferroelectricity and electronic defect characteristics of c-oriented Sr _{0.25} Ba _{0.75} Nb ₂ O ₆ thin films deposited on Si substrates. Applied Physics Letters, 2000, 76, 3472-3474.	1.5	25
1722	Electrical and structural properties of nanoscale NiSi ₂ precipitates in silicon. Physical Review B, 2000, 62, 7150-7156.	1.1	55
1723	Capacitance transient spectroscopy models of coupled trapping kinetics among multiple defect states: Application to the study of trapping kinetics of defects in heavy-ion-damaged silicon. Physical Review B, 2000, 62, 2496-2504.	1.1	8
1724	DLTS and capacitance transients study of defects induced by neutron irradiation in MOS structures CCD process. , 0, , .		1
1725	Conduction-band offset of single InAs monolayers on GaAs. Applied Physics Letters, 2000, 76, 1146-1148.	1.5	24
1726	A deep level transient spectroscopy study of beryllium implanted n-type 6H-SiC. Journal of Applied Physics, 2000, 88, 4558.	1.1	11
1727	Tungsten in silicon carbide: Band-gap states and their polytype dependence. Physical Review B, 2000, 62, 12888-12895.	1.1	23

#	ARTICLE	IF	CITATIONS
1728	Effect of fill-pulse parameters on deep-level transient spectroscopy peaks in highly doped p-type InP. Journal of Applied Physics, 2000, 88, 794-799.	1.1	37
1729	Lifetime of excess electron-hole pairs measured with white noise performance of the photocurrent. Journal of Applied Physics, 2000, 87, 1836-1840.	1.1	2
1730	Study of electron, proton, and swift heavy ion irradiation of n-type germanium using deep level transient spectroscopy. Journal of Applied Physics, 2000, 88, 3082-3084.	1.1	10
1731	Theory of scanning tunneling microscopy of defects on semiconductor surfaces. Physical Review B, 2000, 61, 2138-2145.	1.1	30
1732	Effects of gamma-ray irradiation on the microstructural and luminescent properties of radio-frequency magnetron-sputtered GaN thin films. Journal of Applied Physics, 2000, 88, 6355-6358.	1.1	30
1733	Deep-level transient spectroscopy of Pd-H complexes in silicon. Physical Review B, 2000, 61, 1924-1934.	1.1	17
1734	Investigation of deep levels in CdTe/CdS solar cells. , 0, , .		2
1735	Electronic levels in MEH-PPV. Synthetic Metals, 2000, 111-112, 535-537.	2.1	25
1736	Deep level transient spectroscopy (DLTS) of a poly(p-phenylene vinylene) Schottky diode. Synthetic Metals, 2000, 111-112, 273-276.	2.1	43
1737	Observation of a band of fast responding metastable deep traps for charge carriers in crystalline Si(n)/SiNx:H/amorphous Si:H/Al structures. Journal of Non-Crystalline Solids, 2000, 277, 207-218.	1.5	1
1738	Evidence of an oxygen recombination center in p+ n GaInNAs solar cells. Applied Physics Letters, 2000, 76, 2397-2399.	1.5	28
1739	Electronic properties of CuGaSe2-based heterojunction solar cells. Part II. Defect spectroscopy. Journal of Applied Physics, 2000, 87, 594-602.	1.1	96
1740	Deep level transient capacitance measurements of GaSb self-assembled quantum dots. Journal of Applied Physics, 2000, 88, 5843-5849.	1.1	35
1741	Activation energies of the EL6 trap and of the 0.15 eV donor and their correlation in GaAs. Semiconductor Science and Technology, 2000, 15, 1039-1044.	1.0	4
1742	The field-assisted emission effect on the acceptor energy of GaN:Mg in admittance spectroscopy measurements. Journal of Applied Physics, 2000, 88, 1929-1934.	1.1	8
1743	Properties of metastable hydrogen-related defects in n-type GaAs studied by isothermal deep-level transient spectroscopy. Journal of Applied Physics, 2000, 88, 1943-1947.	1.1	12
1744	Defects density distribution of AlN films produced by RF sputtering in argon-nitrogen-hydrogen mixture. , 0, , .		0
1745	Shallow level analysis in irradiated silicon. IEEE Transactions on Nuclear Science, 2000, 47, 1474-1477.	1.2	2

#	ARTICLE	IF	CITATIONS
1746	Effects of O/sub 2/ rapid thermal annealing on the microstructural properties and reliability of RF-sputtered Ta/sub 2/O/sub 5/ films. IEEE Transactions on Dielectrics and Electrical Insulation, 2000, 7, 316-321.	1.8	2
1747	Hole and electron emission from InAs quantum dots. Applied Physics Letters, 2000, 76, 1573-1575.	1.5	110
1748	Many-particle effects in Ge quantum dots investigated by time-resolved capacitance spectroscopy. Applied Physics Letters, 2000, 77, 4169-4171.	1.5	47
1749	Deep-level impurities in CdTe/CdS thin-film solar cells. Journal of Applied Physics, 2000, 88, 7175-7178.	1.1	148
1750	Space charge spectroscopy of diamond. Diamond and Related Materials, 2001, 10, 639-644.	1.8	5
1751	Charge deep-level transient spectroscopy of Al/intrinsic diamond/p+-Si Schottky diodes. Semiconductor Science and Technology, 2001, 16, 527-533.	1.0	8
1752	Electrical properties of thick boron and nitrogen contained CVD diamond films. Diamond and Related Materials, 2001, 10, 593-600.	1.8	35
1753	Radiation damage in silicon detectors for high-energy physics experiments. IEEE Transactions on Nuclear Science, 2001, 48, 960-971.	1.2	77
1754	Determination of traps in poly(p-phenylene vinylene) light emitting diodes by charge-based deep level transient spectroscopy. Journal of Applied Physics, 2001, 90, 4196-4204.	1.1	35
1755	Millisecond phosphorescence of free electrons in pure GaAs. Applied Physics Letters, 2001, 79, 3455-3457.	1.5	13
1756	Tunneling carrier escape from InAs self-assembled quantum dots. Applied Physics Letters, 2001, 79, 2013-2015.	1.5	19
1757	Characterization of near-surface traps in semiconductors: GaN. Applied Physics Letters, 2001, 79, 84-86.	1.5	36
1758	Variable-temperature scanning capacitance microscopy: A way to probe charge traps in oxide or semiconductor. Applied Physics Letters, 2001, 78, 613-615.	1.5	11
1759	Deep levels in ion implanted field effect transistors on SiC. , 0, , .		0
1760	Charging of embedded InAs self-assembled quantum dots by space-charge techniques. Physical Review B, 2001, 64, .	1.1	44
1761	A comparison of deep level effects on the DC characteristics of In/sub x/Ga/sub 1-x/P/In/sub 0.20/Ga/sub 0.80/As/GaAs and Al/sub 0.24/Ga/sub 0.76/As/In/sub 0.20/Ga/sub 0.80/As/GaAs high electron mobility transistors grown by solid source MBE. , 0, , .		0
1762	Molecular Beam Epitaxy. , 2001, , 381-461.		3
1763	Electrical Properties of n-GaN/p-SiC and n-AlGaIn/p-SiC Heterojunction Diodes. Materials Research Society Symposia Proceedings, 2001, 693, 132.	0.1	0

#	ARTICLE	IF	CITATIONS
1764	Electrical Properties of n-GaN/p-SiC and n-AlGaIn/p-SiC Heterojunction Diodes. Materials Research Society Symposia Proceedings, 2001, 693, 57.	0.1	0
1765	Deep Centers and Their Capture Barriers in MOCVD-Grown GaN. Materials Research Society Symposia Proceedings, 2001, 692, 1.	0.1	6
1766	Charge-Based Deep Level Transient Spectroscopy of Semiconducting and Insulating Materials. Materials Research Society Symposia Proceedings, 2001, 699, 341.	0.1	0
1767	Electrical characterization of growth-induced defects in n-GaN. Radiation Effects and Defects in Solids, 2001, 156, 255-259.	0.4	4
1768	Defect creation kinetics in swift heavy ions, protons and electrons irradiated germanium. EPJ Applied Physics, 2001, 13, 89-96.	0.3	7
1769	Influence of carrier freeze-out on SiC Schottky junction admittance. Journal of Electronic Materials, 2001, 30, 235-241.	1.0	14
1770	Deep-level transient spectroscopy (DLTS) of CdS/CuIn _{1-x} Ga _x Se ₂ -based solar cells prepared from electroplated and auto-plated precursors, and by physical vapor deposition. Thin Solid Films, 2001, 384, 65-68.	0.8	13
1771	The use of hydrogen passivation to fabricate Schottky diodes for DLTS measurements of heavily-doped p+ Si. Materials Science in Semiconductor Processing, 2001, 4, 167-169.	1.9	2
1772	High-temperature spreading-resistance profiling for the characterization of impurity distributions in n-type silicon. Materials Science in Semiconductor Processing, 2001, 4, 67-70.	1.9	1
1773	Electrically active centers in light emitting Si:Er/Si structures grown by the sublimation MBE method. Physica B: Condensed Matter, 2001, 308-310, 361-364.	1.3	2
1774	Study of depth distribution of metastable hydrogen-related defects in n-type GaAs. Physica B: Condensed Matter, 2001, 308-310, 827-830.	1.3	4
1775	High resolution minority carrier transient spectroscopy of defects in Si and Si/SiGe quantum wells. Physica B: Condensed Matter, 2001, 308-310, 554-557.	1.3	6
1776	Space charge spectroscopy of integrated quantum well infrared photodetector—light emitting diode. Infrared Physics and Technology, 2001, 42, 259-265.	1.3	7
1777	Cadmium zinc telluride and its use as a nuclear radiation detector material. Materials Science and Engineering Reports, 2001, 32, 103-189.	14.8	792
1778	Hole Emission from Ge/Si Quantum Dots Studied by Time-Resolved Capacitance Spectroscopy. Physica Status Solidi (B): Basic Research, 2001, 224, 261-264.	0.7	3
1779	Defect Levels in n-Type Gallium Arsenide and Gallium Aluminum Arsenide Layers. Physica Status Solidi A, 2001, 183, 281-297.	1.7	4
1780	Electron traps and growth rate of buffer layers in unintentionally doped GaN. Journal of Crystal Growth, 2001, 223, 38-42.	0.7	68
1781	Deep level effects on the characteristics of Al _{0.25} Ga _{0.75} As/In _{0.20} Ga _{0.80} As/GaAs high electron mobility transistors grown by solid source MBE. Journal of Crystal Growth, 2001, 233, 150-160.	0.7	0

#	ARTICLE	IF	CITATIONS
1782	Title is missing!. Russian Physics Journal, 2001, 44, 734-737.	0.2	1
1783	Observation of minority-carrier traps in Schottky diodes with a high barrier and a compensated near-contact region using deep-level transient spectroscopy. Semiconductors, 2001, 35, 48-53.	0.2	1
1784	Hydrogen-related defect centers in float-zone and epitaxial n-type proton implanted silicon. Nuclear Instruments & Methods in Physics Research B, 2001, 174, 297-303.	0.6	31
1785	New regularization algorithm for DLTS data analysis in amorphous and polycrystalline insulators and semiconductors. Radiation Effects and Defects in Solids, 2001, 154, 261-265.	0.4	10
1786	Gamma-Ray Induced Deep Electron Traps in GaInP. Japanese Journal of Applied Physics, 2001, 40, 5306-5307.	0.8	1
1787	Anomalous Charge Transport and Polarization in Semiconductors Oxides and Porous Film Electrodes. , 2001, , 727-791.		1
1788	Distributions of Interface States and Bulk Traps in ZnO Varistors. Japanese Journal of Applied Physics, 2001, 40, 213-219.	0.8	30
1789	THERMAL OXIDATION OF SILICON AND Si-SiO ₂ INTERFACE MORPHOLOGY, STRUCTURE AND LOCALIZED STATES. , 2001, , 115-216.		9
1790	<title>GaN deep-level capture barriers</title>. , 2001, 4288, 209.		1
1791	Surface states on n-type Al _{0.24} Ga _{0.76} As characterized by deep-level transient spectroscopy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 615.	1.6	9
1792	Deep Hole Traps Created by Gamma-Ray Irradiation of GaInP. Japanese Journal of Applied Physics, 2001, 40, 6807-6808.	0.8	1
1793	Pinning Effect by Interface States in Pr-type ZnO Varistors. Japanese Journal of Applied Physics, 2001, 40, 5985-5989.	0.8	0
1794	Molecular beam epitaxy growth and characterization of ZnTe:Cr ²⁺ layers on GaAs(100). Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 1483.	1.6	4
1795	Title is missing!. Journal of Physics Condensed Matter, 2001, 13, 8989-8999.	0.7	47
1796	Thermal-Treatment Induced Deep Electron Traps in AlInP. Japanese Journal of Applied Physics, 2001, 40, 4864-4865.	0.8	1
1797	Deep-Level Transient Spectroscopy Detection of Iron in Hydrogenated p+ Silicon. Japanese Journal of Applied Physics, 2001, 40, L533-L535.	0.8	1
1798	Deep Level Transient Spectroscopy Analysis of an Anatase Epitaxial Film Grown by Metal Organic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2001, 40, L404-L406.	0.8	18
1799	Pseudodonor nature of the DI defect in 4H-SiC. Applied Physics Letters, 2001, 78, 46-48.	1.5	88

#	ARTICLE	IF	CITATIONS
1800	Back-channel-type scanning charge pumping method for characterization of interface traps in silicon-on-insulator wafer. Applied Physics Letters, 2001, 79, 1825-1827.	1.5	5
1801	Estimating the model parameters of deep-level transient spectroscopy data using a combined wavelet/singular value decomposition Prony method. Review of Scientific Instruments, 2001, 72, 1800.	0.6	5
1802	Interesting trends in direct current electrical conductivity of chemical vapor deposited diamond sheets. Journal of Applied Physics, 2001, 90, 1642-1649.	1.1	2
1803	Minority-carrier effects in poly-phenylenevinylene as studied by electrical characterization. Journal of Applied Physics, 2001, 89, 1713.	1.1	22
1804	Separation of vacancy and interstitial depth profiles in ion-implanted silicon: Experimental observation. Applied Physics Letters, 2001, 78, 3442-3444.	1.5	32
1805	Deep levels of tantalum in silicon carbide and incorporation during crystal growth. Applied Physics Letters, 2001, 79, 2405-2407.	1.5	4
1806	Origin and annealing of deep-level defects in p-type GaAs/Ga(As,N)/GaAs heterostructures grown by molecular beam epitaxy. Journal of Applied Physics, 2001, 89, 6294-6301.	1.1	39
1807	Formation, evolution, and annihilation of interstitial clusters in ion-implanted Si. Physical Review B, 2001, 63, .	1.1	73
1808	Electronic states in modulation dopedp-AlGaN/GaN superlattices. Journal of Applied Physics, 2001, 90, 4032-4038.	1.1	22
1809	Electrical characterization of vapor-phase-grown single-crystal ZnO. Applied Physics Letters, 2002, 80, 1340-1342.	1.5	171
1810	Neutron irradiation effects on visible-blind Au/GaN Schottky barrier detectors grown on Si(111). Applied Physics Letters, 2002, 80, 1568-1570.	1.5	15
1811	Ground state splitting of vertically stacked indium arsenide self-assembled quantum dots. Applied Physics Letters, 2002, 81, 3594-3596.	1.5	4
1812	Electronic characterization of n-ScN/p+ Si heterojunctions. Applied Physics Letters, 2002, 80, 995-997.	1.5	7
1813	Deep-level defect characteristics in pentacene organic thin films. Applied Physics Letters, 2002, 80, 1595-1597.	1.5	145
1814	Deep-level transient spectroscopy in InGaAsN lattice-matched to GaAs. , 0, , .		5
1815	Applying device simulation for lifetime-controlled devices. , 0, , .		4
1816	Gamma-ray-irradiation effects on the leakage current and reliability of sputtered TiO ₂ gate oxide in metal-oxide-semiconductor capacitors. Journal of Applied Physics, 2002, 91, 9198-9203.	1.1	37
1817	High resolution minority carrier transient spectroscopy of Si/SiGe/Si quantum wells. Journal of Applied Physics, 2002, 92, 5252-5258.	1.1	3

#	ARTICLE	IF	CITATIONS
1818	Deep levels in strongly Si-compensated GaAs and AlGaAs. Journal of Applied Physics, 2002, 91, 5158-5162.	1.1	4
1819	Graphical peak analysis method for determining densities and emission rates of traps in dielectric film from transient discharge current. Journal of Applied Physics, 2002, 91, 2085-2092.	1.1	14
1820	Hole emission processes in InAs/GaAs self-assembled quantum dots. Physical Review B, 2002, 66, .	1.1	47
1821	Defect states in red-emitting $\text{In}_x\text{Al}_{1-x}\text{As}$ quantum dots. Physical Review B, 2002, 66, .	1.1	2
1822	Effects of deposition temperature on the conduction mechanisms and reliability of radio frequency sputtered TiO_2 thin films. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 263.	1.6	6
1823	Parameters of radiation-induced centers for simulation of irradiated power devices. , 0, , .		0
1824	Neutron irradiation effect on radio-frequency magnetron-sputtered GaN thin films and Au/GaN Schottky diodes. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 1821.	1.6	18
1825	Epitaxially overgrown, stable $\text{W}\epsilon\text{-GaAs}$ Schottky contacts with sizes down to 50 nm. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 580.	1.6	9
1826	Electrically active defects in $\text{Ni}\hat{\text{A}}\text{Si}$ silicide studied by deep-level transient spectroscopy. Semiconductor Science and Technology, 2002, 17, 83-86.	1.0	21
1827	Characterization of Interface States in Degraded ZnO Varistors. Japanese Journal of Applied Physics, 2002, 41, 190-196.	0.8	14
1828	Partial annealing of defects in boron-implanted p-type silicon by hydrogen implantation. Materials Research Society Symposia Proceedings, 2002, 719, 861.	0.1	1
1829	DLTS studies of defects produced in n-type silicon by hydrogen implantation at low temperature. Materials Research Society Symposia Proceedings, 2002, 744, 1.	0.1	0
1830	Growth Temperature Effects on Deep-Levels in Si Grown by Low Temperature Molecular Beam Epitaxy. Materials Research Society Symposia Proceedings, 2002, 745, 691.	0.1	0
1831	Ion mass effect on vacancy-related deep levels in Si induced by ion implantation. Physical Review B, 2002, 65, .	1.1	40
1832	Atomic structure and defect densities in low dielectric constant carbon doped hydrogenated silicon oxide films, deposited by plasma-enhanced chemical vapor deposition. Journal of Applied Physics, 2002, 92, 4605-4611.	1.1	38
1833	Lifetime spectroscopy for defect characterization: Systematic analysis of the possibilities and restrictions. Journal of Applied Physics, 2002, 91, 2059-2070.	1.1	97
1834	High resolution deep level transient spectroscopy studies of the vacancy-oxygen and related defects in ion-implanted silicon. Journal of Applied Physics, 2002, 92, 3755-3760.	1.1	12
1835	Violation of the rate-window concept in the charge deep-level transient spectroscopy using second-order filtering. Semiconductor Science and Technology, 2002, 17, 461-464.	1.0	3

#	ARTICLE	IF	CITATIONS
1836	Investigation of barrier layers on ceramics for silicon thin film solar cells. , 0, , .		1
1837	Preliminary study of a novel scanning charge-pumping method using extra gates for SOI wafer inspection. IEEE Electron Device Letters, 2002, 23, 630-632.	2.2	1
1838	Drain current collapse in GaN metal-semiconductor field-effect transistors due to surface band-bending effects. Semiconductor Science and Technology, 2002, 17, 1293-1301.	1.0	13
1839	The long-term annealing of the cluster damage in high resistivity n-type silicon. IEEE Transactions on Nuclear Science, 2002, 49, 2599-2604.	1.2	6
1840	Response of electrically active defects in P/sup +/N junctions when applying a magnetic field. , 0, , .		2
1841	Deep electron and hole traps in freestandingn-GaN grown by hydride vapor phase epitaxy. Journal of Applied Physics, 2002, 92, 5241-5247.	1.1	30
1842	Integrated AlN/diamond heat spreaders for silicon device processing. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2002, 20, 1974.	0.9	8
1843	PICTS analysis of extended defects in heavily irradiated silicon. IEEE Transactions on Nuclear Science, 2002, 49, 2431-2435.	1.2	2
1844	Physics of Copper in Silicon. Journal of the Electrochemical Society, 2002, 149, G21.	1.3	331
1845	Determination of Traps in Poly(p-phenylene vinylene) Light Emitting Diodes by Chargebased Deep Level Transient Spectroscopy. Materials Research Society Symposia Proceedings, 2002, 725, 1.	0.1	0
1846	Photonic high-frequency capacitance-voltage characterization of interface states in metal-oxide-semiconductor capacitors. IEEE Transactions on Electron Devices, 2002, 49, 526-528.	1.6	136
1847	Separation of vacancy and interstitial depth profiles in proton- and boron-implanted silicon. Nuclear Instruments & Methods in Physics Research B, 2002, 186, 334-338.	0.6	5
1848	Defect generation in crystalline silicon irradiated with high energy particles. Nuclear Instruments & Methods in Physics Research B, 2002, 186, 144-151.	0.6	26
1849	Dose-rate influence on the defect production in MeV proton-implanted float-zone and epitaxial n-type silicon. Nuclear Instruments & Methods in Physics Research B, 2002, 186, 375-379.	0.6	14
1850	Defect distribution in MeV proton irradiated silicon measured by high-voltage current transient spectroscopy. Nuclear Instruments & Methods in Physics Research B, 2002, 192, 291-300.	0.6	20
1851	Deep Levels in Br-Doped ZnSe Single Crystals Grown by Physical Vapor Transport. Physica Status Solidi (B): Basic Research, 2002, 229, 291-295.	0.7	4
1852	Preparation and electronic defect characteristics of pentacene organic field effect transistors. Macromolecular Research, 2002, 10, 75-79.	1.0	10
1853	Hydrogen introduction into p+ silicon by boiling in water and its application to deep-level transient spectroscopy measurements. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 91-92, 152-155.	1.7	5

#	ARTICLE	IF	CITATIONS
1854	Defect specific topography of GaAs wafers by microwave-detected photo induced current transient spectroscopy. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2002, 91-92, 371-375.	1.7	8
1855	Size-selective optically excited capacitance transient spectroscopy of InAs/GaAs quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002, 13, 259-262.	1.3	6
1856	The annealing of interstitial carbon atoms in high-resistivity n-type silicon after proton irradiation. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2002, 485, 140-145.	0.7	4
1857	New defect spectroscopies. <i>Applied Surface Science</i> , 2002, 194, 224-233.	3.1	2
1858	Determination of parameters of radiation induced traps in silicon. <i>Solid-State Electronics</i> , 2002, 46, 891-901.	0.8	28
1859	Electron and hole trapping in the bulk and interface with Si of a thermal oxide grown on the sidewalls and base of a U-shaped silicon trench. <i>Solid-State Electronics</i> , 2002, 46, 837-845.	0.8	6
1860	Deformation of a deep-level transient spectroscopy spectrum by an inhomogeneous carrier concentration depth profile. <i>Solid-State Electronics</i> , 2002, 46, 1307-1313.	0.8	2
1861	Gold injection into germanium occurring during hydrogen atom recombination. <i>Vacuum</i> , 2002, 68, 269-273.	1.6	1
1862	Electrically active centers in Si:Er light-emitting layers grown by sublimation molecular-beam epitaxy. <i>Semiconductors</i> , 2002, 36, 171-175.	0.2	4
1863	Study of polycrystalline diamond layers deposited from gas phase. <i>Crystallography Reports</i> , 2002, 47, 298-307.	0.1	1
1864	Emission and capture processes in radiation-damaged silicon semiconductor diodes. <i>Current Applied Physics</i> , 2002, 2, 359-364.	1.1	8
1865	Deep levels and trapping mechanisms in chemical vapor deposited diamond. <i>Journal of Applied Physics</i> , 2002, 91, 5765-5774.	1.1	50
1866	Deep-Level Effects in GaAs Microelectronics: A Review. <i>Russian Microelectronics</i> , 2003, 32, 257-274.	0.1	17
1867	Determination of damage profiles in semiconductors using differential reflectance. <i>Journal of Materials Science: Materials in Electronics</i> , 2003, 14, 187-193.	1.1	2
1868	Mechanisms of gate lag in GaN/AlGaIn/GaN high electron mobility transistors. <i>Superlattices and Microstructures</i> , 2003, 34, 33-53.	1.4	114
1869	Effect of boron on the resistivity of compensated 4H-SiC. <i>Journal of Electronic Materials</i> , 2003, 32, 452-457.	1.0	5
1870	A possible explanation for high quantum efficiency of PtSi/porous Si schottky detectors. <i>IEEE Transactions on Electron Devices</i> , 2003, 50, 1134-1137.	1.6	24
1871	Deep-depletion high-frequency capacitance-voltage responses under photonic excitation and distribution of interface states in MOS capacitors. <i>IEEE Transactions on Electron Devices</i> , 2003, 50, 1131-1134.	1.6	13

#	ARTICLE	IF	CITATIONS
1872	Radiation defect distribution in silicon irradiated with 600 keV electrons. Nuclear Instruments & Methods in Physics Research B, 2003, 201, 513-519.	0.6	8
1873	Electrical and optical isolation of GaN by high energy ion irradiation. Nuclear Instruments & Methods in Physics Research B, 2003, 207, 308-313.	0.6	10
1874	The effect of the CdCl ₂ treatment on CdTe/CdS thin film solar cells studied using deep level transient spectroscopy. Thin Solid Films, 2003, 431-432, 143-147.	0.8	48
1875	Surface electronic states in metal-oxide porous silicon structures. Thin Solid Films, 2003, 445, 144-150.	0.8	9
1876	Deep level transient spectroscopy of vertically stacked InAs/Al _{0.5} Ga _{0.5} As self-assembled quantum dots. Solid State Communications, 2003, 126, 563-566.	0.9	0
1877	Deep levels in ion implanted field effect transistors on SiC. Solid-State Electronics, 2003, 47, 193-198.	0.8	9
1878	Non-destructive deep trap diagnostics of epitaxial structures. Solid-State Electronics, 2003, 47, 1569-1575.	0.8	6
1879	Study on variable capacitance diode of (p)nc-Si:H/(n)c-Si heterojunction. Vacuum, 2003, 71, 465-469.	1.6	6
1880	Deep defect levels in standard and oxygen enriched silicon detectors before and after ⁶⁰ Co- β -irradiation. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2003, 512, 111-116.	0.7	14
1881	Electronic structure of vertically stacked InAs self-assembled quantum dots by deep level transient spectroscopy. Physica B: Condensed Matter, 2003, 325, 41-45.	1.3	4
1882	Electron traps in metalorganic chemical vapor deposition grown Al _{0.2} Ga _{0.8} As. Physica B: Condensed Matter, 2003, 327, 15-19.	1.3	1
1883	Electrical field effect on the optical threshold energy of donor and acceptor levels in chromium-doped GaP. Physica B: Condensed Matter, 2003, 336, 362-368.	1.3	0
1884	Hole trapping in self-assembled SiGe quantum nanostructures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 101, 338-344.	1.7	6
1885	Hydrogenation effect on silicon on sapphire grown by rapid thermal chemical vapor deposition. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 16, 489-494.	1.3	3
1886	Hole storage in GaSb/GaAs quantum dots for memory devices. Physica Status Solidi (B): Basic Research, 2003, 238, 258-261.	0.7	14
1887	Chemical etching-induced defects in n-type ZnSe crystal grown by physical vapor transport. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 635-639.	0.8	1
1888	Investigation of AlGaIn/GaN HEMTs on Si Substrate Using Backgating. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 65-68.	0.8	1
1889	Determination of the absolute value of the semiconductor surface potential by the quasi-static capacitance-voltage characteristics of an MIS structure. Semiconductors, 2003, 37, 661-666.	0.2	1

#	ARTICLE	IF	CITATIONS
1890	Charge-based deep level transient spectroscopy of undoped and nitrogen-doped ultrananocrystalline diamond films. <i>Diamond and Related Materials</i> , 2003, 12, 1776-1782.	1.8	30
1891	Saddle point for oxygen reorientation in the vicinity of a silicon vacancy. <i>Physical Review B</i> , 2003, 67, .	1.1	13
1892	Investigation of buffer traps in an AlGaIn/GaN/Si high electron mobility transistor by backgating current deep level transient spectroscopy. <i>Applied Physics Letters</i> , 2003, 82, 633-635.	1.5	77
1893	450 meV hole localization in GaSb/GaAs quantum dots. <i>Applied Physics Letters</i> , 2003, 82, 2706-2708.	1.5	156
1894	Evidence of the Meyer-Neldel rule in InGaAsN alloys and the problem of determining trap capture cross sections. <i>Applied Physics Letters</i> , 2003, 83, 908-910.	1.5	22
1895	High resolution electrical studies of vacancy-rich and interstitial-rich regions in ion-implanted silicon. <i>Journal of Applied Physics</i> , 2003, 93, 5118-5124.	1.1	20
1896	Chapter 6 Transport and defect properties of intrinsic and boron-doped diamond. <i>Semiconductors and Semimetals</i> , 2003, 76, 261-324.	0.4	9
1897	Erbium-related band gap states in 4H- and 6H-silicon carbide. <i>Journal of Applied Physics</i> , 2003, 93, 2289-2291.	1.1	12
1898	Charge-sensitive deep level transient spectroscopy of boron-doped and gamma-irradiated mono- and polycrystalline diamond. <i>Diamond and Related Materials</i> , 2003, 12, 1783-1787.	1.8	9
1899	Origin of hole-like peaks in current deep level transient spectroscopy of n-channel AlGaAs/GaAs heterostructure field-effect transistors. <i>Journal of Applied Physics</i> , 2003, 94, 5297.	1.1	16
1900	Analysis of Emission Rate Measurements in a Material Showing a Meyer-Neldel- Rule. <i>Materials Research Society Symposia Proceedings</i> , 2003, 799, 47.	0.1	1
1901	A Deep Erbium-Related Bandgap State in 4H Silicon Carbide. <i>Materials Science Forum</i> , 2003, 433-436, 487-490.	0.3	4
1902	Effect of dopant (Nb) concentration on the grain boundary electrical properties of Nb-doped barium titanate. <i>Journal of Materials Research</i> , 2003, 18, 88-96.	1.2	4
1903	Deep Levels in Multilayer Structures of Si/Si _{0.8} Ge _{0.2} Grown by Low-Pressure Chemical Vapor Deposition. <i>Materials Research Society Symposia Proceedings</i> , 2003, 799, 221.	0.1	0
1904	Electrically active defects in n-type 4H-silicon carbide grown in a vertical hot-wall reactor. <i>Journal of Applied Physics</i> , 2003, 93, 4708-4714.	1.1	169
1905	Temperature- and injection-dependent lifetime spectroscopy for the characterization of defect centers in semiconductors. <i>Applied Physics Letters</i> , 2003, 82, 2178-2180.	1.5	77
1906	Bulk-grain resistivity and positive temperature coefficient of ZnO-based varistors. <i>Applied Physics Letters</i> , 2003, 82, 212-214.	1.5	27
1907	Superior Schottky electrode of RuO ₂ for deep level transient spectroscopy on anatase TiO ₂ . <i>Applied Physics Letters</i> , 2003, 83, 1782-1784.	1.5	14

#	ARTICLE	IF	CITATIONS
1908	Charge-based deep level transient spectroscopy of phosphorous-doped homoepitaxial diamond. Journal of Applied Physics, 2003, 94, 5832-5843.	1.1	8
1909	Native hole traps of ferromagnetic Ga _{1-x} MnxAs layers on (100) GaAs substrates. Applied Physics Letters, 2003, 83, 4354-4356.	1.5	2
1910	Substitutional Zn in SiGe: Deep-level transient spectroscopy and electron density calculations. Physical Review B, 2003, 68, .	1.1	4
1911	Vacancy and interstitial depth profiles in ion-implanted silicon. Journal of Applied Physics, 2003, 93, 871-877.	1.1	22
1912	Deep level transient spectroscopic study of neutron-irradiated n-type 6H-SiC. Journal of Applied Physics, 2003, 94, 3004-3010.	1.1	28
1913	Electron capture behaviors of deep level traps in unintentionally doped and intentionally doped n-type GaN. Journal of Applied Physics, 2003, 94, 1485-1489.	1.1	122
1914	Growth temperature and dopant species effects on deep levels in Si grown by low temperature molecular beam epitaxy. Journal of Applied Physics, 2003, 93, 9104-9110.	1.1	16
1915	Nitrogen-related electron traps in Ga(As,N) layers (x=1/2, 3/4). Journal of Applied Physics, 2003, 93, 6095-6099.	1.1	78
1916	Picosecond time-resolved bleaching dynamics of self-assembled quantum dots. , 0, , .		0
1917	Limitations of electrical detection of x-ray absorption fine structure. Physical Review B, 2003, 68, .	1.1	5
1918	Beryllium implantation induced deep level defects in p-type 6H-silicon carbide. Journal of Applied Physics, 2003, 93, 3117-3119.	1.1	8
1919	Correlated analysis of deep level transient spectroscopy and thermally stimulated current spectra. Journal of Applied Physics, 2003, 93, 390-395.	1.1	2
1920	Inductance deep-level transient spectroscopy for determining temperature-dependent resistance and capacitance of Schottky diodes. Review of Scientific Instruments, 2003, 74, 4561-4563.	0.6	5
1921	Deep level transient spectroscopy of defects introduced in Si and SiGe by low energy particles. Journal of Physics Condensed Matter, 2003, 15, S2859-S2886.	0.7	3
1922	33.2: Invited Paper: Electronic Traps in Polymeric Semiconductors. Digest of Technical Papers SID International Symposium, 2003, 34, 1072.	0.1	2
1923	Thermal detection of trapped charge carriers in organic transport materials. , 2003, 4800, 164.		5
1924	Identification of hydrogen related defects in proton implanted float-zone silicon. EPJ Applied Physics, 2003, 23, 5-9.	0.3	14
1925	Evolution of Electronic Properties of Cu(In, Ga)Se ₂ (CIGS)-Based Solar Cells During a 3-stage Growth Process. Materials Research Society Symposia Proceedings, 2003, 763, 5251.	0.1	2

#	ARTICLE	IF	CITATIONS
1926	Evidence of the Meyer-Neldel Rule in InGaAsN Alloys: Consequences for Photovoltaic Materials. Materials Research Society Symposia Proceedings, 2003, 763, 261.	0.1	1
1927	Deep Level Transient Spectroscopy. , 2003, , 1-9.		0
1928	Inductance deep-level transient spectroscopy for determining temperature-dependent resistance and capacitance of Schottky diodes. Physica Scripta, 2004, T114, 16-17.	1.2	1
1929	Method for Detecting Defects in Silicon-On-Insulator Using Capacitance Transient Spectroscopy. Japanese Journal of Applied Physics, 2004, 43, 2402-2408.	0.8	12
1930	Swift heavy-ion irradiation effects on electrical and defect properties of NPN transistors. Semiconductor Science and Technology, 2004, 19, 1029-1039.	1.0	27
1931	Annealing of defect density and excess currents in Si-based tunnel diodes grown by low-temperature molecular-beam epitaxy. Journal of Applied Physics, 2004, 96, 747-753.	1.1	17
1932	Anomalous current transients related to defect discharge in irradiated silicon diodes. Physical Review B, 2004, 70, .	1.1	9
1933	Nonohmic behavior of SnO ₂ -MnO polycrystalline ceramics. II. Analysis of admittance and dielectric spectroscopy. Journal of Applied Physics, 2004, 96, 3811-3817.	1.1	26
1934	Parameters required to simulate electric characteristics of SiC devices for n-type 4H-SiC. Journal of Applied Physics, 2004, 96, 5601-5606.	1.1	65
1935	Low Energy Electron Irradiation Induced Deep Level Defects in 6H-SiC: The Implication for the Microstructure of the Deep Levels E1/E2. Physical Review Letters, 2004, 92, 125504.	2.9	23
1936	Deep-level-transient spectroscopy of heavily Al-doped ZnSe layers grown by molecular-beam epitaxy. Journal of Applied Physics, 2004, 96, 7332-7337.	1.1	7
1937	Electroreflectance studies of Stark shifts and polarization-induced electric fields in InGaN/GaN single quantum wells. Journal of Applied Physics, 2004, 95, 4905-4913.	1.1	27
1938	Determination of densities and energy levels of donors in free-standing undoped 3C-SiC epilayers with thicknesses of 80 ¹ / ₄ μm. Journal of Applied Physics, 2004, 96, 7346-7351.	1.1	16
1939	Photoluminescence and deep levels in lattice-matched InGaAsN-GaAs. Journal of Applied Physics, 2004, 96, 4176-4180.	1.1	11
1940	Bias-Dependent Generation and Quenching of Defects in Pentacene. Physical Review Letters, 2004, 93, 076601.	2.9	124
1941	Anomalous capture and emission from internal surfaces of semiconductor voids: Nanopores in SiC. Physical Review B, 2004, 69, .	1.1	13
1942	Deep-level transient spectroscopy study on double implanted n ⁺ -p and p ⁺ -n 4H-SiC diodes. Journal of Applied Physics, 2004, 95, 69-75.	1.1	30
1943	Charge-state dependence of InAs quantum-dot emission energies. Physical Review B, 2004, 69, .	1.1	55

#	ARTICLE	IF	CITATIONS
1944	Synchrotron-radiation deep level transient spectroscopy for defect characterization of semiconductors. <i>Applied Physics Letters</i> , 2004, 85, 413-415.	1.5	8
1945	Electrical properties of GaSe doped with Er. <i>Journal of Applied Physics</i> , 2004, 96, 1563-1567.	1.1	21
1946	Energy dependence of majority carrier defect introduction rates in p+n GaAs photodiodes irradiated with protons. <i>Journal of Applied Physics</i> , 2004, 96, 7225-7228.	1.1	11
1947	Interpretation of Fermi level pinning on 4H-SiC using synchrotron photoemission spectroscopy. <i>Applied Physics Letters</i> , 2004, 84, 538-540.	1.5	26
1948	Hydrogenation of the dominant interstitial defect in irradiated boron-doped silicon. <i>Physical Review B</i> , 2004, 69, .	1.1	11
1949	Dependence of acceptor levels and hole mobility on acceptor density and temperature in Al-doped p-type 4H-SiC epilayers. <i>Journal of Applied Physics</i> , 2004, 96, 2708-2715.	1.1	79
1950	Carrier capture cross-section of nonradiative recombination centres introduced by proton implantation in GaAs. <i>Semiconductor Science and Technology</i> , 2004, 19, 1325-1328.	1.0	1
1951	Radiotracer Investigation of Gadolinium Induced Deep Levels in Hexagonal Silicon Carbide. <i>Materials Science Forum</i> , 2004, 457-460, 783-786.	0.3	2
1952	A critical analysis of investigation of deep levels in high-resistivity CdS single crystals by photoelectric transient spectroscopy. <i>Semiconductors</i> , 2004, 38, 298-303.	0.2	7
1953	Capacitance study of electron traps in low-temperature-grown GaAs. <i>Semiconductors</i> , 2004, 38, 387-392.	0.2	1
1954	The Meyer-Neldel rule in the processes of thermal emission and hole capture in Ge/Si quantum dots. <i>JETP Letters</i> , 2004, 80, 321-325.	0.4	8
1955	$\mu\text{-V}$ and deep level transient spectroscopy studies on 60 MeV oxygen ion irradiated NPN transistors. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2004, 215, 457-470.	0.6	30
1956	Analysis of dynamic impatt oscillations caused by radiation induced deep centres with local and homogenous vertical distribution. <i>IET Circuits, Devices and Systems</i> , 2004, 151, 219.	0.6	2
1957	The Analysis of Dark Signals in the CMOS APS Imagers From the Characterization of Test Structures. <i>IEEE Transactions on Electron Devices</i> , 2004, 51, 178-184.	1.6	103
1958	Possibilities and limits of axial lifetime control by radiation induced centers in fast recovery diodes. <i>Microelectronics Journal</i> , 2004, 35, 259-267.	1.1	16
1959	Schottky diode back contacts for high frequency capacitance studies on semiconductors. <i>Solid-State Electronics</i> , 2004, 48, 231-238.	0.8	15
1960	Properties of ZnO/CdS/CuInSe ₂ solar cells with improved performance. <i>Progress in Photovoltaics: Research and Applications</i> , 2004, 12, 39-45.	4.4	118
1961	Electrical characterization of ion bombarded AlGaIn Schottky photodetectors. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2004, 1, 2328-2332.	0.8	1

#	ARTICLE	IF	CITATIONS
1962	Copper-related defects in silicon. <i>Materials Science in Semiconductor Processing</i> , 2004, 7, 125-141.	1.9	28
1963	Deep level transient spectroscopy of lead zirconate titanate grown on La _{0.5} Sr _{0.5} CoO ₃ /LaAlO ₃ substrate. <i>Thin Solid Films</i> , 2004, 458, 336-343.	0.8	3
1964	Investigation of defect properties in Cu(In,Ga)Se ₂ solar cells by deep-level transient spectroscopy. <i>Solid-State Electronics</i> , 2004, 48, 1579-1586.	0.8	93
1965	Local properties of grain boundaries in semiconducting ceramics. <i>Solid State Ionics</i> , 2004, 173, 41-50.	1.3	14
1966	Energy-selective charging of type-II GaSb/GaAs quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004, 21, 474-478.	1.3	6
1967	High resolution deep level transient spectroscopy and process-induced defects in silicon. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2004, 114-115, 307-311.	1.7	1
1968	A reliable procedure for the analysis of multiexponential transients that arise in deep level transient spectroscopy. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2004, 114-115, 322-329.	1.7	6
1969	Analysis of deep traps in 4,4'-bis(4-dimethylaminostyryl benzene) based light emitting diode devices. <i>Organic Electronics</i> , 2004, 5, 53-58.	1.4	2
1970	Poole-Frenkel electron emission from the traps in AlGaIn/GaN transistors. <i>Journal of Applied Physics</i> , 2004, 95, 6414-6419.	1.1	169
1971	Deep level transient spectroscopy measurements on heterostructure InSb/InAlSb diodes. <i>Semiconductor Science and Technology</i> , 2004, 19, 468-471.	1.0	2
1972	Deep-level transient spectroscopy using low-frequency capacitance measurements. , 2004, , .		1
1973	Redistribution dynamics of optically generated charges in In(Ga)As/GaAs self-assembled quantum dots. <i>Applied Physics Letters</i> , 2004, 85, 2592-2594.	1.5	6
1974	Deep Level Transient Spectroscopy of Defects in High-Energy Light-Particle Irradiated Si. <i>Critical Reviews in Solid State and Materials Sciences</i> , 2004, 29, 1-44.	6.8	37
1975	A reliable guideline to maximize the detection and analysis of deep defects in deep level transient spectroscopy. , 0, , .		0
1976	Deep levels created by low energy electron irradiation in 4H-SiC. <i>Journal of Applied Physics</i> , 2004, 96, 4909-4915.	1.1	247
1977	Electron capture cross sections of InAs/GaAs quantum dots. <i>Applied Physics Letters</i> , 2004, 85, 2908-2910.	1.5	34
1978	Defect Spectroscopy. , 2004, , 171-190.		0
1979	Defects induced in GaN by europium implantation. <i>Applied Physics Letters</i> , 2004, 85, 2244-2246.	1.5	24

#	ARTICLE	IF	CITATIONS
1980	High-energy proton irradiation effects in GaAs devices. IEEE Transactions on Nuclear Science, 2004, 51, 2887-2895.	1.2	54
1981	Picosecond Time-Resolved Bleaching Dynamics of Self-Assembled Quantum Dots. IEEE Nanotechnology Magazine, 2004, 3, 348-352.	1.1	5
1982	Classification of charge relaxation processes in diamond on silicon based devices. Diamond and Related Materials, 2004, 13, 965-968.	1.8	0
1983	Slow Relaxation of Nonequilibrated Photo-carriers in Semiconductors. Phase Transitions, 2004, 77, 791-821.	0.6	2
1984	Investigation and Identification of Transition Metals in p-Type Boron-Doped Silicon by Non-Invasive Techniques. Defect and Diffusion Forum, 2004, 230-232, 125-134.	0.4	1
1985	Influence of the hole injection layer on the luminescent performance of organic light-emitting diodes. Applied Physics Letters, 2004, 85, 765-767.	1.5	84
1986	Laplace-transform deep-level spectroscopy: The technique and its applications to the study of point defects in semiconductors. Journal of Applied Physics, 2004, 96, 4689-4728.	1.1	270
1987	Particle Detectors made of High Resistivity Czochralski Grown Silicon. Physica Scripta, 2004, T114, 88-90.	1.2	5
1988	Experimental Study of Internal Gettering Efficiency of Iron in Silicon. Physica Scripta, 2004, T114, 91-93.	1.2	6
1989	Unusual properties of C-T characteristics of hydrogen implanted and annealed Si. EPJ Applied Physics, 2004, 27, 141-144.	0.3	0
1990	Thermal Annealing Behaviour of Several Deep Levels in GaInNAs Grown by Molecular Beam Epitaxy. Physica Scripta, 2004, T114, 12-15.	1.2	1
1992	Entropies associated with electron emission from InAs/GaAs quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 27, 380-384.	1.3	5
1993	Continuous wave operation of a 250mW AlGaAs laser diode. Solid-State Electronics, 2005, 49, 1674-1677.	0.8	0
1994	Determination of the Concentration of Deep Levels in Semi-insulating CdS Single Crystals by Photoinduced-Current Transient Spectroscopy. Semiconductors, 2005, 39, 629.	0.2	6
1995	Multistage Radiation-Stimulated Changes in the Microhardness of Silicon Single Crystals Exposed to Low-Intensity I^2 Irradiation. Physics of the Solid State, 2005, 47, 1278.	0.2	7
1996	Bandlike and localized defect states in CuInSe ₂ solar cells. Journal of Physics and Chemistry of Solids, 2005, 66, 1855-1857.	1.9	14
1997	Electronic Properties of Modified CuGaSe ₂ Solar Cells. Materials Research Society Symposia Proceedings, 2005, 865, 1121.	0.1	2
1998	Characterization of a Dominant Electron Trap in GaNAs Using Deep-Level Transient Spectroscopy. Materials Research Society Symposia Proceedings, 2005, 891, 1.	0.1	0

#	ARTICLE	IF	CITATIONS
1999	Investigating Minority-Carrier Traps in p-type Cu(InGa)Se ₂ Using Deep Level Transient Spectroscopy. Materials Research Society Symposia Proceedings, 2005, 865, 5351.	0.1	0
2000	Complex defect behavior in Cu(In,Ga)Se ₂ solar cells with different gallium content. Materials Research Society Symposia Proceedings, 2005, 865, 5341.	0.1	0
2001	Gap States Induced by Local Oxidation of Silicon in Iron-Contaminated p on p+Epitaxial Silicon Wafers. Japanese Journal of Applied Physics, 2005, 44, 8293-8299.	0.8	1
2002	Modified three terminal charge pumping technique applied to vertical transistor structures. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 2189.	1.6	10
2003	Deep level transient spectroscopy studies on BaTiO ₃ and Ba _{1-x} CaxTiO ₃ thin films deposited on Si substrates. Semiconductor Science and Technology, 2005, 20, 250-255.	1.0	5
2004	Electron traps in p-type GaAsN characterized by deep-level transient spectroscopy. , 0, , .		1
2005	Observation of recombination enhanced defect annealing in 4H-SiC. Applied Physics Letters, 2005, 86, 091903.	1.5	14
2006	Native and radiation induced defects in lattice mismatched InGaAs and InGaP. , 0, , .		0
2007	Ionization of deep Te donor in Te-doped Al _{0.6} Ga _{0.4} Sb epilayers. Journal of Applied Physics, 2005, 97, 093711.	1.1	6
2008	Infrared capacity mapping of semiconductor junctions by lock-in thermography. Applied Physics Letters, 2005, 87, 032104.	1.5	2
2009	Strongly temperature-dependent free-energy barriers measured in a polycrystalline semiconductor. Applied Physics Letters, 2005, 86, 262107.	1.5	15
2010	Deep level emission from high-power diode laser bars detected by multispectral infrared imaging. Applied Physics Letters, 2005, 87, 153503.	1.5	23
2011	Interaction of deep impurities with radiation defects in n-Si at ⁶⁰ Co-irradiation. Radiation Effects and Defects in Solids, 2005, 160, 349-356.	0.4	2
2012	Observed trapping of minority-carrier electrons in p-type GaAsN during deep-level transient spectroscopy measurement. Applied Physics Letters, 2005, 86, 072109.	1.5	27
2013	Dislocation in lattice-mismatched InGaAs/GaAs heterostructures as a factor of optoelectronic. , 0, , .		0
2014	Alternative electronic parts for multiphonon-broadened photoionization cross sections of deep levels in SiC. Journal of Applied Physics, 2005, 97, 113533.	1.1	12
2015	Coexistence of deep levels with optically active InAs quantum dots. Physical Review B, 2005, 72, .	1.1	47
2016	An Electrical, Compositional, and Structural Study on Low-k Silsesquioxane Dielectric Thin Films. Journal of the Electrochemical Society, 2005, 152, F83.	1.3	1

#	ARTICLE	IF	CITATIONS
2017	Electronic Properties of Improved Amorphous Silicon-Germanium Alloys Deposited by a Low Temperature Hot Wire Chemical Vapor Deposition Process. Materials Research Society Symposia Proceedings, 2005, 862, 721.	0.1	4
2018	Properties of 6H α -SiC crystals grown by hydrogen-assisted physical vapor transport. Applied Physics Letters, 2005, 86, 202102.	1.5	12
2019	Study of photoluminescence and deep-level defects in be-doped InGaAsN. , 0, , .		0
2020	Deep-level optical spectroscopy investigation of N-doped TiO ₂ films. Applied Physics Letters, 2005, 86, 132104.	1.5	191
2021	Unusual capacitance emission transients in CIGS caused by large defect entropy changes. , 0, , .		0
2022	Defect energy levels in hydrogen-implanted and electron-irradiated n-type 4H silicon carbide. Journal of Applied Physics, 2005, 98, 113524.	1.1	51
2024	Theory of lifetime spectroscopy. Springer Series in Materials Science, 2005, , 69-255.	0.4	2
2025	Defect characterization on intentionally metal-contaminated silicon samples. Springer Series in Materials Science, 2005, , 257-395.	0.4	0
2026	Capacitance-spectroscopy identification of a key defect in N-degraded GaInNAs solar cells. Applied Physics Letters, 2005, 86, 113506.	1.5	39
2027	Meyer-Neldel rule and the influence of entropy on capture cross-section determination in Cu(In,Ga)Se ₂ . Applied Physics Letters, 2005, 87, 123502.	1.5	13
2028	Effect of hydrogen peroxide treatment on the characteristics of Pt Schottky contact on n-type ZnO. Applied Physics Letters, 2005, 86, 112101.	1.5	138
2029	Study of deep electronic states in CdTe solar cells through the detection and DLTS treatment of slow transients. , 0, , .		0
2030	Effect of pulsed laser action on hole-energy spectrum of Ge α -Si self-assembled quantum dots. Physical Review B, 2005, 72, .	1.1	22
2031	Deep-level transient spectroscopy of TiO ₂ α -CuInS ₂ heterojunctions. Applied Physics Letters, 2005, 87, 242103.	1.5	15
2032	Defects in Cu ₂ O studied by deep level transient spectroscopy. Applied Physics Letters, 2006, 88, 141901.	1.5	88
2033	Combined optical and electrical studies of the effects of annealing on the intrinsic states and deep levels in a self-assembled InAs quantum-dot structure. Journal of Applied Physics, 2006, 100, 043703.	1.1	7
2034	Gallium Arsenide. , 2006, , 499-536.		2
2035	Comparison of a dominant electron trap in n-type and p-type GaNAs using deep-level transient spectroscopy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2006, 24, 1252-1257.	0.9	29

#	ARTICLE	IF	CITATIONS
2036	Properties of Si/SiO ₂ /Interfaces in Vertical Trench MOSFETs. , 2006, , .		0
2037	DLTS: A Promising Technique for the Identification of the Recombination and Compensator Centers in Solar Cell Materials. , 2006, , .		1
2038	Hole emission processes from InAs quantum dots grown on p-type InAlAs/InP(O ₂). Semiconductor Science and Technology, 2006, 21, 311-315.	1.0	5
2039	Thermal donors formation via isothermal annealing in magnetic Czochralski high resistivity silicon. Journal of Applied Physics, 2006, 99, 093706.	1.1	31
2040	Trap levels in tris(8-hydroxyquinoline) aluminum studied by deep-level optical spectroscopy. Applied Physics Letters, 2006, 88, 252104.	1.5	8
2041	Investigation of deep levels in n-type 4H-SiC epilayers irradiated with low-energy electrons. Journal of Applied Physics, 2006, 100, 113728.	1.1	142
2042	Electrical Properties. , 2006, , 431-484.		1
2043	Residual impurities and native defects in 6H-SiC bulk crystals grown by halide chemical-vapor deposition. Journal of Applied Physics, 2006, 99, 013508.	1.1	19
2044	Laplace DLTS studies on deep levels coexisted with InAs quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 3844-3847.	0.8	1
2045	Advanced defect and impurity diagnostics in silicon based on carrier lifetime measurements. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 732-746.	0.8	16
2046	Electrical characterization of proton irradiated ³¹ P Si diode. Physica B: Condensed Matter, 2006, 376-377, 181-184.	1.3	8
2047	Defect engineering for 650nm high-power AlGaInP laser diodes. Physica B: Condensed Matter, 2006, 376-377, 610-613.	1.3	2
2048	Deep levels in GaInAs grown by molecular beam epitaxy and their concentration reduction with annealing treatment. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2006, 130, 5-10.	1.7	2
2049	Deep levels in GaInNAs grown by molecular beam epitaxy and their concentration reduction with annealing treatment. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2006, 129, 222-227.	1.7	1
2050	Statistics of electron emission from InAs/GaAs quantum dots. Materials Science and Engineering C, 2006, 26, 739-744.	3.8	13
2051	Scanning probe microscopy of single Au ion implants in Si. Materials Science and Engineering C, 2006, 26, 782-787.	3.8	0
2052	Charged point defects in semiconductors. Materials Science and Engineering Reports, 2006, 55, 57-149.	14.8	115
2053	Electric-field-enhanced electron emission from the EL5 deep-level defect in GaAs. Materials Science in Semiconductor Processing, 2006, 9, 351-354.	1.9	1

#	ARTICLE	IF	CITATIONS
2054	Development of current-based microscopic defect analysis method using optical filling techniques for the defect study on heavily irradiated high-resistivity Si sensors/detectors. <i>Materials Science in Semiconductor Processing</i> , 2006, 9, 283-287.	1.9	4
2055	Interface characterization of Si-passivated HfO ₂ germanium capacitors using DLTS measurements. <i>Materials Science in Semiconductor Processing</i> , 2006, 9, 749-752.	1.9	4
2056	Characterization of radiation-related damage in bulk-grown silicon-germanium detectors. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2006, 562, 311-319.	0.7	0
2057	Passivation of Si and a-Si:H surfaces by thin oxide and oxy-nitride layers. <i>Applied Surface Science</i> , 2006, 252, 7713-7721.	3.1	2
2058	Direct observation of tunneling emission to determine localization energies in self-organized In(Ga)As quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2006, 32, 171-174.	1.3	6
2059	A reliable guideline to maximize the detection and analysis of deep level defects: Comparison between DLTS analysis techniques. <i>Microelectronics Journal</i> , 2006, 37, 1188-1193.	1.1	2
2060	Electrical properties of GaAs/Al _{0.46} Ga _{0.54} As superlattice within a wider quantum well. <i>Microelectronics Journal</i> , 2006, 37, 1404-1407.	1.1	1
2061	Luminescence properties of hole traps in homojunction gallium nitride diodes grown by metal organic vapour phase epitaxy. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2006, 130, 173-176.	1.7	4
2062	Deep levels in Yb-Al co-doped GaAs grown by liquid phase epitaxy. <i>Materials Science in Semiconductor Processing</i> , 2006, 9, 366-370.	1.9	4
2063	Optical and electrical activity of defects in rare earth implanted Si. <i>Optical Materials</i> , 2006, 28, 802-809.	1.7	5
2064	Characteristics of Pt Schottky contacts on hydrogen peroxide-treated n-type ZnO(0001) layers. <i>Superlattices and Microstructures</i> , 2006, 39, 211-217.	1.4	10
2065	Traps identification in Copper-Indium-Gallium-Sulfur-Selenide solar cells completed with various buffer layers by deep level transient spectroscopy. <i>Thin Solid Films</i> , 2006, 515, 2625-2631.	0.8	4
2066	Overcharging of porous silicon localized states at gas adsorption. <i>Semiconductor Science and Technology</i> , 2006, 21, 1605-1608.	1.0	11
2067	Coupling of electron states in the InAs/GaAs quantum dot molecule. <i>Semiconductors</i> , 2006, 40, 331-337.	0.2	6
2068	Nonmonotonic variations in the concentration of the donor-and acceptor-type radiation defects in silicon irradiated with low-intensity fluxes of \hat{I}^2 particles. <i>Semiconductors</i> , 2006, 40, 1375-1377.	0.2	2
2069	The effect of thermal treatment on the charge-carrier lifetime in nickel-doped silicon. <i>Russian Physics Journal</i> , 2006, 49, 183-187.	0.2	0
2070	Defect engineering for high-power 780nm AlGaAs laser diodes. <i>Journal of Materials Science</i> , 2006, 41, 7319-7323.	1.7	2
2071	Deep electronic states in ion-implanted Si. <i>Journal of Materials Science</i> , 2006, 41, 1007-1012.	1.7	0

#	ARTICLE	IF	CITATIONS
2072	The effect of sintering temperature on the development of grain boundary traps in zinc oxide based varistors. <i>Journal of Materials Science</i> , 2006, 41, 3815-3819.	1.7	10
2073	Shallow energy levels induced by \hat{I}^3 rays in standard and oxygenated floating zone silicon. <i>Applied Physics A: Materials Science and Processing</i> , 2006, 84, 449-453.	1.1	3
2074	Influence of radiation energy on the response of a bipolar power transistor tested as dosimeter in radiation processing. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2006, 564, 521-524.	0.7	3
2075	Transport-controlling deep defects in MOVPE grown GaSb. <i>Semiconductor Science and Technology</i> , 2006, 21, 180-183.	1.0	4
2076	Si Substrate Suitable for Radiation-Resistant Space Solar Cells. <i>Japanese Journal of Applied Physics</i> , 2006, 45, 2648-2655.	0.8	16
2077	Electron capture cross-section of Au \hat{e} Fe complex in silicon. <i>Physica Scripta</i> , 2006, 74, 450-451.	1.2	2
2078	Neutron irradiation effects in p-GaN. <i>Journal of Vacuum Science & Technology B</i> , 2006, 24, 2256.	1.3	32
2079	Irradiation-Induced Deep Levels in Silicon for Power Device Tailoring. <i>Journal of the Electrochemical Society</i> , 2006, 153, G108.	1.3	29
2080	Relationship between the EPR SI-5 Signal and the 0.65 eV Electron Trap in 4H- and 6H-SiC Polytypes. <i>Materials Science Forum</i> , 2006, 527-529, 547-550.	0.3	4
2081	Electrical Characterization of Proton Irradiated n-Type ZnO. <i>Materials Research Society Symposia Proceedings</i> , 2006, 957, 1.	0.1	0
2082	Transport Properties and Conduction Band Offset of n-ZnO/n-6H-SiC Heterostructures. <i>Materials Research Society Symposia Proceedings</i> , 2006, 957, 1.	0.1	0
2083	Europium Induced Deep Levels in Hexagonal Silicon Carbide. <i>Materials Science Forum</i> , 2006, 527-529, 659-662.	0.3	0
2085	Lifetime-limiting defects in n \hat{a} 4H-SiC epilayers. <i>Applied Physics Letters</i> , 2006, 88, 052110.	1.5	177
2086	Hole capture into self-organized InGaAs quantum dots. <i>Applied Physics Letters</i> , 2006, 89, 232105.	1.5	42
2087	Band offset measurements of ZnO \hat{a} 6H-SiC heterostructure system. <i>Applied Physics Letters</i> , 2006, 89, 152115.	1.5	18
2088	Carrier storage time of milliseconds at room temperature in self-organized quantum dots. <i>Applied Physics Letters</i> , 2006, 89, 072103.	1.5	31
2089	Tunneling emission from self-organized In(Ga)As \hat{a} GaAs quantum dots observed via time-resolved capacitance measurements. <i>Physical Review B</i> , 2006, 73, .	1.1	51
2090	Study of coupling effect in double-layer quantum dots by admittance spectroscopy. <i>Applied Physics Letters</i> , 2006, 89, 072112.	1.5	7

#	ARTICLE	IF	CITATIONS
2091	Tunneling emission from self-assembled InAs quantum dots probed with capacitance transients. Physical Review B, 2006, 74, .	1.1	29
2092	Identification of sulfur double donors in 4H-, 6H-, and 3C-silicon carbide. Journal of Applied Physics, 2006, 99, 123717.	1.1	5
2093	Measuring the role of surface chemistry in silicon microphotonics. Applied Physics Letters, 2006, 88, 131114.	1.5	87
2094	Effect of C ⁺ Si ratio on deep levels in epitaxial 4H-SiC. Applied Physics Letters, 2006, 88, 121914.	1.5	28
2095	Determination of the concentration of recombination centers in thin asymmetrical p-n junctions from capacitance transient spectroscopy. Applied Physics Letters, 2006, 89, 112107.	1.5	11
2096	Discovery of the deep level related to hydrogen in anatase TiO ₂ . Applied Physics Letters, 2006, 88, 132101.	1.5	6
2097	Observation of minority-carrier traps in InGaN/GaN multiple-quantum-well light-emitting diodes during deep-level transient spectroscopy measurements. Applied Physics Letters, 2006, 88, 182103.	1.5	17
2098	Capture barrier for DX centers in gallium doped Cd _{1-x} MnxTe. Journal of Applied Physics, 2006, 99, 083510.	1.1	3
2100	The impact of negative-bias-temperature-instability on the carrier generation lifetime of metal-oxynitride-silicon capacitors. Journal of Applied Physics, 2006, 100, 124103.	1.1	23
2101	DLTS and PR Studies of Partially Relaxed InGaAs/GaAs Heterostructures Grown by MOVPE. Solid State Phenomena, 2007, 131-133, 485-490.	0.3	0
2102	Point defect reduction in GaN layers grown with the aid of SiN _x nanonet by metalorganic chemical vapor deposition. , 2007, , .		4
2103	Analysis of generation and annihilation of deep level defects in a silicon-irradiated bipolar junction transistor. Semiconductor Science and Technology, 2007, 22, 963-969.	1.0	11
2104	Drain-Current Deep Level Transient Spectroscopy Study of Carrier Emission Process from InAs Quantum Dots in GaAs Narrow-Wire Field Effect Transistors. Japanese Journal of Applied Physics, 2007, 46, 4344-4350.	0.8	3
2105	Deep-Level Characterization of Tris(8-hydroxyquinoline) Aluminum with and without Quinacridone Doping. Japanese Journal of Applied Physics, 2007, 46, 2636-2639.	0.8	6
2106	Impacts of growth parameters on deep levels in n-type 4H-SiC. Journal of Applied Physics, 2007, 101, 053709.	1.1	39
2107	Determining the defect parameters of the deep aluminum-related defect center in silicon. Applied Physics Letters, 2007, 91, 122109.	1.5	45
2108	Activation energies in diamond films evaluated using admittance spectroscopy and resistivity measurements. Journal of Applied Physics, 2007, 101, 033714.	1.1	7
2109	Meyer-Neldel rule in ZnO. Applied Physics Letters, 2007, 91, 232110.	1.5	11

#	ARTICLE	IF	CITATIONS
2110	Defect-driven gain bistability in neutron damaged, silicon bipolar transistors. Applied Physics Letters, 2007, 90, 172105.	1.5	38
2111	106years extrapolated hole storage time in GaSb ⁺ AlAs quantum dots. Applied Physics Letters, 2007, 91, 242109.	1.5	109
2112	Deep level transient spectroscopy of SnO ₂ -based varistors. Applied Physics Letters, 2007, 90, 093511.	1.5	9
2113	Noncontact deep level photo-thermal spectroscopy: Technique and application to semi-insulating GaAs Wafers. Applied Physics Letters, 2007, 90, 062119.	1.5	14
2114	Improvement of GaInNAs p-i-n photodetector responsivity by antimony incorporation. Journal of Applied Physics, 2007, 101, 033122.	1.1	10
2115	Electronic properties and dopant pairing behavior of manganese in boron-doped silicon. Journal of Applied Physics, 2007, 102, 103716.	1.1	17
2116	Formation of Hydrogen-Related Shallow Donors in Ge _{1-x} Si _x Crystals Implanted with Protons. Solid State Phenomena, 2008, 131-133, 131-136.	0.3	1
2117	Nanoscale Analysis of Defects in Semiconductors and Dielectrics by Means of Charge-transient Spectroscopy/microscopy. Materials Research Society Symposia Proceedings, 2007, 1025, 1.	0.1	0
2118	Defect study on the indium-gallium alloy system of copper chalcopyrites performed on solar cell heterostructures. Journal of Applied Physics, 2007, 101, 104507.	1.1	10
2119	DLTS: A Promising Technique for Understanding the Physics and Engineering of the Point Defects in Si and III-V Alloys. Materials Research Society Symposia Proceedings, 2007, 994, 1.	0.1	0
2120	Electrical Properties of Atomic-Layer-Deposited Thin Gadolinium Oxide High-k Gate Dielectrics. Journal of the Electrochemical Society, 2007, 154, G207.	1.3	36
2121	Electrical, Physical, and Chemical Characterization. , 2007, , 28-1-28-79.		0
2122	Photorefractive Materials and Their Applications 2. Springer Series in Optical Sciences, 2007, , .	0.5	35
2123	Room-temperature annealing of vacancy-type defect in high-purity n -type Si. Physical Review B, 2007, 76, .	1.1	14
2124	Effect of growth temperature on defect states of GaAsSbN intrinsic layer in GaAs ⁺ GaAsSbN ⁺ GaAs photodiode for 1.3 μ m application. Journal of Applied Physics, 2007, 102, .	1.1	18
2125	Defect-induced trap-assisted tunneling current in GaInNAs grown on GaAs substrate. Journal of Applied Physics, 2007, 102, .	1.1	21
2126	Effect of swift heavy ion irradiation on deep levels in Au ⁿ -Si (100) Schottky diode studied by deep level transient spectroscopy. Journal of Applied Physics, 2007, 102, 113709.	1.1	4
2127	Effects of deep defect concentration on junction space charge capacitance measurements. Journal of Applied Physics, 2007, 101, 094503.	1.1	5

#	ARTICLE	IF	CITATIONS
2128	Characterization of Traveling Heater Method (THM) Grown $\text{Cd}_{0.9}\text{Zn}_{0.1}\text{Te}$ Crystals. IEEE Transactions on Nuclear Science, 2007, 54, 811-816.	1.2	85
2129	Effects of clustering on the properties of defects in neutron irradiated silicon. Journal of Applied Physics, 2007, 102, .	1.1	48
2130	Characterization of impurities in GaInNAs pn junctions from capacitance transient spectroscopy. , 2007, , .		0
2131	Metrics for Comparison Between Displacement Damage due to Ion Beam and Neutron Irradiation in Silicon BJTs. IEEE Transactions on Nuclear Science, 2007, 54, 2282-2287.	1.2	14
2132	Characterization of energy levels related to impurities in epitaxial 4H-SiC ion implanted p+n junctions. Diamond and Related Materials, 2007, 16, 6-11.	1.8	9
2133	Particle interaction and displacement damage in silicon devices operated in radiation environments. Reports on Progress in Physics, 2007, 70, 493-625.	8.1	104
2134	Advances in Contactless Silicon Defect and Impurity Diagnostics Based on Lifetime Spectroscopy and Infrared Imaging. Advances in OptoElectronics, 2007, 2007, 1-9.	0.6	6
2135	Properties of dominant electron trap center in n-type SiC epilayers by means of deep level transient spectroscopy. Journal of Applied Physics, 2007, 101, 073706.	1.1	10
2136	Origin of visible-light sensitivity in N-doped TiO ₂ films. Chemical Physics, 2007, 339, 20-26.	0.9	58
2137	Discovery of classes among deep level centers in gallium arsenide. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2007, 138, 12-15.	1.7	4
2138	DLTS study of deep level defects in Li-ion irradiated bipolar junction transistor. Nuclear Instruments & Methods in Physics Research B, 2007, 254, 98-104.	0.6	22
2139	Electrical characterization of H ⁺ ion irradiated n-ZnO. Nuclear Instruments & Methods in Physics Research B, 2007, 257, 311-314.	0.6	15
2140	Recalling the origins of DLTS. Physica B: Condensed Matter, 2007, 401-402, 7-9.	1.3	7
2141	Gain and defect bi-stability in radiation damaged silicon bipolar transistors. Physica B: Condensed Matter, 2007, 401-402, 21-24.	1.3	2
2142	Effects of defect clustering in neutron irradiated silicon. Physica B: Condensed Matter, 2007, 401-402, 491-494.	1.3	5
2143	Application of DLTS and Laplace-DLTS to defect characterization in high-resistivity semiconductors. Physica B: Condensed Matter, 2007, 401-402, 666-669.	1.3	5
2144	Electronic states at misfit dislocations in partially relaxed InGaAs/GaAs heterostructures. Physica B: Condensed Matter, 2007, 388, 195-199.	1.3	11
2145	Shape transformation of self-assembled InAs quantum dots by overgrowth with GaAs and AlAs. Journal of Crystal Growth, 2007, 301-302, 748-750.	0.7	6

#	ARTICLE	IF	CITATIONS
2146	Evaluation of dislocation-related defects in GaN using deep-level transient spectroscopy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007, 4, 2568-2571.	0.8	21
2147	Dislocation-related electronic states in partially strain-relaxed InGaAs/GaAs heterostructures grown by MOVPE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007, 4, 3037-3042.	0.8	3
2148	Electrical characterization of He ⁺ irradiated n-ZnO. <i>Physica Status Solidi (B): Basic Research</i> , 2007, 244, 1544-1548.	0.7	15
2149	Bonding state of a hole in Ge/Si double quantum dots. <i>JETP Letters</i> , 2007, 86, 478-481.	0.4	6
2150	Direct observation of charge-carrier capture in an array of self-assembled InAs/GaAs quantum dots. <i>Bulletin of the Russian Academy of Sciences: Physics</i> , 2007, 71, 106-108.	0.1	1
2151	Analysis of the parameters of deep centers in the Al/i-GaAs detectors of charged particles and X-ray radiation. <i>Journal of Communications Technology and Electronics</i> , 2007, 52, 1165-1170.	0.2	1
2152	Annealing kinetics of gold and iron-gold complex. <i>Journal of Materials Science</i> , 2007, 42, 4753-4756.	1.7	1
2153	Iron and gold related defects in water quenched silicon. <i>Journal of Materials Science: Materials in Electronics</i> , 2007, 18, 421-425.	1.1	2
2154	Deep level transient spectroscopy studies at low temperature of In _{0.52} Al _{0.48} As epilayers. <i>Physica B: Condensed Matter</i> , 2007, 391, 18-21.	1.3	2
2155	Analysis of defects in microcrystalline islands in amorphous silicon films with a Scanning Charge-Transient Microscope. <i>Ultramicroscopy</i> , 2007, 107, 963-968.	0.8	3
2156	Investigation of capacitance transients in CuInS ₂ due to ionic migration. <i>Solar Energy Materials and Solar Cells</i> , 2008, 92, 1579-1585.	3.0	8
2157	Investigation of deep level defects in copper irradiated bipolar junction transistor. <i>Solid-State Electronics</i> , 2008, 52, 1237-1243.	0.8	21
2158	Effect of temperature on thermally induced defects in silicon. <i>Journal of Materials Science: Materials in Electronics</i> , 2008, 19, 267-269.	1.1	0
2159	Electronic characterization of several 100-Å thick epitaxial GaAs layers. <i>Journal of Materials Science: Materials in Electronics</i> , 2008, 19, 487-492.	1.1	2
2160	Characterization of deep centers in semi-insulating SiC and HgI ₂ : Application of discharge current transient spectroscopy. <i>Journal of Materials Science: Materials in Electronics</i> , 2008, 19, 810-814.	1.1	5
2161	Effect of electrical operation on the defect states in organic semiconductors. <i>Journal of Materials Science: Materials in Electronics</i> , 2008, 19, 92-95.	1.1	5
2162	Deep Level Transient Spectroscopy in Quantum Dot Characterization. <i>Nanoscale Research Letters</i> , 2008, 3, 179-185.	3.1	10
2163	Defects in organic electronic devices. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008, 205, 162-166.	0.8	29

#	ARTICLE	IF	CITATIONS
2164	Charge deep level transient spectroscopy of electron traps in MOVPE grown n-GaN on sapphire. <i>Physica Status Solidi (B): Basic Research</i> , 2008, 245, 2567-2571.	0.7	10
2166	Towards an universal memory based on self-organized quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2008, 40, 1811-1814.	1.3	28
2167	Nanostructures for nanoelectronics: No potential for room temperature applications?. <i>Microelectronics Journal</i> , 2008, 39, 302-306.	1.1	2
2168	Deep level transient spectroscopy of cyanide treated polycrystalline p-Cu ₂ O/n-ZnO solar cell. <i>Chemical Physics Letters</i> , 2008, 463, 117-120.	1.2	53
2169	Laser doping of chromium as a double acceptor in silicon carbide with reduced crystalline damage and nearly all dopants in activated state. <i>Acta Materialia</i> , 2008, 56, 1857-1867.	3.8	9
2170	Electron irradiation induced defects in undoped and Te doped gallium phosphide. <i>Solid State Communications</i> , 2008, 145, 332-336.	0.9	8
2171	Thermal dynamics of Au-Fe pair in silicon. <i>Solid State Communications</i> , 2008, 148, 50-54.	0.9	0
2172	Characterization of electron irradiated GaN n-p diode. <i>Thin Solid Films</i> , 2008, 516, 3482-3485.	0.8	21
2173	Spatially-resolved photocapacitance measurements to study defects in a-Si:H based p-n particle detectors. <i>Thin Solid Films</i> , 2008, 516, 5118-5121.	0.8	8
2174	Deep traps and optical properties of partially strain-relaxed InGaAs/GaAs heterostructures. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2008, 147, 166-170.	1.7	1
2175	Comparative study on EOR and deep level defects in preamorphised Si implanted with B ⁺ , and F ⁺ -B ⁺ . <i>Nuclear Instruments & Methods in Physics Research B</i> , 2008, 266, 3565-3576.	0.6	7
2176	Interaction of $\hat{\mu}$ radiation with iron-doped n-type silicon. <i>Microelectronics Journal</i> , 2008, 39, 797-801.	1.1	1
2177	Noncontact Deep Level Photo-Thermal Spectroscopy of semi-insulating GaAs. <i>European Physical Journal: Special Topics</i> , 2008, 153, 283-285.	1.2	2
2178	Defects in quantum dots of II-VI semiconductors. <i>Opto-electronics Review</i> , 2008, 16, .	2.4	45
2179	Deep levels and electron transport in AlGaIn/GaN heterostructures. <i>Semiconductors</i> , 2008, 42, 52-58.	0.2	8
2180	Determination of radiation-defect symmetry by high-resolution Laplace DLTS. <i>Bulletin of the Russian Academy of Sciences: Physics</i> , 2008, 72, 1584-1588.	0.1	0
2181	Electrical characterization of nanostructures. , 2008, , 55-91.		3
2182	Centers with low correlation energy in deep-level transient spectroscopy studies. <i>Semiconductor Science and Technology</i> , 2008, 23, 125031.	1.0	1

#	ARTICLE	IF	CITATIONS
2183	Analysis of electronic memory traps in the oxide-nitride-oxide structure of a polysilicon-oxide-nitride-oxide-semiconductor flash memory. Applied Physics Letters, 2008, 92, .	1.5	26
2184	Trapping Phenomena in Nanocrystalline Semiconductors. Nanostructure Science and Technology, 2008, , 191-222.	0.1	5
2185	Si/SiGe heterostructures for advanced microelectronic devices. Phase Transitions, 2008, 81, 751-772.	0.6	3
2186	Self-organized quantum dots for future semiconductor memories. Journal of Physics Condensed Matter, 2008, 20, 454202.	0.7	6
2187	Development of power devices for hybrid vehicles. , 2008, , .		1
2188	Interpretation of the DLTS spectra of silicon p-n junctions prepared by diffusion technique. , 2008, , .		4
2189	Dark Current Spectroscopy of Irradiated CCD Image Sensors. IEEE Transactions on Nuclear Science, 2008, 55, 1719-1724.	1.2	15
2191	Electrical and deep levels characteristics of ZnO/ Si heterostructure by MOCVD deposition. Chinese Physics B, 2008, 17, 2292-2296.	0.7	22
2192	Microwave probed photoconductivity spectroscopy of deep levels in Ni doped Ge. Applied Physics Letters, 2008, 92, 222102.	1.5	9
2193	Characterization of Intrinsic Defects in High-Purity High-Resistivity p-Type 6H-SiC. Japanese Journal of Applied Physics, 2008, 47, 7052-7055.	0.8	3
2194	Detailed Carrier Lifetime Analysis of Iron-Contaminated Boron-Doped Silicon by Comparison of Simulation and Measurement. Journal of the Electrochemical Society, 2008, 155, H117.	1.3	2
2195	Silicon carbide and its use as a radiation detector material. Measurement Science and Technology, 2008, 19, 102001.	1.4	228
2196	Investigation of Electron Traps in SnO ₂ Based Varistor Ceramics. Key Engineering Materials, 0, 368-372, 517-520.	0.4	0
2197	Characterization of amorphous/crystalline silicon interfaces from electrical measurements. Materials Research Society Symposia Proceedings, 2008, 1066, 1.	0.1	5
2198	Swift heavy ion irradiation-induced defects and electrical characteristics of Au/n-Si Schottky structure. Journal Physics D: Applied Physics, 2008, 41, 105105.	1.3	6
2199	Mechanisms of Reduction in Hole Concentration in Al-Implanted p-Type 6H-SiC by 1 MeV Electron Irradiation. Japanese Journal of Applied Physics, 2008, 47, 5355.	0.8	2
2200	Emissive Interface States in Organic Light-Emitting Diodes Based on Tris(8-hydroxyquinoline) Aluminum. Japanese Journal of Applied Physics, 2008, 47, 464-467.	0.8	6
2201	Rapid annealing of the vacancy-oxygen center and the divacancy center by diffusing hydrogen in silicon. Physical Review B, 2008, 77, .	1.1	9

#	ARTICLE	IF	CITATIONS
2202	Mechanisms of unexpected reduction in hole concentration in Al-doped 4H-SiC by 200 keV electron irradiation. <i>Journal of Applied Physics</i> , 2008, 104, 043702.	1.1	13
2203	Deep level photothermal spectroscopy: Physical principles and applications to semi-insulating GaAs band-gap multiple trap states. <i>Journal of Applied Physics</i> , 2008, 103, .	1.1	14
2204	Impact of thermal annealing on deep-level defects in strained-Si ^δ -SiGe heterostructure. <i>Journal of Applied Physics</i> , 2008, 103, 103506.	1.1	8
2205	Studies of oxide/ZnO near-interfacial defects by photoluminescence and deep level transient spectroscopy. <i>Applied Physics Letters</i> , 2008, 92, 042105.	1.5	14
2206	Deep level defects in a nitrogen-implanted ZnO homogeneous p-n junction. <i>Applied Physics Letters</i> , 2008, 92, 222109.	1.5	42
2207	A bistable divacancylike defect in silicon damage cascades. <i>Journal of Applied Physics</i> , 2008, 104, .	1.1	35
2208	Setup for <i>in situ</i> deep level transient spectroscopy of semiconductors during swift heavy ion irradiation. <i>Review of Scientific Instruments</i> , 2008, 79, 056103.	0.6	2
2209	Acceptor levels in GaSe:In crystals investigated by deep-level transient spectroscopy and photoluminescence. <i>Journal of Applied Physics</i> , 2008, 103, .	1.1	18
2210	Suppression of competing tunneling processes in thermally-activated carrier emission on self-assembled InAs quantum dots. <i>Physical Review B</i> , 2008, 77, .	1.1	16
2211	Electrical Characterization of Defects in Gate Dielectrics. , 2008, , .		6
2212	Study of metal-related deep-level defects in germanide Schottky barriers on n-type germanium. <i>Journal of Applied Physics</i> , 2008, 104, .	1.1	22
2213	GaN Lateral Epitaxy Growth Using Porous SiN _x , TiN _x and SiC. , 0, , 121-170.		0
2217	The effect of ZnO replacement by ZnMgO ON ZnO/CdS/Cu(In,Ga)Se₂ solar cells. , 2009, , .		0
2218	Thermionic tunneling through Coulomb barriers in charged self-assembled quantum dots. <i>Physical Review B</i> , 2009, 80, .	1.1	9
2219	Broadening effects and ergodicity in deep level photothermal spectroscopy of defect states in semi-insulating GaAs: A combined temperature-, pulse-rate-, and time-domain study of defect state kinetics. <i>Journal of Applied Physics</i> , 2009, 105, .	1.1	15
2220	Isochronal annealing study of low energy electron irradiated Al-doped p-type 6H silicon carbide with deep level transient spectroscopy. <i>Journal of Applied Physics</i> , 2009, 105, 063711.	1.1	7
2221	Experimental Methods for Defect Introduction Rates Determination in Multijunction Solar Cells. <i>IEEE Transactions on Nuclear Science</i> , 2009, 56, 2237-2241.	1.2	6
2222	Investigation of the effect of different dopants on the trap states of ZnO-based and SnO ₂ -based varistors. <i>Journal of Physics: Conference Series</i> , 2009, 152, 012060.	0.3	3

#	ARTICLE	IF	CITATIONS
2223	Study of luminescent centers in ZnO nanorods catalytically grown on 4H-p-SiC. Semiconductor Science and Technology, 2009, 24, 125015.	1.0	32
2224	Defects in zinc-implanted ZnO thin films. Journal of Vacuum Science & Technology B, 2009, 27, 1597.	1.3	12
2225	Anisotropic electric-field-enhanced electron emission from deep-level defects in GaAs. Semiconductor Science and Technology, 2009, 24, 105021.	1.0	8
2226	Radiative defect state identification in semi-insulating GaAs using photo-carrier Radiometry. Semiconductor Science and Technology, 2009, 24, 125002.	1.0	10
2227	Extended defect states of Ge/Si quantum dots using optical isothermal capacitance transient spectroscopy. Nanotechnology, 2009, 20, 055201.	1.3	5
2228	Radio frequency electrical pulse characterization of defect states in a GaAs/AlGaAs narrow channel field effect transistor. Semiconductor Science and Technology, 2009, 24, 085018.	1.0	1
2229	Effect of Intrinsic Defects in High-Purity Semi-Insulating 4H-SiC on Reverse Current-Voltage Characteristics of Schottky Barrier Diodes. Japanese Journal of Applied Physics, 2009, 48, 056504.	0.8	3
2230	Study of trap states in polyspirobifluorene based devices: Influence of aging by electrical stress. Journal of Applied Physics, 2009, 106, 053707.	1.1	14
2231	Arsenic antisite defects in p-GaAs grown by metal-organic chemical-vapor deposition and the EL2 defect. Journal of Applied Physics, 2009, 106, .	1.1	9
2232	Charge-sensitive deep level transient spectroscopy of helium-ion-irradiated silicon, as-irradiated and after thermal annealing. Chinese Physics B, 2009, 18, 246-250.	0.7	1
2233	Analysis of nonexponential capacitance relaxation signals. Russian Physics Journal, 2009, 52, 733-741.	0.2	1
2234	Depletion-Mode Photoconductivity Study of Deep Levels in GaN Nanowires. Journal of Electronic Materials, 2009, 38, 484-489.	1.0	20
2235	A novel nonvolatile memory based on self-organized quantum dots. Microelectronics Journal, 2009, 40, 492-495.	1.1	15
2236	Deep-level defects study of arsenic-implanted ZnO single crystal. Microelectronics Journal, 2009, 40, 286-288.	1.1	10
2237	Characterization of power transistors as high dose dosimeters. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2009, 599, 284-288.	0.7	2
2238	Deep level transient spectroscopy signatures of majority traps in GaN n diodes grown by metal-organic vapor-phase epitaxy technique on GaN substrates. Physica B: Condensed Matter, 2009, 404, 4889-4891.	1.3	22
2239	Thermal stability study of palladium and cobalt Schottky contacts on n-Ge (100) and defects introduced during contacts fabrication and annealing process. Physica B: Condensed Matter, 2009, 404, 4482-4484.	1.3	12
2240	Defect-impurity complexes with high thermal stability in epi-Si n+-p diodes irradiated with MeV electrons. Vacuum, 2009, 83, S131-S133.	1.6	1

#	ARTICLE	IF	CITATIONS
2241	Effect of electron irradiation on characteristics of Mo Schottky barriers on epitaxial silicon. Vacuum, 2009, 83, S134-S136.	1.6	0
2242	Temperature Dependence of Electron Transport in CdSe Quantum Dot Films. Journal of Physical Chemistry C, 2009, 113, 15992-15996.	1.5	9
2243	Hopping and drift mechanisms of photoconductivity in ZnO:Li films. Journal of Contemporary Physics, 2009, 44, 29-35.	0.1	2
2244	Laplace-DLTS method with the regularization parameter chosen from the L curve. Semiconductors, 2009, 43, 586-589.	0.2	2
2245	Capacitance Oscillations in Cylindrical Nanowire Gate-All-Around MOS Devices at Low Temperatures. IEEE Electron Device Letters, 2009, 30, 395-397.	2.2	1
2246	Electrical properties of nanocrystalline GaN film prepared by magnetron sputtering. Journal of Alloys and Compounds, 2009, 467, 61-64.	2.8	14
2247	Improved mathematical model for the investigation of deep traps into semiconductor devices: application to Metamorphic HEMT. , 2009, , .		0
2248	Temperature and electric field dependence of the carrier emission processes in a quantum dot-based memory structure. Applied Physics Letters, 2009, 94, 042108.	1.5	31
2249	Damage Formation and Evolution in Alon-Implanted Crystalline Si. Topics in Applied Physics, 2009, , 147-212.	0.4	15
2251	Interface effects on the defect state formation in organic devices. Proceedings of SPIE, 2009, , .	0.8	4
2252	Electric field effect on the emission rate of H4F and H4S hole traps in InP. Journal of Applied Physics, 2009, 105, 103517.	1.1	3
2253	Deep level optical spectroscopy of GaN nanorods. Journal of Applied Physics, 2009, 106, .	1.1	34
2254	Deep levels in GaTe and GaTe:In crystals investigated by deep-level transient spectroscopy and photoluminescence. Journal of Applied Physics, 2009, 105, .	1.1	29
2255	Investigation of Ion implantation induced electrically active defects in p-type silicon. , 2009, , .		0
2256	Experimental and Computational Characterization. Engineering Materials and Processes, 2009, , 39-61.	0.2	0
2257	Low temperature reaction of point defects in ion irradiated 4Hâ€“SiC. Diamond and Related Materials, 2009, 18, 39-42.	1.8	4
2258	Synthesis and Characterization of ZnO/Glass/ZnO Structures Showing Highly Nonlinear Current-Voltage Characteristics. Materials Transactions, 2009, 50, 1060-1066.	0.4	5
2259	Fractional photoconductivity glow curves of β -rhombohedral boron. Journal of Physics: Conference Series, 2009, 176, 012020.	0.3	2

#	ARTICLE	IF	CITATIONS
2260	Photocurrent radiometric study of defect states in semi-insulating GaAs. Journal of Physics: Conference Series, 2010, 214, 012107.	0.3	4
2261	Broadening effects and ergodicity in deep level photo-thermal spectroscopy of defect states in semi-insulating GaAs: A combined temperature-, pulse-rate- and time-domain study of defect state kinetics. Journal of Physics: Conference Series, 2010, 214, 012001.	0.3	0
2262	Deep levels in GaAs(001)/InAs/InGaAs/GaAs self-assembled quantum dot structures and their effect on quantum dot devices. Journal of Applied Physics, 2010, 107, 073111.	1.1	28
2263	Identification of the nature of trapping centers in polyspirobifluorene based diodes by using electrical characterization. Journal of Applied Physics, 2010, 107, .	1.1	14
2264	Photoinduced current transient spectroscopy of high-resistivity layered GaSe crystals. Semiconductors, 2010, 44, 854-856.	0.2	3
2265	Study of defects in heterostructures with GaPAsN and GaPN quantum wells in the GaP matrix. Semiconductors, 2010, 44, 893-897.	0.2	8
2266	Statistical method of deep-level transient spectroscopy in semiconductors. Semiconductors, 2010, 44, 997-1003.	0.2	1
2267	Analysis of mechanisms of carrier emission in the p-i-n structures with In(Ga)As quantum dots. Semiconductors, 2010, 44, 1308-1312.	0.2	10
2268	Relaxation spectroscopy of deep levels in semiconductors: Laplace-DLTS method. Technical Physics Letters, 2010, 36, 1001-1005.	0.2	1
2269	I-V, C-V and deep level transient spectroscopy study of 24 MeV proton-irradiated bipolar junction transistor. Pramana - Journal of Physics, 2010, 74, 97-107.	0.9	2
2270	Classification of Energy Levels in Quantum Dot Structures by Depleted Layer Spectroscopy. Journal of Electronic Materials, 2010, 39, 766-772.	1.0	7
2271	Characterization of Generation Lifetime and Surface Generation Velocity of Semiconductor Wafers by a Contactless Zerst Method. Journal of Electronic Materials, 2010, 39, 773-776.	1.0	2
2272	Deep-level Transient Spectroscopy of GaAs/AlGaAs Multi-Quantum Wells Grown on (100) and (311)B GaAs Substrates. Nanoscale Research Letters, 2010, 5, 1948-1951.	3.1	12
2273	An advanced description of oxide traps in MOS transistors and its relation to DFT. Journal of Computational Electronics, 2010, 9, 135-140.	1.3	14
2274	Deep level transient spectroscopy study of the effect of Mn and Bi doping on trap formation in ZnO. Journal of Electroceramics, 2010, 25, 188-197.	0.8	14
2275	Investigation on deep level defects in rapid thermal annealed undoped n-type InP. Journal of Materials Science: Materials in Electronics, 2010, 21, 285-290.	1.1	4
2276	Avalanche Breakdown Delay in ESD Protection Diodes. IEEE Transactions on Electron Devices, 2010, 57, 2470-2476.	1.6	10
2277	Modified Potential Well Formed by $\text{Si/SiO}_2/\text{TiN/TiO}_2/\text{SiO}_2/\text{TaN}$ for Flash Memory Application. IEEE Transactions on Electron Devices, 2010, 57, 2794-2800.	1.6	5

#	ARTICLE	IF	CITATIONS
2278	High-Sensitivity Tracking of MOSFET Damage Using Dynamic-Mode Transient Measurements. IEEE Transactions on Instrumentation and Measurement, 2010, 59, 1734-1742.	2.4	5
2279	Characterization of a power bipolar transistor as high-dose dosimeter for 1.9–2.2 MeV electron beams. Radiation Physics and Chemistry, 2010, 79, 513-518.	1.4	0
2280	Silicon detectors for the SLHC—An overview of recent RD50 results. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2010, 624, 396-400.	0.7	9
2281	Doping compensation for increased robustness of fast recovery silicon diodes. Microelectronics Reliability, 2010, 50, 32-38.	0.9	3
2282	Deep level transient spectroscopy on charge traps in high-k ZrO ₂ . Thin Solid Films, 2010, 518, 6382-6384.	0.8	8
2283	Effect of illumination intensity on cell parameters of a silicon solar cell. Solar Energy Materials and Solar Cells, 2010, 94, 1473-1476.	3.0	138
2284	Scanning Probe Microscope based Deep-Level Spectroscopy of semiconductor films. Ultramicroscopy, 2010, 110, 655-658.	0.8	4
2285	A technique for recording and analyzing the isothermal relaxation of the capacitance of semiconductor heterostructures. Instruments and Experimental Techniques, 2010, 53, 430-433.	0.1	2
2286	Electrical Characterization of Deep Trap Properties in High- k Thin-Film HfO ₂ . Chinese Physics Letters, 2010, 27, 077102.	1.3	2
2287	AlGaAs/GaAs Photovoltaic Cells with InGaAs Quantum Dots. Advances in Science and Technology, 0, , .	0.2	15
2288	DLTS Studies of Al Diffused n-Si. Key Engineering Materials, 2010, 442, 393-397.	0.4	0
2289	Direct-search deep level photothermal spectroscopy: An enhanced reliability method for overlapped semiconductor defect state characterization. Applied Physics Letters, 2010, 96, .	1.5	9
2290	Effect of Au contamination on the electrical characteristics of a “model”-small-angle grain boundary in n-type direct silicon bonded wafer. Journal of Applied Physics, 2010, 108, 053719.	1.1	8
2291	Deep level transient spectroscopy in plasma-assisted molecular beam epitaxy grown Al _{0.2} Ga _{0.8} N/GaN interface and the rapid thermal annealing effect. Applied Physics Letters, 2010, 97, .	1.5	29
2292	Time-dependent defect spectroscopy for characterization of border traps in metal-oxide-semiconductor transistors. Physical Review B, 2010, 82, .	1.1	136
2293	Influence of background concentration induced field on the emission rate signatures of an electron trap in zinc oxide Schottky devices. Journal of Applied Physics, 2010, 107, .	1.1	8
2294	Measuring temperature-dependent activation energy in thermally activated processes: A 2D Arrhenius plot method. Review of Scientific Instruments, 2010, 81, 033910.	0.6	32
2295	Study of electric field enhanced emission rates of an electron trap in n-type GaN grown by hydride vapor phase epitaxy. Journal of Applied Physics, 2010, 108, 103708.	1.1	15

#	ARTICLE	IF	CITATIONS
2296	Growth of Gallium Arsenide. , 0, , 43-71.		1
2297	Nitrogen Related Electron Trap with High Capture Cross Section in n-Type GaAsN Grown by Chemical Beam Epitaxy. Applied Physics Express, 2010, 3, 051002.	1.1	18
2298	Defect characterization by admittance spectroscopy techniques based on temperature-rate duality. , 2010, , .		0
2299	Nitrogen-Related Recombination Center in GaAsN Grown by Chemical Beam Epitaxy. Japanese Journal of Applied Physics, 2010, 49, 051001.	0.8	13
2300	The Development of Semi-Insulating Silicon Substrates for Microwave Devices. Journal of the Electrochemical Society, 2010, 157, H540.	1.3	7
2301	Cathodoluminescence Microcharacterization of Radiative Recombination Centers in Lifetime-Controlled Insulated Gate Bipolar Transistors. Japanese Journal of Applied Physics, 2010, 49, 04DP15.	0.8	7
2302	Properties of a Nitrogen-Related Hole Trap Acceptor-Like State in p-Type GaAsN Grown by Chemical Beam Epitaxy. Japanese Journal of Applied Physics, 2010, 49, 121001.	0.8	13
2303	Effects of Gold Diffusion on n-Type Doping of GaAs Nanowires. Nano Letters, 2010, 10, 4584-4589.	4.5	47
2304	Oxide traps in MOS transistors: Semi-automatic extraction of trap parameters from time dependent defect spectroscopy. , 2010, , .		2
2305	Capacitance Spectroscopy on Self-Assembled Quantum Dots. Nanoscience and Technology, 2010, , 51-77.	1.5	0
2306	Defects. , 2010, , 169-307.		2
2307	Electrical properties of self-assembled InAs/InAlAs quantum dots on InP. Semiconductor Science and Technology, 2010, 25, 065011.	1.0	3
2308	Developing a high volume manufacturing method to eliminate P Buried Layer implant defects. , 2010, , .		0
2309	Spatially-discriminating trap characterization methods for HEMTs and their application to RF-stressed AlGaIn/GaN HEMTs. , 2010, , .		30
2310	Coordinated electrical characterization system for photovoltaic devices. , 2010, , .		0
2311	A modular system of Deep Level Transient Spectroscopy. , 2011, , .		0
2312	Towards printable organic thin film transistor based flash memory devices. Journal of Materials Chemistry, 2011, 21, 5203.	6.7	133
2313	Infrared absorption and admittance spectroscopy of Ge quantum dots on a strained SiGe layer. Semiconductor Science and Technology, 2011, 26, 125002.	1.0	5

#	ARTICLE	IF	CITATIONS
2314	Negative Differential Resistance Devices and Circuits. , 2011, , 176-241.		27
2315	Distinguishing bulk traps and interface states in deep-level transient spectroscopy. Journal Physics D: Applied Physics, 2011, 44, 305303.	1.3	23
2317	NIEL Scaling: Comparison With Measured Defect Introduction Rate in Silicon. IEEE Transactions on Nuclear Science, 2011, 58, 756-763.	1.2	16
2318	Transport in Metal-Oxide-Semiconductor Structures. Engineering Materials, 2011, , .	0.3	41
2319	A New Method to Measure Trap Characteristics of Silicon Solar Cells. Chinese Physics Letters, 2011, 28, 028801.	1.3	3
2320	Electrical characterization of Au/n-GaN metal-insulator-semiconductor and Au/SiO ₂ /n-GaN metal-insulator-semiconductor structures. Journal of Alloys and Compounds, 2011, 509, 8001-8007.	2.8	75
2321	Pulsed laser processing of electrodeposited CuInSe ₂ ; Photovoltaic absorber thin films. , 2011, , .		3
2322	Voltage modulated electro-luminescence spectroscopy to understand negative capacitance and the role of sub-bandgap states in light emitting devices. Journal of Applied Physics, 2011, 110, .	1.1	17
2323	The MOS Oxide and Its Defects. Engineering Materials, 2011, , 17-28.	0.3	0
2324	Structure and Properties of Dislocations in Silicon. , 0, , .		7
2325	Nonlinear characterization and modeling of dispersive effects in high-frequency power transistors. , 0, , 206-256.		3
2326	Radiation-hard silicon for LH-LHC trackers. Journal of Instrumentation, 2011, 6, C12035-C12035.	0.5	3
2327	Signature of a back contact barrier in DLTS spectra. Journal of Applied Physics, 2011, 109, .	1.1	22
2328	Determination of Defect Densities in High Electron Mobility Transistors Using Current Transient DLTS. , 2011, , .		0
2329	Tin-vacancy complex in germanium. Journal of Applied Physics, 2011, 109, .	1.1	27
2330	Properties of ultrafast laser textured silicon for photovoltaics. Solar Energy Materials and Solar Cells, 2011, 95, 2745-2751.	3.0	53
2331	Influence of deep level defects on the performance of crystalline silicon solar cells: Experimental and simulation study. Solar Energy Materials and Solar Cells, 2011, 95, 2805-2810.	3.0	22
2332	Current transport mechanisms and deep level transient spectroscopy of Au/n-Si Schottky barrier diodes. Microelectronic Engineering, 2011, 88, 3353-3359.	1.1	28

#	ARTICLE	IF	CITATIONS
2333	Detection of traps induced and activated by high field stress in an N-channel VDMOSFET transistor using current deep level transient spectroscopy (CDLTS). <i>Microelectronic Engineering</i> , 2011, 88, 3333-3337.	1.1	1
2334	Simultaneous measurement of carrier density and mobility of organic semiconductors using capacitance techniques. <i>Organic Electronics</i> , 2011, 12, 1879-1885.	1.4	53
2335	Electron transport through molecular junctions. <i>Physics Reports</i> , 2011, 509, 1-87.	10.3	161
2336	A Current-Transient Methodology for Trap Analysis for GaN High Electron Mobility Transistors. <i>IEEE Transactions on Electron Devices</i> , 2011, 58, 132-140.	1.6	394
2337	Monte Carlo Simulation of Leakage Currents in $\text{TiN}/\text{ZrO}_2/\text{TiN}$ Capacitors. <i>IEEE Transactions on Electron Devices</i> , 2011, 58, 327-334.	1.6	36
2338	Extraction of Trap Densities in ZnO Thin-Film Transistors and Dependence on Oxygen Partial Pressure During Sputtering of ZnO Films. <i>IEEE Transactions on Electron Devices</i> , 2011, 58, 3018-3024.	1.6	24
2339	The QD-Flash: a quantum dot-based memory device. <i>Semiconductor Science and Technology</i> , 2011, 26, 014026.	1.0	81
2340	Electrically active defects in SiC Schottky barrier diodes. <i>Materials Science-Poland</i> , 2011, 29, 70-75.	0.4	1
2341	A Comment to the paper by E.A. Tatokhin, A.V. Kadantsev, A.E. Bormontov, and V.G. Zadorozhniy – a statistical method of deep-level transient spectroscopy in semiconductors. <i>Semiconductors</i> , 2011, 45, 832-834.	0.2	0
2342	Transient spectroscopy of Rykkin's \pm centers. <i>Semiconductors</i> , 2011, 45, 857-860.	0.2	0
2343	Admittance spectroscopy as a method for investigating relaxation processes in quantum-sized heterostructures. <i>Bulletin of the Russian Academy of Sciences: Physics</i> , 2011, 75, 1406-1412.	0.1	5
2344	A deep level transient spectroscopy study on the interface states across grain boundaries in multicrystalline silicon. <i>Physica Status Solidi - Rapid Research Letters</i> , 2011, 5, 277-279.	1.2	7
2345	Electrical characterisation of deep level defects in Be-doped AlGaAs grown on (100) and (311)A GaAs substrates by MBE. <i>Nanoscale Research Letters</i> , 2011, 6, 180.	3.1	9
2346	Contactless electrical defect characterization in semiconductors by microwave detected photo induced current transient spectroscopy (MDP-ICTS) and microwave detected photoconductivity (MDP). <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2011, 208, 769-776.	0.8	24
2347	Nickel-related defects in ZnO – A deep level transient spectroscopy and photo-capacitance study. <i>Physica Status Solidi (B): Basic Research</i> , 2011, 248, 1949-1955.	0.7	5
2348	Electronic Transport in Organic Materials: Comparison of Band Theory with Percolation/(Variable) Tj ETQq1 1 0.784314 rgBT /Overlock 11.1 124	11.1	124
2350	Double carriers pulse DLTS for the characterization of electron-hole recombination process in GaAsN grown by chemical beam epitaxy. <i>Physica B: Condensed Matter</i> , 2011, 406, 1070-1075.	1.3	19
2351	Molybdenum and low-temperature annealing of a silicon power P-i-n diode. <i>Microelectronics Reliability</i> , 2011, 51, 566-571.	0.9	1

#	ARTICLE	IF	CITATIONS
2352	A recombination center in p-type GaAsN grown by chemical beam epitaxy. <i>Solar Energy Materials and Solar Cells</i> , 2011, 95, 281-283.	3.0	6
2353	High-speed and low-voltage performance in a charge-trapping flash memory using a NiO tunnel junction. <i>Journal Physics D: Applied Physics</i> , 2011, 44, 155105.	1.3	6
2354	Optically-aligned visible/near-infrared dual-band photodetector materials and devices on GaAs using metamorphic epitaxy. <i>Journal of Applied Physics</i> , 2011, 110, .	1.1	24
2355	Electrochemical isothermal-capacitance-transient spectroscopy: A new depth profiling method of deep levels. <i>Review of Scientific Instruments</i> , 2011, 82, 093905.	0.6	0
2356	CuIn(Ga)Se ₂ based thin film solar cells with electrodeposited absorber on flexible steel foils. , 2011, , .		0
2357	Analysis of leakage current mechanisms in Pt/Au Schottky contact on Ga-polarity GaN by Frenkel-Poole emission and deep level studies. <i>Journal of Applied Physics</i> , 2011, 110, .	1.1	43
2358	Capacitance-voltage and deep-level-transient spectroscopy characterization of defects near SiO ₂ /SiC interfaces. <i>Journal of Applied Physics</i> , 2011, 109, .	1.1	52
2359	Defect levels in the epitaxial and polycrystalline CuGaSe ₂ by photocurrent and capacitance methods. <i>Journal of Applied Physics</i> , 2011, 110, 103711.	1.1	24
2360	Effects of irradiation and annealing on deep levels in rhodium-doped p-GaAs grown by metal-organic chemical-vapor deposition. <i>Journal of Applied Physics</i> , 2011, 109, 113705.	1.1	0
2361	Electronic properties and deep level transient spectroscopy of CdS/CdTe thin film solar cells. <i>Chinese Physics B</i> , 2011, 20, 037103.	0.7	6
2362	Deep level transient spectroscopic study of oxygen implanted melt grown ZnO single crystal. <i>Semiconductor Science and Technology</i> , 2011, 26, 095016.	1.0	4
2363	Origin Investigation of a Nitrogen-Related Recombination Center in GaAsN Grown by Chemical Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 051001.	0.8	14
2364	Deep level defects in GaAs _{1-x} Bix/GaAs heterostructures. <i>Semiconductor Science and Technology</i> , 2011, 26, 055020.	1.0	17
2365	Deep Level Defects in 4H-SiC Schottky Diodes Examined by DLTS. <i>Solid State Phenomena</i> , 0, 178-179, 366-371.	0.3	1
2366	Deep Energy Levels Formed by Se Implantation in Si. <i>Chinese Physics Letters</i> , 2011, 28, 036108.	1.3	5
2367	Antimony-based quantum dot memories. <i>Proceedings of SPIE</i> , 2011, , .	0.8	8
2368	Determination of bandgap states in p-type In _{0.49} Ga _{0.51} P grown on SiGe/Si and GaAs by deep level optical spectroscopy and deep level transient spectroscopy. <i>Journal of Applied Physics</i> , 2011, 109, 063709.	1.1	9
2369	Deep levels in H-irradiated GaAs _{1-x} N _x (x<math>\leq 0.01</math>) grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2011, 110, .	1.1	11

#	ARTICLE	IF	CITATIONS
2370	Optical detection of deep electron traps in poly(<i>p</i> -phenylene vinylene) light-emitting diodes. Applied Physics Letters, 2011, 99, .	1.5	16
2371	Isothermal depolarization current spectroscopy of localized states in metal oxide varistors. Journal Physics D: Applied Physics, 2012, 45, 465305.	1.3	6
2372	Investigation of deep-level defects in conductive polymer on n-type 4H- and 6H-silicon carbide substrates using I-V and deep level transient spectroscopy techniques. Journal of Applied Physics, 2012, 112, .	1.1	14
2373	Effects of Sacrifice Oxidation on Characterization of Defects in High-Purity Semi-Insulating 4H-SiC by Discharge Current Transient Spectroscopy. Materials Science Forum, 0, 717-720, 271-274.	0.3	0
2374	Electrical Characterisation of Defects in Polycrystalline B-Doped Diamond Films. Materials Science Forum, 0, 717-720, 1315-1318.	0.3	2
2375	Investigation of Additional States in the Silicon Carbide Surface after Diffusion Welding. Materials Science Forum, 0, 717-720, 275-278.	0.3	0
2376	Interface studies on high-k/GaAs MOS capacitors by deep level transient spectroscopy. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, .	0.6	9
2377	Investigation of vertically trapped charge locations in Cr-doped-SrTiO ₃ -based charge trapping memory devices. Journal of Applied Physics, 2012, 112, 074505.	1.1	1
2378	Semi-quantitative analysis of the depth distribution of radiative recombination centers in silicon power devices by cross-sectional cathodoluminescence. Journal of Applied Physics, 2012, 112, 033507.	1.1	8
2379	Parameterisation of injection-dependent lifetime measurements in semiconductors in terms of Shockley-Read-Hall statistics: An application to oxide precipitates in silicon. Journal of Applied Physics, 2012, 111, .	1.1	106
2380	Annealing dynamics of irradiation-induced defects in high-purity silicon in the presence of hydrogen. Physical Review B, 2012, 85, .	1.1	7
2381	Low frequency parasitic effects in RF transistors and their impact on power amplifier performances. , 2012, , .		7
2382	A deep acceptor defect responsible for the yellow luminescence in GaN and AlGaN. Journal of Applied Physics, 2012, 111, .	1.1	47
2383	Sidewall GaAs tunnel junctions fabricated using molecular layer epitaxy. Science and Technology of Advanced Materials, 2012, 13, 013002.	2.8	3
2384	Effect of Thermal Stress on a N-Related Recombination Center in GaAsN Grown by Chemical Beam Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 02BP02.	0.8	1
2385	Electron Emission Properties of GaAsN/GaAs Quantum Well Containing N-Related Localized States: The Influence of Illuminance. Japanese Journal of Applied Physics, 2012, 51, 02BJ12.	0.8	2
2386	DLTS of p-type Czochralski Si wafers containing processing-induced macropores. Semiconductor Science and Technology, 2012, 27, 015013.	1.0	6
2387	A new approach for surface state modelling using charge pumping technique in submicron TMOS. International Journal of Surface Science and Engineering, 2012, 6, 35.	0.4	0

#	ARTICLE	IF	CITATIONS
2388	Theory of charging and charge transport in "intermediate" thickness dielectrics and its implications for characterization and reliability. Journal of Applied Physics, 2012, 111, .	1.1	29
2389	Effects of hydrogen, oxygen, and argon annealing on the electrical properties of ZnO and ZnO devices studied by current-voltage, deep level transient spectroscopy, and Laplace DLTS. Journal of Applied Physics, 2012, 111, 094504.	1.1	29
2390	On the microscopic origin of the frequency dependence of hole trapping in pMOSFETs. , 2012, , .		22
2391	Study of point defects in ns pulsed-laser annealed CuInSe2 thin films. , 2012, , .		0
2392	Deep levels in InGaAsN/GaAs and InGaAs/GaAs heterojunctions. , 2012, , .		0
2393	Experimental study of surface distortions in silicon carbide caused by diffusion welding. , 2012, , .		0
2394	A Q-DLTS investigation of aluminum nitride surface termination. Journal of Materials Research, 2012, 27, 1198-1204.	1.2	11
2395	Linking structural and electronic properties of high-purity self-assembled GaSb/GaAs quantum dots. Physical Review B, 2012, 86, .	1.1	35
2396	Defect levels in low-doped 4H-SiC Schottky barrier diodes detected by using alpha particles. , 2012, , .		0
2397	Iodine irradiation induced defects in crystalline silicon. , 2012, , .		0
2398	Donor-Based Single Electron Pumps with Tunable Donor Binding Energy. Nano Letters, 2012, 12, 763-768.	4.5	41
2399	Characterization of deep level defects in sublimation grown p-type 6H-SiC epilayers by deep level transient spectroscopy. Physica B: Condensed Matter, 2012, 407, 3041-3043.	1.3	1
2400	A contribution to the identification of the E5 defect level as tri-vacancy (V3). Physica B: Condensed Matter, 2012, 407, 3013-3015.	1.3	4
2401	Laplace deep level transient spectroscopy: Embodiment and evolution. Physica B: Condensed Matter, 2012, 407, 3026-3030.	1.3	13
2402	Electronic properties of dislocations introduced mechanically at room temperature on a single crystal silicon surface. Physica B: Condensed Matter, 2012, 407, 3034-3037.	1.3	3
2403	Investigation of electronic trap states in organic photovoltaic materials by current-based deep level transient spectroscopy. Applied Physics Letters, 2012, 100, 263304.	1.5	31
2404	Tailoring the Absorption Properties of Black Silicon. Energy Procedia, 2012, 27, 480-484.	1.8	11
2407	Detection of Cytochrome c with Calixarenes Incorporated into Supported Lipid Membranes Via Charge Transient Measurements. Procedia Chemistry, 2012, 6, 60-68.	0.7	1

#	ARTICLE	IF	CITATIONS
2408	Dual roles of doping and trapping of semiconductor defect levels and their ramification to thin film photovoltaics. <i>Journal of Applied Physics</i> , 2012, 111, 104509.	1.1	13
2409	Modeling of high-frequency capacitance-voltage characteristics to quantify trap distributions near SiO ₂ /SiC interfaces. <i>Journal of Applied Physics</i> , 2012, 111, .	1.1	12
2410	Determination of conduction band offset between strained CdSe and ZnSe layers using deep level transient spectroscopy. <i>Applied Physics Letters</i> , 2012, 100, .	1.5	7
2411	Determination of detrapping times in semiconductor detectors. <i>Journal of Instrumentation</i> , 2012, 7, P04006-P04006.	0.5	11
2412	An Aluminum Nitride-based chemical sensor using Q-DLTS. <i>Diamond and Related Materials</i> , 2012, 23, 72-75.	1.8	1
2413	Photoconductivity and Transient Spectroscopy. <i>Springer Series in Materials Science</i> , 2012, , 333-365.	0.4	0
2414	Analysis of electronic carrier traps in Cr-SrTiO ₃ -based charge trap flash memory devices. <i>Applied Physics Letters</i> , 2012, 100, 243501.	1.5	5
2415	Effect of doping on electronic states in B-doped polycrystalline CVD diamond films. <i>Semiconductor Science and Technology</i> , 2012, 27, 065019.	1.0	9
2416	Deep Level Saturation Spectroscopy. <i>International Journal of Optics</i> , 2012, 2012, 1-16.	0.6	1
2417	Unification of trap-limited electron transport in semiconducting polymers. <i>Nature Materials</i> , 2012, 11, 882-887.	13.3	395
2418	Low cost high-efficiency amorphous silicon solar cells with improved light-soaking stability. <i>Solar Energy Materials and Solar Cells</i> , 2012, 98, 277-282.	3.0	37
2419	Extended deep level defects in Ge-condensed SiGe-on-Insulator structures fabricated using proton and helium implantations. <i>Thin Solid Films</i> , 2012, 520, 5593-5596.	0.8	1
2420	Electrical characterisation of ruthenium Schottky contacts on n-Ge (100). <i>Physica B: Condensed Matter</i> , 2012, 407, 1570-1573.	1.3	4
2421	Theory and Modeling of Oxide Semiconductors. <i>Semiconductors and Semimetals</i> , 2013, 88, 1-37.	0.4	8
2423	Defect-induced performance degradation of 4H-SiC Schottky barrier diode particle detectors. <i>Journal of Applied Physics</i> , 2013, 113, .	1.1	32
2424	Experimental Study of Defect Formations in GaAs Devices Using Gain, Photoluminescence and Deep Level Transient Spectroscopy. <i>IEEE Transactions on Nuclear Science</i> , 2013, 60, 219-223.	1.2	1
2426	Electronic surface properties of SrTiO ₃ derived from a surface photovoltage study. <i>Surface Science</i> , 2013, 612, 1-9.	0.8	10
2427	The identification, characterization and mitigation of defect states in organic photovoltaic devices: a review and outlook. <i>Energy and Environmental Science</i> , 2013, 6, 3414.	15.6	124

#	ARTICLE	IF	CITATIONS
2428	Electrically active centers formed in silicon during the high-temperature diffusion of boron and aluminum. <i>Semiconductors</i> , 2013, 47, 289-291.	0.2	2
2429	Defect formation in Cu(In,Ga)Se ₂ thin films due to the presence of potassium during growth by low temperature co-evaporation process. <i>Journal of Applied Physics</i> , 2013, 114, .	1.1	80
2430	800-meV localization energy in GaSb/GaAs/Al _{0.3} Ga _{0.7} As quantum dots. <i>Applied Physics Letters</i> , 2013, 102, .	1.5	38
2431	Deep level defects in Ga- and N-polarity GaN grown by molecular beam epitaxy on si(111). <i>Journal of Crystal Growth</i> , 2013, 378, 299-302.	0.7	7
2432	Electrically active sodium-related defect centres in silicon. <i>Semiconductor Science and Technology</i> , 2013, 28, 105010.	1.0	7
2433	Transient photoresponse in amorphous In-Ga-Zn-O thin films under stretched exponential analysis. <i>Journal of Applied Physics</i> , 2013, 113, .	1.1	41
2434	Deep Levels Characterization in GaN HEMTs—Part II: Experimental and Numerical Evaluation of Self-Heating Effects on the Extraction of Traps Activation Energy. <i>IEEE Transactions on Electron Devices</i> , 2013, 60, 3176-3182.	1.6	46
2435	Deep level defects in n-type GaAsBi and GaAs grown at low temperatures. <i>Journal of Applied Physics</i> , 2013, 113, .	1.1	43
2436	Electrical characterization of the AlInB _{0.5} N heterostructures by capacitance methods. <i>Applied Surface Science</i> , 2013, 269, 175-179.	3.1	7
2437	Transport Properties of Molecular Junctions. <i>Springer Tracts in Modern Physics</i> , 2013, , .	0.1	22
2438	A donor-like trap at the InGa _{0.5} N/GaN interface with net negative polarization and its possible consequence on internal quantum efficiency. <i>Semiconductor Science and Technology</i> , 2013, 28, 105021.	1.0	12
2439	Photo-Excited Charge Collection Spectroscopy. <i>SpringerBriefs in Physics</i> , 2013, , .	0.2	4
2440	Materials and Reliability Handbook for Semiconductor Optical and Electron Devices. , 2013, , .		42
2441	Synthesis and electrophysical characteristics of VO ₂ -based nanostructures with a complicated architecture on a silicon surface. <i>Russian Journal of General Chemistry</i> , 2013, 83, 1586-1588.	0.3	2
2442	Influence of device self-heating on trap activation energy extraction. , 2013, , .		2
2443	Analysis of MIS equivalent electrical circuit of Au/Pd/Ti-SiO ₂ -GaAs structure based on DLTS measurements. <i>Materials Science-Poland</i> , 2013, 31, 446-453.	0.4	1
2444	540-meV Hole Activation Energy for GaSb/GaAs Quantum Dot Memory Structure Using AlGaAs Barrier. <i>IEEE Electron Device Letters</i> , 2013, 34, 759-761.	2.2	10
2445	A new method to analyze closely spaced deep defect levels caused by multiexponential transients. , 2013, , .		0

#	ARTICLE	IF	CITATIONS
2446	Improved 750 °C epitaxial crystal silicon solar cells through impurity reduction. , 2013, , .		1
2447	Advanced characterization of oxide traps: The dynamic time-dependent defect spectroscopy. , 2013, , .		38
2448	In Situ Investigation of Current Transport Across Pt/n-Si (100) Schottky Junction During 100 \$hbox{MeV Ni}^{+7}\$ Ion Irradiation. IEEE Transactions on Device and Materials Reliability, 2013, 13, 98-102.	1.5	20
2449	Capacitanceâ€“voltage and currentâ€“voltage characteristics for the study of high background doping and conduction mechanisms in GaAsN grown by chemical beam epitaxy. Journal of Alloys and Compounds, 2013, 552, 469-474.	2.8	6
2450	Effects of pulsed laser annealing on deep level defects in electrochemically-deposited and furnace annealed CuInSe2 thin films. Thin Solid Films, 2013, 531, 566-571.	0.8	9
2451	Classification of Defective Regions in p-type Multicrystalline Silicon by Comparing Luminescence Images Measured under Different Conditions. Energy Procedia, 2013, 38, 101-107.	1.8	3
2452	Energy level(s) of the dissociation product of the 1.014â€“eV photoluminescence copper center in n-type silicon determined by photoluminescence and deep-level transient spectroscopy. Journal of Applied Physics, 2013, 114, 033508.	1.1	3
2453	Effect of electron and proton irradiation on recombination centers inÂGaAsN grown by chemical beam epitaxy. Current Applied Physics, 2013, 13, 1269-1274.	1.1	10
2454	Lattice-matched InGaAs on InP thermophovoltaic cells. Semiconductor Science and Technology, 2013, 28, 015013.	1.0	17
2455	An experimental analysis of illumination intensity and temperature dependency of photovoltaic cell parameters. Applied Energy, 2013, 111, 374-382.	5.1	186
2456	Failure Analysis of Semiconductor Optical Devices. , 2013, , 19-53.		2
2457	Radiation damage in n-type silicon diodes after electron irradiation with energies between 1.5MeV and 15MeV. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2013, 730, 84-90.	0.7	20
2458	Interface trap characterization of atomic layer deposition Al2O3/GaN metal-insulator-semiconductor capacitors using optically and thermally based deep level spectroscopies. Journal of Applied Physics, 2013, 113, .	1.1	44
2459	Electrical Properties, Reliability Issues, and ESD Robustness of InGaN-Based LEDs. Topics in Applied Physics, 2013, , 197-229.	0.4	4
2460	The structural, electronic and optical properties of GaSb/GaAs nanostructures for charge-based memory. Journal Physics D: Applied Physics, 2013, 46, 264001.	1.3	44
2461	Deep Level Transient Spectroscopy (DLTS) on Colloidal-Synthesized Nanocrystal Solids. ACS Applied Materials & Interfaces, 2013, 5, 2915-2919.	4.0	41
2462	Direct-current and radio-frequency characteristics of passivated AlGaN/GaN/Si high electron mobility transistors. Current Applied Physics, 2013, 13, 1359-1364.	1.1	12
2463	GalnAs(Sb) Long-Wavelength VCSELs. Springer Series in Optical Sciences, 2013, , 353-377.	0.5	4

#	ARTICLE	IF	CITATIONS
2464	Investigation of ion beam induced radiation damage in Si PN diodes. Nuclear Instruments & Methods in Physics Research B, 2013, 306, 176-180.	0.6	6
2465	Impact of varied sulfur incorporation on the device performance of sequentially processed Cu(In,Ga)(Se,S) ₂ thin film solar cells. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 1392-1399.	0.8	38
2466	Effects of radiation-induced defects on the charge collection efficiency of a silicon carbide particle detector. , 2013, , .		0
2467	Spectroscopic study of polysilicon traps by means of fast capacitance transients. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, 01A110.	0.6	7
2468	Effects of deep-level dopants on the electronic potential of thin Si <i>pn</i> junctions observed by Kelvin probe force microscope. Applied Physics Letters, 2013, 102, .	1.5	22
2469	Native defects in MBE-grown CdTe. , 2013, , .		0
2470	Regenerative feedback resonant circuit to detect transient changes in electromagnetic properties of semi-insulating materials. Review of Scientific Instruments, 2013, 84, 084703.	0.6	6
2471	New Results on the Electrical Activity of <i>3d</i>-Transition Metal Impurities in Silicon. Solid State Phenomena, 2013, 205-206, 245-254.	0.3	2
2472	Digitized Multi-Exponential Deep-Level Transient Spectroscopy (DLTS) Using the PadÃ©-Laplace Algorithm. Advanced Materials Research, 2013, 710, 575-578.	0.3	0
2473	Charge Coupled Devices as Particle Detectors. Advances in High Energy Physics, 2013, 2013, 1-12.	0.5	5
2474	Materials for Future Quantum Dot-Based Memories. Journal of Nanomaterials, 2013, 2013, 1-6.	1.5	27
2475	Temperature-independent slow carrier emission from deep-level defects in p-type germanium. Journal Physics D: Applied Physics, 2013, 46, 425101.	1.3	2
2476	Defects Related to Sb-Mediated Ge Quantum Dots. Solid State Phenomena, 0, 205-206, 497-501.	0.3	0
2477	GaAsN Grown by Chemical Beam Epitaxy for Solar Cell Application. , 2013, , .		1
2478	Trap levels in the atomic layer deposition-ZnO/GaN heterojunctionâ€™Thermal admittance spectroscopy studies. Journal of Applied Physics, 2013, 113, .	1.1	9
2479	Broad defect depth distribution in germanium substrates induced by CF4 plasma. Applied Physics Letters, 2013, 103, .	1.5	3
2480	Electrical characterisation and predictive simulation of defects induced by keV Si-implantation in n-type Si. Journal of Applied Physics, 2013, 113, 184508.	1.1	5
2481	Investigation of deep levels in bulk GaN material grown by halide vapor phase epitaxy. Journal of Applied Physics, 2013, 114, .	1.1	36

#	ARTICLE	IF	CITATIONS
2482	Pentacene Schottky diodes studied by impedance spectroscopy: Doping properties and trap response. Physical Review B, 2013, 88, .	1.1	65
2483	Electron and hole deep levels related to Sb-mediated Ge quantum dots embedded in n-type Si, studied by deep level transient spectroscopy. Applied Physics Letters, 2013, 102, 232106.	1.5	4
2484	Effects of sodium incorporation in Co-evaporated Cu ₂ ZnSnSe ₄ thin-film solar cells. Applied Physics Letters, 2013, 102, .	1.5	125
2485	Deep-level transient spectroscopy of interfacial states in "buffer-free" p-i-n GaSb/GaAs devices. Journal of Applied Physics, 2013, 114, 134507.	1.1	12
2486	Defect states in hybrid solar cells consisting of Sb ₂ S ₃ quantum dots and TiO ₂ nanoparticles. Applied Physics Letters, 2013, 103, 023901.	1.5	20
2487	III-V Materials for Super-High Efficiency Multi Junction Solar Cells. Japanese Journal of Applied Physics, 2013, 52, 08JH11.	0.8	1
2488	Measurements and simulations of the turn-off behaviour of diodes with deep energy levels of Se implanted in Si. , 2013, , .		1
2489	The analysis of filling pulse parameters influence on ICTS data of GaAs MIS structures. Proceedings of SPIE, 2013, , .	0.8	0
2490	Interface trap evaluation of Pd/Al ₂ O ₃ /GaN metal oxide semiconductor capacitors and the influence of near-interface hydrogen. Applied Physics Letters, 2013, 103, 201607.	1.5	54
2491	Study of point defects in ns pulsed-laser annealed CuInSe ₂ thin films. , 2013, , .		2
2492	Investigation of deep-level defects in InGaAsN/GaAs 3xQWs structures grown by AP-MOVPE. , 2013, , .		2
2493	Electronic Properties and Density of States of Self-Assembled GaSb/GaAs Quantum Dots. Journal of Nanotechnology, 2013, 2013, 1-5.	1.5	2
2494	Comparing Spreading Resistance Profiling and C-V characterisation to identify defects in silicon sensors. Journal of Instrumentation, 2013, 8, C02018-C02018.	0.5	0
2495	A model for arsenic anti-site incorporation in GaAs grown by hydride vapor phase epitaxy. Journal of Applied Physics, 2014, 116, .	1.1	8
2496	Direct estimation of capture cross sections in the presence of slow capture: application to the identification of quenched-in deep-level defects in Ge. Semiconductor Science and Technology, 2014, 29, 125007.	1.0	7
2497	Emission of photoexcited charge carriers from InAs/GaAs quantum dots grown by gas-phase epitaxy. JETP Letters, 2014, 100, 156-161.	0.4	10
2498	Integrated-differential method of thermal spectroscopy of energy levels in semiconductors by their charge trap. Russian Microelectronics, 2014, 43, 581-586.	0.1	0
2500	Charge transition levels of Mn-doped Si calculated with the GGA-1/2 method. Physical Review B, 2014, 90, .	1.1	10

#	ARTICLE	IF	CITATIONS
2501	DLTS Investigations of (Ga,In)(N,As)/GaAs Quantum Wells before and after Rapid Thermal Annealing. Acta Physica Polonica A, 2014, 126, 1195-1198.	0.2	4
2502	The Si Nanocrystal Trap Center Studied by Deep Level Transient Spectroscopy (DLTS). Journal of Nanomaterials, 2014, 2014, 1-6.	1.5	5
2503	Surface defect states in MBE-grown CdTe layers. , 2014, , .		1
2504	H ⁺ implantation profile formation in m:Cz and Fz silicon. , 2014, , .		2
2505	Fourier spectrum based extraction of an equivalent trap state density in indium gallium zinc oxide transistors. Applied Physics Letters, 2014, 104, 203505.	1.5	1
2506	Defects study in IR SWIR HgCdTe photodetectors using DLTS. , 2014, , .		0
2507	Multi layer precursor method for Cu(In,Ga)Se ₂ solar cells fabricated on flexible substrates. Japanese Journal of Applied Physics, 2014, 53, 05FW03.	0.8	7
2508	Field dependent emission rates in radiation damaged GaAs. Journal of Applied Physics, 2014, 116, .	1.1	10
2509	Photoelectric activity of defects in La-doped layered TlInS ₂ crystals. Low Temperature Physics, 2014, 40, 830-836.	0.2	7
2510	Impact of strain on electronic defects in (Mg,Zn)O thin films. Journal of Applied Physics, 2014, 116, .	1.1	3
2511	Interaction of Sn atoms with defects introduced by ion implantation in Ge substrate. Journal of Applied Physics, 2014, 115, .	1.1	4
2512	Radiation-induced defects in GaN bulk grown by halide vapor phase epitaxy. Applied Physics Letters, 2014, 105, .	1.5	21
2513	Intensity dependency of photovoltaic cell parameters under high illumination conditions: An analysis. Applied Energy, 2014, 133, 356-362.	5.1	74
2514	Light-assisted recharging of graphene quantum dots in fluorographene matrix. Journal of Applied Physics, 2014, 116, 134310.	1.1	6
2515	Effect of Z1/2, EH5, and Ci1 deep defects on the performance of n-type 4H-SiC epitaxial layers Schottky detectors: Alpha spectroscopy and deep level transient spectroscopy studies. Journal of Applied Physics, 2014, 115, .	1.1	40
2516	Defect studies on Ar-implanted ZnO thin films. Physica Status Solidi (B): Basic Research, 2014, 251, 937-941.	0.7	1
2517	Study of deep hole trap levels associated with bias-induced metastabilities in Cu(In,Ga)Se ₂ thin films using isothermal capacitance transient spectroscopy. Journal of Applied Physics, 2014, 115, 054507.	1.1	4
2518	Traps signature in steady state current-voltage characteristics of organic diode. Journal of Applied Physics, 2014, 115, .	1.1	22

#	ARTICLE	IF	CITATIONS
2519	TCAD-based DLTS simulation for analysis of extended defects. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 136-142.	0.8	5
2520	Deep-level transient spectroscopy characterization of In(Ga)As quantum dots fabricated using Bi as a surfactant. Japanese Journal of Applied Physics, 2014, 53, 06JG11.	0.8	0
2521	Effect of surface morphology on the density of energy states in GaAsN grown by chemical beam epitaxy. Japanese Journal of Applied Physics, 2014, 53, 04ER08.	0.8	2
2522	Shallow carrier traps in hydrothermal ZnO crystals. New Journal of Physics, 2014, 16, 083040.	1.2	12
2523	Trap characterization of microwave GaN HEMTs based on frequency dispersion of the output-admittance. , 2014, , .		3
2524	Trap characterization of microwave GaN HEMTs based on frequency dispersion of the output-admittance. , 2014, , .		9
2525	Investigation of low leakage current radiation detectors on n-type 4H-SiC epitaxial layers. , 2014, , .		0
2526	Spectroscopy of Technological Defects in Si Solar Cells by Analysis of Temperature Dependent Generation Currents. Medziagotyra, 2014, 20, .	0.1	0
2527	Postsynthetic Doping Control of Nanocrystal Thin Films: Balancing Space Charge to Improve Photovoltaic Efficiency. Chemistry of Materials, 2014, 26, 153-162.	3.2	34
2528	Photo-induced current transient spectroscopy of the ferroelectric-semiconductor TlGaSe ₂ . Physics of the Solid State, 2014, 56, 335-340.	0.2	7
2529	25th Anniversary Article: Charge Transport and Recombination in Polymer Light-Emitting Diodes. Advanced Materials, 2014, 26, 512-531.	11.1	194
2530	Deep-level transient spectroscopy on an amorphous InGaZnO ₄ Schottky diode. Applied Physics Letters, 2014, 104, 082112.	1.5	24
2531	A fast slewing cryostat for small sample in vacuo electrical/optical testing in the range 30 K–500 K. Review of Scientific Instruments, 2014, 85, 013903.	0.6	1
2532	Characterization of the deep levels responsible for non-radiative recombination in InGaN/GaN light-emitting diodes. Applied Physics Letters, 2014, 104, .	1.5	49
2533	Mapping Defect Density in MBE Grown $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ Epitaxial Layers on Si Substrate Using Esaki Diode Valley Characteristics. IEEE Transactions on Electron Devices, 2014, 61, 2049-2055.	1.6	13
2534	Investigation of deep level defects in electron irradiated indium arsenide quantum dots embedded in a gallium arsenide matrix. Materials Science in Semiconductor Processing, 2014, 25, 76-83.	1.9	9
2535	On the capability of deep level transient spectroscopy for characterizing multi-crystalline silicon. Journal of Applied Physics, 2014, 115, .	1.1	3
2536	Using Room Temperature Current Noise To Characterize Single Molecular Spectra. ACS Nano, 2014, 8, 2111-2117.	7.3	5

#	ARTICLE	IF	CITATIONS
2537	Deep traps and temperature effects on the capacitance of p-type Si-doped GaAs Schottky diodes on (211) and (311) oriented GaAs substrates. Superlattices and Microstructures, 2014, 65, 319-331.	1.4	9
2538	Solar Cell Efficiency Losses Due to Impurities From the Crucible in Multicrystalline Silicon. IEEE Journal of Photovoltaics, 2014, 4, 122-129.	1.5	32
2539	Study of deep levels in InAlAsSb grown via organometallic vapor phase epitaxy. , 2014, , .		0
2540	Basics of MIS-type gas sensors with thin nanoporous silicon. , 2014, , .		5
2541	Dislocation-related trap levels in nitride-based light emitting diodes. Applied Physics Letters, 2014, 104, .	1.5	17
2542	Optimization of the selenium field-stop profile with respect to softness and robustness. , 2014, , .		3
2543	A Fast Technique to Screen Carrier Generation Lifetime Using DLTS on MOS Capacitors. IEEE Transactions on Electron Devices, 2014, 61, 3282-3288.	1.6	5
2544	Photoelectric activity of structural defects of a single crystal of the ferroelectric-semiconductor TlInS ₂ : La. Physics of the Solid State, 2014, 56, 1605-1609.	0.2	12
2545	Toward a physical understanding of the reliability-limiting E _{tr} >C</inf>-0.57 eV trap in GaN HEMTs. , 2014, , .		4
2546	Depth profiles of the nickel donor center in p-type silicon diffused with dilute nickel measured by deep-level transient spectroscopy. Japanese Journal of Applied Physics, 2014, 53, 091301.	0.8	4
2548	Gigahertz single-trap electron pumps in silicon. Nature Communications, 2014, 5, 5038.	5.8	59
2549	Impact of nanostructures and radiation environment on defect levels in III–V solar cells. , 2014, , .		2
2550	Interface engineering for efficient and stable chemical-doping-free graphene-on-silicon solar cells by introducing a graphene oxide interlayer. Journal of Materials Chemistry A, 2014, 2, 16877-16883.	5.2	93
2551	Modeling of capacitance transients of thin-film solar cells: A valuable tool to gain information on perturbing layers or interfaces. Applied Physics Letters, 2014, 104, 053502.	1.5	8
2552	Determination of In Situ Trap Properties in CCDs Using a "Single-Trap Pumping" Technique. IEEE Transactions on Nuclear Science, 2014, 61, 1826-1833.	1.2	48
2554	Identification of nitrogen- and host-related deep-level traps in n-type GaNAs and their evolution upon annealing. Journal of Applied Physics, 2014, 116, 013705.	1.1	12
2555	Electrical characterization of nanocrystal solids. Journal of Materials Chemistry C, 2014, 2, 3172-3184.	2.7	22
2556	Investigation of Cu(In,Ga)Se ₂ absorber by time-resolved photoluminescence for improvement of its photovoltaic performance. Solar Energy Materials and Solar Cells, 2014, 130, 567-572.	3.0	32

#	ARTICLE	IF	CITATIONS
2557	Using ellipsometry with lock-in detection to measure activation energy of ion diffusion in ionic and mixed conductors. <i>Solid State Ionics</i> , 2014, 264, 7-16.	1.3	4
2558	AC characterization of bulk organic solar cell in the dark and under illumination. <i>Applied Surface Science</i> , 2014, 312, 176-181.	3.1	1
2559	GaSb quantum dots on GaAs with high localization energy of 710 meV and an emission wavelength of 1.3 μm . <i>Journal of Crystal Growth</i> , 2014, 404, 48-53.	0.7	11
2560	Correlation of Deep Levels With Detector Performance in 4H-SiC Epitaxial Schottky Barrier Alpha Detectors. <i>IEEE Transactions on Nuclear Science</i> , 2014, 61, 2338-2344.	1.2	40
2561	On the process of hole trapping in Ge/Si heterostructures with Ge quantum dots. <i>Semiconductors</i> , 2014, 48, 1036-1040.	0.2	4
2562	Near-interfacial thermal donor generation during processing of (100)Si/low- $\hat{\nu}$ Si-oxycarbide insulator structures revealed by electron spin resonance. <i>Semiconductor Science and Technology</i> , 2014, 29, 095008.	1.0	0
2563	Effect of antimony on the deep-level traps in GaInNAsSb thin films. <i>Applied Physics Letters</i> , 2014, 105, .	1.5	11
2564	Effect of crystal orientation in Cu(In,Ga)Se ₂ fabricated by multi-layer precursor method on its cell performance. <i>Applied Surface Science</i> , 2014, 314, 845-849.	3.1	5
2565	The role of continuous and discrete water structures in protein function. <i>European Physical Journal: Special Topics</i> , 2014, 223, 915-926.	1.2	7
2566	Molecular Beam Epitaxy of Ultra-High-Quality AlGaAs/GaAs Heterostructures: Enabling Physics in Low-Dimensional Electronic Systems. <i>Annual Review of Condensed Matter Physics</i> , 2014, 5, 347-373.	5.2	97
2567	Defect levels in Cu ₂ ZnSn(SxSe _{1-x}) ₄ solar cells probed by current-mode deep level transient spectroscopy. <i>Applied Physics Letters</i> , 2014, 104, .	1.5	39
2568	Electrical properties of deuteron irradiated high resistivity silicon. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2014, 325, 107-114.	0.6	11
2569	Investigation of the relative density of deep defects in Cu(In,Ga)Se ₂ thin films dependent on Ga content by transient photocapacitance method. <i>Japanese Journal of Applied Physics</i> , 2014, 53, 068008.	0.8	12
2570	Characterization of deep electron traps in 4H-SiC Junction Barrier Schottky rectifiers. <i>Solid-State Electronics</i> , 2014, 94, 56-60.	0.8	37
2571	Low rate deep level transient spectroscopy - a powerful tool for defect characterization in wide bandgap semiconductors. <i>Solid-State Electronics</i> , 2014, 92, 40-46.	0.8	8
2572	Numerical simulation of the response of substrate traps to a voltage applied to the gate of a gallium arsenide field effect transistor. <i>Materials Science in Semiconductor Processing</i> , 2014, 24, 34-39.	1.9	0
2573	Effect of hydrogen at room temperature on electronic and mechanical properties of dislocations in silicon. <i>Materials Letters</i> , 2014, 120, 236-238.	1.3	7
2574	Zinc oxide thin films on silicon carbide substrates (ZnO/SiC): electro-optical properties and electrically active defects. <i>Semiconductor Science and Technology</i> , 2014, 29, 045021.	1.0	14

#	ARTICLE	IF	CITATIONS
2575	Correlation between barrier inhomogeneities of 4H-SiC 1A/600V Schottky rectifiers and deep-level defects revealed by DLTS and Laplace DLTS. Solid-State Electronics, 2014, 99, 1-6.	0.8	16
2576	Electrical characterization by thermal activation. , 0, , 168-195.		0
2577	Isochronal annealing on n-type 4H-SiC epitaxial schottky barriers and investigation of defect levels by deep level transient spectroscopy. , 2014, , .		1
2578	Highlighting trapping phenomena in microwave GaN HEMTs by low-frequency <i>S</i> -parameters. International Journal of Microwave and Wireless Technologies, 2015, 7, 287-296.	1.5	17
2579	Direct nm-scale spatial mapping of traps in CIGS. , 2015, , .		0
2580	Improvement of S-factor method for evaluation of MOS interface state density. Japanese Journal of Applied Physics, 2015, 54, 04DC07.	0.8	2
2581	Intensity- and Temperature-Dependent Carrier Recombination in $\ln\text{AsS}$ Schottky Diodes. Physical Review Applied, 2015, 3, .	1.5	45
2582	Characterization of defect levels in undoped n-BaSi ₂ epitaxial films on Si(111) by deep-level transient spectroscopy. Japanese Journal of Applied Physics, 2015, 54, 07JE01.	0.8	11
2583	Electrical and Optical Defect Evaluation Techniques for Electronic and Solar Grade Silicon. Lecture Notes in Physics, 2015, , 129-180.	0.3	2
2584	A comprehensive study of the impact of dislocation loops on leakage currents in Si shallow junction devices. Journal of Applied Physics, 2015, 118, .	1.1	10
2585	DLTS analysis of amphoteric interface defects in high-TiO ₂ MOS structures prepared by sol-gel spin-coating. AIP Advances, 2015, 5, .	0.6	19
2586	Analysis of effect of gate oxidation at SiC MOS interface on threshold-voltage shift using deep-level transient spectroscopy. Japanese Journal of Applied Physics, 2015, 54, 04DP05.	0.8	2
2587	Capacitance Transient Spectroscopy Measurements on High-k Metal Gate Field Effect Transistors Fabricated Using 28nm Technology Node. Solid State Phenomena, 0, 242, 459-465.	0.3	1
2588	Deep level transient spectroscopy in III-Nitrides: Decreasing the effects of series resistance. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2015, 33, .	0.6	48
2589	Dielectric properties of semi-insulating silicon at microwave frequencies. Applied Physics Letters, 2015, 107, .	1.5	19
2590	Point defect states in Sb-doped germanium. Journal of Applied Physics, 2015, 118, 155702.	1.1	13
2591	Injection deep level transient spectroscopy: An improved method for measuring capture rates of hot carriers in semiconductors. Journal of Applied Physics, 2015, 118, 015703.	1.1	3
2592	Diffusion and Point Defects in Silicon Materials. Lecture Notes in Physics, 2015, , 1-67.	0.3	2

#	ARTICLE	IF	CITATIONS
2593	Electronic levels in silicon MaWCE nanowires: evidence of a limited diffusion of Ag. Nanotechnology, 2015, 26, 425702.	1.3	4
2594	Electrically Active and Inactive Single Grain Boundaries in Semiconducting BaTiO ₃ . Journal of the American Ceramic Society, 2015, 98, 3243-3249.	1.9	5
2595	Electronic structure. , 0, , 86-116.		0
2596	Photoluminescence Characterization of Nonradiative Recombination Centers in Light Emitting Materials by Utilizing Below-Gap Excitation: A Mini Review of Two-Wavelength Excited Photoluminescence. Rajshahi University Journal of Science and Engineering, 0, 43, 1-9.	1.0	0
2597	Deep Level Transient Spectroscopy: A Powerful Experimental Technique for Understanding the Physics and Engineering of Photo-Carrier Generation, Escape, Loss and Collection Processes in Photovoltaic Materials. , 2015, , .		1
2598	Correlation Between Epitaxial Layer Quality and Drain Current Stability of GaN/AlGaN/GaN Heterostructure Field-Effect Transistors. IEEE Transactions on Electron Devices, 2015, 62, 1440-1447.	1.6	9
2599	Deep traps in GaN-based structures as affecting the performance of GaN devices. Materials Science and Engineering Reports, 2015, 94, 1-56.	14.8	191
2600	Electronic properties of manganese impurities in germanium. Journal Physics D: Applied Physics, 2015, 48, 175101.	1.3	3
2601	A study on III-nitride recessed-gate field-effect transistors using a remote-oxygen-plasma treatment. Semiconductor Science and Technology, 2015, 30, 045010.	1.0	1
2602	Influence of surface pre-treatment on the electronic levels in silicon MaWCE nanowires. Nanotechnology, 2015, 26, 195705.	1.3	7
2603	Material science and device physics in SiC technology for high-voltage power devices. Japanese Journal of Applied Physics, 2015, 54, 040103.	0.8	790
2604	Spatially Resolved Impurity Identification via Temperature- and Injection-Dependent Photoluminescence Imaging. IEEE Journal of Photovoltaics, 2015, 5, 1503-1509.	1.5	20
2605	Defect analysis of sputter grown cupric oxide for optical and electronics application. Journal Physics D: Applied Physics, 2015, 48, 495104.	1.3	18
2606	Test simulation of neutron damage to electronic components using accelerator facilities. Nuclear Instruments & Methods in Physics Research B, 2015, 365, 294-299.	0.6	2
2607	Depth-Resolved Imaging of Radiation-Induced Doping Changes in Silicon. ECS Journal of Solid State Science and Technology, 2015, 4, P462-P467.	0.9	3
2608	Excess noise and deep levels in GaAs detectors of nuclear particles and ionizing radiation. Journal of Communications Technology and Electronics, 2015, 60, 517-542.	0.2	5
2609	Investigations on Al _x Ga _{1-x} As Solar Cells Grown by MOVPE. IEEE Journal of Photovoltaics, 2015, 5, 446-453.	1.5	39
2610	Long range annealing of defects in germanium by low energy plasma ions. Physica D: Nonlinear Phenomena, 2015, 297, 56-61.	1.3	33

#	ARTICLE	IF	CITATIONS
2611	Detection of dislocation-related midgap levels in pulsed laser deposited GaN by photo-induced current transient spectroscopy. <i>Physica Status Solidi (B): Basic Research</i> , 2015, 252, 800-803.	0.7	2
2612	Hole traps associated with high-concentration residual carriers in p-type GaAsN grown by chemical beam epitaxy. <i>Journal of Applied Physics</i> , 2015, 117, .	1.1	2
2613	Effects of surface ligands on energetic disorder and charge transport of P3HT: CdSe hybrid solar cells. <i>Physica Status Solidi (B): Basic Research</i> , 2015, 252, 1325-1333.	0.7	5
2614	Development of diagnostic method for deep levels in semiconductors using charge induced by heavy ion microbeams. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2015, 348, 240-245.	0.6	5
2615	Semiclassical simulation of trap-assisted tunneling in GaN-based light-emitting diodes. <i>Journal of Computational Electronics</i> , 2015, 14, 444-455.	1.3	34
2616	Impact of tungsten contamination on the sensing margin of a CMOS image sensor cell. <i>Japanese Journal of Applied Physics</i> , 2015, 54, 016501.	0.8	2
2617	Using light and heat to controllably switch and reset disorder configuration in nanoscale devices. <i>Physical Review B</i> , 2015, 91, .	1.1	6
2618	Analytical Techniques for Electrically Active Defect Detection. <i>Semiconductors and Semimetals</i> , 2015, 91, 205-250.	0.4	22
2619	230% room-temperature storage time and 1.14% eV hole localization energy in In _{0.5} Ga _{0.5} As quantum dots on a GaAs interlayer in GaP with an AlP barrier. <i>Applied Physics Letters</i> , 2015, 106, .	1.5	23
2620	First-principles determination of defect energy levels through hybrid density functionals and GW. <i>Journal of Physics Condensed Matter</i> , 2015, 27, 133202.	0.7	47
2621	Investigation of the effects of gamma radiation on the electrical properties of dilute GaAs _{1-x} N _x layers grown by Molecular Beam Epitaxy. <i>Current Applied Physics</i> , 2015, 15, 1230-1237.	1.1	14
2622	Nanoscale determinant to brighten up GaN:Eu red light-emitting diode: Local potential of Eu-defect complexes. <i>Journal of Applied Physics</i> , 2015, 117, 155307.	1.1	17
2623	Measuring complex for analysis of recombination deep traps in semiconductor solar cells. , 2015, , .		2
2624	Identification of N-H related acceptor defects in GaAsN grown by chemical beam epitaxy using hydrogen isotopes. <i>Journal of Alloys and Compounds</i> , 2015, 649, 815-818.	2.8	2
2625	Electrochemical Spectroscopic Methods for the Fine Band Gap Electronic Structure Mapping in Organic Semiconductors. <i>Journal of Physical Chemistry C</i> , 2015, 119, 15926-15934.	1.5	42
2626	Design and optimization of GaAs photovoltaic converter for laser power beaming. <i>Infrared Physics and Technology</i> , 2015, 71, 144-150.	1.3	31
2627	Correlation of a generation-recombination center with a deep level trap in GaN. <i>Applied Physics Letters</i> , 2015, 106, .	1.5	20
2628	Identification of deep trap energies and influences of oxygen plasma ashing on semiconductor carrier lifetime. <i>Semiconductor Science and Technology</i> , 2015, 30, 035004.	1.0	1

#	ARTICLE	IF	CITATIONS
2629	Characterization of transport properties of organic semiconductors using impedance spectroscopy. <i>Journal of Materials Science: Materials in Electronics</i> , 2015, 26, 4463-4474.	1.1	17
2630	Point Defects in GaN. <i>Semiconductors and Semimetals</i> , 2015, , 315-367.	0.4	14
2631	Deep level transient spectroscopy on light-emitting diodes based on (In,Ga)N/GaN nanowire ensembles. <i>Proceedings of SPIE</i> , 2015, , .	0.8	2
2632	Analysis of the photocurrent relaxation in semi-insulating GaAs in the temperature range of 150â€“200 K. <i>Semiconductors</i> , 2015, 49, 285-289.	0.2	3
2633	Double acceptor in p-type GaAsN grown by chemical beam epitaxy. <i>Journal of Crystal Growth</i> , 2015, 432, 45-48.	0.7	1
2634	Physical properties of Cu(In,Ga)Se ₂ film on flexible stainless steel substrate for solar cell application: A multi-layer precursor method. <i>Solar Energy Materials and Solar Cells</i> , 2015, 143, 510-516.	3.0	13
2635	The Efficiency of Hydrogen-Doping as a Function of Implantation Temperature. <i>Solid State Phenomena</i> , 0, 242, 175-183.	0.3	0
2636	Interface State Artefact in Long Gate-Length AlGaIn/GaN HEMTs. <i>IEEE Transactions on Electron Devices</i> , 2015, 62, 2464-2469.	1.6	21
2637	Characterization of deep level defects and thermally stimulated depolarization phenomena in La-doped TlInS ₂ layered semiconductor. <i>Journal of Applied Physics</i> , 2015, 117, .	1.1	13
2638	High-performance organic/inorganic hybrid heterojunction based on Gallium Arsenide (GaAs) substrates and a conjugated polymer. <i>Applied Surface Science</i> , 2015, 357, 2189-2197.	3.1	11
2639	Direct nm-Scale Spatial Mapping of Traps in CIGS. <i>IEEE Journal of Photovoltaics</i> , 2015, 5, 1482-1486.	1.5	32
2640	Study of the development of defects in Si PIN diodes exposed to 23 GeV/c protons. <i>Journal of Instrumentation</i> , 2015, 10, P03021-P03021.	0.5	0
2641	Surface passivation and isochronal annealing studies on n-type 4H-SiC epitaxial layer. <i>Proceedings of SPIE</i> , 2015, , .	0.8	0
2642	Estimation of open-circuit voltage of Cu(In,Ga)Se ₂ solar cells before cell fabrication. <i>Renewable Energy</i> , 2015, 76, 575-581.	4.3	8
2643	Phononâ€“assisted tunnel emission of holes from the double donor level of the EL2 defect. <i>Physica Status Solidi (B): Basic Research</i> , 2016, 253, 1916-1922.	0.7	2
2644	Defect levels in Cu(In,Ga)Se ₂ studied using capacitance and photocurrent techniques. <i>Journal of Physics Condensed Matter</i> , 2016, 28, 215801.	0.7	10
2645	Flexible Cu(In,Ga)Se ₂ solar cell on stainless steel substrate deposited by multiâ€“layer precursor method: its photovoltaic performance and deepâ€“level defects. <i>Progress in Photovoltaics: Research and Applications</i> , 2016, 24, 990-1000.	4.4	35
2646	Deep-level transient spectroscopy at platinum/titanium-dioxide hydrogen sensors. <i>Physica Status Solidi (B): Basic Research</i> , 2016, 253, 690-696.	0.7	2

#	ARTICLE	IF	CITATIONS
2647	Electronic properties of defects in high-fluence electron-irradiated bulk GaN. <i>Physica Status Solidi (B): Basic Research</i> , 2016, 253, 521-526.	0.7	3
2648	Photonic nanostructures for advanced light trapping in silicon solar cells: the impact of etching on the material electronic quality. <i>Physica Status Solidi - Rapid Research Letters</i> , 2016, 10, 158-163.	1.2	10
2649	Effect of deep native defects on ultrasound propagation in TlInS ₂ layered crystal. <i>Physica B: Condensed Matter</i> , 2016, 497, 86-92.	1.3	6
2651	Deep level traps in GaN LEDs grown by metal organic vapour phase epitaxy on an 8 inch Si(111) substrate. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 060306.	0.8	6
2652	Vanadium interactions in crystalline silicon. <i>Physical Review B</i> , 2016, 94, .	1.1	10
2653	Origin and annealing of deep-level defects in GaNAs grown by metalorganic vapor phase epitaxy. <i>Journal of Applied Physics</i> , 2016, 119, .	1.1	9
2654	Electrical characterization of dry and wet processed interface layer in Ge/High-K devices. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2016, 34, 021203.	0.6	3
2655	Photocapacitance spectroscopy of InAlN nearly lattice-matched to GaN. <i>Applied Physics Letters</i> , 2016, 109, .	1.5	4
2656	Semiconductor steady state defect effective Fermi level and deep level transient spectroscopy depth profiling. <i>Journal of Semiconductors</i> , 2016, 37, 092003.	2.0	2
2657	Comparative study of defect levels in GaInNAs, GaNAsSb, and GaInNAsSb for high-efficiency solar cells. <i>Applied Physics Letters</i> , 2016, 108, .	1.5	13
2658	Identifying the source of reduced performance in 1-stage-grown Cu(In, Ga)Se ₂ solar cells. , 2016, , .		3
2659	Transport Effects on Capacitance-Frequency Analysis for Defect Characterization in Organic Photovoltaic Devices. <i>Physical Review Applied</i> , 2016, 6, .	1.5	36
2660	Deep levels in as-grown and electron-irradiated n-type GaN studied by deep level transient spectroscopy and minority carrier transient spectroscopy. <i>Journal of Applied Physics</i> , 2016, 119, .	1.1	8
2661	A physical model for the reverse leakage current in (In,Ga)N/GaN light-emitting diodes based on nanowires. <i>Journal of Applied Physics</i> , 2016, 119, .	1.1	33
2662	Recombination centers resulting from reactions of hydrogen and oxygen in n-type Czochralski silicon. , 2016, , .		4
2663	Design and manufacture of hardware and software platform of universal measurement complex for research of deep level defects in semiconductors. , 2016, , .		0
2664	Transformation of the nickel donor center by annealing in silicon measured by deep-level transient spectroscopy. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 011302.	0.8	1
2665	Donor and double-donor transitions of the carbon vacancy related EH6 ⁷ deep level in 4H-SiC. <i>Journal of Applied Physics</i> , 2016, 119, .	1.1	16

#	ARTICLE	IF	CITATIONS
2666	Study of GaP/Si Heterojunction Solar Cells. Energy Procedia, 2016, 102, 56-63.	1.8	22
2667	Study of defects in polycrystalline CdTe using DLTS. , 2016, , .		6
2668	Migration processes of the As interstitial in GaAs. Journal of Applied Physics, 2016, 120, .	1.1	15
2669	Detection of electron emission as DLTS signal in CdTe solar cells. Journal of Applied Physics, 2016, 120, .	1.1	2
2670	Impact of the Ga/In ratio on defects in Cu(In, Ga)Se ₂ . , 2016, , .		7
2671	Anneal induced transforms of radiation defects in heavily electron irradiated Si diodes. Journal of Instrumentation, 2016, 11, P09004-P09004.	0.5	3
2672	GaSb on GaAs interfacial misfit solar cells. , 2016, , .		3
2673	Temperature dependent dielectric studies of Al/Dy ₂ O ₃ /porous Si heterostructure by capacitance and conductance measurements. Journal of Alloys and Compounds, 2016, 685, 28-33.	2.8	6
2674	Effect of ramping on oxygen precipitates and Cu-vacancy complex in Czochralski silicon. Journal of Crystal Growth, 2016, 445, 53-57.	0.7	0
2675	Deep Levels in n-Type 4H-Silicon Carbide Epitaxial Layers Investigated by Deep-Level Transient Spectroscopy and Isochronal Annealing Studies. IEEE Transactions on Nuclear Science, 2016, 63, 1083-1090.	1.2	22
2676	Deep level traps in semi-polar GaN grown on patterned sapphire substrate by metalorganic vapor phase epitaxy. Physica Status Solidi (B): Basic Research, 2016, 253, 2225-2229.	0.7	5
2677	Optical and Electrical Study of Defects in GaN In Situ Doped with Eu ³⁺ Ion Grown by OMVPE. Journal of Electronic Materials, 2016, 45, 6355-6362.	1.0	4
2678	Characterization of high pressure hydrogen annealing effect on polysilicon channel field effect transistors using isothermal deep level trap spectroscopy. , 2016, , .		2
2679	Chapter 1 Purity Requirements for Silicon in Photovoltaic Applications. , 2016, , 1-48.		0
2680	Enhanced Electrical Resistivity and Properties via Ion Bombardment of Ferroelectric Thin Films. Advanced Materials, 2016, 28, 10750-10756.	11.1	52
2681	Oxidation-Induced Deep Levels in GaN. $\frac{1}{n} - \frac{1}{n_0} = \frac{1}{n_0} \left(\frac{N_D}{N_A} - 1 \right) \left(\frac{N_D}{N_A} + 1 \right)$ and $\frac{1}{p} - \frac{1}{p_0} = \frac{1}{p_0} \left(\frac{N_A}{N_D} - 1 \right) \left(\frac{N_A}{N_D} + 1 \right)$	1.5	9
2682	Defect visualization of Cu(InGa)(SeS) ₂ thin films using DLTS measurement. Scientific Reports, 2016, 6, 30554.	1.6	22
2683	Hole localization energy of 1.18 eV in GaSb quantum dots embedded in GaP. Physica Status Solidi (B): Basic Research, 2016, 253, 1877-1881.	0.7	10

#	ARTICLE	IF	CITATIONS
2684	Nondestructive interface state measurement by pulse photoconductivity method. Surface and Interface Analysis, 2016, 48, 1244-1247.	0.8	1
2685	Local deep level transient spectroscopy using super-higher-order scanning nonlinear dielectric microscopy. Microelectronics Reliability, 2016, 64, 566-569.	0.9	8
2686	Deep level study of Mg-doped GaN using deep level transient spectroscopy and minority carrier transient spectroscopy. Physical Review B, 2016, 94, .	1.1	12
2688	Deep level defects in dilute GaAsBi alloys grown under intense UV illumination. Semiconductor Science and Technology, 2016, 31, 085014.	1.0	9
2689	Amorphous silica containers for germanium ultrapurification by zone refining. Inorganic Materials, 2016, 52, 1091-1095.	0.2	2
2690	Choice of quantum dot materials for fabricating memory devices with longer storage and faster writing of information. Superlattices and Microstructures, 2016, 100, 1042-1056.	1.4	7
2691	Study of deep levels in GaAs μ n structures. Semiconductors, 2016, 50, 924-928.	0.2	9
2692	Evolution of proton-induced defects in a cryogenically irradiated p-channel CCD. , 2016, , .		0
2693	Local mapping of interface traps using contactless capacitance transient technique. AIP Advances, 2016, 6, 105004.	0.6	0
2694	Investigation of the Influence of Deep-Level Defects on the Conversion Efficiency of Si-based Solar Cells. MRS Advances, 2016, 1, 911-916.	0.5	5
2695	Proposal of local deep level transient spectroscopy using super-higher-order scanning nonlinear dielectric microscopy and 2-dimensional imaging of trap distribution in SiO ₂ /SiC interface. , 2016, , .		1
2696	Influence of precursor gas on SiGe epitaxial material quality in terms of structural and electrical defects. Japanese Journal of Applied Physics, 2016, 55, 04EJ11.	0.8	0
2697	A random telegraph signal in tunneling silicon μ n junctions with GeSi nanoislands. Technical Physics Letters, 2016, 42, 435-437.	0.2	0
2698	Mobility Enhancement in Solution-Processed Transparent Conductive Oxide TFTs due to Electron Donation from Traps in High- κ Gate Dielectrics. Advanced Functional Materials, 2016, 26, 955-963.	7.8	87
2699	Effect of interface and bulk traps on the C_V characterization of a LPCVD-SiN _x /AlGaIn/GaN metal-insulator-semiconductor structure. Semiconductor Science and Technology, 2016, 31, 065014.	1.0	19
2700	Investigation of the energy spectra and the electron-hole alignment of the InAs/GaAs quantum dots with an ultrathin cap layer. Solid State Communications, 2016, 240, 20-23.	0.9	3
2701	Ru-Induced Deep Levels in Ru/4H-SiC Epilayer Schottky Diodes by Deep Level Transient Spectroscopy. ECS Journal of Solid State Science and Technology, 2016, 5, P3078-P3081.	0.9	6
2702	Electrical properties of as-grown and proton-irradiated high purity silicon. Nuclear Instruments & Methods in Physics Research B, 2016, 380, 76-83.	0.6	14

#	ARTICLE	IF	CITATIONS
2703	The regularities of radiation defect formation at the interface metal -n-InP. , 2016, , .		0
2704	Investigation of electrically-active deep levels in single-crystalline diamond by particle-induced charge transient spectroscopy. Nuclear Instruments & Methods in Physics Research B, 2016, 372, 151-155.	0.6	3
2705	Defect charge states in Si doped hexagonal boron-nitride monolayer. Journal of Physics Condensed Matter, 2016, 28, 055501.	0.7	13
2706	Determination of Majority Carrier Capture Rates via Deep Level Transient Spectroscopy. ECS Journal of Solid State Science and Technology, 2016, 5, P3041-P3047.	0.9	1
2707	Temperature dependent dielectric studies of Ni/n-GaP Schottky diodes by capacitance and conductance measurements. Materials Science in Semiconductor Processing, 2016, 42, 378-382.	1.9	48
2708	Valence band offset at the Si/SiSn interface by applying deep level transient spectroscopy. Nanotechnology, 2016, 27, 075705.	1.3	1
2709	Resistive switching effect and traps in partially fluorinated graphene films. Journal Physics D: Applied Physics, 2016, 49, 095303.	1.3	16
2710	Material requirements for the adoption of unconventional silicon crystal and wafer growth techniques for high efficiency solar cells. Progress in Photovoltaics: Research and Applications, 2016, 24, 122-132.	4.4	24
2711	Charge collection efficiency degradation induced by MeV ions in semiconductor devices: Model and experiment. Nuclear Instruments & Methods in Physics Research B, 2016, 372, 128-142.	0.6	14
2712	Influence of As/group-III flux ratio on defects formation and photovoltaic performance of GaInNAs solar cells. Solar Energy Materials and Solar Cells, 2016, 149, 213-220.	3.0	32
2713	Correlation between electrical parameters and defect states of polythiophene:fullerene based solar cell. Thin Solid Films, 2016, 614, 16-24.	0.8	3
2714	Review "Defect Identification with Positron Annihilation Spectroscopy in Narrow Band Gap Semiconductors. ECS Journal of Solid State Science and Technology, 2016, 5, P3166-P3171.	0.9	7
2715	Capacitive Properties of MIS Structures with SiO _x and Si _x O _y N _z Films Containing Si Nanoclusters. Journal of Nano Research, 2016, 39, 162-168.	0.8	3
2716	Bi-induced acceptor level responsible for partial compensation of native free electron density in InP _{1-x} Bi _x dilute bismide alloys. Journal Physics D: Applied Physics, 2016, 49, 115107.	1.3	14
2717	Study of Defects in GaN In Situ Doped with Eu ³⁺ Ion Grown by OMVPE. Journal of Electronic Materials, 2016, 45, 2001-2007.	1.0	4
2718	A charge-based deep level transient spectroscopy measurement system and characterization of a ZnO-based varistor and a Fe-doped SrTiO ₃ dielectric. Japanese Journal of Applied Physics, 2016, 55, 026601.	0.8	9
2719	Influence of EL2 deep level on photoconduction of semi-insulating GaAs under ultrashort pulse photoinjection. Laser Physics Letters, 2016, 13, 025301.	0.6	1
2720	Identification of intrinsic deep level defects responsible for electret behavior in TiGaSe ₂ layered semiconductor. Physica B: Condensed Matter, 2016, 483, 82-89.	1.3	13

#	ARTICLE	IF	CITATIONS
2721	Deep levels in silicon-oxide oxygen superlattices. <i>Semiconductor Science and Technology</i> , 2016, 31, 025015.	1.0	4
2722	Formation of Ni Diffusion-Induced Surface Traps in GaN/Al _x Ga _{1-x} N/GaN Heterostructures on Silicon Substrate During Gate Metal Deposition. <i>Journal of Electronic Materials</i> , 2016, 45, 493-498.	1.0	6
2723	Nuclear microprobe investigation of the effects of ionization and displacement damage in vertical, high voltage GaN diodes. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2017, 404, 264-268.	0.6	3
2724	Noise spectroscopy of nanowire structures: fundamental limits and application aspects. <i>Semiconductor Science and Technology</i> , 2017, 32, 043002.	1.0	29
2725	Deep-level spectroscopy in metal-insulator-semiconductor structures. <i>Journal Physics D: Applied Physics</i> , 2017, 50, 065104.	1.3	6
2726	Indirect excitons in hydrogen-doped ZnO. <i>Journal Physics D: Applied Physics</i> , 2017, 50, 115104.	1.3	3
2727	Energy conversion modeling of the intrinsic persistent luminescence of solids via energy transfer paths between transition levels. <i>Physical Chemistry Chemical Physics</i> , 2017, 19, 9457-9469.	1.3	8
2728	Deep traps in the ZnO nanorods/Si solar cells. <i>Journal of Alloys and Compounds</i> , 2017, 708, 247-254.	2.8	15
2729	MBE growth and doping of AlGaP. <i>Journal of Crystal Growth</i> , 2017, 466, 6-15.	0.7	3
2730	Nanoscale imaging and spectroscopy of band gap and defects in polycrystalline photovoltaic devices. <i>Nanoscale</i> , 2017, 9, 7771-7780.	2.8	23
2731	Reduction of interface traps between poly-Si and SiO ₂ layers through the dielectric recovery effect during delayed pulse bias stress. <i>Nanotechnology</i> , 2017, 28, 225702.	1.3	2
2732	Synaptic transistor with a reversible and analog conductance modulation using a Pt/HfO ₂ /n-IGZO memcapacitor. <i>Nanotechnology</i> , 2017, 28, 225201.	1.3	20
2733	Experimental evidences of charge transition levels in ZrO ₂ and at the Si: ZrO ₂ interface by deep level transient spectroscopy. <i>Applied Physics Letters</i> , 2017, 110, .	1.5	17
2734	Evidence of minority carrier traps contribution in deep level transient spectroscopy measurement in GaN Schottky diode. <i>Superlattices and Microstructures</i> , 2017, 101, 529-536.	1.4	4
2735	Identifying the Real Minority Carrier Lifetime in Nonideal Semiconductors: A Case Study of Kesterite Materials. <i>Advanced Energy Materials</i> , 2017, 7, 1700167.	10.2	106
2736	Electrical Properties, Reliability Issues, and ESD Robustness of InGaN-Based LEDs. <i>Topics in Applied Physics</i> , 2017, , 363-395.	0.4	1
2737	Degradation Mechanisms of Heterogeneous III-V/Silicon 1.55- μm DBR Laser Diodes. <i>IEEE Journal of Quantum Electronics</i> , 2017, 53, 1-8.	1.0	12
2738	Characterization of Defects in AlGaIn/GaN HEMTs Based on Nonlinear Microwave Current Transient Spectroscopy. <i>IEEE Transactions on Electron Devices</i> , 2017, 64, 2135-2141.	1.6	9

#	ARTICLE	IF	CITATIONS
2739	Defect generation in deep-UV AlGaIn-based LEDs investigated by electrical and spectroscopic characterisation. Proceedings of SPIE, 2017, , .	0.8	3
2740	Arsenic antistite and oxygen incorporation trends in GaAs grown by water-mediated close-spaced vapor transport. Journal of Applied Physics, 2017, 121, 093102.	1.1	5
2741	Role of Charge Traps in the Performance of Atomically Thin Transistors. Advanced Materials, 2017, 29, 1605598.	11.1	46
2742	The carrier transport mechanism and band offset at the interface of ZnO/n-Si(111) heterojunction. Journal of Electron Spectroscopy and Related Phenomena, 2017, 217, 1-5.	0.8	2
2743	Influence of built-in charge on photogeneration and recombination processes in InAs/GaAs quantum dot solar cells. Journal Physics D: Applied Physics, 2017, 50, 165101.	1.3	5
2744	Deposition of CZTSe thin films and illumination effects on the device properties of Ag/n-Si/p-CZTSe/In heterostructure. Journal of Alloys and Compounds, 2017, 709, 337-343.	2.8	16
2745	Investigation of defects in indium doped TiO ₂ thin films using electrical and optical techniques. Journal of Alloys and Compounds, 2017, 698, 883-891.	2.8	16
2746	In Situ and Ex Situ Investigations of KF Postdeposition Treatment Effects on CIGS Solar Cells. IEEE Journal of Photovoltaics, 2017, 7, 665-669.	1.5	43
2747	Defect-Related Degradation of AlGaIn-Based UV-B LEDs. IEEE Transactions on Electron Devices, 2017, 64, 200-205.	1.6	62
2748	Effect of Cu ²⁺ doping on the structural, electronic and optical properties of ZnAl ₂ O ₄ : A combined experimental and DFT+ U study. Journal of Luminescence, 2017, 184, 7-16.	1.5	20
2749	Comparison of Gain Degradation and Deep Level Transient Spectroscopy in pnp Si Bipolar Junction Transistors Irradiated With Different Ion Species. IEEE Transactions on Nuclear Science, 2017, 64, 190-196.	1.2	2
2750	Investigation of electrically active defects in InGaAs quantum wire intermediate-band solar cells using deep-level transient spectroscopy technique. Nanotechnology, 2017, 28, 045707.	1.3	11
2751	Characterization of deep defects in boron-doped CVD diamond films using transient photocapacitance method. Materials Science in Semiconductor Processing, 2017, 70, 203-206.	1.9	5
2752	Local deep level transient spectroscopy using super-higher-order scanning nonlinear dielectric microscopy and its application to imaging two-dimensional distribution of SiO ₂ /SiC interface traps. Journal of Applied Physics, 2017, 122, .	1.1	21
2753	An open circuit voltage decay system for performing injection dependent lifetime spectroscopy. Review of Scientific Instruments, 2017, 88, 095105.	0.6	4
2754	Two-Dimensional Imaging of Trap Distribution in SiO ₂ /SiC Interface Using Local Deep Level Transient Spectroscopy Based on Super-Higher-Order Scanning Nonlinear Dielectric Microscopy. Materials Science Forum, 2017, 897, 127-130.	0.3	0
2755	Influence of PE-ALD of GaP on the Silicon Wafers Quality. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1700685.	0.8	2
2756	Simultaneous determination of defect distributions and energies near InGaIn/GaN quantum wells by capacitance-voltage measurement. Journal Physics D: Applied Physics, 2017, 50, 39LT03.	1.3	1

#	ARTICLE	IF	CITATIONS
2757	Deep-level defects in n-type GaAsBi alloys grown by molecular beam epitaxy at low temperature and their influence on optical properties. Scientific Reports, 2017, 7, 12824.	1.6	31
2758	Current-mode deep level transient spectroscopy of a semiconductor nanowire field-effect transistor. Journal of Applied Physics, 2017, 122, .	1.1	3
2759	On Deep Level Transient Spectroscopy of Extended Defects in n-Type 4H-SiC. Materials Science Forum, 0, 897, 201-204.	0.3	4
2760	Evaluation of the concentration of point defects in GaN. Scientific Reports, 2017, 7, 9297.	1.6	55
2761	High resolution characterizations of fine structure of semiconductor device and material using scanning nonlinear dielectric microscopy. Japanese Journal of Applied Physics, 2017, 56, 100101.	0.8	22
2762	Investigation of electrophysical characteristics of organic solar cells based on P3HT:PEDOT blend. , 2017, , .		0
2763	Long-term degradation of InGaN-based laser diodes: Role of defects. Microelectronics Reliability, 2017, 76-77, 584-587.	0.9	3
2764	Carbon-related defects in microelectronics. Microelectronics Reliability, 2017, 76-77, 145-148.	0.9	0
2765	Characterisation of defects generated during constant current InGaN-on-silicon LED operation. Microelectronics Reliability, 2017, 76-77, 561-565.	0.9	8
2766	Interface traps in 28nm node field effect transistors detected by capacitance transient spectroscopy. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1700182.	0.8	0
2767	Perspective and potential of smart optical materials. Smart Materials and Structures, 2017, 26, 093001.	1.8	26
2768	Capacitance spectroscopy of hole traps in high-resistance gallium-arsenide structures grown by liquid-phase epitaxy. Semiconductors, 2017, 51, 1485-1489.	0.2	1
2769	Photoexcited Muon Spin Spectroscopy: A New Method for Measuring Excess Carrier Lifetime in Bulk Silicon. Physical Review Letters, 2017, 119, 226601.	2.9	10
2770	Nanosecond microscopy of capacitance at SiO ₂ /4H-SiC interfaces by time-resolved scanning nonlinear dielectric microscopy. Applied Physics Letters, 2017, 111, .	1.5	23
2771	Oxygen- and photoresist-related interface states of 4H-SiC Schottky diode observed by deep-level transient spectroscopy. Journal of Applied Physics, 2017, 122, 094504.	1.1	4
2772	Delayed avalanche breakdown of high-voltage silicon diodes: Various structures exhibit different picosecond-range switching behavior. Journal of Applied Physics, 2017, 122, .	1.1	17
2773	Investigation of Deep-Level Defects Lateral Distribution in Active Layers of Multicrystalline Silicon Solar Cells. MRS Advances, 2017, 2, 3141-3146.	0.5	1
2774	Properties of a previously unobserved donor-related electrically active defect in Ge induced by alpha particle irradiation. Nuclear Instruments & Methods in Physics Research B, 2017, 406, 680-682.	0.6	1

#	ARTICLE	IF	CITATIONS
2775	Dynamic Electronic Junctions in Organic-Inorganic Hybrid Perovskites. Nano Letters, 2017, 17, 4831-4839.	4.5	26
2776	Effect of Growth Temperature on GaAs Solar Cells at High MOCVD Growth Rates. IEEE Journal of Photovoltaics, 2017, 7, 340-346.	1.5	34
2777	Deep-Level Characterization: Electrical and Optical Methods. Power Electronics and Power Systems, 2017, , 145-163.	0.6	1
2778	Elucidation of carrier trapping and emission mechanism in quantum dots for information storage applications. , 2017, , .		0
2779	Low-frequency noise versus deep level transient spectroscopy of InAs/GaSb superlattice mid-wavelength infrared detectors. , 2017, , .		0
2780	Defect-related temperature dependence of THz emission from GaAs/AlGaAs MQWs grown on off- and on-axis substrates. AIP Advances, 2017, 7, 125210.	0.6	3
2783	In situ trap properties in CCDs: the donor level of the silicon divacancy. Journal of Instrumentation, 2017, 12, P01025-P01025.	0.5	7
2784	Impact of the silicon substrate resistivity and growth condition on the deep levels in Ni-Au/AlN/Si MIS Capacitors. Semiconductor Science and Technology, 2017, 32, 105002.	1.0	3
2785	Wide injection range OCVD system for lifetime spectroscopy techniques. , 2017, , .		0
2786	Capacitance characterization of GaP/n-Si structures grown by PE-ALD. Journal of Physics: Conference Series, 2017, 917, 052027.	0.3	1
2787	Evolution and Impact of Defects in a p-Channel CCD After Cryogenic Proton-Irradiation. IEEE Transactions on Nuclear Science, 2017, 64, 2814-2821.	1.2	7
2788	Toward Stationary Concentrator Photovoltaic Panels. , 2017, , .		1
2790	Fast C-V method to mitigate effects of deep levels in CIGS doping profiles. , 2017, , .		3
2791	Defect Characterization of III-V Quantum Structure Solar Cells Using Photo-Induced Current Transient Spectroscopy. , 2017, , .		0
2792	Deep Level Transient Spectroscopy and Pulse Height Measurements on High Resolution n-Type 4H-SiC Epitaxial Schottky Barrier Radiation Detectors. , 2017, , .		0
2793	Notice of Removal Effect of growth temperature on GaAs solar cells at high MOCVD growth rates. , 2017, , .		1
2794	Charge-Based Modeling of Radiation Damage in Symmetric Double-Gate MOSFETs. IEEE Journal of the Electron Devices Society, 2018, 6, 85-94.	1.2	24
2795	Evolution of traps in TiN/O ₃ -sourced Al ₂ O ₃ /GaN gate structures with thermal annealing temperature. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2018, 36, 022202.	0.6	3

#	ARTICLE	IF	CITATIONS
2796	Opto-electronic characterization of third-generation solar cells. <i>Science and Technology of Advanced Materials</i> , 2018, 19, 291-316.	2.8	91
2797	Defects in metal triiodide perovskite materials towards high-performance solar cells: origin, impact, characterization, and engineering. <i>Chemical Society Reviews</i> , 2018, 47, 4581-4610.	18.7	455
2798	Comparison of methods applied in photoinduced transient spectroscopy to determining the defect center parameters: The correlation procedure and the signal analysis based on inverse Laplace transformation. <i>Review of Scientific Instruments</i> , 2018, 89, 044702.	0.6	3
2799	Negative-U Properties of the Deep Level E3 in ZnO. <i>Physica Status Solidi (B): Basic Research</i> , 2018, 255, 1700670.	0.7	4
2800	Noncontact evaluation for interface states by photocarrier counting. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 031301.	0.8	1
2801	Tutorial: Junction spectroscopy techniques and deep-level defects in semiconductors. <i>Journal of Applied Physics</i> , 2018, 123, .	1.1	82
2802	Reduction in interface defect density in p-BaSi ₂ /n-Si heterojunction solar cells by a modified pretreatment of the Si substrate. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 025501.	0.8	11
2803	Influence of annealing atmosphere on formation of electrically-active defects in rutile TiO ₂ . <i>Journal of Applied Physics</i> , 2018, 123, 161572.	1.1	6
2804	Anneal induced transformations of defects in hadron irradiated Si wafers and Schottky diodes. <i>Materials Science in Semiconductor Processing</i> , 2018, 75, 157-165.	1.9	8
2805	Determination of Suitable Indicators of AlGaIn/GaN HEMT Wafer Quality Based on Wafer Test and Device Characteristics. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018, 215, 1700628.	0.8	2
2806	Reversed double-beam photoacoustic spectroscopy of metal-oxide powders for estimation of their energy-resolved distribution of electron traps and electronic-band structure. <i>Electrochimica Acta</i> , 2018, 264, 83-90.	2.6	40
2807	Deep Level Assessment of n-Type Si/SiO ₂ /Metal-Oxide-Semiconductor Capacitors with Embedded Ge Quantum Dots. <i>ECS Journal of Solid State Science and Technology</i> , 2018, 7, P24-P28.	0.9	1
2808	Deep level transient spectroscopic investigation of phosphorus-doped silicon by self-assembled molecular monolayers. <i>Nature Communications</i> , 2018, 9, 118.	5.8	33
2809	Synaptic behaviors of thin-film transistor with a Pt/HfO _x /n-type indium-gallium-zinc oxide gate stack. <i>Nanotechnology</i> , 2018, 29, 295201.	1.3	4
2810	Displacement Damage in Silicon Detectors for High Energy Physics. <i>IEEE Transactions on Nuclear Science</i> , 2018, 65, 1561-1582.	1.2	141
2811	Mechanism of phosphorus passivation of near-interface oxide traps in 4H-SiC MOS devices investigated by CCDLTS and DFT calculation. <i>Semiconductor Science and Technology</i> , 2018, 33, 065005.	1.0	7
2812	Defect properties of InGaAsN layers grown as sub-monolayer digital alloys by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2018, 123, .	1.1	8
2813	Chip-Level Degradation of InGaN-Based Optoelectronic Devices. <i>Solid State Lighting Technology and Application Series</i> , 2018, , 15-48.	0.3	0

#	ARTICLE	IF	CITATIONS
2814	Hysteresis in the transfer characteristics of MoS ₂ transistors. 2D Materials, 2018, 5, 015014.	2.0	209
2815	Electrical characterization and comparison of CIGS solar cells made with different structures and fabrication techniques. Solar Energy Materials and Solar Cells, 2018, 174, 77-83.	3.0	41
2816	Electronic Transport and Ferroelectric Switching in Ion-Bombarded, Defect-Engineered BiFeO ₃ Thin Films. Advanced Materials Interfaces, 2018, 5, 1700991.	1.9	29
2817	Species, engineering and characterizations of defects in TiO ₂ -based photocatalyst. Chinese Chemical Letters, 2018, 29, 671-680.	4.8	67
2818	Investigation of electrically active defects in undoped BaSi ₂ light absorber layers using deep-level transient spectroscopy. Japanese Journal of Applied Physics, 2018, 57, 075801.	0.8	12
2819	Experimental evidence of trap level modulation in silicon nitride thin films by hydrogen annealing. Japanese Journal of Applied Physics, 2018, 57, 06KB04.	0.8	7
2820	Impact of dislocations on DLTS spectra and degradation of InGaN-based laser diodes. Microelectronics Reliability, 2018, 88-90, 864-867.	0.9	4
2821	Microscopic Imaging of Inversion Layer Formation in Insulator/Semiconductor Structure by Scanning Capacitance Transient Microscopy. , 2018, , .		0
2822	Development of Highly-Sensitive Transient Photocapacitance Measurement System for Deep Defects in Boron-Doped Diamond (100) Films. , 2018, , .		0
2823	Designing a Robust Kelvin Probe Setup Optimized for Long-Term Surface Photovoltage Acquisition. Sensors, 2018, 18, 4068.	2.1	3
2824	Influence of Platinum-Hydrogen Complexes on Silicon p+/n-Diode Characteristics. , 2018, , .		1
2825	Defect identification based on first-principles calculations for deep level transient spectroscopy. Applied Physics Letters, 2018, 113, .	1.5	51
2826	N-H-related deep-level defects in dilute nitride semiconductor GaInNAs for four-junction solar cells. Japanese Journal of Applied Physics, 2018, 57, 08RD11.	0.8	6
2827	Acceptor levels of the carbon vacancy in 4H-SiC: Combining Laplace deep level transient spectroscopy with density functional modeling. Journal of Applied Physics, 2018, 124, 245701.	1.1	19
2828	MOVPE-Growth of InGaSb/AlP/GaP(001) Quantum Dots for Nanoscale Memory Applications. Physica Status Solidi (B): Basic Research, 2018, 255, 1800182.	0.7	24
2829	Deep level transient spectroscopy study of heavy ion implantation induced defects in silicon. Journal of Applied Physics, 2018, 124, .	1.1	3
2830	Laplace deep level transient spectroscopy on self-assembled quantum dots. Journal of Applied Physics, 2018, 124, 104301.	1.1	2
2831	High resolution observation of defects at SiO ₂ /4H-SiC interfaces using time-resolved scanning nonlinear dielectric microscopy. Microelectronics Reliability, 2018, 88-90, 242-245.	0.9	4

#	ARTICLE	IF	CITATIONS
2832	Bandlike and localized states of extended defects in n-type In _{0.53} Ga _{0.47} As. Journal of Applied Physics, 2018, 124, .	1.1	10
2833	Analog reversible nonvolatile memcapacitance in metal-oxide-semiconductor memcapacitor with ITO/HfO _x /Si structure. Applied Physics Letters, 2018, 113, .	1.5	27
2834	Laplace DLTS study of the fine structure and metastability of the radiation-induced E3 defect level in GaAs. Semiconductor Science and Technology, 2018, 33, 125011.	1.0	2
2835	Research Update: Recombination and open-circuit voltage in lead-halide perovskites. APL Materials, 2018, 6, .	2.2	56
2836	Quantitative Imaging of MOS Interface Trap Distribution by Using Local Deep Level Transient Spectroscopy. , 2018, , .		0
2837	Effect of BaSi ₂ template growth duration on the generation of defects and performance of p-BaSi ₂ /n-Si heterojunction solar cells. Japanese Journal of Applied Physics, 2018, 57, 042301.	0.8	8
2838	Comparison of techniques for detecting metal contamination in silicon wafers. Spectrochimica Acta, Part B: Atomic Spectroscopy, 2018, 149, 313-321.	1.5	5
2839	Nonstoichiometry, structure, and properties of Ba _x Ti _y thin films. Journal of Materials Chemistry C, 2018, 6, 10751-10759.	2.7	16
2840	Effect of growth techniques on the structural, optical and electrical properties of indium doped TiO ₂ thin films. Journal of Alloys and Compounds, 2018, 766, 194-203.	2.8	17
2841	Investigation of Traps in Thin-Film Organic Semiconductors Using Differential Analysis of Steady-State Current-Voltage Characteristics. IEEE Transactions on Electron Devices, 2018, 65, 3430-3437.	1.6	7
2842	Do we have to worry about extended defects in high-mobility materials?. , 2018, , .		1
2843	Understanding of DC degradation of ZnO varistor ceramics from the aspect of high-temperature relaxation. , 2018, , .		2
2844	C-DLTS interface defects in Al _{0.22} Ga _{0.78} N/GaN HEMTs on SiC: Spatial location of E2 traps. Physica E: Low-Dimensional Systems and Nanostructures, 2018, 104, 216-222.	1.3	10
2845	Accurate method for estimating hole trap concentration in n-type GaN via minority carrier transient spectroscopy. Applied Physics Express, 2018, 11, 071002.	1.1	25
2846	Trapping Effects in Si-Doped -Ga ₂ O ₃ MESFETs on an Fe-Doped -Ga ₂ O ₃ Substrate. IEEE Electron Device Letters, 2018, 39, 1042-1045.	2.2	78
2847	An Automated Measuring System for Current Deep-Level Transient Spectroscopy. Instruments and Experimental Techniques, 2018, 61, 277-282.	0.1	4
2848	Determining the charge states and capture mechanisms of defects in silicon through accurate recombination analyses: A review. Solar Energy Materials and Solar Cells, 2018, 187, 263-272.	3.0	31
2849	Characterization and Detection of Metals in Silicon and Germanium. Springer Series in Materials Science, 2018, , 75-123.	0.4	0

#	ARTICLE	IF	CITATIONS
2850	Vapor transport deposition of antimony selenide thin film solar cells with 7.6% efficiency. Nature Communications, 2018, 9, 2179.	5.8	426
2851	Improvement of Local Deep Level Transient Spectroscopy for Microscopic Evaluation of SiO ₂ /4H-SiC Interfaces. Materials Science Forum, 2018, 924, 289-292.	0.3	0
2852	Spatial correlation of the EC-0.57 eV trap state with edge dislocations in epitaxial n-type gallium nitride. Journal of Applied Physics, 2018, 123, .	1.1	11
2853	Excess noise and deep level defects diagnostics in semiconductor barrier structures. , 2018, , .		0
2854	Study of Deep Levels in a HIT Solar Cell. Semiconductors, 2018, 52, 926-930.	0.2	3
2855	Investigation of the Universal Mobility of SiC MOSFETs Using Wet Oxide Insulators on Carbon Face With Low Interface State Density. IEEE Transactions on Electron Devices, 2018, 65, 2707-2713.	1.6	21
2856	Dry etch damage in n-type crystalline silicon wafers assessed by deep-level transient spectroscopy and minority carrier lifetime. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2018, 36, 041201.	0.6	5
2857	Identification of swift heavy ion induced defects in Pt/n-GaN Schottky diodes by in-situ deep level transient spectroscopy. Semiconductor Science and Technology, 2018, 33, 085008.	1.0	11
2858	High Resolution Observation of Subsurface Defects at SiO ₂ /4H-SiC Interfaces by Local Deep Level Transient Spectroscopy Based on Time-Resolved Scanning Nonlinear Dielectric Microscopy. , 2019, , .		0
2859	V _{TH} -Hysteresis and Interface States Characterisation in SiC Power MOSFETs with Planar and Trench Gate. , 2019, , .		12
2860	Direct Nanoscale Characterization of Deep Levels in AgCuInGaSe ₂ Using Electron Energy-Loss Spectroscopy in the Scanning Transmission Electron Microscope. Advanced Energy Materials, 2019, 9, 1901612.	10.2	16
2861	Deep-level transient spectroscopy studies of electron and hole traps in n-type GaN homoepitaxial layers grown by quartz-free hydride-vapor-phase epitaxy. Applied Physics Letters, 2019, 115, .	1.5	37
2862	Influence of native structural defects activated by illumination and under the memory effect conditions on ultrasonic wave propagation in TlInS ₂ ferroelectric semiconductor with incommensurate phase. Materials Research Express, 2019, 6, 085914.	0.8	1
2863	High-temperature deep-level transient spectroscopy system for defect studies in wide-bandgap semiconductors. Review of Scientific Instruments, 2019, 90, 063903.	0.6	3
2864	Capacitance spectroscopy of structures with Si nanoparticles deposited onto crystalline silicon p-Si. Semiconductor Science and Technology, 2019, 34, 085003.	1.0	5
2865	DLTS study of extended defects in HgCdTe photodiodes. Journal of Physics: Conference Series, 2019, 1190, 012012.	0.3	0
2866	Boron-Oxygen Complex Responsible for Light-Induced Degradation in Silicon Photovoltaic Cells: A New Insight into the Problem. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1900315.	0.8	23
2867	Spectroscopy of defects in CdZnTe structures. Semiconductor Science and Technology, 2019, 34, 115012.	1.0	1

#	ARTICLE	IF	CITATIONS
2868	Contactless transient carrier spectroscopy and imaging technique using lock-in free carrier emission and absorption. Scientific Reports, 2019, 9, 14268.	1.6	2
2869	Defect states of organic lead halide single crystals grown by inverse-temperature crystallization. Applied Physics Letters, 2019, 115, .	1.5	9
2870	Investigation of spatial and energy profiles of plasma process-induced latent defects in Si substrate using capacitance-voltage characteristics. Journal Physics D: Applied Physics, 0, , .	1.3	5
2871	Trap parameters in the infrared InAsSb absorber found by capacitance and noise measurements. Semiconductor Science and Technology, 2019, 34, 105017.	1.0	4
2872	Application of the Concept of Lifetime-Equivalent Defect Density in Defect Systems Comprising a Multitude of Defect Species. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1900322.	0.8	4
2873	Capture and emission mechanisms of defect states at interface between nitride semiconductor and gate oxides in GaN-based metal-oxide-semiconductor power transistors. Journal of Applied Physics, 2019, 126, .	1.1	24
2874	Simulation of deep level transient spectroscopy using circuit simulator with deep level trap model implemented by Verilog-A language. , 2019, , .		0
2875	Breakdown Walkout in Polarization-Doped Vertical GaN Diodes. IEEE Transactions on Electron Devices, 2019, 66, 4597-4603.	1.6	9
2876	Energy dispersive spectroscopic measurement of charge traps in MoTe ₂ . Physical Review B, 2019, 100, .	1.1	1
2877	Study of electronic properties on the n-GaN (0001) surface with points defects. Applied Physics A: Materials Science and Processing, 2019, 125, 1.	1.1	3
2878	Impact of In Situ Annealing on the Deep Levels in Ni-Au/AlN/Si Metal-Insulator-Semiconductor Capacitors. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1900248.	0.8	3
2879	Engineering CIGS grains qualities to achieve high efficiency in ultrathin Cu(In Ga)Se ₂ solar cells with a single-gradient band gap profile. Results in Physics, 2019, 12, 704-711.	2.0	37
2880	DLTS study of defect distribution in metal-porous silicon-silicon structures for solar application. AIP Conference Proceedings, 2019, , .	0.3	0
2881	Combined DLTS/MCTS investigations of deep electrical levels of regular dislocation networks in silicon. Journal of Physics: Conference Series, 2019, 1190, 012005.	0.3	0
2882	Identifying the Traps in the Channel Region in GaN-Based HEMTs Using a Nonmonotone Drain Current Transient. IEEE Transactions on Device and Materials Reliability, 2019, 19, 509-513.	1.5	5
2883	Characterization of sputtered a-Si:H passivated silicon surface by temperature- and injection-dependent lifetime spectroscopy. AIP Conference Proceedings, 2019, , .	0.3	0
2884	Characterization of Near-Interface Traps at Dielectric/SiC Interfaces Using CCDLTS. Materials Science Forum, 2019, 963, 217-221.	0.3	0
2885	Effect of radiation on the performance of activated carbon base supercapacitor: Part II. Influence of electron irradiation exposure on full cell. Energy Procedia, 2019, 158, 4560-4565.	1.8	0

#	ARTICLE	IF	CITATIONS
2886	Output Voltage Changes in PV Solar Modules after Electrical and Thermal Stresses. Experimental Analysis.. Energy Procedia, 2019, 157, 1404-1411.	1.8	11
2887	A Pentacene -Based Organic Mis Structures. Energy Procedia, 2019, 162, 231-240.	1.8	2
2888	Nonequilibrium carrier dynamics in self-assembled quantum dots. Applied Physics Reviews, 2019, 6, .	5.5	12
2889	Ultrasensitive, flexible, and low-cost nanoporous piezoresistive composites for tactile pressure sensing. Nanoscale, 2019, 11, 2779-2786.	2.8	72
2890	High Velocity Microparticles in Space. , 2019, , .		3
2891	Signatures of extended defects in Cu(In,Ga)Se ₂ observed using capacitance spectroscopy techniques. Journal of Physics and Chemistry of Solids, 2019, 134, 58-63.	1.9	3
2892	Deep levels in metal-oxide-semiconductor capacitors fabricated on n-type In _{0.53} Ga _{0.47} As lattice matched to InP substrates. Semiconductor Science and Technology, 2019, 34, 075024.	1.0	1
2893	Deep traps localization in AlGaIn/GaN MIS-HEMTs by a comparative study using capacitance and current deep level transient spectroscopies. Journal of Physics: Conference Series, 2019, 1190, 012013.	0.3	1
2894	Deep defect levels in CuInSe ₂ single crystals using DLTS, MCTS and photoacoustic spectroscopy. Infrared Physics and Technology, 2019, 99, 172-177.	1.3	1
2895	Transport and storage dynamics of 30% In-rich InGaIn/GaN MQW LED p-i-n structure. Journal Physics D: Applied Physics, 2019, 52, 345302.	1.3	2
2896	Analysis of admittance measurements of MOS capacitors on CVD grown bilayer MoS ₂ . 2D Materials, 2019, 6, 035035.	2.0	19
2897	Proximity Gettering Design of Hydrocarbon-Molecular-Ion-Implanted Silicon Wafers Using Dark Current Spectroscopy for CMOS Image Sensors. Sensors, 2019, 19, 2073.	2.1	20
2898	Evaluation of electron traps in SiN _x by discharge current transient spectroscopy: verification of validity by comparing with conventional DLTS. Japanese Journal of Applied Physics, 2019, 58, SBBK02.	0.8	5
2899	Deep Defect States in Wide-Band-Gap ABX ₃ Halide Perovskites. ACS Energy Letters, 2019, 4, 1150-1157.	8.8	54
2900	Quantification of ion migration in CH ₃ NH ₃ Pb ₃ perovskite solar cells by transient capacitance measurements. Materials Horizons, 2019, 6, 1497-1503.	6.4	297
2901	Ultrathin TiO _x Interface-Mediated ZnO-Nanowire Memristive Devices Emulating Synaptic Behaviors. Advanced Electronic Materials, 2019, 5, 1900142.	2.6	9
2902	Analysis of Leakage Mechanisms in AlN Nucleation Layers on p-Si and p-SOI Substrates. IEEE Transactions on Electron Devices, 2019, 66, 1849-1855.	1.6	10
2903	Impedance Spectroscopy for Emerging Photovoltaics. Journal of Physical Chemistry C, 2019, 123, 11329-11346.	1.5	248

#	ARTICLE	IF	CITATIONS
2904	Electrical properties of vertical GaN Schottky diodes on Ammono-GaN substrate. Materials Science in Semiconductor Processing, 2019, 96, 132-136.	1.9	14
2905	Peak shape analysis of deep level transient spectra: An alternative to the Arrhenius plot. Journal of Materials Research, 2019, 34, 1654-1668.	1.2	2
2906	Light Sum Accumulation in ZnSe Crystals at X-Ray Excitation. Advances in Condensed Matter Physics, 2019, 2019, 1-9.	0.4	1
2907	Full characterization of electronic transport properties in working polymer light-emitting diodes via impedance spectroscopy. Journal of Applied Physics, 2019, 125, 115501.	1.1	6
2908	Gate length effect on trapping properties in AlGaIn/GaN high-electron-mobility transistors. Semiconductor Science and Technology, 2019, 34, 045011.	1.0	4
2909	Giant, Anomalous Piezoimpedance in Silicon-on-insulator. Physical Review Applied, 2019, 11, .	1.5	2
2910	Causes and Solutions of Recombination in Perovskite Solar Cells. Advanced Materials, 2019, 31, e1803019.	11.1	422
2911	Density of defect states retrieved from the hysteretic gate transfer characteristics of monolayer MoS2 field effect transistors. AIP Advances, 2019, 9, .	0.6	11
2912	Local trap spectroscopy on cross-sectioned AlGaIn/GaN devices with <i>in situ</i> biasing. Applied Physics Letters, 2019, 114, .	1.5	2
2913	High Resolution Mapping of Defects at SiO2/SiC Interfaces by Local-DLTS Based on Time-Resolved Scanning Nonlinear Dielectric Microscopy. , 2019, , .		0
2914	Capacitance characterization of GaP/Si superlattice grown by time-modulated PECVD. Journal of Physics: Conference Series, 2019, 1410, 012116.	0.3	2
2915	Device-Based Threading Dislocation Assessment in Germanium Hetero-Epitaxy. , 2019, , .		1
2916	Process-induced defects in Au-hyperdoped Si photodiodes. Journal of Applied Physics, 2019, 126, .	1.1	14
2917	On the alloying and strain effects of divacancy energy level in n-type Si1â€‰%âˆ™â€™â€™xGex. Journal of Applied Physics, 2019, 126, 235707.	1.1	2
2918	Analysis of Deep Level and Oxide Interface Defects Using 100V HF Schottky Diodes and MOS CV for Silicon and 4H SiC HV MOSFETs, Advanced Power Electronics, and RF ASIC. MRS Advances, 2019, 4, 2377-2382.	0.5	1
2919	Three-step growth of highly photoresponsive BaSi2 light absorbing layers with uniform Ba to Si atomic ratios. Journal of Applied Physics, 2019, 126, .	1.1	16
2920	Analysis of Recombination Mechanisms in RbF-Treated CIGS Solar Cells. IEEE Journal of Photovoltaics, 2019, 9, 313-318.	1.5	58
2921	Basics of semiconducting metal oxideâ€™based gas sensors. , 2019, , 61-165.		17

#	ARTICLE	IF	CITATIONS
2922	Capacitance methodology for investigating defect states in energy gap of organic semiconductor. <i>Organic Electronics</i> , 2019, 65, 275-299.	1.4	26
2923	Investigation of the effects of GaAs substrate orientations on the electrical properties of sulfonated polyaniline based heterostructures. <i>Applied Surface Science</i> , 2020, 504, 144315.	3.1	4
2924	Ac conductivity and impedance spectroscopy study and dielectric response of MgPc/GaAs organic heterojunction for solar energy application. <i>Physica B: Condensed Matter</i> , 2020, 578, 411782.	1.3	9
2925	Deep-Level Defects and Impurities in InGaN Alloys. <i>Physica Status Solidi (B): Basic Research</i> , 2020, 257, 1900534.	0.7	13
2926	Effect of Cryogenic Dry Etching on Minority Charge Carrier Lifetime in Silicon. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020, 217, 1900534.	0.8	3
2927	Degradation Mechanisms of GaN-Based Vertical Devices: A Review. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020, 217, 1900750.	0.8	8
2928	Understanding and monitoring the capacitance-voltage technique for the characterization of tandem solar cells. <i>Progress in Photovoltaics: Research and Applications</i> , 2020, 28, 601-608.	4.4	2
2929	Charge carrier traps in organic semiconductors: a review on the underlying physics and impact on electronic devices. <i>Journal of Materials Chemistry C</i> , 2020, 8, 759-787.	2.7	368
2930	Radiation detection using fully depleted 50-µm thick Ni/n-4H-SiC epitaxial layer Schottky diodes with ultra-low concentration of Z1/2 and EH6/7 deep defects. <i>Journal of Applied Physics</i> , 2020, 128, .	1.1	24
2931	Study of the heavily p-type doping of cubic GaN with Mg. <i>Scientific Reports</i> , 2020, 10, 16858.	1.6	25
2932	Probing the trap states in n-PbS ₂ (S,Se) ₃ solar cells by deep-level transient spectroscopy. <i>Journal of Chemical Physics</i> , 2020, 153, 124703.	1.2	16
2933	Ultra-slow dynamic annealing of neutron-induced defects in n-type silicon: role of charge carriers. <i>European Physical Journal Plus</i> , 2020, 135, 1.	1.2	3
2934	Progress and prospects of CZTSSe/CdS interface engineering to combat high open-circuit voltage deficit of kesterite photovoltaics: a critical review. <i>Journal of Materials Chemistry A</i> , 2020, 8, 21547-21584.	5.2	91
2935	Origin of Irradiation Synergistic Effects in Silicon Bipolar Transistors. <i>ACS Applied Electronic Materials</i> , 2020, 2, 3783-3793.	2.0	10
2936	Defect states and their electric field-enhanced electron thermal emission in heavily Zr-doped Ga ₂ O ₃ crystals. <i>Applied Physics Letters</i> , 2020, 117, .	1.5	13
2937	Probing the ionic defect landscape in halide perovskite solar cells. <i>Nature Communications</i> , 2020, 11, 6098.	5.8	75
2938	Deep level transient spectroscopy investigation of ultra-wide bandgap (2̄,01) and (001) Ga ₂ O ₃ . <i>Journal of Applied Physics</i> , 2020, 128, .	1.1	14
2939	Underlying mechanism of the efficiency loss in CZTSSe solar cells: Disorder and deep defects. <i>Science China Materials</i> , 2020, 63, 2371-2396.	3.5	37

#	ARTICLE	IF	CITATIONS
2940	Defect properties of solar cells with layers of GaP based dilute nitrides grown by molecular beam epitaxy. Journal of Applied Physics, 2020, 128, 023105.	1.1	4
2941	Defect spectroscopy on the dielectric material aluminum oxide. Scientific Reports, 2020, 10, 12533.	1.6	2
2942	How Much Physics is in a Current-Voltage Curve? Inferring Defect Properties From Photovoltaic Device Measurements. IEEE Journal of Photovoltaics, 2020, 10, 1532-1537.	1.5	5
2943	Chemical trends of deep levels in van der Waals semiconductors. Nature Communications, 2020, 11, 5373.	5.8	24
2944	Improved rectification and transport properties of hybrid PEDOT:PSS/Ge/Si heterojunctions with Ge nanoclusters. Journal of Applied Physics, 2020, 128, 085503.	1.1	1
2945	Deep Level Transient Spectroscopy of GaAs Nanoridge Diodes Grown on Si Substrates. Physical Review Applied, 2020, 14.	1.5	5
2946	A Fast Extraction Method of Energy Distribution of Border Traps in AlGaIn/GaN MIS-HEMT. IEEE Journal of the Electron Devices Society, 2020, 8, 905-910.	1.2	5
2947	Reliability of Miniaturized Transistors from the Perspective of Single-Defects. Micromachines, 2020, 11, 736.	1.4	11
2948	A New Approach to the Fabrication of Memristive Neuromorphic Devices: Compositionally Graded Films. Materials, 2020, 13, 3680.	1.3	2
2949	Spatial scale dependent impact of non-uniform interface defect distribution on field effect mobility in SiC MOSFETs. Microelectronics Reliability, 2020, 114, 113829.	0.9	4
2950	Deep levels model identification in semiconductor barrier structures. IOP Conference Series: Materials Science and Engineering, 2020, 896, 012125.	0.3	1
2951	Studying Properties of Defects. , 2020, , 1-20.		0
2952	Capacitance Spectroscopy of Heteroepitaxial AlGaAs/GaAs n Structures. Semiconductors, 2020, 54, 1260-1266.	0.2	1
2953	Identifying, understanding and controlling defects and traps in halide perovskites for optoelectronic devices: a review. Journal Physics D: Applied Physics, 2020, 53, 373001.	1.3	20
2954	Investigation of the structural, optical and electrical properties of indium-doped TiO ₂ thin films grown by Pulsed Laser Deposition technique on low and high index GaAs planes. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2020, 259, 114578.	1.7	9
2955	Fabrication and characterization of Schottky barrier diodes on rutile TiO ₂ . Materials Research Express, 2020, 7, 065903.	0.8	5
2956	A Deep Level Transient Spectroscopy Study of Hole Traps in GexSe1-x-based Layers for Ovonic Threshold Switching Selectors. ECS Journal of Solid State Science and Technology, 2020, 9, 044006.	0.9	0
2957	Effects of sputtering pressure and temperature of ITO electrodes on the performance of p-BaSi ₂ /n-Si heterojunction solar cells. Japanese Journal of Applied Physics, 2020, 59, SFFA07.	0.8	0

#	ARTICLE	IF	CITATIONS
2958	Experimental Characterization of Charge Trapping Dynamics in 100-nm AlN/GaN/AlGaIn-on-Si HEMTs by Wideband Transient Measurements. IEEE Transactions on Electron Devices, 2020, 67, 3069-3074.	1.6	16
2959	Significant enhancement of photoresponsivity in As-doped n-BaSi ₂ epitaxial films by atomic hydrogen passivation. Applied Physics Express, 2020, 13, 051001.	1.1	8
2960	Defect Dynamic Model of the Synergistic Effect in Neutron- and ¹³⁷ Cs-Ray-Irradiated Silicon NPN Transistors. ACS Applied Materials & Interfaces, 2020, 12, 29993-29998.	4.0	5
2961	Atomic hydrogen passivation for photoresponsivity enhancement of boron-doped p-BaSi ₂ films and performance improvement of boron-doped p-BaSi ₂ /n-Si heterojunction solar cells. Journal of Applied Physics, 2020, 127, .	1.1	13
2962	Combining steady-state photo-capacitance spectra with first-principles calculations: the case of Fe and Ti in $\hat{\Gamma}^2$ -Ga ₂ O ₃ . New Journal of Physics, 2020, 22, 063033.	1.2	10
2963	Identification of Trap States in p-GaN Layer of a p-GaN/AlGaIn/GaN Power HEMT Structure by Deep-Level Transient Spectroscopy. IEEE Electron Device Letters, 2020, 41, 685-688.	2.2	52
2964	Ionic-Defect Distribution Revealed by Improved Evaluation of Deep-Level Transient Spectroscopy on Perovskite Solar Cells. Physical Review Applied, 2020, 13, .	1.5	50
2965	Electrical Defect State Distribution in Single Crystal ZnO Schottky Barrier Diodes. Coatings, 2020, 10, 206.	1.2	10
2966	Local deep-level transient spectroscopy. , 2020, , 189-219.		0
2967	Time-resolved scanning nonlinear dielectric microscopy. , 2020, , 221-238.		0
2968	The influence of point defects on AlGaIn-based deep ultraviolet LEDs. Journal of Alloys and Compounds, 2020, 845, 156177.	2.8	16
2969	Experimental investigation of buffer traps physical mechanisms on the gate charge of GaN-on-Si devices under various substrate biases. Applied Physics Letters, 2020, 116, .	1.5	14
2970	Determination of capture barrier energy of the E-center in palladium Schottky barrier diodes of antimony-doped germanium by varying the pulse width. Materials Research Express, 2020, , .	0.8	2
2971	Full bandgap defect state characterization of $\hat{\Gamma}^2$ -Ga ₂ O ₃ grown by metal organic chemical vapor deposition. APL Materials, 2020, 8, .	2.2	52
2972	Analysis of hole-like traps in deep level transient spectroscopy spectra of AlGaIn/GaN heterojunctions. Journal Physics D: Applied Physics, 2020, 53, 185105.	1.3	2
2973	Origin and anomalous behavior of dominant defects in 4H-SiC studied by conventional and Laplace deep level transient spectroscopy. Journal of Applied Physics, 2020, 127, .	1.1	7
2974	Reliability Study of c-Si PV Module Mounted on a Concrete Slab by Thermal Cycling Using Electroluminescence Scanning: Application in Future Solar Roadways. Materials, 2020, 13, 470.	1.3	16
2975	Electrical characterization of RuOx/n-GaN Schottky diodes formed by oxidizing ruthenium thin-films in normal laboratory air. AIP Advances, 2020, 10, 015116.	0.6	0

#	ARTICLE	IF	CITATIONS
2976	Quantifying mobile ions and electronic defects in perovskite-based devices with temperature-dependent capacitance measurements: Frequency vs time domain. Journal of Chemical Physics, 2020, 152, 044202.	1.2	46
2977	Scanning optical microscopy. Advances in Imaging and Electron Physics, 2020, 213, 227-325.	0.1	10
2978	Contamination of TiO ₂ thin films spin coated on rutile and soda lime silica substrates. Journal of Materials Science, 2020, 55, 8061-8087.	1.7	5
2979	Effects of current transportation and deep traps on leakage current and capacitance hysteresis of AlGaIn/GaN HEMT. Materials Science in Semiconductor Processing, 2020, 115, 105100.	1.9	14
2980	Influence of plasma on electrophysical properties of the GaP/n-Si isotype heterojunction grown by PE-ALD. Journal of Physics: Conference Series, 2020, 1482, 012017.	0.3	1
2981	In Situ Positron Annihilation Spectroscopy Analysis on Low Temperature Irradiated Semiconductors, Challenges and Possibilities. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2000232.	0.8	2
2982	Integration of electrochemical capacitance voltage characteristics: a new procedure for obtaining free charge carrier depth distribution profiles with high resolution. Journal of Solid State Electrochemistry, 2021, 25, 797-802.	1.2	0
2983	Revealing Dynamic Effects of Mobile Ions in Halide Perovskite Solar Cells Using Time-Resolved Microspectroscopy. Small Methods, 2021, 5, e2000731.	4.6	18
2984	Silicon carbide diodes for neutron detection. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2021, 986, 164793.	0.7	28
2985	Spectroscopy of Nonradiative Recombination Levels by Two-Wavelength Excited Photoluminescence. Physica Status Solidi (B): Basic Research, 2021, 258, 2000370.	0.7	2
2986	Modelling and simulation of carrier transport in quantum dot memory device for longer data retention and minimized power consumption. Journal of Computational Electronics, 2021, 20, 178-194.	1.3	2
2987	Degradation mechanisms of InGaIn visible LEDs and AlGaIn UV LEDs. , 2021, , 273-312.		6
2988	Review of injection dependent charge carrier lifetime spectroscopy. Progress in Energy, 2021, 3, 012001.	4.6	8
2989	Physical Modeling of Charge Trapping Effects in GaN/Si Devices and Incorporation in the ASM-HEMT Model. IEEE Journal of the Electron Devices Society, 2021, 9, 748-755.	1.2	9
2990	Defects in ferroelectric HfO ₂ . Nanoscale, 2021, 13, 11635-11678.	2.8	53
2991	Deep Level Defects in GaN Grown at Low Temperature by Metalorganic Vapor Phase Epitaxy. Lecture Notes in Mechanical Engineering, 2021, , 246-251.	0.3	0
2992	Analysis of Deep Traps in Mist Chemical Vapor Deposition-Grown n-Type Ga ₂ O ₃ by Photocapacitance Method. Physica Status Solidi (B): Basic Research, 2021, 258, 2000622.	0.7	6
2993	Electrical property of iron-related defects in n-type dislocated Czochralski silicon crystal used for solar cells. Applied Physics Express, 2021, 14, 035502.	1.1	2

#	ARTICLE	IF	CITATIONS
2994	Super Single Pulse Charge Pumping Technique for Profiling Interfacial Defects. IEEE Transactions on Electron Devices, 2021, 68, 726-732.	1.6	7
2995	Deep level transient spectroscopy characterization without the Arrhenius plot. Review of Scientific Instruments, 2021, 92, 023902.	0.6	4
2996	Current-voltage characteristics and deep-level study of GaN nanorod Schottky-diode-based photodetector. Semiconductor Science and Technology, 2021, 36, 035010.	1.0	17
2997	Laplace DLTS studies of the 0.25 eV electron trap properties in n-GaN. Semiconductor Science and Technology, 2021, 36, 035014.	1.0	4
2998	Quantum Sensor for Nanoscale Defect Characterization. Physical Review Applied, 2021, 15, .	1.5	6
2999	EFFECT OF TEMPERATURE TREATMENT ON THE ENERGY SPECTRUM OF DEFECTS IN SILICON DOPED WITH MOLYBDENUM. EurasianUnionofScientists, 2021, 5, 50-53.	0.0	0
3000	Characterization of carrier behavior in photonically excited 6H silicon carbide exhibiting fast, high voltage, bulk transconductance properties. Scientific Reports, 2021, 11, 6859.	1.6	9
3001	A first-principles understanding of point defects and impurities in GaN. Journal of Applied Physics, 2021, 129, .	1.1	55
3002	Structural defects in MBE-grown CdTe-basing heterojunctions designed for photovoltaic applications. Semiconductor Science and Technology, 2021, 36, 045022.	1.0	3
3003	Atomistic Mechanism of H_2 Defects in GaN. http://www.w3.org/1998/Math/MathML display="inline" overflow="scroll" < mml:mrow > < mml:mi > Si </mml:mi> < mml:mi mathvariant="normal" > C </mml:mi> </mml:mrow> < mml:mo > / </mml:mo> < mml:msub > < mml:mrow > < mml:mi > Si </mml:mi> < mml:mi mathvariant="normal" > O </mml:mi> </mml:mrow> < mml:mn > 2 </mml:mn> </mml:msub > </mml:math> Interface Carrier-Trapping Effects on Breakdown-Voltage Degradation in Power Devices. Physical Review Applied, 2021, 15, .	1.5	7
3004	Analysis of degradation mechanisms in GaN-based light-emitting diodes under reverse-bias stress: effects of defects and junction-temperature increase. Japanese Journal of Applied Physics, 2021, 60, 032006.	0.8	0
3005	A defect characterization technique for the sidewall surface of Nano-ridge and Nanowire based Logic and RF technologies. , 2021, , .		0
3006	Tunable Electronic Trap Energy in Sol-Gel Processed Dielectrics. IEEE Transactions on Electron Devices, 2021, 68, 1190-1195.	1.6	35
3007	The influence of Mn doping on the leakage current mechanisms and resistance degradation behavior in lead zirconate titanate films. Acta Materialia, 2021, 208, 116680.	3.8	16
3008	Study of defect properties and recombination mechanism in rubidium treated Cu(In, Ga)Se ₂ solar cells. Journal of Applied Physics, 2021, 129, .	1.1	9
3009	Dynamics of hole injection from p-GaN drain of a hybrid drain embedded GIT. AIP Advances, 2021, 11, 055101.	0.6	1
3010	Revealing composition and structure dependent deep-level defect in antimony trisulfide photovoltaics. Nature Communications, 2021, 12, 3260.	5.8	113
3011	Intrinsic and complex defect engineering of quasi-one-dimensional ribbons http://www.w3.org/1998/Math/MathML < mml:mrow > < mml:msub > < mml:mi > Sb </mml:mi> < mml:mn > 2 </mml:mn> </mml:msub > </mml:mrow> < mml:mi mathvariant="normal" > S </mml:mi> < mml:mn > 3 </mml:mn> </mml:msub > </mml:mrow> </mml:math> for photovoltaics performance. Physical Review Materials, 2021, 5, .	0.9	9

#	ARTICLE	IF	CITATIONS
3012	An Open Circuit Voltage Decay System for a Flexible Method for Characterization of Carriers' Lifetime in Semiconductor. <i>Key Engineering Materials</i> , 0, 886, 3-11.	0.4	0
3013	Assessing the Impact of Defects on Lead-Free Perovskite-Inspired Photovoltaics via Photoinduced Current Transient Spectroscopy. <i>Advanced Energy Materials</i> , 2021, 11, 2003968.	10.2	26
3014	Ion implantation in In^{2+} -Ga $_{2}\text{O}_3$: Physics and technology. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2021, 39, .	0.9	45
3015	Deep-level transient spectroscopy of GaN grown by electrochemical deposition and irradiated with alpha particles. <i>Materials Science in Semiconductor Processing</i> , 2021, 127, 105685.	1.9	3
3016	Characterization and role of deep traps on the radio frequency performances of high resistivity substrates. <i>Journal of Applied Physics</i> , 2021, 129, 215701.	1.1	0
3017	Deep levels and carrier capture kinetics in n-GaAsBi alloys investigated by deep level transient spectroscopy. <i>Journal Physics D: Applied Physics</i> , 2021, 54, 345109.	1.3	11
3018	Impact of Defect Engineering on High-Power Devices. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2021, 218, 2100169.	0.8	0
3019	Defect characterization and charge transport measurements in high-resolution Ni/n-4H-SiC Schottky barrier radiation detectors fabricated on 250-nm epitaxial layers. <i>Journal of Applied Physics</i> , 2021, 129, .	1.1	34
3020	Impurity defect absorption and photochromic effect in KNbWO $_6$. <i>Journal of Solid State Chemistry</i> , 2021, 298, 122099.	1.4	5
3021	Analysis of Current Transport Mechanism in AP-MOVPE Grown GaAsN p-i-n Solar Cell. <i>Energies</i> , 2021, 14, 4651.	1.6	9
3023	The Role of Defects on the Performance of Quantum Dot Intermediate Band Solar Cells. <i>IEEE Journal of Photovoltaics</i> , 2021, 11, 1022-1031.	1.5	2
3024	Electron capture and emission dynamics of self-assembled quantum dots far from equilibrium with the environment. <i>Physical Review B</i> , 2021, 104, .	1.1	3
3025	Role of deep levels and barrier height lowering in current-flow mechanism in 150-nm thick epitaxial n-type 4H-SiC Schottky barrier radiation detectors. <i>Applied Physics Letters</i> , 2021, 119, .	1.5	19
3026	High-resolution radiation detection using Ni/SiO $_2$ /n-4H-SiC vertical metal-oxide-semiconductor capacitor. <i>Journal of Applied Physics</i> , 2021, 130, .	1.1	17
3027	Ferroelectric semiconductor junctions based on graphene/ In_2Se_3 /graphene van der Waals heterostructures. <i>2D Materials</i> , 2021, 8, 045020.	2.0	16
3028	Dynamic Performance Characterization Techniques in Gallium Nitride-Based Electronic Devices. <i>Crystals</i> , 2021, 11, 1037.	1.0	4
3029	Radiation Detection Using n-Type 4H-SiC Epitaxial Layer Surface Barrier Detectors. , 2022, , 183-209.		9
3030	Depth profiles of electron traps generated during reactive ion etching in n-type 4H-SiC characterized by using isothermal capacitance transient spectroscopy. <i>Journal of Applied Physics</i> , 2021, 130, .	1.1	2

#	ARTICLE	IF	CITATIONS
3031	Observation of minority carrier traps using C-DLTS in Au/SiO ₂ /n-4H-SiC vertical MOS capacitor. , 2021, , .		0
3032	High-resolution 4H-SiC Schottky barrier detectors on 250 micron epitaxial layers for harsh environment applications. , 2021, , .		1
3033	Effects of deep-level traps on the transport properties of high-flux X-ray CdZnTe detectors. Materials Science in Semiconductor Processing, 2021, 133, 105974.	1.9	6
3034	Generation-recombination in disordered organic semiconductor: Application to the characterization of traps. Organic Electronics, 2021, , 106350.	1.4	3
3035	Investigation of the effect of substrate orientation on the structural, electrical and optical properties of n-type GaAs _{1-x} Bi _x layers grown by Molecular Beam Epitaxy. Journal of Alloys and Compounds, 2021, 885, 161019.	2.8	4
3036	Defect engineering in lanthanide doped luminescent materials. Coordination Chemistry Reviews, 2021, 448, 214178.	9.5	26
3037	Defect engineering in thermoelectric materials: what have we learned?. Chemical Society Reviews, 2021, 50, 9022-9054.	18.7	201
3040	Electrical and optical measuring techniques for flaw states. , 1983, , 59-72.		1
3041	Impurities and Defects. , 2010, , 5-124.		2
3043	The Properties of the Electrode and Their Effect on Electrochemical Measurements. , 1980, , 153-188.		4
3044	Coated Electrodes. , 1980, , 299-333.		3
3045	Defect Production During Neutron Doping of Si. , 1981, , 101-140.		4
3046	The Time-Dependent Defect Spectroscopy. , 2014, , 75-109.		11
3047	Defects Characterization in GaAs-GaAlAs Superlattices. NATO ASI Series Series B: Physics, 1988, , 107-120.	0.2	1
3048	Structure and Properties of Point Defects in Semiconductors. NATO ASI Series Series B: Physics, 1989, , 1-14.	0.2	6
3049	Optical and Thermal Properties of Cr in GaAs. , 1980, , 233-240.		1
3050	Dark Capacitance, Photocapacitance, Dark Conductance and Photoconductance Transients on GaAs Mesfets. , 1980, , 329-334.		3
3051	Characterization of Surface States at the Si-SiO ₂ Interface. , 1979, , 105-148.		5

#	ARTICLE	IF	CITATIONS
3052	Semiconductor Material Evaluation by Means of Schottky Contacts. , 1979, , 201-256.		2
3053	Electronic States and Structural Properties of Deep Centers in Semiconductors. , 1986, , 243-304.		2
3054	Transient Spectroscopy on Individual Interface Traps in Mosfets. , 1988, , 327-333.		1
3055	Experimental Observation of Intrinsic Localized Modes in Germanium. Springer Series in Materials Science, 2015, , 343-362.	0.4	5
3056	The Origin of Defects Induced in Ultra-Pure Germanium by Electron Beam Deposition. Springer Series in Materials Science, 2015, , 363-380.	0.4	6
3057	Photothermal Detection at Surfaces and Interfaces: Developments in Non-Conventional Diagnostics. Springer Series in Optical Sciences, 1992, , 657-663.	0.5	1
3058	Application of Scanning Capacitance Microscopy to Analysis at the Nanoscale. , 2008, , 377-420.		3
3059	Radiotracer Deep Level Transient Spectroscopy. Advanced Texts in Physics, 2004, , 537-561.	0.5	4
3060	MIS Structure. Springer Series in Electrophysics, 1997, , 23-74.	0.2	7
3061	Electronic States at Grain Boundaries in Semiconductors. Springer Series in Solid-state Sciences, 1985, , 95-117.	0.3	7
3062	Phonon-Induced Electrical Conductance in Semiconductors. Springer Series in Solid-state Sciences, 1986, , 116-122.	0.3	4
3063	Hydrogen in Crystalline Semiconductors. Springer Series in Materials Science, 1992, , .	0.4	552
3064	Passivation of Deep Levels by Hydrogen. Springer Series in Materials Science, 1992, , 28-62.	0.4	1
3065	Properties of Transition Metals in Silicon. Springer Series in Materials Science, 1995, , 19-64.	0.4	1
3066	Basic Radiation Damage Mechanisms in Semiconductor Materials and Devices. Springer Series in Materials Science, 2002, , 9-52.	0.4	10
3067	Lineare und nicht-lineare WiderstÄnde. Werkstoffe Und Bauelemente Der Elektrotechnik, 1994, , 129-218.	0.0	1
3068	Device Stability and Photo-Excited Charge-Collection Spectroscopy. SpringerBriefs in Physics, 2013, , 1-16.	0.2	1
3069	Silicon Epitaxy. , 1989, , 25-78.		2

#	ARTICLE	IF	CITATIONS
3070	Effect of Laser Irradiation on the Characteristics of Implanted Layers for Silicon Solar Cells. , 1979, , 213-221.		3
3071	Diamond Photovoltaics: Characterization of CVD Diamond Film-Based Heterostructures for Light to Electricity Conversion. , 1995, , 171-185.		1
3072	Light-Emitting Diode Displays. , 1985, , 289-331.		11
3073	On the applicability of deep-level transient spectroscopy for the investigation of deep centers in silicon created by fast neutron irradiation. Applied Physics A: Materials Science and Processing, 1995, 61, 107-109.	1.1	1
3074	DEGRADATION. , 1978, , 277-313.		4
3075	Scanning Deep Level Transient Spectroscopy. Techniques in Physics, 1989, 12, 339-371.	0.2	3
3076	Cathodoluminescence Characterization of Semiconductors. Techniques in Physics, 1989, , 373-423.	0.2	13
3077	A COMPARISON OF ION-IMPLANTATION-INDUCED DEEP LEVELS IN SCANNED ELECTRON-BEAM-ANNEALED AND CW LASER-ANNEALED SILICON. , 1980, , 423-429.		5
3078	Electronic properties of defects introduced during sputter deposition of Cr Schottky contacts on GaAs. , 1996, , 870-873.		1
3079	INTERFACE STATES AT THE SiO ₂ â€“Si INTERFACE. , 1983, , 422-455.		3
3080	Semiconductor Statistics. , 1992, , 197-280.		7
3081	Radiation and processed induced defects in GaN. , 2000, , 251-286.		2
3084	Nonlinear Transistor Model Parameter Extraction Techniques. , 2011, , .		43
3086	Title is missing!. Journal of Materials Science: Materials in Electronics, 1998, 9, 65-76.	1.1	15
3087	CaractÃ©risation du piÃ©ge Ã©lectrons responsable des Ã©chos acoustiques holographiques dans le CdS photoconducteur. Journal De Physique, 1978, 39, 1299-1309.	1.8	2
3088	Energy levels in electron irradiated n-type germanium. Journal De Physique (Paris), Lettres, 1979, 40, 19-22.	2.8	17
3089	Strongly anisotropic field ionization of a common deep level in GaAs. Journal De Physique (Paris), Lettres, 1979, 40, 31-33.	2.8	23
3090	Dipolar relaxation effects in Al/SiO ₂ /Si structures investigated by Transient Capacitance Spectroscopy. Journal De Physique (Paris), Lettres, 1984, 45, 493-499.	2.8	2

#	ARTICLE	IF	CITATIONS
3091	Minority carrier trap measurements in schottky barriers on N-type LPE GaAs. Revue De Physique Appliquée, 1977, 12, 1819-1821.	0.4	2
3092	Energy dependence of defect energy levels in electron irradiated silicon. Revue De Physique Appliquée, 1979, 14, 481-484.	0.4	15
3093	Niveaux profonds dans le GaAs implanté bore. Revue De Physique Appliquée, 1980, 15, 869-874.	0.4	1
3094	Analyse d'une méthode D.L.T.S. utilisant une détection synchrone mesurant l'harmonique deux du signal de capacité. Revue De Physique Appliquée, 1982, 17, 759-767.	0.4	4
3095	Méthode DDLTS utilisant une détection synchrone : application au GaAs implanté en oxygène. Revue De Physique Appliquée, 1986, 21, 489-499.	0.4	4
3096	Nouvelle méthode de profilométrie capacitive des porteurs libres et des centres profonds dans les semiconducteurs. Revue De Physique Appliquée, 1987, 22, 1381-1388.	0.4	1
3097	The base line problem in DLTS technique. Revue De Physique Appliquée, 1989, 24, 243-249.	0.4	5
3098	Origine des centres recombinants aux joints de grains de bicristaux de silicium $\xi = 13$. Revue De Physique Appliquée, 1990, 25, 1121-1128.	0.4	1
3099	Defect characterization of unannealed neutron transmutation doped silicon by means of deep temperature microwave detected photo induced current transient spectroscopy. Journal of Applied Physics, 2020, 127, 035704.	1.1	1
3100	Deep-level defects in gallium oxide. Journal Physics D: Applied Physics, 2021, 54, 043002.	1.3	57
3101	Characterisation of negative-U defects in semiconductors. Journal of Physics Condensed Matter, 2020, 32, 323001.	0.7	19
3102	Impact of defects on photoexcited carrier relaxation dynamics in GeSn thin films. Journal of Physics Condensed Matter, 2020, 33, 065702.	0.7	6
3103	Investigation of silicon surface passivation by sputtered amorphous silicon and thermally evaporated molybdenum oxide films using temperature- and injection-dependent lifetime spectroscopy. Semiconductor Science and Technology, 2020, 35, 125017.	1.0	2
3104	Electrically-active defects in reduced and hydrogenated rutile TiO_2 . Semiconductor Science and Technology, 2021, 36, 014006.	1.0	1
3105	Radioactive ion beams in solid state physics. Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences, 1998, 356, 2137-2162.	1.6	8
3106	Ion Dynamics in Single and Multi-Cation Perovskite. ECS Journal of Solid State Science and Technology, 2020, 9, 065015.	0.9	5
3107	Defects. Advances in Condensed Matter Science, 2003, , 158-202.	0.3	2
3108	Synthesis and Characterization of Germanium Nanocrystals. , 2014, , 135-180.		1

#	ARTICLE	IF	CITATIONS
3111	Misfit Dislocations Study in MOVPE Grown Lattice-Mismatched InGaAs/GaAs Heterostructures by Means of DLTS Technique. <i>Acta Physica Polonica A</i> , 2004, 106, 265-272.	0.2	5
3112	Defect Analysis of Pentacene Diode. <i>Acta Physica Polonica A</i> , 2014, 125, 1038-1041.	0.2	5
3113	Radiation hardness of AlAs/GaAs-based resonant tunneling diodes. <i>Semiconductor Physics, Quantum Electronics and Optoelectronics</i> , 1999, 2, 98-101.	0.3	2
3114	Response of 4H-SiC Detectors to Ionizing Particles. <i>Crystals</i> , 2021, 11, 10.	1.0	13
3115	Optically induced current deep level spectroscopy of radiation defects in neutron irradiated Si pad detectors. <i>Lithuanian Journal of Physics</i> , 2013, 53, 215-218.	0.1	2
3116	Origin Investigation of a Nitrogen-Related Recombination Center in GaAsN Grown by Chemical Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 051001.	0.8	5
3117	Electron Emission Properties of GaAsN/GaAs Quantum Well Containing N-Related Localized States: The Influence of Illuminance. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 02BJ12.	0.8	1
3118	Effect of Thermal Stress on a N-Related Recombination Center in GaAsN Grown by Chemical Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 02BP02.	0.8	3
3119	Deciphering the capacitance frequency technique for performance-limiting defect-state parameters in energy-harvesting perovskites. <i>Physical Chemistry Chemical Physics</i> , 2021, 23, 24421-24427.	1.3	4
3120	Local capacitance-voltage profiling and high voltage stress effect study of SiO ₂ /SiC structures by time-resolved scanning nonlinear dielectric microscopy. <i>Microelectronics Reliability</i> , 2021, 126, 114284.	0.9	3
3121	Mapping Charge Recombination and the Effect of Point-Defect Insertion in GaAs Nanowire Heterojunctions. <i>Physical Review Applied</i> , 2021, 16, .	1.5	1
3122	Nanoscale capacitance-voltage profiling of DC bias induced stress on a high- $\hat{\nu}$ /SiO ₂ /Si gate stack. <i>Microelectronics Reliability</i> , 2021, 126, 114278.	0.9	1
3123	Investigation of recombination mechanisms in Cu(In,Ga)Se ₂ solar cells using numerical modelling. <i>Solar Energy</i> , 2021, 228, 464-473.	2.9	7
3124	Review article on the lattice defect and interface loss mechanisms in kesterite materials and their impact on solar cell performance. <i>Solar Energy</i> , 2021, 230, 13-58.	2.9	20
3125	Properties of Transition Metals in Silicon. <i>Springer Series in Materials Science</i> , 2000, , 20-75.	0.4	0
3126	Uniaxial Stress Effect on Copper Energy Levels in Silicon. , 2001, , 1362-1365.		0
3128	Spectrum of Defect States in Porous Organic Low- κ Dielectric Films, Annealed in Argon and Nitrogen. <i>Materials Research Society Symposia Proceedings</i> , 2003, 766, 851.	0.1	0
3129	Evaluation of Copper Ion Drift in Low-Dielectric-Constant Interlayer Films by Transient Capacitance Spectroscopy. <i>Materials Research Society Symposia Proceedings</i> , 2003, 766, 171.	0.1	1

#	ARTICLE	IF	CITATIONS
3130	Deep level defects in high temperature annealed InP. Science in China Series D: Earth Sciences, 2004, 47, 320.	0.9	0
3131	CERN Large Hadron Collider projects to improve the radiation hardness of ionizing radiation detectors: The role and control of defects in Si and potential of GaN. Lithuanian Journal of Physics, 2005, 45, 437-443.	0.1	0
3132	Shallow Levels Characterization in Epitaxial GaAs by Acousto-Optic Reflectance. Acta Universitaria, 2012, 15, 42-49.	0.2	0
3133	III-V Semiconductors. , 0, , .		0
3134	Quantum Dots for Memories. Nanoscience and Technology, 2008, , 221-235.	1.5	0
3135	Selected High-Impact Journal Articles on Defects in Microelectronic Materials and Devices. , 2008, , .		2
3136	Electrical Properties of GaN and ZnO. Advances in Materials Research, 2009, , 355-414.	0.2	1
3137	10.1007/s11453-008-1007-z. , 2010, 42, 52.		2
3138	Electrical Properties. , 2011, , 485-540.		0
3139	Investigation of Lattice Defects in GaAsN Grown by Chemical Beam Epitaxy Using Deep Level Transient Spectroscopy. , 0, , .		0
3140	New Method for Diagnostics of Ion Implantation Induced Charge Carrier Traps in Micro- and Nanoelectronic Devices. World Journal of Nuclear Science and Technology, 2012, 02, 174-180.	0.2	0
3141	Detector Fabrication. Series in Sensors, 2012, , 119-206.	0.0	0
3143	ARTIFICIAL NEURAL NETWORKS METHOD FITTING FOR DEEP-LEVEL TRANSIENT SPECTROSCOPY SIGNALS ANALYSIS. Sensor Electronics and Microsystem Technologies, 2014, 9, .	0.1	0
3145	Nanoelectronic Applications of Molecular Junctions. Springer Tracts in Modern Physics, 2013, , 231-272.	0.1	0
3146	DLTS Evaluation of Near-Interface Traps in Ge-MIS Structures Fabricated by ECR-Plasma Techniques. IEEJ Transactions on Electronics, Information and Systems, 2013, 133, 1481-1484.	0.1	0
3147	Measurement Methods. Springer Theses, 2014, , 51-68.	0.0	0
3148	Deep Level Transient Spectroscopy of AlGaInP LEDs. Journal of Modern Physics, 2014, 05, 2075-2079.	0.3	0
3149	Bulk Trapping. , 1976, , 91-106.		0

#	ARTICLE	IF	CITATIONS
3150	Low Frequency Noise and Deep Traps in Schottky Barrier Diodes. , 1978, , 175-180.		2
3151	MEASUREMENT TECHNIQUES. , 1978, , 105-141.		0
3152	Applications of Luminescence. , 1978, , 539-546.		0
3153	Overview and Trends of Luminescent Research. , 1978, , 1-13.		0
3154	Centres profonds associ�s au palladium dans le silicium. Revue De Physique Appliqu�e, 1979, 14, 635-638.	0.4	0
3155	Defect Levels Controlling the Behavior of NTD Silicon During Annealing. , 1979, , 317-328.		3
3156	Oberfl�chen-Elektronenmikroskopie. , 1979, , 235-262.		0
3157	Material and Structure Factors Affecting the Large-Signal Operation of GaAs Mesfets. , 1980, , 313-320.		2
3158	R�le des centres profonds dans la d�gradation lente des dispositifs �lectroluminescents. Revue De Physique Appliqu�e, 1980, 15, 1-8.	0.4	1
3159	Light-Emitting Diodes and Injection Lasers. , 1980, , 814-890.		0
3160	Application of the Methods of Analysis to Experimental Results�Possibilities and Limitations. , 1981, , 269-295.		0
3161	Optical Properties of Irradiated Semiconductors. Shinku/Journal of the Vacuum Society of Japan, 1981, 24, 445-455.	0.2	0
3162	Electronic States in Hydrogenated Amorphous Si. Shinku/Journal of the Vacuum Society of Japan, 1982, 25, 91-97.	0.2	0
3163	Intervalle de confiance de la signature obtenue par D.L.T.S., d'un pi�ge profond. Revue De Physique Appliqu�e, 1982, 17, 787-792.	0.4	0
3164	Carrier Diffusion Processes. Springer Series in Solid-state Sciences, 1982, , 113-152.	0.3	0
3165	Experience with Neutron Transmutation Doped Silicon in the Production of High Power Thyristors. , 1984, , 205-224.		0
3166	Growth and electron trap characterization of GaAs by molecular beam epitaxy.. Shinku/Journal of the Vacuum Society of Japan, 1985, 28, 587-595.	0.2	0
3167	Carrier Diffusion Processes. Springer Series in Solid-state Sciences, 1985, , 113-152.	0.3	0

#	ARTICLE	IF	CITATIONS
3168	GaAs Material Preparation and Characterization. Edpacs, 1985, , 41-86.	0.5	1
3169	Is the DLTS Density of States for Amorphous Silicon Correct?. , 1985, , 299-314.		1
3170	Characterization of the Si-SiO ₂ Interface. Edpacs, 1985, 10, 29-77.	0.5	0
3171	Na ⁺ -Induced Surface States at the Si-SiO ₂ Interface. , 1985, , 237-240.		1
3172	Space-Charge Layers at Semiconductor Interfaces. , 1986, , 425-481.		0
3173	Deep Level Transient Spectroscopy for Semiconductor Surface and Interface Analysis. Springer Proceedings in Physics, 1987, , 273-281.	0.1	1
3174	Electron trap characterization of GaAs grown by the liquid encapsulated czochralski method.. IEEJ Transactions on Fundamentals and Materials, 1987, 107, 522-528.	0.2	0
3175	Electrical Properties of DX Center in Selectively Doped AlGaAs/GaAs Heterostructure. , 1987, , 133-140.		0
3176	InP MISFETs Technology. , 1987, , 99-110.		0
3177	GaAs Technology. , 1987, , 105-172.		0
3178	Characterization of semiconductors by capacitance transient spectroscopy.. Denki-seiko, 1988, 59, 233-242.	0.0	0
3179	Characterization techniques for localized electronic states at semiconductor surfaces and interfaces.. Hyomen Kagaku, 1988, 9, 200-206.	0.0	0
3181	MEASUREMENT OF ION IMPLANTATION. , 1988, , 165-218.		0
3182	Shallow and Deep Impurity Investigations: The Important Step Towards a Microwave Field-Effect Transistor Working at Cryogenic Temperatures. NATO ASI Series Series B: Physics, 1988, , 135-146.	0.2	1
3183	Direct observation of effective mass filtering in InGaAs/InP superlattices. Perspectives in Condensed Matter Physics, 1988, , 150-152.	0.1	1
3184	Gap States of Highly Photosensitive a-SiC:H. Springer Proceedings in Physics, 1989, , 74-79.	0.1	0
3185	Electronic Properties of $\hat{\epsilon} = 25$ Silicon Bicrystals by Deep Level Transient Spectroscopy. Springer Proceedings in Physics, 1989, , 58-63.	0.1	0
3186	Carrier Diffusion Processes. Springer Series in Solid-state Sciences, 1989, , 113-152.	0.3	0

#	ARTICLE	IF	CITATIONS
3187	Electrical Properties and Sputter-etched Induced Defects in Ti-W/Si Schottky Diodes. , 1989, , 565-568.		1
3188	Electron traps in the surface region of n-type silicon.. Hyomen Kagaku, 1989, 10, 320-325.	0.0	0
3189	Characterization of III-V Semiconductors. The Materials Processing and Practices, 1989, 7, 429-494.	0.1	0
3190	Characterization of Defects in VPE grown InGaAs/InP Avalanche Photodiode. , 1990, , 1255-1260.		0
3191	STUDIES OF DX-CENTERS IN Al _x Ga _{1-x} As: Te BY C2-SADLTS. , 1990, , 1073-1078.		0
3192	Persistent Photoconductivity And Thermal Recovery Kinetics Of Low Energy Ar + Bombarded GaAs. Materials Research Society Symposia Proceedings, 1991, 223, 203.	0.1	0
3193	Carrier Diffusion Processes. Springer Series in Solid-state Sciences, 1991, , 116-155.	0.3	0
3194	Diffusion von Ladungsträgern. , 1992, , 154-210.		0
3195	ICTS Measurement of Si-MOS Interface States. IEEJ Transactions on Electronics, Information and Systems, 1992, 112, 231-238.	0.1	0
3196	Impurities in Semiconductors: Experimental. , 1992, , 161-196.		2
3197	Rate-Window Transient Thermomodulation Spectrometry: Technique and Measurements in Semiconductors. Springer Series in Optical Sciences, 1992, , 556-558.	0.5	0
3198	Junction Transient Spectroscopy. , 1992, , 261-264.		0
3199	Methods for Electrical Resistivity Measurement Applicable to Medium and Good Electrical Conductors. , 1992, , 239-277.		0
3201	Electrical properties of polycrystalline diamond / hydrogenated amorphous silicon interfaces. , 1994, , 155-160.		0
3202	Diode Measurements. , 1995, , 185-207.		0
3203	Detection Methods. Springer Series in Materials Science, 1995, , 132-153.	0.4	0
3204	Point defects in MeV ion-implanted silicon studied by deep level transient spectroscopy. , 1996, , 183-190.		0
3205	A comparative study of deep levels created by low dose implantation of hydrogen, oxygen and silicon into MOCVD grown n-GaAs. , 1996, , 313-317.		0

#	ARTICLE	IF	CITATIONS
3206	Deep Level Characterization in Semi-Insulating GaAs by Photo-Induced Current and Photo-Hall Effect Transient Spectroscopy.. Journal of the Japan Society for Precision Engineering, 1997, 63, 264-268.	0.0	7
3207	Carrier Diffusion Processes. Springer Series in Solid-state Sciences, 1997, , 120-160.	0.3	0
3208	Evaluation of Deep Levels in Si-MOS Structure using ICTS Measurement. IEEJ Transactions on Electronics, Information and Systems, 1998, 118, 1299-1308.	0.1	0
3209	Carrier Diffusion Processes. , 1999, , 120-160.		0
3211	Analysis of deep level spectrum in GaAs+p-i-n+structures. , 2015, , .		0
3212	Characterization of deep level traps in semiconductor structures using numerical experiments. , 2015, , .		0
3214	Electrophysical Properties of GaAs Pâ€“N Structures for Concentrator Solar Cell Applications. Journal of Electrical Engineering, 2016, 67, 377-382.	0.4	3
3215	Interface Scavenging. Springer Theses, 2017, , 125-140.	0.0	0
3216	Plasma Oxidation of Gd2O3 and Sc2O3. Springer Theses, 2017, , 77-108.	0.0	0
3217	Characterization Techniques. Springer Theses, 2017, , 41-62.	0.0	0
3218	Identifying the source of reduced performance in 1-stage-grown Cu(In,Ga)Se2 solar cells. , 2017, , .		1
3220	High Resolution Characterizations of Semiconductor Device Using Scanning Nonlinear Dielectric Microscopy. Vacuum and Surface Science, 2018, 61, 221-226.	0.0	0
3221	Defect-related degradation of III-V/Silicon 1.55 Åµm DBR laser diodes. , 2018, , .		0
3222	Plant Growth under High Power Operation of White-Light-Emitting-Diodes by Operating-Current-Pulse-Width Control. Zairyo/Journal of the Society of Materials Science, Japan, 2018, 67, 834-839.	0.1	0
3223	Sol-Jel Yâ€“ntemi ile Åœretilen ZnO(Al)/p-Si Heteroekleminin Elektriksel Karakterizasyonu. SDU Journal of Science, 2018, 13, 121-131.	0.1	0
3226	Estimation of the Occupied Density of States Using Capacitanceâ€“Voltage Measurement in the NPB System. Springer Proceedings in Physics, 2019, , 1065-1070.	0.1	0
3228	Deep level relaxation spectroscopy and nondestructive testing of potential defects in the semiconductor electronic component base. Radio Industry, 2019, 29, 35-44.	0.1	3
3230	Reliability improvement of electrically active defect investigations by analytical and experimental deep level transient: Fourier spectroscopy investigations. Journal of Electrical Engineering, 2019, 70, 27-35.	0.4	2

#	ARTICLE	IF	CITATIONS
3231	Investigation on origin of Ru-induced deep-level defects in 4H-SiC epilayer based Schottky diodes by DLTS and theoretical calculations. , 2019, , .		1
3232	4H-SiC epitaxial Schottky detectors: deep-level transient spectroscopy (DLTS) and pulse height spectroscopy (PHS) measurements. , 2019, , .		0
3233	DEEP LEVELS' ACTIVATION ENERGY DEPENDENCE ON MEASUREMENT MODES. , 2019, , .		0
3234	Experimental equipment to investigate deep energy levels in semiconductor barrier structures with high leakage current. , 2020, , .		0
3235	Impact of Dynamic Trapping on High Frequency Organic Field-Effect Transistors. , 2020, , .		0
3236	Minority carrier traps in Czochralski-grown p-type silicon crystals doped with B, Al, Ga, or In impurity atoms. , 2020, , .		0
3237	Direct imaging method of frequency response of capacitance in dual bias modulation electrostatic force microscopy. Japanese Journal of Applied Physics, 2020, 59, 078001.	0.8	5
3238	Deep traps concentrations in ZnSe single crystals. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2020, 258, 114570.	1.7	2
3239	Technology computer aided design based deep level transient spectra: Simulation of high-purity germanium crystals. Journal Physics D: Applied Physics, 0, , .	1.3	2
3241	Valeur du signal de la méthode D.L.T.S. À double corrélation. Revue De Physique Appliquée, 1983, 18, 561-564.	0.4	0
3242	Photovoltaic Measurements, Junction Analysis, and Material Characterization. , 1983, , 153-194.		0
3243	Effects of Pulsed Laser Irradiation on the Electrical Properties of GaAs. , 1983, , 562-589.		0
3244	Carrier Emission and Recombination. Springer Series in Solid-state Sciences, 1983, , 154-204.	0.3	3
3246	Application of selective contacts for study of silicon surface degradation. Journal of Physics: Conference Series, 2020, 1695, 012084.	0.3	0
3247	Influence of wet etching in KOH on defects in silicon nanowires formed by cryogenic dry etching. Journal of Physics: Conference Series, 2020, 1697, 012060.	0.3	1
3248	DLTS spectra of radiation-induced defects in silicon detectors with heavily damaged Bragg peak region. Journal of Physics: Conference Series, 2020, 1697, 012071.	0.3	0
3249	Leakage current analysis of silicon diode with anode activated by furnace annealing or laser annealing using deep level transient spectroscopy. AIP Advances, 2020, 10, .	0.6	4
3250	Using MoOx/p-Si Selective Contact for Evaluation of the Degradation of a Near-Surface Region of Silicon. Technical Physics Letters, 2020, 46, 1245-1248.	0.2	0

#	ARTICLE	IF	CITATIONS
3251	Capacitance characterization of silicon nanowires formed by cryogenic dry etching. Journal of Physics: Conference Series, 2020, 1695, 012089.	0.3	1
3252	Advanced Electrical Characterization of Single Oxide Defects Utilizing Noise Signals. , 2020, , 229-257.		5
3253	Analysis of defects of PV solar modules using deep level transient spectroscopy. Feasibility and limits. AIP Conference Proceedings, 2020, , .	0.3	0
3254	Characterization of defect states in Mg-doped GaN-on-Si p+n diodes using deep-level transient Fourier spectroscopy. Semiconductor Science and Technology, 2020, 36, 024002.	1.0	1
3255	GaN-based power devices: Physics, reliability, and perspectives. Journal of Applied Physics, 2021, 130, .	1.1	191
3257	Photorefractive Semiconductors and Quantum-Well Structures. , 2007, , 363-389.		0
3258	Measurement methods, part B. , 0, , 1-12.		0
3259	Measurement methods, part C. , 0, , 1-19.		0
3260	Measurement methods, part D. , 0, , 1-10.		0
3262	Theoretical Aspects of Point Defects in Semiconductor Nanowires. , 2021, , 349-367.		0
3263	Local Capacitance-Voltage Profiling and Deep Level Transient Spectroscopy of SiO ₂ /SiC Interfaces by Scanning Nonlinear Dielectric Microscopy. , 2021, , .		1
3264	Characterization of deep interface states in SiO ₂ /B-doped diamond using the transient photocapacitance method. Thin Solid Films, 2022, 741, 139026.	0.8	1
3265	Analysis of semi-insulating carbon-doped GaN layers using deep-level transient spectroscopy. Journal of Applied Physics, 2021, 130, 205701.	1.1	1
3266	Effect of Schottky barrier height on quantitative analysis of deep-levels in n-type GaN by deep-level transient spectroscopy. AIP Advances, 2021, 11, 115124.	0.6	3
3267	Hysteretic capacitance-voltage characteristics of self-assembled quantum dots far from equilibrium with their environment. Physical Review B, 2021, 104, .	1.1	1
3268	Transient tunneling spectroscopy (TTS) study of electron tunneling from phosphorus atoms in silicon. Applied Physics A: Materials Science and Processing, 1991, 52, 13-18.	1.1	8
3270	First Principle Defect Analysis in 150 Åµm 4H-SiC Epitaxial Layer Schottky Barrier Detectors. , 2020, , .		0
3271	Study of Emission and Capture Processes in Semi-vertical GaN-on-Si Trench-MOSFETs. , 2020, , .		0

#	ARTICLE	IF	CITATIONS
3272	Materials and Defect Aspects of III-V and III-N Devices for High-Speed Analog/RF Applications. , 2020, , .		1
3273	Effects of electrical stress on the characteristics and defect behaviors in GaN-based near-ultraviolet light emitting diodes. Chinese Physics B, 2022, 31, 068101.	0.7	2
3274	Deep level transient spectroscopy and photoluminescence studies of hole and electron traps in ZnSnP ₂ bulk crystals. Japanese Journal of Applied Physics, 2022, 61, 020905.	0.8	1
3275	Majority and Minority Carrier Traps in NiO/Î ² -Ga ₂ O ₃ p ⁺ -n Heterojunction Diode. IEEE Transactions on Electron Devices, 2022, 69, 981-987.	1.6	23
3276	Identification of the defect dominating high temperature reverse leakage current in vertical GaN power diodes through deep level transient spectroscopy. Applied Physics Letters, 2022, 120, .	1.5	2
3277	Rich Device Physics Found in Photoresponses of Low-Dimensional Photodetectors by Fitting With Explicit Photogain Theory. IEEE Electron Device Letters, 2022, 43, 422-425.	2.2	4
3278	Effect of oxide layer growth conditions on radiation detection performance of Ni/SiO ₂ /epi-4H-SiC MOS capacitors. Journal of Crystal Growth, 2022, 584, 126566.	0.7	3
3279	Influence of carrier trapping on radiation detection properties in CVD grown 4H-SiC epitaxial layers with varying thickness up to 250Åµm. Journal of Crystal Growth, 2022, 583, 126532.	0.7	9
3280	Capacitance spectroscopy of thin-film formamidinium lead iodide based perovskite solar cells. Solar Energy Materials and Solar Cells, 2022, 238, 111618.	3.0	4
3281	Defects and Reliability of GaN-Based LEDs: Review and Perspectives. Physica Status Solidi (A) Applications and Materials Science, 2022, 219, .	0.8	28
3282	Acoustoelectric Investigation of Deep Centers in Bulk and Multilayered Semiconductors. Communications - Scientific Letters of the University of Zilina, 2003, 5, 5-13.	0.3	1
3283	DLTS investigations on CIGS solar cells from an inline co-evaporation system with RbF post-deposition treatment. EPJ Photovoltaics, 2022, 13, 7.	0.8	5
3284	Experimental study on shallow and deep dopant properties at the interface of PtO _x /ZnO Schottky diodes. Japanese Journal of Applied Physics, 0, , .	0.8	0
3285	Role of Defects and Power Dissipation on Ferroelectric Memristive Switching. Advanced Electronic Materials, 2022, 8, .	2.6	10
3286	Deep level defect states in Î ² -, Î [±] -, and <i>É</i>-Ga ₂ O ₃ crystals and films: Impact on device performance. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2022, 40, .	0.9	35
3287	DLTS with Bayesian Inference for Analyzing RPD Induced Defects in Bulk near SiO ₂ /Si Interface. ECS Journal of Solid State Science and Technology, 2022, 11, 035002.	0.9	4
3288	Breakdown characteristics of deep-ultraviolet Al _{0.6} Ga _{0.4} N p-i-n avalanche photodiodes. Journal of Applied Physics, 2022, 131, 103102.	1.1	5
3289	Investigation of deep level defects in n-type GaAsBi. , 2022, , .		0

#	ARTICLE	IF	CITATIONS
3290	Influence of heat treatments in H ₂ and Ar on the E_{1c} center in In^{2+} -Ga ₂ O ₃ . Journal of Applied Physics, 2022, 131, .	1.1	11
3291	Analysis of dislocation-related and point-defects in III-As layers by extensive DLTS study. , 2022, , .		0
3292	Thin-Film Ferroelectrics. Advanced Materials, 2022, 34, e2108841.	11.1	33
3293	How to perform admittance spectroscopy and DLTS in multijunction solar cells. Solar Energy Materials and Solar Cells, 2022, 240, 111699.	3.0	3
3294	Structure, optical absorption and photochromic effect in Rb _{0.95} Nb _{1.375} Mo _{0.625} O _{5.79} . Journal of Solid State Chemistry, 2022, 310, 123083.	1.4	1
3295	Fine structure in electronic transitions attributed to nitrogen donor in silicon carbide. Applied Physics Letters, 2021, 119, 262101.	1.5	1
3296	Defect Spectroscopy in Halide Perovskites Is Dominated by Ionic Rather than Electronic Defects. ACS Energy Letters, 2022, 7, 140-144.	8.8	20
3297	Impact of thermal annealing on deep levels in nitrogen-implanted In^{2+} -Ga ₂ O ₃ Schottky barrier diodes. Journal of Applied Physics, 2021, 130, .	1.1	3
3298	Acceptor-oxygen defects in silicon: The electronic properties of centers formed by boron, gallium, indium, and aluminum interactions with the oxygen dimer. Journal of Applied Physics, 2021, 130, 245703.	1.1	5
3299	Quantitative analysis of electrically active defects in Au/AlGaIn/GaN HEMTs structure using capacitance-frequency and DLTS measurements. Journal of Physics Communications, 2021, 5, 125010.	0.5	0
3300	Performance-Improved Vertical Ni/SiO ₂ /4H-SiC Metal-Oxide-Semiconductor Capacitors for High-Resolution Radiation Detection. IEEE Transactions on Nuclear Science, 2022, 69, 1965-1971.	1.2	3
3301	On the nature of thermally activated defects in n-type FZ silicon grown in nitrogen atmosphere. AIP Advances, 2022, 12, .	0.6	4
3302	Effect of SiC polytypes on the electrical properties of polyaniline based heterojunctions. Applied Physics A: Materials Science and Processing, 2022, 128, 1.	1.1	1
3303	Toward Understanding Chalcopyrite Solar Cells via Advanced Characterization Techniques. Advanced Materials Interfaces, 2022, 9, .	1.9	1
3304	Transient analysis of photomultiplication-type organic photodiodes. Applied Physics Reviews, 2022, 9, .	5.5	13
3307	Defect-controlled Resistance Degradation of Sputtered Lead Zirconate Titanate Thin Films. , 2022, , .		1
3308	A Critical Examination of the TCAD Modeling of Hot Carrier Degradation for LDMOS Transistors. , 2022, , .		3
3309	Laser-combined multiprobe microscopy and its application to the materials with atomic layer thickness. Japanese Journal of Applied Physics, 0, , .	0.8	1

#	ARTICLE	IF	CITATIONS
3310	Large-Area (Ag,Cu)(In,Ga)Se ₂ Thin-Film Solar Cells with Increased Bandgap and Reduced Voltage Losses Realized with Bulk Defect Reduction and Front-Grading of the Absorber Bandgap. Solar Rrl, 2022, 6, .	3.1	6
3311	Electronic defects in metal oxide photocatalysts. Nature Reviews Materials, 2022, 7, 503-521.	23.3	129
3312	Shallow- and deep-levels analysis in irradiated medium-resistivity silicon detectors. Il Nuovo Cimento A, 1999, 112, 1359-1367.	0.1	2
3313	Mathematical Models for Acoustic Spectra Simulation. Communications - Scientific Letters of the University of Zilina, 2010, 12, 44-49.	0.3	3
3314	The Sliding-Aperture Transform and Its Applicability to Deep-Level Transient Spectroscopy. Applied Sciences (Switzerland), 2022, 12, 5317.	1.3	0
3315	Field-effect conductivity scaling for two-dimensional materials with tunable impurity density. 2D Materials, 0, , .	2.0	1
3316	Engineering the charge extraction and trap states of Sb ₂ S ₃ solar cells. Applied Physics Letters, 2022, 120, .	1.5	17
3317	Microscopic Evaluation of Al ₂ O ₃ /p-Type Diamond (111) Interfaces Using Scanning Nonlinear Dielectric Microscopy. Materials Science Forum, 0, 1062, 298-303.	0.3	1
3318	Current state-of-the-art characterization methods for probing defect passivation towards efficient perovskite solar cells. Journal of Materials Chemistry A, 2022, 10, 19278-19303.	5.2	10
3319	Electronic transport mechanism and defect states for p-InP/i-InGaAs/n-InP photodiodes. Journal of Materials Research and Technology, 2022, 19, 2742-2749.	2.6	3
3320	Local capacitance-voltage profiling and deep level transient spectroscopy of SiO ₂ /SiC interfaces by scanning nonlinear dielectric microscopy. Microelectronics Reliability, 2022, 135, 114588.	0.9	2
3321	Physics of defects in metal halide perovskites. Reports on Progress in Physics, 2022, 85, 096501.	8.1	13
3322	Enhancement of radiation detection performance with reduction of EH _{6/7} deep levels in n-type 4H-SiC through thermal oxidation. Applied Physics Letters, 2022, 121, .	1.5	6
3323	Permittivity modulation in Si based PIN diode by electron irradiation. Semiconductor Science and Technology, 0, , .	1.0	0
3324	Theoretical Simulation and Experimental Verification of the Competition between Different Recombination Channels in GaN Semiconductor. Journal of Materials Chemistry C, 0, , .	2.7	2
3325	Identification and Suppression of Majority Surface States in the Dry-Etched In ₂ Ga ₂ O ₃ . Journal of Physical Chemistry Letters, 2022, 13, 7094-7099.	2.1	11
3326	Photothermal radiometry methods in materials science and applied chemical research. Journal of Applied Physics, 2022, 132, .	1.1	7
3327	Anomalous Photocurrent Reversal Due to Hole Traps in AlGaN-Based Deep-Ultraviolet Light-Emitting Diodes. Micromachines, 2022, 13, 1233.	1.4	0

#	ARTICLE	IF	CITATIONS
3328	Electrical characterization and extraction of activation energies of the defect states in the LaAlO ₃ /SrTiO ₃ heterostructure. Applied Physics Letters, 2022, 121, 081904.	1.5	1
3329	Electrical characteristics and deep-level transient spectroscopy of a fast-neutron-irradiated 4H-SiC Schottky barrier diode. Nuclear Engineering and Technology, 2022, .	1.1	0
3330	Inspection of the Defect State Using the Mobility Spectrum Analysis Method. Nanomaterials, 2022, 12, 2773.	1.9	0
3331	A new approach to electrically detected magnetic resonance: Spin-dependent transient spectroscopy. Journal of Applied Physics, 2022, 132, .	1.1	2
3332	To define nonradiative defects in semiconductors: An accurate DLTS simulation based on first-principle. Computational Materials Science, 2022, 215, 111760.	1.4	4
3333	Ag, Ti dual-cation substitution in Cu ₂ ZnSn(S,Se) ₄ induced growth promotion and defect suppression for high-efficiency solar cells. Journal of Materials Chemistry A, 2022, 10, 22791-22802.	5.2	35
3334	Investigation of proton irradiation induced EC-0.9 eV traps in AlGaN/GaN high electron mobility transistors. Applied Physics Letters, 2022, 121, .	1.5	4
3335	Interfacial Engineering towards Enhanced Photovoltaic Performance of Sb ₂ Se ₃ Solar Cell. Advanced Functional Materials, 2022, 32, .	7.8	21
3336	Polar Species for Effective Dielectric Regulation to Achieve High-Performance CsPbI ₃ Solar Cells. Advanced Materials, 2022, 34, .	11.1	27
3337	A new lock-in amplifier-based deep-level transient spectroscopy test and measurement system for solar cells. Solar Energy, 2022, 244, 507-515.	2.9	2
3338	Thermal-annealing behavior of in-core neutron-irradiated epitaxial 4H SiC. Nuclear Engineering and Technology, 2023, 55, 209-214.	1.1	1
3339	Analysis of recombination centers near an interface of a metal-SiO ₂ -Si structure by double carrier pulse deep-level transient spectroscopy. AIP Advances, 2022, 12, 095316.	0.6	1
3340	Investigation of Ni/Y ₂ O ₃ /n-4H-SiC metal-oxide-semiconductor structure for high-resolution radiation detection. , 2022, , .		0
3341	Current-induced degradation behaviors of InGaN/GaN multiple-quantum-well UV photodetectors: Role of electrically active defects. Sensors and Actuators A: Physical, 2022, 347, 113935.	2.0	4
3342	Improved Interface of Encapsulating Sm-Doped TiO ₂ /Thin Films/RuO ₂ /Schottky Diodes for a Junction Spectroscopy Measurement. Optics and Photonics Journal, 2022, 12, 215-224.	0.3	0
3343	How small changes make a difference: Influence of low silver contents on the effect of RbF-PDT in CIGS solar cells. Progress in Photovoltaics: Research and Applications, 0, .	4.4	1
3344	Band Gap and Defect Engineering for High-Performance Cadmium-free Sb ₂ (S,Se) ₃ Solar Cells and Modules. Advanced Functional Materials, 2022, 32, .	7.8	29
3345	Deep Level Transient Fourier Spectroscopy (DLTFS) and Isothermal Transient Spectroscopy (ITS) in vertical GaN-on-GaN Schottky barrier diodes. , 2022, 172, 207433.		2

#	ARTICLE	IF	CITATIONS
3346	Experimental and theoretical studies of native deep-level defects in transition metal dichalcogenides. <i>Npj 2D Materials and Applications</i> , 2022, 6, .	3.9	10
3347	Reliability Analysis of AlGaIn-Based Deep UV-LEDs. <i>Nanomaterials</i> , 2022, 12, 3731.	1.9	2
3348	Investigation of a defect in the $\text{In}^{2-}\text{Ga}_{2-2}\text{O}_{3-3}$ substrate material from capacitance transients. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2022, 40, 064001.	0.6	0
3349	Point Defects in GaN. <i>Semiconductors and Semimetals</i> , 2022, , 153-205.	0.4	0
3350	Stability of Silicon Heterojunction solar cells having hydrogen plasma treated intrinsic layer. , 2022, , .		0
3351	Thermally Driven Point Defect Transformation in Antimony Selenosulfide Photovoltaic Materials. <i>Advanced Materials</i> , 2023, 35, .	11.1	11
3352	Emission and capture characteristics of electron trap ($E_{\text{emi}} = 0.8 \text{ eV}$) in Si-doped $\text{In}^{2-}\text{Ga}_{2-2}\text{O}_{3-3}$ epilayer. <i>Semiconductor Science and Technology</i> , 2023, 38, 015001.	1.0	4
3353	Carrier Capture Dynamics of Deep-Level Defects in Neutron-Irradiated Si With Improved Intracascade Potential. <i>IEEE Transactions on Nuclear Science</i> , 2023, 70, 113-122.	1.2	0
3354	Optimisation of Sb ₂ S ₃ thin-film solar cells via Sb ₂ Se ₃ post-treatment. <i>Journal of Power Sources</i> , 2023, 556, 232451.	4.0	6
3355	A machine-learning interatomic potential to understand primary radiation damage of silicon. <i>Computational Materials Science</i> , 2023, 218, 111970.	1.4	3
3356	Electric Field Enhancement of Electron Emission Rates for Deep-Level Traps in n-Type GaN. <i>Physica Status Solidi (B): Basic Research</i> , 0, , .	0.7	4
3357	Defect characterization studies on irradiated boron-doped silicon pad diodes and Low Gain Avalanche Detectors. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2023, 1048, 167977.	0.7	2
3358	Comparison of the properties of defect states in nitrogen-containing n- and p-type float-zone silicon: a combined DLTS and MCTS study. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 0, , .	0.8	0
3359	Introduction of deep level impurities, S, Se, and Zn, into Si wafers for high-temperature operation of a Si qubit. <i>Japanese Journal of Applied Physics</i> , 0, , .	0.8	1
3360	Study of deep levels in the Mg ₂ Si grown by vertical Bridgeman method. <i>Japanese Journal of Applied Physics</i> , 2023, 62, SD1012.	0.8	1
3361	Carrier Transport Enhancement Mechanism in Highly Efficient Antimony Selenide Thin-Film Solar Cell. <i>Advanced Functional Materials</i> , 2023, 33, .	7.8	36
3362	Influences of Orientation and Remote O ₂ Plasma Exposure on the Interface Properties of SiO ₂ /In ²⁻ Ga ₂₋₂ O ₃₋₃ MOS Capacitors. <i>IEEE Transactions on Electron Devices</i> , 2023, 70, 1188-1193.	1.6	2
3363	Electrical spectroscopy of defect states and their hybridization in monolayer MoS ₂ . <i>Nature Communications</i> , 2023, 14, .	5.8	13

#	ARTICLE	IF	CITATIONS
3364	Investigation of Charge Transport Properties and the Role of Point Defects in CdZnTeSe Room Temperature Radiation Detectors. , 2023, , 171-188.		0
3365	Correlation between non-ionizing energy loss and production rate of electron trap at $E_C \hat{=}$ (0.12 $\hat{=}$ 0.20) eV formed in gallium nitride by various types of radiation. Applied Physics Letters, 2023, 122, .	1.5	2
3366	Mikrodenetleyici Tabanlı Esnek, G $\frac{1}{4}$ Si $\frac{1}{4}$ Dijital Gecikmeli Darbe Ėereteci Sistem Tasarım ve Optoelektronik Uygulamalar. Deu Muhendislik Fakultesi Fen Ve Muhendislik, 2023, 25, 255-262.	0.1	0
3367	Consequences of grain boundary barriers on electrical characteristics of CIGS solar cells. Solar Energy Materials and Solar Cells, 2023, 253, 112252.	3.0	0
3368	Transient photocapacitance spectroscopy of deep-levels in (001) $\hat{=}$ -Ga ₂ O ₃ . Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2023, 41, 033205.	0.9	0
3369	Proton radiation effects on electronic defect states in MOCVD-grown (010) $\hat{=}$ -Ga ₂ O ₃ . Journal of Applied Physics, 2023, 133, .	1.1	7
3370	Unraveling the Turn-On Limitation of Quantum-Dot Electroluminescence via a Stepwise-Increasing Voltage Measurement. Physical Review Applied, 2023, 19, .	1.5	4
3371	Origin, Nature, and Location of Defects in PM6:Y6 Organic Solar Cells. Advanced Energy Materials, 2023, 13, .	10.2	10
3372	Generation of Oxygen-Related Defects in Crystal Silicon Processed by the RPD. Crystals, 2023, 13, 310.	1.0	1
3373	Transient photocapacitance spectroscopy on Au/TiO ₂ Schottky diodes with rolled-up nanomembrane electrodes. Journal of Applied Physics, 2023, 133, 065704.	1.1	0
3374	Advanced Thermoluminescence Spectroscopy as a Research Tool for Semiconductor and Photonic Materials: A Review and Perspective. Physica Status Solidi (A) Applications and Materials Science, 2023, 220, .	0.8	2
3375	Modeling of carrier lifetime based on Deep-Level Transient Spectroscopy for power PIN diodes. , 2022, , .		0
3376	Characterization of the defect in CIGSe solar cell by admittance spectroscopy. AIP Advances, 2023, 13, 025264.	0.6	0
3377	Deep-level traps in as-grown and electron-irradiated homo-epitaxial n-GaN layers grown by MOVPE. Microelectronic Engineering, 2023, 274, 111977.	1.1	1
3378	Proton-irradiation-induced degradation in GaN-based UV LEDs: Role of unintentionally doped carbon. Applied Physics Letters, 2023, 122, .	1.5	2
3379	Ultrafast GaAs MOVPE growth for power electronics. Journal of Crystal Growth, 2023, 613, 127201.	0.7	1
3380	Inductive Type Impedance of Mo$\frac{1}{2}$-Si Barrier Structures Irradiated with Alpha Particles. Pribory I Metody Izmerenij, 2023, 14, 38-43.	0.1	1
3381	Trap analysis on Pt-AlGaN/GaN Schottky barrier diode through deep level transient spectroscopy. Journal of Semiconductors, 2023, 44, 042802.	2.0	0

#	ARTICLE	IF	CITATIONS
3390	Investigation of BV _{dss} instability in trench power MOSFET through DLTS, electrical characterization and TCAD simulations. , 2023, , .		0
3395	Density functional theory to calculate accurate defect energy levels in silicon. AIP Conference Proceedings, 2023, , .	0.3	0
3396	Advanced spectroscopic techniques for characterizing defects in perovskite solar cells. Communications Materials, 2023, 4, .	2.9	9
3408	Negative-pressure sulfurization of antimony sulfide thin films for generating a record open-circuit voltage of 805 mV in solar cell applications. Journal of Materials Chemistry A, 2023, 11, 19298-19307.	5.2	2
3416	Electrical Characterization of Semiconductors: I _V , C _V and Hall Measurements. Lecture Notes in Nanoscale Science and Technology, 2023, , 197-240.	0.4	0
3427	A high-dimensional in-sensor reservoir computing system with optoelectronic memristors for high-performance neuromorphic machine vision. Materials Horizons, 2024, 11, 499-509.	6.4	1